# TSMC 65nm CLN65G+ RVT Process 1.0-Volt 10-Track Advantage<sup>TM</sup> v2.1 Standard Cell Library Databook



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# **Preface**

#### **Revision History**

This document contains the release history for the TSMC 65nm CLN65G+ RVT Process 1.0-Volt 10-Track Advantage<sup>TM</sup> v2.1 Standard Cell Library Databook.

Part Number	Release Number	Date of Release	Updates
DB-Advantage-TSM087-1.0/65@1.0-1.0	1.0	August 2006	Initial Release
DB-Advantage-TSM087-2.0/65@1.0-1.0	2.0	December 2006	Updated for LAT Family functional descriptions
DB-Advantage-TSM087-3.0/65@1.0-1.0	3.0	March 2007	Recharacterized with new Spectre models

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• United States and North America 877-ARTILIB (877-278-4542)

• International 408-548-3298

• Email support-artisan@arm.com

# Introduction

ARM's Artisan Physical IP Advantage<sup>TM</sup> standard cell library builds upon the SAGE architecture, producing the optimum combination of high-density with high-performance. The cell line-up is derived from extensive customer design, synthesis, and place-and-route benchmark analysis. Library optimization is achieved by carefully matching the library functions and drive strengths to leading synthesis and place-and-route tools, producing superior RTL-to-GDSII results.

# **How This Book Is Organized**

This introduction is organized into three sections:

- Global Parameters provides an overview of parameters specific to your Advantage library.
- Special Cells details the types of special cells that may be included in your library.
- Reading the Datasheet describes the components of each datasheet.

Datasheets for each cell in this library are provided after the introduction. The datasheets are included in alphabetical order.

# **Global Parameters**

This section specifies global parameters for the TSMC 65nm CLN65G+ RVT Process 1.0-Volt 10-Track Advantage<sup>TM</sup> v2.1 Standard Cell Library. Some of the following sections may be covered: physical specifications, electrical specifications, derating factors, propagation delay calculation, timing constraints, power calculation, and power-rail strapping.

# **Physical Specifications**

Table 1 shows the physical design specifications of this library.

Table 1. Physical Specifications

J	
Drawn Gate Length (um)	0.06
Layers of Metal	1
Layout Grid (um)	0.005
Vertical Pin Grid (um)	0.2
Horizontal Pin Grid (um)	0.2
Cell Power and Ground Rail Width (um)	0.3
Cell Height (um)	2.0

In the Advantage library, all pins are located on the vertical and horizontal pin grids. Most place-and-route tools work more efficiently with all pins on grids, and some tools even require it.

The Advantage library also supports designs with six, seven, eight, or nine layers of metal. You may need to change the design rules in the technology file, because the top-level metal has a greater minimum width and greater minimum spacing requirement. See "TSMC 65nm CMOS Logic Design Rule Manual Version 1.2" design rule manual. You must define these rules correctly for the place-and-route tool.

Table 2 describes the electrical specifications for this library.

Table 2. Electrical Specifications

Parameter	Minimum	Typical	Maximum
DC Supply Voltage (Vdd)	0.9V	1.0V	1.1V
Junction Temperature	-40°C	25°C	125°C

Table 3 shows the derating factors for this library.

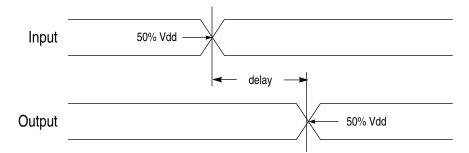
Table 3. Derating Factors

K <sub>Process</sub> (slow)	1.375
K <sub>Process</sub> (typical)	1.000 (by definition)
K <sub>Process</sub> (fast)	0.76
K <sub>Volt</sub> (1.0V to 0.9V)	-2.507/V
K <sub>Volt</sub> (1.0V to 1.1V)	-1.636/V
$K_{\text{Temp}}$ (25°C to -40°C)	0.00029/°C
K <sub>Temp</sub> (25°C to 125°C)	0.00041/°C

# **Propagation Delay and Transition Time**

The propagation delay through a cell is the sum of the intrinsic delay, the load-dependent delay, and the input-slew dependent delay. Delays are defined as the time interval between the input stimulus crossing 50% of Vdd and the output crossing 50% of Vdd. Figure 1 illustrates the propagation delay.

Figure 1. Propagation Delay



The transition times (slews) on input and output pins are defined as the time interval between the signal crossing 10% of Vdd and 90% of Vdd. Figure 2 illustrates transition time measurements for rising and falling signals.

Figure 2. Transition Time

90% Vdd

10% Vdd

Rising Time

Falling Time

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Factors that affect propagation delays and transition time include: temperature, supply voltage, process variations, fanout loading, interconnect loading, input-transition time, input-signal polarity, and timing constraints. The timing models provided with this library include the effects of input-transition time on propagation delays. Also, all timing models use a table lookup method to calculate accurate timing. To simplify calculations, the standard cell datasheets provide all timing numbers for an input slew of 0.01055ns and a linearized load factor,  $K_{load}$ , which is not as accurate as the timing models. All cells have been characterized with a fully populated metal2 (0.2um horizontal pitch) and metal3 (0.2um vertical pitch) routing grid across the entire cell layout.

The Advantage library may contain negative propagation delays. Although most third-party verification tools can handle negative propagation delays, some tools will turn negative delays into a zero value.

# **Derating Factors**

Derating factors are coefficients that the typical process characterization data is multiplied by to arrive at timing data that reflects appropriate operating conditions. The deratings table provides derating factors for variations in process case, temperature, and voltage.

Derating factors are derived by averaging the performance of many different cells in the library. A particular combination of cells may perform better or worse than indicated by these derating factors.

# **Delay Calculation**

Using the delay data in the datasheets ( $t_{intrinsic}$ ,  $K_{load}$ , and  $C_{load}$ ) and the delay derating factors, the estimated total propagation delay is calculated as such:

$$\begin{split} t_{TPD} &= (K_{Process}) * [1 + (K_{Volt} * \Delta Vdd)] * [1 + (K_{Temp} * \Delta T)] * t_{typical} \\ t_{typical} &= t_{intrinsic} + (K_{load} * C_{load}) \end{split}$$

where:

 $t_{TPD}$  = total propagation delay (ns);

 $t_{typical}$  = delay at typical corner-1.0V, 25°C, typical process (ns);

t<sub>intrinsic</sub> = delay through the cell when there is no output load (ns);

 $K_{load} = load delay multiplier (ns/pF);$ 

C<sub>load</sub> = total output load capacitance (pF);

 $K_{Process}$  = process derating factor, where process is slow, typical, or fast;

 $K_{Volt}$  = voltage derating factor (/V);

 $\Delta Vdd = Vdd - 1.0V$ ;

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 $K_{Temp}$  = temperature derating factor (/°C);

 $\Delta T$  = junction temperature - 25°C.

# **Timing Constraints**

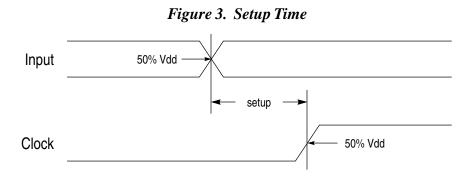
Timing constraints define minimum time intervals during which specific signals must be held steady in order to ensure the correct functioning of any given cell. Timing constraints include: setup time, hold time, recovery time, and minimum pulse width.

The sequential-cell timing models provided with this library include the effects of input-transition time and data-signal and clock-signal polarity on timing constraints. To simplify calculations, the datasheets specify timing constraint values for 0.01055ns data slew and 0.01055ns clock slew. Other factors that affect timing constraints include temperature, supply voltage, and process case variations. All cells have been characterized with a fully populated metal2 (0.2um horizontal pitch) and metal3 (0.2um vertical pitch) routing grid across the entire cell layout.

Timing constraints can affect propagation delays. The intrinsic delays given in the datasheets are measured with relaxed timing constraints (longer than necessary setup times, hold times, recovery times, and pulse widths). The use of shorter timing constraint intervals may increase delay. Each cell is considered functional as long as the actual delay does not exceed the delay given in the datasheets by more than 10%.

# **Setup Time**

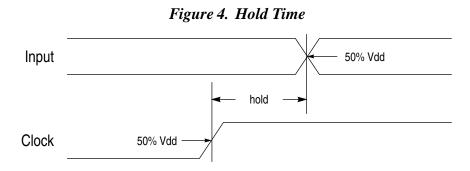
The setup time for a sequential cell is the minimum length of time the data-input signal must remain stable before the active edge of the clock (or other specified signal) to ensure correct functioning of the cell. The cell is considered functional as long as the delay for the output reaching its expected value does not exceed the reference delay (measured with a large setup time) by more than 10%. Setup-constraint values are measured as the interval between the data signal crossing 50% of Vdd for rising data (or 50% of Vdd for falling data) and the clock signal crossing 50% of Vdd for rising clocks (or 50% of Vdd for falling clocks). For the measurement of setup time, the data input signal is kept stable after the active clock edge for an infinite hold time. Figure 3 illustrates setup time for a positive-edge-triggered sequential cell.



### **Hold Time**

The hold time for a sequential cell is the minimum length of time the data-input signal must remain stable after the active edge of the clock (or other specified signal) to ensure correct functioning of the cell. The cell is considered functional as long as the delay for the output reaching its expected value does not exceed the reference delay (measured with a large hold time) by more than 10%. Hold-constraint values are measured as the interval between the data signal crossing 50% of Vdd for rising data (or 50% of Vdd for falling data) and the clock signal crossing 50% of Vdd for rising clocks (or 50% of Vdd for falling clocks). For the measurement of hold time, the data input signal is held stable before the active clock edge for an infinite setup time. Figure 4 illustrates hold time for a positive-edge-triggered sequential cell.

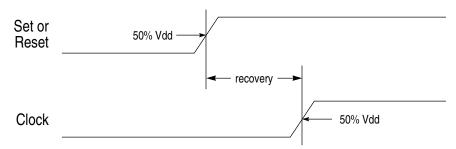
**NOTE:** ARM does not incorporate any hold time margins in the Synopsys, TLF, StarDC, or any other timing models. Chip designers should develop a timing methodology to account for chip-level timing inaccuracies inherent to extraction and timing analysis tools.



# **Recovery Time**

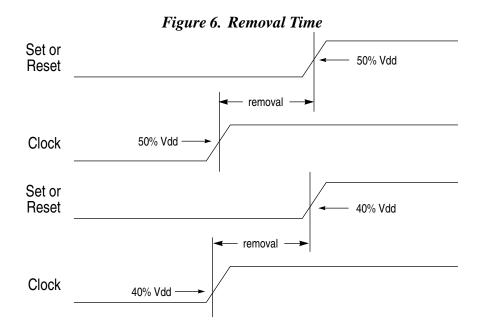
Recovery time for sequential cells is the minimum length of time that the active-low set or reset signal must remain high before the active edge of the clock to ensure correct functioning of the cell. The cell is considered functional as long as the delay for the output reaching its expected value does not exceed the reference delay (measured with a large recovery time) by more than 10%. Recovery constraint values are measured as the interval between the set or reset signal crossing 50% of Vdd and the clock signal crossing 50% of Vdd for rising clocks (or 50% of Vdd for falling clocks). For the measurement of recovery time, the set or reset signal is held stable after the active clock edge for an infinite hold time. Figure 5 illustrates recovery time.

Figure 5. Recovery Time



#### **Removal Time**

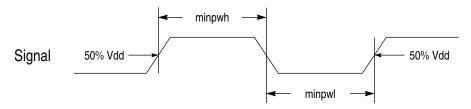
Removal time for sequential cells is the minimum length of time that the active low set or reset signal must remain low after the active edge of the clock to ensure correct functioning of the cell. The cell is considered functional as long as the active clock edge does not latch in a new data value from that programmed by the asynchronous set or reset signal. Removal constraint values are measured as the interval between the set or reset signal crossing 50% of Vdd and the clock signal crossing 50% of Vdd for rising clocks (or 50% of Vdd for falling clocks). For the measurement of removal time, the set or reset signal is held stable before the active clock edge for an infinite setup time. Figure 6 illustrates removal time.



#### Minimum Pulse Width

Minimum pulse width is the minimum length of time between the leading and trailing edges of a pulse waveform. Minimum pulse width high (minpwh) is measured as the interval between the rising edge of the signal crossing 50% of Vdd and the falling edge of the signal crossing 50% of Vdd. Minimum pulse width low (minpwl) is measured as the interval between the falling edge of the signal crossing 50% of Vdd and the rising edge of the signal crossing 50% of Vdd. Figure 7 illustrates minimum pulse width.

Figure 7. Minimum Pulse Width



Minimum pulse width is defined as 0.883028ns for all set/reset pins (SN, RN) and 0.883028ns for all clock pins (G, GN, CK, CKN). These are the largest minimum pulse widths measured from all the cells in the library. An input pulse of shorter duration will produce unpredictable results.

# **Electromigration**

#### min\_period Property

All sequential cells in the .lib file have this clock pin property set:

min\_period: 1.000000;

This property has the effect of limiting a design's clock frequency to 1.0GHz. Commonly used design flows may not be able to support the required accuracy for designs targeted for clock frequencies higher than this limit. Contact ARM technical support for designs targeting higher clock frequencies.

### Electromigration Guideline Compliance

Artisan standard cell libraries are designed to meet foundry electromigration guidelines for normal chip design usage; however, it is the chip designer's responsibility to ensure that electromigration guidelines are met at the chip level with regard to foundry guidelines as well as ARM's guidelines for how the library will be used. The following three Electromigration guidelines must be met in order to ensure safe use of the standard cell library within the electromigration guidelines of the foundry.

- 1. The width of the Metal1 VDD and VSS power buses in the standard cells has been sized to provide adequate current to the cells. Vertical power straps must be placed with sufficient frequency to provide adequate current distribution to the standard cell power buses. For more details, see the section entitled Power-Rail Strapping in the standard cell user guide.
- 2. The output pin metal for each standard cell has been sized to accommodate multiple vias necessary (for worst case electromigration conditions) to meet via electromigration guidelines, although oversized Metal1 output pins do not necessarily require multiple vias. The number of vias required to meet electromigration guidelines is design dependent, and the chip designer must use an appropriate number of vias and wire width when routing from an output pin.
- 3. The internal layouts of the standard cells have been designed and verified to comply with the manufacturer's electromigration guidelines under normal usage. Normal usage is defined as follows:
- The current required by the cell does not exceed the maximum current that can be supplied by the Metal1 power buses.

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• The output transition times (measured using 10% and 90% thresholds), for a cell outside the clock tree network, must be no greater than 20% of the total cycle time, or must be no greater than 10% of the cycle time for any of the output pins of that particular cell. Limiting the output transition time has the effect of limiting the load driven by the cell which will reduce the cell's current draw, making it comply with electromigration guidelines. Ratios larger than 20% are not appropriate for commonly used design flows and are unlikely to be encountered in normal designs.

• For a cell in the clock tree network, transition times must not exceed 10% of the total cycle time for that cell.

# **Power Dissipation**

The Advantage library is designed to dissipate only AC power, except for the small reverse-bias leakage currents which are normally present in all CMOS circuits.

The power dissipation internal to a cell when a given input switches is primarily dependent upon the cell design itself. The power dissipation of a complete design, or part of a design, using cells from the library is primarily a function of the switching frequency of the design's internal nets. These nets include the inputs and outputs of each cell and the capacitive load associated with the outputs of each cell.

The Advantage library datasheets contain both an AC power table which documents the internal energy consumption of each cell and a pin capacitance table which gives input-pin capacitance data used to compute output loading. This information, coupled with design-specific information, can be used to estimate the total power dissipation of a cell within a design.

The AC power tables specify the amount of energy consumed within a cell (uW/MHz) when the corresponding pin changes state at 25°C, 1.0V, and typical process. The energy data in the tables were measured for an input slew of 0.01055ns and no loading at the outputs.

For combinatorial cells, energy values are provided for only input pins. The energy value for each input pin is the average of energies associated with the input transitions which result in an output transition.

For sequential cells, the energy associated with each input pin is the average energy of those input transitions which *do not* result in an output transition. The energy associated with the output pin of a sequential cell is the average energy of all cases where an output transition is the result of a clock-input transition, minus the energy associated with the clock input pin. In the event that a sequential cell has multiple outputs, all output energy data will be associated with only one output pin.

#### **Power Calculation**

Power dissipation is dependent upon the power-supply voltage, frequency of operation, internal capacitance, and output load. The power dissipated by each cell is:

$$P_{avg} = \sum_{n=1}^{x} (E_{in} * f_{in}) + \sum_{n=1}^{y} (C_{on} * Vdd^{2} * \frac{1}{2} f_{on}) + E_{os} * f_{01}$$

where:

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 $P_{avg}$  = average power (uW);

x = number of input pins;

 $E_{in}$  = energy associated with the nth input pin (uW/MHz);

 $f_{in}$  = frequency at which the nth input pin changes state during the normal operation of the design (MHz);

y = number of output pins;

 $C_{on}$  = external capacitive loading on the nth output pin, including the capacitance of each input pin connected to the output driver, plus the route wire capacitance, actual or estimated (pF);

Vdd =operating voltage = 1.0V;

 $f_{on}$  = frequency at which the nth output pin changes state during the normal operation of the design (MHz);

 $E_{os}$  = energy associated with the output pin for sequential cells only (uW/MHz).

The switching frequency of inputs and outputs of a particular cell in a design can be obtained from a gate-level logic simulator (e.g. Verilog) by applying typical input stimuli and measuring the activity on each node of interest. The total average power for the design can be computed by adding the average power for each cell.

EXAMPLE: Calculating Power for a DFFXL Cell

For this exercise, assume that a DFFXL cell has clock switching at 133MHz (clock frequency = 66.5MHz), input and output pins switching at 20MHz, and an external capacitive loading on the output pin of 0.02pF. Using the AC Power table provided in the **sample** DFF datasheet at the end of the introduction, the power dissipated by the DFFXL can be calculated by using the following equation:

$$P_{avg} = \sum_{n=1}^{x} (E_{in} * f_{in}) + \sum_{n=1}^{y} (C_{on} * Vdd^{2} * \frac{1}{2} f_{on}) + E_{os} * f_{01}$$

Given:

$$x = 2$$
;

$$E_{i1} = 0.0056 < \text{uW/MHz};$$

$$E_{i2} = 0.0063 \text{ uW/MHz};$$

$$f_{i1} = 20 \text{ MHz};$$

# CLN65G+

$$f_{i2} = 133 \text{ MHz};$$

$$y = 2;$$

$$C_{o1} = 0.02 \text{ pF};$$

$$C_{o2} = 0.02 \text{ pF};$$

$$Vdd = 1.0V$$
;

$$f_{01} = 20 \text{ MHz};$$

$$f_{o2} = 20 \text{ MHz};$$

$$E_{os} = 0.0060 \text{ uW/MHz},$$

we have:

$$\begin{split} P_{avg} &= \sum_{n=1}^{2} (E_{in} * f_{in}) + \sum_{n=1}^{2} (C_{on} * Vdd^2 * \frac{1}{2} f_{on}) + E_{os} * f_{01} \\ P_{avg} &= (E_{i1} * f_{i1}) + (E_{i2} * f_{i2}) + (C_{o1} * VDD^2 * \frac{1}{2} f_{o1}) \\ &+ (C_{o2} * VDD^2 * \frac{1}{2} f_{o2}) + (E_{os} * f_{01}) \\ P_{avg} &= (0.0056 * 20) + (0.0063 * 133) + \left(0.02 * 1.0 * \frac{1}{2} (20)\right) \\ &+ \left(0.02 * 1.0 * \frac{1}{2} (20)\right) + (0.0060 * 20) \end{split}$$

# **Power-Rail Strapping**

 $P_{avg} = 1.46 \text{ uW}$ 

You must determine the required amount of vertical power-rail strapping to satisfy all requirements imposed by the design methodology for a given design. Power-rail strapping should be sized small enough to optimize standard cell height and maximize router efficiency, yet it must be large enough to provide sufficient power to the cells.

The guidelines below provide a rough estimate with many simplifying assumptions. For a given module design, you can estimate the amount of vertical power-rail strapping that is required to fulfill electromigration requirements.

Given:

 $I_{avg}$  = total average current for the module, calculated from previous section (mA);

 $w_{m1}$  = VSS/VDD metal1 wire width (um), see Physical Specifications;

r = number of rows in module;

 $d_{m1}$  = maximum metal1 current density allowed for the process (mA/um);

 $d_{m2}$  = maximum metal2 current density allowed for the process (mA/um);

 $I_{m1}$  = maximum current that can be supported by all horizontal metal1 wires (mA);

 $I_{strap}$  = total current that must be supported by the vertical metal2 strapping (mA);

 $w_{m2}$  = metal2 wire width required for vertical strapping (um);

c = minimum number of metal2 straps;

we have:

$$I_{m1} = w_{m1} * r * 2 * d_{m1},$$

where multiplying by 2 assumes metal1 wires are supplied from both ends;

$$I_{strap} = \frac{(I_{avg} - I_{m1})}{2},$$

where dividing by 2 assumes the metal2 vertical strap wires are supplied from both ends;

$$w_{m2} = \frac{I_{strap}}{d_{m2}},$$

It is recommended that the metal 2 wire width,  $w_{m2}$ , be divided into c equal portions which are spaced equidistant across the module, where

$$c = \frac{I_{avg}}{I_{m1}}$$
, rounded up to the next integer.

The same consideration must be given to the number of vias used to connect the metal1 and metal2 straps.

# **Adding Routing Channels**

In the Advantage library, each cell is designed with a uniform cell height of 2.0um (i.e., 10 tracks tall with 0.2um per track). The cell layouts allow neighboring rows of cells to share common power or ground rails when cells abut each other at the top and bottom edges of the cell bounding box. The sea-of-cells layout with no channels between rows will usually yield the minimum area. In case of extremely congested areas, you may want to separate some rows of cells to increase the number of routing channels within a particular layout region. Because geometries must overlap cell boundaries, a particular spacing between the rows may result in DRC violations for layer spacing. It is recommended that you do not use spacings that cause DRC violations. If these spacings must be used, the DRC violations must be fixed manually by filling the void between the rows with the appropriate layer(s).

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Table 4 indicates which DRC violations to expect and how to correct them for a separation between rows of cells.

Table 4. Correcting DRC Violations

Row Separation in Number of Grids	<b>Expected DRC Violations</b>	Action to Correct DRC Violations
0 (Rows Abut)	None	None
1	None	None
2	None	None
3	NWELL space < 0.47um	Draw NWELL layer between rows to merge NWELL regions above and below row separation
4	NWELL space < 0.47um	Draw NWELL layer between rows to merge NWELL regions above and below row separation
5 or more	None	None

# **Special Cells**

This section discusses special cells that may be included in your library.

#### **Antenna-Fix Cell**

The library contains an antenna-fix cell which must be inserted manually. However, most place and route tools will indicate which nets require the antenna-fix cell. The TSMC antenna effect prevention guideline, "TSMC 65nm CMOS Logic Design Rule Manual Version 1.2", specifies a maximum wire length. During place and route, the router may connect wires to the input gates of cells that are longer than the maximum length allowable by the guideline. The antenna cell can be used in this case to add an optional diode on the net close to the input gates which do not meet the guideline. Pin A on the antenna cell connects to a diode, reverse biased to ground. A diode can be added to either P or N.

# **Delay Cells**

The library contains delay cells that have the same width. These delay cells allow you to adjust a given delay path with a simple cell substitution after place and route.

#### **FILL Cells**

The library contains several filler cells named FILL<n>, where <n> in the cell name denotes the width of the cell in tracks.

During place and route, the FILL cells are used to connect power and ground rails across an area containing no cells. The FILL cells are also used to ensure gaps do not occur between well or implant layers which could cause design rule violations. Using wider cells where appropriate reduces the size of the layout database.

#### **FILLCAP Cells**

FILLCAPs function as FILL cells. Inside the FILLCAP, PMOS and NMOS devices form decoupling capacitors between the VDD and VSS rails, reducing ground bounce in the power grids. Figure 8 illustrates the FILLCAP functional schematic.

PMOS NMOS

Figure 8. FILLCAP Functional Schematic

# Low-Power (XL) Cells

The library contains a wide variety of cells, denoted by an "XL" suffix in the cell name, that are designed specifically for low-power applications. Input capacitance for the XL cells is much lower than that for corresponding X1 (1x drive strength) cells. Because XL cells have been designed for the sole purpose of reducing power consumption, output rise and fall times for these cells may not be equal, and due to the low-drive capability of the XL cells, these cells are not intended for use in critical timing paths, or to drive heavily loaded nets.

#### **NWELL and Substrate Tie Cell**

The library does not have well or substrate ties inside the cells. You are required to tie the NWELLS to Vdd and the substrate to Vss before place-and-route using the FILLTIE cell. Before place-and-route, pre-place the FILLTIE cell periodically in every placement row. You must place the FILLTIE cell as frequently as the design requires. For example, if the design rules require a well or substrate connection every 20um, then the FILLTIE cell must be pre-placed every 20um. See Figure 9.

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Figure 9. Sample Placement of FILLTIE Cells for 20um NWELL and Substrate Tie Design Rule

F	F F
	E
F	F
	E
F	F F

*Note:* The letter "F" indicates a FILLTIE cell placed in normal orientation, and the letter "F" flipped upside down indicates a FILLTIE cell placed in MY orientation.

In all rows except for the top and bottom rows, the NWELL and substrate are shared by two adjacent placement rows. This allows you to place the FILLTIE cell only half as frequently as the design rules require. But don't forget to stagger the placement in the adjacent rows by an amount equal to the design row.

Assuming that the rule is every 20um, you will need to place FILLTIE cells every 20um in the top and bottom rows. If you stagger the placement by 20um between adjacent rows, you can place FILLTIE cells every 40um for all rows between the top and bottom rows. This method will allow every row to have well and substrate ties every 20um.

# **Register File Cells**

Register file cells (RF\*) are provided to support creating very small memories from standard cells. The register file bit cells (RF1R1W, RF2R1W) have tri-state outputs. Users must tie these tri-state outputs together on a bit line and have this bit line drive function as an output buffer. The library contains a number of inverting and non-inverting buffers (INV\*, BUF\*, TRI\*) that can buffer the bit lines.

It is possible to make a memory that has a non-power-of-two word depth. If this is employed, it is possible to input an address to the memory such that none of the bit cells are addressed and nothing is driving the bit line. A floating bit line can cause the logic following it to go into a high power state, therefore, users must take special care when designing a memory with a non-power-of-two word depth. Users must guarantee that the bit line is never allowed to float by ensuring that at least one bit cell is always driving the bit line, or that a floating bit line does not cause subsequent logic to go into a high power state. One way to achieve the latter is to use an output buffer with an enable. NAND or AND gates or tri-state output buffers (NAND\*, AND\*, TRI\*) can be used for this purpose. Whichever is used, be sure to generate an enable signal that only enables the output buffer when the bit line is not floating.

Figure 10 shows a sample circuit for generating an enable signal when the bit line is not floating in a register file of up to 64 words.

Figure 10. Enable Signal Circuit Example if\_illegal\_a54[3] 16 if\_illegal\_a54[2] if\_illegal\_a54[1] enable **I2** if\_illegal\_a32[3] if\_illegal\_a32[2] Ι4 if\_illegal\_a32[1] a54 max legal if\_illegal\_a10[3] 13 if\_illegal\_a10[2] **I5** if\_illegal\_a10[1]

The circuit in Figure 10 assumes the address lines are pre-decoded in pairs. The circuit is a comparator. Program it with the number of words in the memory. The circuit compares the address input of the memory to the pre-programmed number of words. When the address is less than or equal to the size of the memory, it generates an enable signal for the output buffers. When the address input is higher than the number of words in the memory, the output of the comparator is false and the outputs are disabled, which prevents them from going into a high power state.

To program the example comparator, connect predecoded address lines to gates I1, I2 and I3 if the address should be larger than the size of the memory when those signals are active, and more significant address bits have not resolved the comparison. If, when those signals are active, the address should not be larger than the size of the memory, either ground that pin or reduce the number of inputs to the gate. To enable the comparison of lower address bits, connect to gates I4 and I5 signals that signify that the higher address bits have not been able to resolve the comparison. To I4, connect the signal that is true when the most significant two address bits are exactly equal to what they are in the highest address that exists in the memory. To I5, connect the signals that are true when the most significant for bits are exactly equal to what they are in the highest address that exists in the memory.

Figure 11 shows an example for a memory that has 21 words.

a32 max legal

Figure 11. 21-Word Memory Example **I**1 16 ra54[3] **I2** enable ra32[3] ra32[2] 14 ra54[2] ra10[3] 13 ra10[2] Ι5 ra10[1] ra32[1]

In binary mode, the highest address that exists in the memory is 100100. The read address RA[5:0] is pre-decoded into RA54[3:0] which are the four possible combinations of the two most significant address bits. RA32[3:0] is the four possible combinations of address bits 3 and 2. RA10[3:0] is the four possible combinations of address bits 1 and 0. If RA54[3] is true, we are accessing address 11XXXX in the memory. This address does not exist, so the comparison does not need to continue to the remaining address bits. Gate I1 needs only RA54[3] as an input because this is the only combination of these 2 address bits which is never in the memory. We connect RA54[2] to gate I4 because if this signal is true we don't know if the address exists and we have to continue the comparison to the next pair of addresses. To gate I2 we connect RA32[3] and RA32[2] because if RA54[2] is true and either of RA32[3] or RA32[2] are true, the address doesn't exist and we are done. If RA54[2] and RA32[1] are true, we are addressing word 1001XX which might be in the memory so we connect these two signals to I5 and check RA10. We connect RA10[3], RA10[2] and RA10[1] to I3 because of the memory addresses 1001XX, only 100100 exists in the memory. I6 generates the enable signal based on the results of all of the comparisons.

#### TIEHI/LO Cells

The library contains a TIEHI cell and a TIELO cell. The outputs of the TIEHI and TIELO cells are driven through diffusion to provide isolation from the power and ground rails for better ESD protection. The standard cell abstract methodology assumes that the TIEHI and TIELO cells are used to tie off any inputs to power and ground. If these cells are not used and the router is allowed to drop vias on the power rail, DRC errors or shorts may result.

# **Advantage Naming Conventions**

#### 1. Cell Name Fields

The Advantage 65 library cell name has four separate fields. They are the root, drive strength, library identifier, and threshold voltage identifier. These four components are concatenated together in the following order: [root][drive strength][library identifier][threshold voltage];

For Example:

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# SDFFQX1MA12TR

SDFFQ : root field (mux-d flop with non-inverting output)

X1M: drive strength field (1 fold output stage with an M beta ratio)
A12: library identifier field (Advantage library at a 12 track pitch)
TR: threshold voltage field (Regular or nominal threshold voltage cell)

#### BUFHX2P5BA10TL

BUFH: root field (high speed buffer)

X2P5B: drive strength field (2.5 fold output stage with a B beta ratio) A10: library identifier field (Advantage library at a 10 track pitch)

TL: threshold voltage field (low threshold voltage cell)

#### 2. Root

This portion of the cell name defines the logical function of the cell. There is a large degree of variation in this field. A full definition of the root names are provided in later sections, broken out by major function. Some examples of what this field includes are NAND2, AOI21, INV, SDFF, etc.

# 3. Drive Strength

The Advantage 65 library contains multiple beta ratios for some of the topologies. This requires a naming convention be adopted which indicates the different beta ratios. The convention is:

X[number][beta ratio letter];

The X plus the number field indicates how many folds are present. One fold is indicated by X1 while X4 indicates four folds. Think of the X as a mnemonic for multiplied by. The library also makes use of non-integer folds. This is useful for improving performance as well as reducing power consumption. When a non-integer fold is present, a P indicates the decimal place. For example, a cell that contains 1.4 folds is indicated with X1P4. If the fold size is less than one, then a zero prefixes the P. Currently, only one significant digit is used after the decimal place as it is believed this provides enough granularity.

There are many potentially useful beta ratios. Table 5 lists all the beta ratios we currently have defined. Note that since the most recent SAGE-X libraries are flood-filled and no letter was used in the SAGE-X naming convention we adopted the convention of null or no character for indicating flood-filled.

Table 5. Beta Ratio Letter Definition

Letter	Description
null	Devices are drawn at the maximum size possible regardless of topology
A	Tuned to minimize the average delay between the input edges
В	The delay for both edges are equal when the input driver is a balanced inverter
Е	The output rising and falling edge rates are equal assuming the input driver has equal rising and falling edge rates
M	Tuned to minimize the maximum delay between the input edges

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With the addition of the beta ratio indicator to the drive strength field the CLK prefix has been dropped since this prefix was really just indicating a B type beta ratio in previous SAGE-X libraries.

# 4. Library Identifier

In order to support the mixing of different libraries on a single die, all ARM libraries have a unique library identifier field. The field has two parts. The first is the library letter and the second is a number indicating the library's cell pitch in tracks. The letter A denotes an Advantage library and the letter M denotes a Metro library. A twelve-track Advantage library's identifier is A12.

# 5. Threshold Voltage

This field differentiates the different threshold voltages versions of a cell. The syntax is:

T[threshold letter]

The defined threshold letters and their meaning are provided in Table 6

Table 6. Threshold Voltage Letter Definition

Letter	Description			
Н	High Threshold Voltage			
L	Low Threshold Voltage			
R	Regular (Nominal) Threshold Voltage			

For a cell containing low threshold voltage devices, this field would be TL.

#### 6. Root Name

# **Flops**

[logic][root][clock][async][scanout][output][ppa];

logic: null, An, On, AOmn, OAmn, Mn, E

null: No logic integration

An: n-input AND (can be used for synchronous reset)

AOmn: AOI style input (can be used for synchronous set and reset with set dominant)

On: n-input OR (can be used for asynchronous set)

OAmn: OAI style input (can be used for synchronous reset and set with reset dominant)

Mn : n-input encoded mux E : mux-hold flop (enable)

root : DFF, DRFF, SDFF, SDRFF

DFF: basic master slave flop

DRFF: basic master slave flop with retention

SDFF: mux-d flop

SDRFF: mux-d flop with retention

clock: null. N

null: positive edge clock and base setup verses clock->q relationship

#### CLN65G+

N : negative edge clock and base setup verses clock->q relationship

async: null, S, R, RS, SR, P

null: no async inputs

S : async set R : async reset

RS: async reset and set with reset dominant SR: async set and reset with set dominant

P: active high

output : null, Q, QN
null : dual output flop

Q : non-inverting output flop (q) QN : inverting output flop (qn)

ppa: null

null: base flop design point with regards to power, delay, and area

# **Integrated Clock Gate**

[logic][test ovrd]ICG[clock][ppa];

logic: null

null: No logic integration

test ovrd: FR, POST, PRE

FR: free running version with no enable designed to match PRE and POST delay

POST: test over-ride input is asynchronous PRE: test over-ride input is synchronous

clock: null

null: ICG produces and active high output

ppa: null

null: base flop design point with regards to power, delay, and area

#### Latches

The naming convention for latches is basically the same as the flops convention for consistency.

[logic][root][clock][async][scanout][output][ppa];

logic : null

null: No logic integration

root:LAT

#### CLN65G+

LAT: basic transparent latch

clock: null, N

null: latch is transparent while clock is high N: latch is transparent while clock is low

**async**: null, S, R, P null: no async inputs

S : async set R : async reset P : active high

scanout: null

null: no dedicated SO pin

output: Q, QN

Q : non-inverting output flop (q) QN : inverting output flop (qn)

ppa: null

null: base flop design point with regards to power, delay, and area

# **Reading the Datasheet**

Please refer to the **sample** datasheet for DFF at the end of the introduction for the arrangement of each of the following datasheet sections. Datasheet titles reference standard Artisan cell names. Cell names for your specific library are reflected in the cell size table on each datasheet.

NOTE: This datasheet contains **sample** characterization values.

#### 1. Base Cell Name

The cell name field contains the cell name. The datasheets are presented alphabetically by cell name. The cell name presented here is the base cell name. The Cell Size table displays cell names for your specific library.

#### 2. Cell Description

The cell description gives the function of the cell. When applicable, the equation(s) for the output pins are provided.

#### 3. Functions

The function table gives all possible combinations of input and output signals for the cell. Table 7 defines the symbols used in datasheet function tables.

Table 7. Functions Key

Symbol	Description				
0	Logic Low				
1	Logic High				
	High to Low Transition				
	Low to High Transition				
X	Don't Care				
IL	Illegal/Undefined				
Z	High Impedance				

# 4. Logic Symbol

The logic symbol is a graphical representation of the cell, similar to the view in the schematic editor when the cell is instantiated. The symbol shows the name and location of the input and output pins.

#### 5. Cell Size

This cell size table gives the height and width (µm) for each drive strength of the cell.

### 6. Functional Schematic

The functional schematic provides a functional representation of the cell.

# 7. Drive Strength

The drive strength of each cell is indicated by an "X" followed by the unit strength.

#### 8. AC Power

The AC power table shows the amount of energy consumed ( $\mu$ W/MHz) within the cell when the corresponding pin changes state. The energy data for each drive strength of the cell in the **sample** DFF datasheet are calculated at 25°C, 1.0V, typical process, input slew of 0.01055ns, and no external load at the output pins.

# 9. Delay

The delay table shows the intrinsic delay (ns) which is the delay through the cell when there is no load on the output, and the load multiplier for load dependent delay,  $K_{load}$  (ns/pF). The delays and load multiplier for each drive strength of the cell in the sample DFF datasheet are calculated at 25°C, 1.0V, typical process, and input slew of 0.01055ns.

# **10. Timing Constraints**

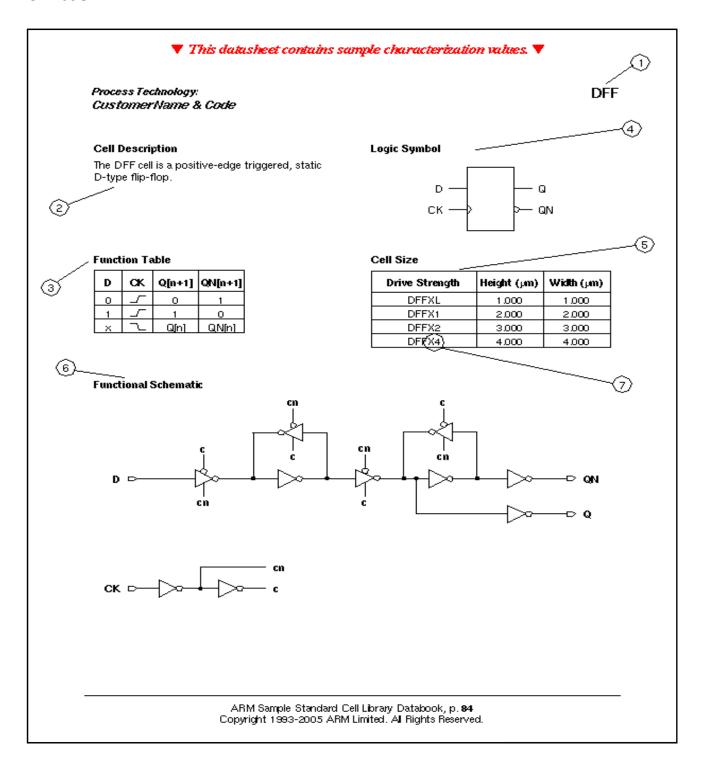
The timing constraints table in the **sample** DFF datasheet shows the timing conditions (ns) required at 25°C, 1.0V, and typical process to maintain proper functionality. Setup constraint values are measured for 0.01055ns data slew and 0.01055ns clock slew. Hold constraint values are measured for 0.01055ns data slew and 0.01055ns clock slew. Minimum pulse width is defined to be 0.883028ns for all set/reset pins and 0.883028ns for all clock pins. These are the largest minimum pulse widths measured from all the cells in the library.

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11. Pin Capacitance
The pin capacitance table shows the typical loading at the input pins of the cell (pF) for each drive strength of the cell.

Introduction

Process Technology:

### CLN65G+



# ▼ This datasheet contains sample characterization values. ▼

Process Technology: CustomerName & Code DFF

(II)

AC Power

_	De.	W/MHz)			
(Z)—	Pin	×	X1	Χ2	X4
	D	1.000	1.000	1.000	1,000
	CK	2.000	2.000	2.000	2,000
	Q	3.000	3.000	3.000	3,000

# Pin Capacitance

De	Capacitance (pF)					
Pin	ЖL	X1	X2	X4		
D	1.000	1.000	1.000	1.000		
CK	2.000	2.000	2.000	2.000		

### Delays at TypTemp°C, TypVoltV, Typical Process

			Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)			
9	Description	ЖL	X1	X2	X4	ХL	X1	X2	X4
	CK → Q↑	1.000	1.000	1.000	1.000	1.000	1.000	1.000	1.000
	CK → Q↓	2.000	2.000	2.000	2,000	2.000	2.000	2.000	2.000
	CK → QN↑	3.000	3.000	3.000	3,000	3.000	3.000	3.000	3.000
	$CK \rightarrow QNJ$	4.000	4.000	4.000	4,000	4.000	4.000	4.000	4.000

#### Timing Constraints at TypTemp°C, TypVoltV, Typical Process

Pin	D	interval (ns)			
	Requirement	ЖL	X1	X2	X4
	se <b>t</b> up↑ → CK	1.000	1.000	1.000	1,000
D	setup↓ → CK	2.000	2.000	2.000	2,000
	hold↑ → CK	3.000	3.000	3.000	3,000
	hold↓ → CK	4.000	4.000	4.000	4.000
СК	minpwh	5.000	5.000	5.000	5,000
	minpwh	6.000	6.000	6.000	6,000

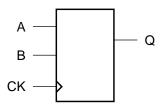
ARM Sample Standard Cell Library Databook, p. **85** Copyright 1993-2005 ARM Limited. A**I** Rights Reserved.

# CLN65G+

#### **Cell Description**

The A2DFFQ cell is a positive-edge triggered, static D-type flip-flop. It provides the logical AND of two inputs (A, B) and has a single output (Q). The cell supports integrated synchronous reset.

# **Logic Symbol**



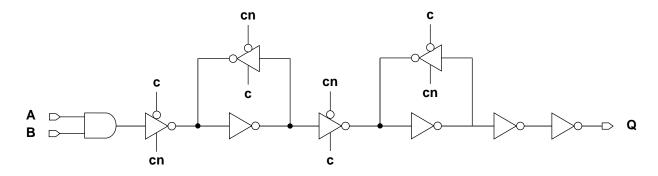
#### **Function Table**

Α	В	CK	Q[n+1]
0	0		0
0	1		0
1	0		0
1	1		1
Х	Х	_	Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
A2DFFQX0P5MA10TR	2.00	4.40
A2DFFQX1MA10TR	2.00	4.40
A2DFFQX2MA10TR	2.00	4.60
A2DFFQX3MA10TR	2.00	5.00
A2DFFQX4MA10TR	2.00	5.60

#### **Functional Schematic**



Pin	Power (uW/MHz)										
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M						
Α	0.0041	0.0052	0.0065	0.0071	0.0074						
CK	0.0037	0.0042	0.0048	0.0054	0.0058						
В	0.0044	0.0056	0.0071	0.0077	0.0080						
Q	0.0030	0.0040	0.0058	0.0079	0.0106						

## Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
Α	0.0012	0.0014	0.0018	0.0018	0.0018				
CK	0.0010	0.0010	0.0011	0.0011	0.0012				
В	0.0011	0.0013	0.0017	0.0017	0.0017				

### Delays at 25°C,1.0V, Typical Process

Description		Intri	nsic Delay	(ns)	
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
CK → Q ↑	0.0914	0.0795	0.0773	0.0757	0.0728
$CK \ \to \ Q \ \downarrow$	0.1029	0.0862	0.0841	0.0825	0.0784

Description		K <sub>load</sub> (ns/pF)							
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
CK → Q ↑	4.1712	2.3340	1.1622	0.7832	0.5830				
$CK \ \to \ Q \ \downarrow$	2.4962	1.3334	0.6611	0.4571	0.3321				

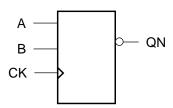
# Timing Constraints at 25°C,1.0V, Typical Process

Pin	Requirement					Interval (ns)					
F 1111	Nequirement			X0P5M	X1P0M	X2P0M	X3P0M	X4P0M			
	setup	$\uparrow$	$\rightarrow$	CK	0.0273	0.0273	0.0234	0.0273	0.0312		
Α	setup	$\downarrow$	$\rightarrow$	CK	0.0273	0.0234	0.0156	0.0195	0.0234		
_ ^	hold	$\uparrow$	$\rightarrow$	CK	-0.0117	-0.0117	-0.0117	-0.0117	-0.0117		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0039	0.0000	0.0039	0.0000	0.0000		
СК	ı	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830		
CIX		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830		
	setup	$\uparrow$	$\rightarrow$	CK	0.0273	0.0273	0.0273	0.0273	0.0312		
В	setup	$\downarrow$	$\rightarrow$	CK	0.0352	0.0273	0.0195	0.0234	0.0273		
В	hold	$\uparrow$	$\rightarrow$	CK	-0.0117	-0.0156	-0.0117	-0.0156	-0.0156		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0078	-0.0039	0.0000	-0.0039	-0.0039		

### **Cell Description**

The A2DFFQN cell is a positive-edge triggered, static D-type flip-flop. It provides the logical AND of two inputs (A, B) and has a single output (QN). The cell supports synchronous reset.

## **Logic Symbol**

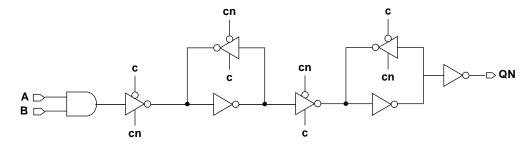


### **Function Table**

Α	В	CK	QN[n+1]
0	0		1
0	1		1
1	0		1
1	1		0
Х	Х	_	QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
A2DFFQNX0P5MA10TR	2.00	4.40
A2DFFQNX1MA10TR	2.00	4.40
A2DFFQNX2MA10TR	2.00	4.60
A2DFFQNX3MA10TR	2.00	5.00



Pin	Power (uW/MHz)									
F	X0P5M	X1P0M	X2P0M	X3P0M						
Α	0.0039	0.0053	0.0064	0.0072						
CK	0.0036	0.0041	0.0047	0.0056						
В	0.0041	0.0058	0.0069	0.0078						
QN	0.0033	0.0038	0.0057	0.0078						

## Pin Capacitance

Pin	Capacitance (pF)							
F 111	X0P5M	X1P0M	X2P0M	X3P0M				
Α	0.0011	0.0014	0.0017	0.0017				
CK	0.0010	0.0010	0.0011	0.0012				
В	0.0010	0.0013	0.0016	0.0016				

## Delays at 25°C,1.0V, Typical Process

Description	K <sub>load</sub> (ns/pF)							
	X0P5M	X0P5M X1P0M X2P0M X3P0I				X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0882	0.0746	0.0733	0.0660	4.2503	2.3523	1.1737	0.7974
$CK \to QN \downarrow$	0.0870	0.0741	0.0772	0.0727	2.8914	1.5234	0.7653	0.5107

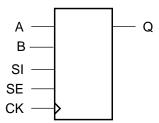
## Timing Constraints at 25°C,1.0V, Typical Process

Pin	Requirement					Interv	al (ns)	
· · · ·					X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0312	0.0273	0.0273	0.0312
Α	setup	$\downarrow$	$\rightarrow$	CK	0.0273	0.0234	0.0234	0.0273
_ ^	hold	$\uparrow$	$\rightarrow$	CK	-0.0156	-0.0117	-0.0117	-0.0117
	hold	$\downarrow$	$\rightarrow$	CK	0.0000	0.0000	0.0000	-0.0039
СК	ا	minp	wh		0.8830	0.8830	0.8830	0.8830
CK		minp	owl		0.8830	0.8830	0.8830	0.8830
	setup	$\uparrow$	$\rightarrow$	CK	0.0352	0.0312	0.0273	0.0312
В	setup	$\downarrow$	$\rightarrow$	CK	0.0312	0.0312	0.0273	0.0352
	hold	$\uparrow$	$\rightarrow$	CK	-0.0156	-0.0156	-0.0117	-0.0117
	hold	$\downarrow$	$\rightarrow$	CK	-0.0039	-0.0039	-0.0039	-0.0078

### **Cell Description**

The A2SDFFQ cell is a positive-edge triggered, static D-type flip-flop with scan input (SI) and active-high scan enable (SE). The cell performs a logical AND of two inputs (A, B) and produces a single output (Q). The cell supports integrated synchronous reset.

## **Logic Symbol**



### **Function Table**

Α	В	S	SE	CK	Q[n+1]
0	0	Х	0		0
0	1	Х	0		0
1	0	Х	0		0
1	1	Х	0		1
Х	Х	Х	Х	_	Q[n]
Х	Х	0	1		0
Х	Х	1	1		1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
A2SDFFQX0P5MA10TR	2.00	5.40
A2SDFFQX1MA10TR	2.00	5.80
A2SDFFQX2MA10TR	2.00	6.00
A2SDFFQX3MA10TR	2.00	6.20
A2SDFFQX4MA10TR	2.00	7.00

Pin	Power (uW/MHz)									
F 1111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
SI	0.0057	0.0074	0.0090	0.0102	0.0105					
SE	0.0056	0.0068	0.0079	0.0087	0.0090					
Α	0.0048	0.0063	0.0075	0.0082	0.0086					
CK	0.0036	0.0042	0.0048	0.0053	0.0056					
В	0.0052	0.0070	0.0082	0.0089	0.0093					
Q	0.0032	0.0042	0.0061	0.0081	0.0106					

## Pin Capacitance

Pin	Capacitance (pF)									
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
SI	0.0007	0.0007	0.0007	0.0007	0.0007					
SE	0.0021	0.0023	0.0024	0.0024	0.0024					
Α	0.0008	0.0010	0.0011	0.0011	0.0011					
CK	0.0009	0.0010	0.0011	0.0012	0.0012					
В	0.0012	0.0016	0.0017	0.0017	0.0017					

## Delays at 25°C,1.0V, Typical Process

Description		Intri	nsic Delay	(ns)		
	X0P5M X1P0M X2P0M X3P0M X4P					
$CK \to Q \uparrow$	0.0910	0.0786	0.0769	0.0755	0.0715	
$CK \to Q \downarrow$	0.1024	0.0859	0.0830	0.0842	0.0775	

Description	K <sub>load</sub> (ns/pF)							
	X0P5M	X0P5M X1P0M X2P0M X3P0M X4P0M						
$CK \to Q \uparrow$	4.1933	2.3366	1.1633	0.7840	0.5833			
$CK \ \to \ Q \ \downarrow$	2.4784	1.3393	0.6627	0.4585	0.3323			

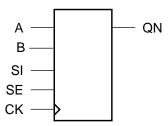
## Timing Constraints at 25°C,1.0V, Typical Process

Pin	Dos	Requirement				lı	nterval (ns	s)	
Pin	Requirement				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0859	0.0938	0.1094	0.1133	0.1172
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1211	0.1172	0.1289	0.1445	0.1484
Si	hold	$\uparrow$	$\rightarrow$	CK	-0.0547	-0.0664	-0.0742	-0.0781	-0.0742
	hold	$\downarrow$	$\rightarrow$	CK	-0.0625	-0.0586	-0.0664	-0.0781	-0.0703
	setup	$\uparrow$	$\rightarrow$	CK	0.1484	0.1523	0.1719	0.1836	0.1875
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0820	0.0586	0.0625	0.0625	0.0664
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0547	-0.0625	-0.0742	-0.0742	-0.0742
	hold	$\downarrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0195	-0.0234	-0.0234
	setup	$\uparrow$	$\rightarrow$	CK	0.0586	0.0312	0.0312	0.0352	0.0391
Α	setup	$\downarrow$	$\rightarrow$	CK	0.0586	0.0391	0.0391	0.0469	0.0508
_ ^	hold	$\uparrow$	$\rightarrow$	CK	-0.0352	-0.0156	-0.0195	-0.0195	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0273	-0.0156	-0.0156	-0.0195	-0.0195
СК	r	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830
OIX	1	minpwl		0.8830	0.8830	0.8830	0.8830	0.8830	
	setup	$\uparrow$	$\rightarrow$	CK	0.0586	0.0352	0.0352	0.0391	0.0430
В	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0469	0.0430	0.0508	0.0547
	hold	$\uparrow$	$\rightarrow$	CK	-0.0352	-0.0195	-0.0195	-0.0234	-0.0234
	hold	$\downarrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0195	-0.0234	-0.0234

### **Cell Description**

The A2SDFFQN cell is a positive-edge triggered, static D-type flip-flop with scan input (SI) and active-high scan enable (SE). The cell performs a logical AND of two inputs (A, B) and produces a single output (QN). The cell supports integrated synchronous reset.

### **Logic Symbol**

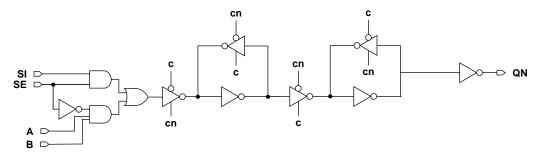


### **Function Table**

Α	В	SI	SE	СК
0	0	Х	0	
0	1	Х	0	
1	0	Х	0	
1	1	Х	0	\
Х	Х	Х	Х	_
Х	Х	0	1	
Х	Х	1	1	

### **Cell Size**

Drive Strength	Height (um)	Width (um)
A2SDFFQNX0P5MA10TR	2.00	5.40
A2SDFFQNX1MA10TR	2.00	5.80
A2SDFFQNX2MA10TR	2.00	6.00
A2SDFFQNX3MA10TR	2.00	6.20



Pin	Power (uW/MHz)									
• •••	X0P5M	X1P0M	X2P0M	X3P0M						
SI	0.0057	0.0075	0.0089	0.0102						
SE	0.0056	0.0067	0.0077	0.0084						
Α	0.0048	0.0063	0.0074	0.0083						
CK	0.0035	0.0041	0.0047	0.0056						
В	0.0052	0.0068	0.0081	0.0090						
QN	0.0033	0.0040	0.0062	0.0079						

## Pin Capacitance

Pin	Capacitance (pF)									
F	X0P5M	X1P0M	X2P0M	X3P0M						
SI	0.0006	0.0007	0.0007	0.0007						
SE	0.0021	0.0023	0.0024	0.0024						
Α	0.0008	0.0010	0.0012	0.0012						
CK	0.0009	0.0010	0.0011	0.0012						
В	0.0012	0.0015	0.0017	0.0017						

## Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns) K <sub>load</sub> (ns/pF)							
	X0P5M X1P0M X2P0M X3P0M				X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0871	0.0737	0.0739	0.0678	4.2418	2.3515	1.1685	0.7929
$CK \to QN \downarrow$	0.0877	0.0877				1.5299	0.7666	0.5272

**A2SDFFQN** 

## Timing Constraints at 25°C,1.0V, Typical Process

Pin	Por	ir	omor	·+		Interv	al (ns)	
FIII	Requirement			X0P5M	X1P0M	X2P0M	X3P0M	
	setup	$\uparrow$	$\rightarrow$	CK	0.0859	0.0977	0.1094	0.1211
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1250	0.1172	0.1328	0.1484
SI	hold	$\uparrow$	$\rightarrow$	CK	-0.0547	-0.0625	-0.0703	-0.0703
	hold	$\downarrow$	$\rightarrow$	CK	-0.0586	-0.0547	-0.0625	-0.0625
	setup	$\uparrow$	$\rightarrow$	CK	0.1523	0.1484	0.1719	0.1836
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0859	0.0625	0.0625	0.0664
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0508	-0.0625	-0.0703	-0.0703
	hold	$\downarrow$	$\rightarrow$	CK	-0.0234	-0.0156	-0.0156	-0.0195
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0352	0.0352	0.0391
_	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0430	0.0391	0.0469
Α	hold	$\uparrow$	$\rightarrow$	CK	-0.0352	-0.0195	-0.0156	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0234	-0.0156	-0.0117	-0.0156
СК	ı	minp	wh		0.8830	0.8830	0.8830	0.8830
CK		minp	owl		0.8830	0.8830	0.8830	0.8830
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0391	0.0352	0.0430
В	setup	$\downarrow$	$\rightarrow$	CK	0.0664	0.0469	0.0469	0.0508
	hold	$\uparrow$	$\rightarrow$	CK	-0.0391	-0.0234	-0.0195	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0156	-0.0195

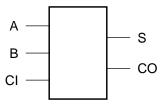
## **Cell Description**

The ADDF cell provides the arithmetic sum (S) and carry out (CO) of two operands (A,B) with carry in (CI). The two outputs (S,CO) are represented by the logic equations:

 $S=(A\oplus B\oplus CI)$ 

 $CO = (A \oplus B) \bullet CI + (A \bullet B)$ 

### **Logic Symbol**

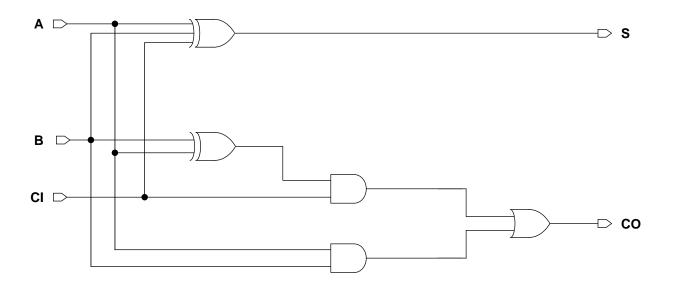


### **Function Table**

CI	Α	В	S	СО
0	0	0	0	0
0	0	1	1	0
0	1	0	1	0
0	1	1	0	1
1	0	0	1	0
1	0	1	0	1
1	1	0	0	1
1	1	1	1	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
ADDFX1MA10TR	2.00	4.20
ADDFX1P4MA10TR	2.00	4.80
ADDFX2MA10TR	2.00	4.80



Pin	Power (uW/MHz)				
• •••	X1P0M	X1P4M	X2P0M		
Α	0.0113	0.0133	0.0154		
В	0.0118	0.0138	0.0159		
CI	0.0102	0.0123	0.0143		

## Pin Capacitance

Pin	Capacitance (pF)				
F 111	X1P0M	X1P4M	X2P0M		
Α	0.0049	0.0049	0.0049		
В	0.0052	0.0052	0.0052		
CI	0.0038	0.0038	0.0038		

## Delays at 25°C,1.0V, Typical Process

C	Description			Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)		
				X1P0M	X1P4M	X2P0M	X1P0M	X1P4M	X2P0M
Α	$\rightarrow$	S	$\uparrow$	0.0872	0.1003	0.1097	2.3682	1.6215	1.1720
Α	$\rightarrow$	S	$\downarrow$	0.0888	0.1010	0.1118	1.5232	1.0525	0.7557
В	$\rightarrow$	S	<b>↑</b>	0.0876	0.1003	0.1100	2.3683	1.6221	1.1720
В	$\rightarrow$	S	$\downarrow$	0.0912	0.1013	0.1118	1.5573	1.0881	0.7816
CI	$\rightarrow$	S	$\uparrow$	0.0796	0.0933	0.1012	2.3681	1.6214	1.1709
CI	$\rightarrow$	S	$\downarrow$	0.0857	0.0974	0.1068	1.5516	1.0746	0.7775
Α	$\rightarrow$	CO	$\uparrow$	0.0501	0.0543	0.0571	2.4289	1.6585	1.1950
Α	$\rightarrow$	CO	$\downarrow$	0.0600	0.0646	0.0690	1.5991	1.0553	0.7692
В	$\rightarrow$	CO	$\uparrow$	0.0486	0.0527	0.0555	2.4284	1.6581	1.1948
В	$\rightarrow$	CO	$\downarrow$	0.0600	0.0646	0.0690	1.5985	1.0550	0.7690
CI	$\rightarrow$	СО	$\uparrow$	0.0421	0.0459	0.0486	2.4174	1.6494	1.1884
CI	$\rightarrow$	СО	$\downarrow$	0.0522	0.0570	0.0607	1.5981	1.0598	0.7669

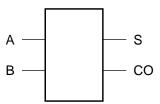
### **Cell Description**

The ADDH cell provides the arithmetic sum (S) and carry out (CO) of two operands (A,B). The two outputs (S,CO) are represented by the logic equations:

$$S = (\overline{A} \bullet B) + (A \bullet \overline{B})$$

$$CO = A \bullet B$$

### **Logic Symbol**

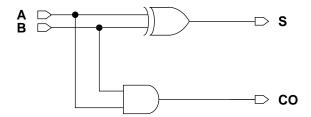


### **Function Table**

Α	В	S	СО
0	0	0	0
0	1	1	0
1	0	1	0
1	1	0	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
ADDHX1MA10TR	2.00	2.60
ADDHX1P4MA10TR	2.00	3.20
ADDHX2MA10TR	2.00	3.20



Pin	Power (uW/MHz)				
' '''	X1P0M	X1P4M	X2P0M		
Α	0.0078	0.0105	0.0121		
В	0.0082	0.0111	0.0128		

## Pin Capacitance

Pin	Сар	Capacitance (pF)			
• •••	X1P0M	X2P0M			
Α	0.0024	0.0030	0.0030		
В	0.0025	0.0031	0.0032		

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)				
				X1P0M	X1P4M	X2P0M	X1P0M	X1P4M	X2P0M
Α	$\rightarrow$	S	$\uparrow$	0.0549	0.0528	0.0583	2.4100	1.6435	1.1762
Α	$\rightarrow$	S	$\rightarrow$	0.0620	0.0603	0.0676	1.4839	1.0280	0.7174
В	$\rightarrow$	S	$\uparrow$	0.0553	0.0548	0.0589	2.4086	1.6426	1.1756
В	$\rightarrow$	S	$\downarrow$	0.0634	0.0618	0.0690	1.4849	1.0290	0.7179
Α	$\rightarrow$	СО	$\uparrow$	0.0356	0.0337	0.0362	2.4865	1.6397	1.1867
Α	$\rightarrow$	СО	$\downarrow$	0.0329	0.0312	0.0335	1.4798	1.0034	0.7127
В	$\rightarrow$	СО	$\uparrow$	0.0369	0.0351	0.0377	2.4857	1.6396	1.1866
В	$\rightarrow$	СО	$\downarrow$	0.0350	0.0346	0.0356	1.4817	1.0067	0.7138

### **Cell Description**

The AND2 cell provides the logical AND of two inputs (A,B). The output (Y) is represented by the logic equation:

$$Y = (A \bullet B)$$

## **Logic Symbol**



#### **Function Table**

Α	В	Υ
0	Х	0
Х	0	0
1	1	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
AND2X0P5MA10TR	2.00	1.20
AND2X0P7MA10TR	2.00	1.20
AND2X1MA10TR	2.00	1.20
AND2X1P4MA10TR	2.00	1.40
AND2X2MA10TR	2.00	1.40
AND2X3MA10TR	2.00	2.20
AND2X4MA10TR	2.00	2.40
AND2X6MA10TR	2.00	3.40
AND2X8MA10TR	2.00	4.60
AND2X11MA10TR	2.00	6.40



### **AC Power**

Pin				Power (u	ıW/MHz)			
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
Α	0.0005	0.0006	0.0007	0.0009	0.0012	0.0019	0.0024	0.0037
В	0.0005	0.0005	0.0006	0.0009	0.0011	0.0018	0.0023	0.0035

## AC Power (Cont'd.)

Pin	Power (uW/MHz)					
	X8P0M	X11P0M				
Α	0.0049	0.0070				
В	0.0047	0.0067				

## Pin Capacitance

Pin				Capacita	nce (pF)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
Α	0.0009	0.0010	0.0011	0.0014	0.0017	0.0028	0.0033	0.0052
В	0.0009	0.0010	0.0011	0.0014	0.0017	0.0028	0.0033	0.0049

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)					
F 111	X8P0M	X11P0M				
Α	0.0067	0.0098				
В	0.0066	0.0094				

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	
$A \rightarrow Y \uparrow$	0.0343	0.0321	0.0303	0.0296	0.0280	0.0276	0.0267	0.0270	
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.0367	0.0353	0.0344	0.0347	0.0335	0.0324	0.0316	0.0318	
$B \to Y \uparrow$	0.0360	0.0338	0.0318	0.0310	0.0293	0.0288	0.0279	0.0281	
$B \to Y \downarrow$	0.0396	0.0377	0.0370	0.0372	0.0359	0.0350	0.0345	0.0344	

AND2

CLN65G+

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description				Intrinsic Delay (ns)				
				X8P0M	X11P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.0264	0.0266			
Α	$\rightarrow$	Υ	$\downarrow$	0.0309	0.0315			
В	$\rightarrow$	Υ	$\uparrow$	0.0276	0.0278			
В	$\rightarrow$	Υ	$\downarrow$	0.0339	0.0343			

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	ptic	n	K <sub>load</sub> (ns/pF)							
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
Α	$\rightarrow$	Υ	$\uparrow$	4.6154	3.3732	2.4273	1.6527	1.1803	0.8009	0.5841	0.3888
Α	$\rightarrow$	Υ	$\downarrow$	2.8042	2.0497	1.4480	1.0154	0.7014	0.4856	0.3540	0.2368
В	$\rightarrow$	Υ	<b>↑</b>	4.6151	3.3728	2.4267	1.6524	1.1802	0.8009	0.5841	0.3888
В	$\rightarrow$	Υ	$\downarrow$	2.8079	2.0518	1.4495	1.0166	0.7024	0.4863	0.3547	0.2372

Description				K <sub>load</sub> (	ns/pF)
				X8P0M	X11P0M
Α	$\rightarrow$	Υ	$\uparrow$	0.2895	0.2096
Α	$\rightarrow$	Υ	$\downarrow$	0.1778	0.1303
В	$\rightarrow$	Υ	<b>↑</b>	0.2895	0.2096
В	$\rightarrow$	Υ	$\downarrow$	0.1781	0.1306

### **Cell Description**

The AND3 cell provides the logical AND of three inputs (A,B,C). The output (Y) is represented by the logic equation:

 $Y = (A \bullet B \bullet C)$ 

## **Logic Symbol**



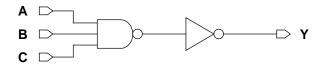
AND3

### **Function Table**

Α	В	С	Υ
0	Х	Х	0
Х	0	Х	0
Х	Х	0	0
1	1	1	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AND3X0P5MA10TR	2.00	1.40
AND3X0P7MA10TR	2.00	1.40
AND3X1MA10TR	2.00	1.40
AND3X1P4MA10TR	2.00	1.80
AND3X2MA10TR	2.00	2.20
AND3X3MA10TR	2.00	3.00
AND3X4MA10TR	2.00	4.00
AND3X6MA10TR	2.00	6.00
AND3X8MA10TR	2.00	7.00
AND3X11MA10TR	2.00	9.40



### **AC Power**

Pin	Power (uW/MHz)							
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
Α	0.0006	0.0007	0.0008	0.0010	0.0014	0.0023	0.0029	0.0042
В	0.0005	0.0005	0.0007	0.0009	0.0011	0.0018	0.0024	0.0035
С	0.0004	0.0005	0.0007	0.0009	0.0013	0.0020	0.0024	0.0035

## AC Power (Cont'd.)

Pin	Power (uW/MHz)					
F 1111	X8P0M	X11P0M				
Α	0.0055	0.0078				
В	0.0047	0.0066				
С	0.0047	0.0066				

# Pin Capacitance

Pin		Capacitance (pF)											
F 1111	X0P5M	X0P7M	X1P0M X1P4M		X2P0M	X3P0M	X4P0M	X6P0M					
Α	0.0011	0.0013	0.0014	0.0018	0.0025	0.0040	0.0046	0.0065					
В	0.0011	0.0012	0.0014	0.0017	0.0023	0.0036	0.0045	0.0063					
С	0.0010	0.0011	0.0014	0.0018	0.0027	0.0038	0.0044	0.0064					

## Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)						
FIII	X8P0M	<b>X11P0M</b> 0.0119 0.0116					
Α	0.0084	0.0119					
В	0.0082	0.0116					
С	0.0082	0.0116					

## Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
$A \rightarrow Y \uparrow$	0.0358	0.0350	0.0334	0.0327	0.0298	0.0323	0.0290	0.0279		
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.0363	0.0368	0.0365	0.0361	0.0335	0.0346	0.0333	0.0324		
$B \to Y \uparrow$	0.0384	0.0374	0.0361	0.0355	0.0323	0.0345	0.0328	0.0319		
$B \to Y \downarrow$	0.0395	0.0399	0.0398	0.0397	0.0372	0.0380	0.0387	0.0382		
$C \rightarrow Y \uparrow$	0.0396	0.0385	0.0377	0.0369	0.0342	0.0363	0.0346	0.0339		
$C \rightarrow Y \downarrow$	0.0426	0.0428	0.0430	0.0429	0.0412	0.0419	0.0440	0.0433		

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	iptic	n	Intrinsic Delay (ns)				
				X8P0M	X11P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.0279	0.0278			
Α	$\rightarrow$	Υ	$\downarrow$	0.0326	0.0322			
В	$\rightarrow$	Υ	$\uparrow$	0.0315	0.0314			
В	$\rightarrow$	Υ	$\downarrow$	0.0380	0.0376			
С	$\rightarrow$	Υ	$\uparrow$	0.0333	0.0332			
С	$\rightarrow$	Υ	$\downarrow$	0.0431	0.0427			

Description	K <sub>load</sub> (ns/pF)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M			
$A \rightarrow Y \uparrow$	4.5833	3.3428	2.5914	1.6630	1.1924	0.8033	0.5829	0.3876			
$A \rightarrow Y \downarrow$	2.7715	2.0225	1.4391	0.9875	0.6993	0.4894	0.3594	0.2403			
$B \to Y \uparrow$	4.5825	3.3421	2.5907	1.6630	1.1923	0.8033	0.5829	0.3876			
$B \to Y \downarrow$	2.7787	2.0277	1.4423	0.9899	0.7014	0.4907	0.3608	0.2413			
$C \rightarrow Y \uparrow$	4.5799	3.3403	2.5899	1.6627	1.1922	0.8032	0.5829	0.3876			
$C \rightarrow Y \downarrow$	2.7861	2.0330	1.4459	0.9928	0.7036	0.4922	0.3630	0.2427			

Process Technology:

CLN65G+

AND3

D	escri	iptic	n	K <sub>load</sub> (ns/pF)				
				X8P0M	X11P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.2895	0.2109			
Α	$\rightarrow$	Υ	$\downarrow$	0.1804	0.1325			
В	$\rightarrow$	Υ	$\uparrow$	0.2895	0.2109			
В	$\rightarrow$	Υ	$\downarrow$	0.1812	0.1330			
С	$\rightarrow$	Υ	<b>↑</b>	0.2895	0.2109			
С	$\rightarrow$	Υ	$\downarrow$	0.1821	0.1337			

### **Cell Description**

The AND4 cell provides the logical AND of four inputs (A,B,C,D). The output (Y) is represented by the logic equation:

 $Y = (A \bullet B \bullet C \bullet D)$ 

## **Logic Symbol**



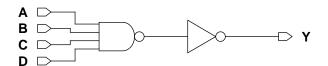
AND4

### **Function Table**

Α	В	С	D	Υ
0	Х	Х	Х	0
Х	0	Х	Х	0
Х	Х	0	Х	0
Х	Х	Х	0	0
1	1	1	1	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AND4X0P5MA10TR	2.00	1.60
AND4X0P7MA10TR	2.00	1.60
AND4X1MA10TR	2.00	2.00
AND4X1P4MA10TR	2.00	3.00
AND4X2MA10TR	2.00	4.20
AND4X3MA10TR	2.00	4.80
AND4X4MA10TR	2.00	6.40
AND4X6MA10TR	2.00	7.80
AND4X8MA10TR	2.00	9.60



Pin		Power (uW/MHz)													
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M						
Α	0.0006	0.0007	0.0009	0.0013	0.0020	0.0025	0.0034	0.0049	0.0065						
В	0.0005	0.0006	0.0007	0.0010	0.0015	0.0020	0.0027	0.0039	0.0052						
С	0.0005	0.0006	0.0007	0.0011	0.0014	0.0019	0.0027	0.0039	0.0052						
D	0.0006	0.0006	0.0007	0.0013	0.0014	0.0019	0.0026	0.0039	0.0052						

## Pin Capacitance

Pin		Capacitance (pF)												
	X0P5M X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M						
Α	0.0014	0.0015	0.0017	0.0026	0.0036	0.0045	0.0060	0.0084	0.0111					
В	0.0013	0.0014	0.0016	0.0025	0.0035	0.0043	0.0058	0.0083	0.0109					
С	0.0013	0.0014	0.0016	0.0028	0.0035	0.0043	0.0058	0.0082	0.0109					
D	0.0014	0.0015	0.0017	0.0030	0.0034	0.0042	0.0060	0.0081	0.0108					

## Delays at 25°C,1.0V, Typical Process

D	escr	iptic	n		Intrinsic Delay (ns)										
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.0386	0.0372	0.0349	0.0343	0.0318	0.0303	0.0306	0.0298	0.0299			
Α	$\rightarrow$	Υ	$\downarrow$	0.0373	0.0370	0.0359	0.0342	0.0351	0.0341	0.0345	0.0332	0.0332			
В	$\rightarrow$	Υ	$\uparrow$	0.0430	0.0416	0.0392	0.0382	0.0377	0.0358	0.0367	0.0352	0.0357			
В	$\rightarrow$	Υ	$\downarrow$	0.0420	0.0418	0.0410	0.0388	0.0423	0.0411	0.0418	0.0400	0.0403			
С	$\rightarrow$	Υ	$\uparrow$	0.0460	0.0447	0.0422	0.0418	0.0414	0.0392	0.0402	0.0386	0.0390			
С	$\rightarrow$	Υ	$\downarrow$	0.0463	0.0462	0.0456	0.0442	0.0486	0.0470	0.0477	0.0458	0.0460			
D	$\rightarrow$	Υ	$\uparrow$	0.0477	0.0462	0.0438	0.0438	0.0432	0.0409	0.0420	0.0403	0.0408			
D	$\rightarrow$	Υ	$\downarrow$	0.0501	0.0500	0.0499	0.0486	0.0541	0.0521	0.0532	0.0508	0.0512			

AND4

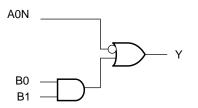
Description	K <sub>load</sub> (ns/pF)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
$A \ \rightarrow \ Y \ \uparrow$	4.7670	3.5338	2.4777	1.6395	1.1834	0.7915	0.5879	0.3895	0.2921		
$A \ \rightarrow \ Y \ \downarrow$	2.7395	1.9977	1.4581	1.0001	0.7156	0.4874	0.3612	0.2411	0.1812		
$B \ \to \ Y \ \uparrow$	4.7660	3.5333	2.4777	1.6394	1.1834	0.7916	0.5879	0.3896	0.2921		
$B \ \to \ Y \ \downarrow$	2.7487	2.0044	1.4634	1.0036	0.7193	0.4898	0.3631	0.2422	0.1821		
$C \to Y \uparrow$	4.7656	3.5326	2.4777	1.6391	1.1834	0.7915	0.5879	0.3896	0.2921		
$C \ \to \ Y \ \downarrow$	2.7589	2.0119	1.4696	1.0085	0.7244	0.4929	0.3653	0.2437	0.1832		
$D \ \to \ Y \ \uparrow$	4.7648	3.5319	2.4777	1.6389	1.1834	0.7915	0.5879	0.3896	0.2921		
$D \ \to \ Y \ \downarrow$	2.7723	2.0213	1.4774	1.0137	0.7306	0.4965	0.3683	0.2455	0.1846		

### **Cell Description**

The AO1B2 cell provides the logical inverted OR of one AND group consisting of two inputs each: (A0N) and (B0, B1). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = \overline{A0N} + (B0 \bullet B1)$$

## **Logic Symbol**

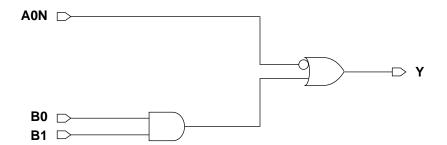


#### **Function Table**

В0	B1	A0N	Υ
х	х	0	1
1	1	Х	1
0	х	1	0
х	0	1	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
AO1B2X0P5MA10TR	2.00	1.40
AO1B2X0P7MA10TR	2.00	1.40
AO1B2X1MA10TR	2.00	1.40
AO1B2X1P4MA10TR	2.00	2.00
AO1B2X2MA10TR	2.00	2.00
AO1B2X3MA10TR	2.00	3.00
AO1B2X4MA10TR	2.00	3.40
AO1B2X6MA10TR	2.00	5.00



Pin		Power (uW/MHz)										
FIII	X0P5M	X0P7M	X1P0M	X1P0M X1P4M X2P0M		X3P0M	X4P0M	X6P0M				
В0	0.0005	0.0006	0.0006	0.0009	0.0011	0.0018	0.0021	0.0033				
B1	0.0004	0.0005	0.0006	0.0008	0.0010	0.0017	0.0021	0.0032				
A0N	0.0006	0.0007	0.0010	0.0016	0.0021	0.0031	0.0043	0.0065				

## Pin Capacitance

Pin		Capacitance (pF)										
FIII	X0P5M	X0P7M	X1P0M X1P4M X		X2P0M	X2P0M X3P0M		X6P0M				
В0	0.0009	0.0009	0.0011	0.0014	0.0016	0.0027	0.0032	0.0050				
B1	0.0008	0.0009	0.0010	0.0014	0.0016	0.0028	0.0033	0.0047				
A0N	0.0012	0.0014	0.0018	0.0030	0.0037	0.0054	0.0074	0.0111				

## Delays at 25°C,1.0V, Typical Process

De	scrip	tion	l				Intrinsic I	Delay (ns)			
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
В0	$\rightarrow$	Υ	$\uparrow$	0.0423	0.0407	0.0375	0.0388	0.0353	0.0353	0.0339	0.0346
В0	$\rightarrow$	Υ	$\downarrow$	0.0378	0.0368	0.0355	0.0360	0.0330	0.0324	0.0314	0.0318
B1	$\rightarrow$	Υ	$\uparrow$	0.0429	0.0415	0.0384	0.0402	0.0367	0.0365	0.0351	0.0356
B1	$\rightarrow$	Υ	$\downarrow$	0.0385	0.0377	0.0364	0.0374	0.0345	0.0342	0.0331	0.0334
A0N	$\rightarrow$	Υ	$\uparrow$	0.0115	0.0109	0.0103	0.0107	0.0101	0.0100	0.0100	0.0099
A0N	$\rightarrow$	Υ	$\downarrow$	0.0125	0.0119	0.0117	0.0118	0.0113	0.0111	0.0111	0.0111

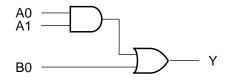
De	scrip	tion			K <sub>load</sub> (ns/pF)							
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	
В0	$\rightarrow$	Υ	$\uparrow$	4.5893	3.3576	2.4160	1.6203	1.1673	0.7727	0.5771	0.3825	
В0	$\rightarrow$	Υ	$\downarrow$	4.8721	3.5209	2.5638	1.7865	1.2652	0.8395	0.6291	0.4191	
B1	$\rightarrow$	Υ	$\uparrow$	4.5893	3.3571	2.4158	1.6201	1.1673	0.7727	0.5771	0.3825	
B1	$\rightarrow$	Υ	$\downarrow$	4.8735	3.5222	2.5641	1.7867	1.2658	0.8399	0.6291	0.4191	
AON	$\rightarrow$	Υ	$\uparrow$	4.4258	3.2339	2.3311	1.6022	1.1539	0.7634	0.5778	0.3808	
AON	$\rightarrow$	Υ	$\downarrow$	4.8617	3.5143	2.5591	1.7825	1.2634	0.8383	0.6281	0.4184	

### **Cell Description**

The AO21 cell provides the logical OR of one AND group and an additional input. The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (A0 \bullet A1) + \overline{B0}$$

## **Logic Symbol**

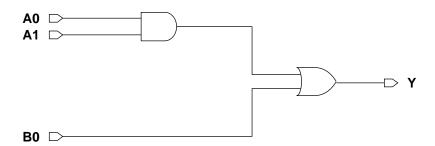


### **Function Table**

A0	<b>A</b> 1	В0	Υ
0	Х	0	0
х	0	0	0
х	х	1	1
1	1	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
AO21X0P5MA10TR	2.00	1.60
AO21X0P7MA10TR	2.00	1.60
AO21X1MA10TR	2.00	1.60
AO21X1P4MA10TR	2.00	2.60
AO21X2MA10TR	2.00	2.60
AO21X3MA10TR	2.00	3.60
AO21X4MA10TR	2.00	4.00
AO21X6MA10TR	2.00	5.60



Pin	Power (uW/MHz)										
F 1111	X0P5M	X0P7M	X1P0M	X1P4M X2P0M		X3P0M	X4P0M	X6P0M			
A0	0.0006	0.0007	0.0009	0.0012	0.0017	0.0026	0.0032	0.0049			
A1	0.0006	0.0007	0.0009	0.0012	0.0017	0.0025	0.0033	0.0049			
В0	0.0004	0.0005	0.0007	0.0010	0.0014	0.0019	0.0024	0.0037			

## Pin Capacitance

Pin	Capacitance (pF)										
F 111	X0P5M	X0P7M	X1P0M	X1P4M X2P0M		X3P0M	X4P0M	X6P0M			
A0	0.0012	0.0013	0.0016	0.0022	0.0029	0.0044	0.0052	0.0071			
A1	0.0011	0.0012	0.0015	0.0019	0.0029	0.0041	0.0048	0.0071			
В0	0.0011	0.0013	0.0015	0.0019	0.0024	0.0035	0.0044	0.0064			

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
$A0 \rightarrow Y \uparrow$	0.0380	0.0384	0.0354	0.0338	0.0316	0.0338	0.0322	0.0297		
$A0 \rightarrow Y \downarrow$	0.0451	0.0456	0.0428	0.0411	0.0404	0.0413	0.0396	0.0382		
A1 $\rightarrow$ Y $\uparrow$	0.0388	0.0393	0.0363	0.0349	0.0328	0.0346	0.0331	0.0322		
A1 $\rightarrow$ Y $\downarrow$	0.0487	0.0493	0.0464	0.0442	0.0439	0.0442	0.0427	0.0439		
$B0 \rightarrow Y \uparrow$	0.0281	0.0279	0.0263	0.0267	0.0262	0.0259	0.0256	0.0258		
$B0 \rightarrow Y \downarrow$	0.0434	0.0435	0.0408	0.0387	0.0372	0.0381	0.0375	0.0382		

Description	K <sub>load</sub> (ns/pF)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
A0 → Y ↑	4.6290	3.3738	2.4158	1.6654	1.1868	0.7902	0.5854	0.3878
$A0 \rightarrow Y \downarrow$	2.8746	2.0815	1.4604	1.0287	0.7251	0.4899	0.3616	0.2411
A1 $\rightarrow$ Y $\uparrow$	4.6288	3.3738	2.4158	1.6655	1.1868	0.7902	0.5854	0.3877
A1 $\rightarrow$ Y $\downarrow$	2.8845	2.0885	1.4652	1.0318	0.7270	0.4911	0.3626	0.2422
$B0 \rightarrow Y \uparrow$	4.6013	3.3526	2.4034	1.6579	1.1821	0.7868	0.5830	0.3868
$B0 \rightarrow Y \downarrow$	2.8846	2.0885	1.4651	1.0317	0.7269	0.4911	0.3626	0.2422

### **Cell Description**

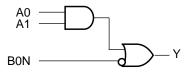
The AO21B cell provides the logical AND of two inputs (A0, A1) and the logical OR of one inverted signal (B0N). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (A0 + A1) \bullet \overline{B0N}$$

### **Function Table**

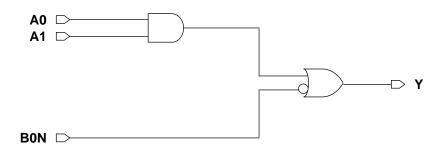
A0	<b>A</b> 1	B0N	Υ
1	1	Х	1
Х	х	0	1
Х	0	1	0
0	Х	1	0

## **Logic Symbol**



### **Cell Size**

Drive Strength	Height (um)	Width (um)
AO21BX0P5MA10TR	2.00	1.40
AO21BX0P7MA10TR	2.00	1.40
AO21BX1MA10TR	2.00	1.40
AO21BX1P4MA10TR	2.00	2.00
AO21BX2MA10TR	2.00	2.00
AO21BX3MA10TR	2.00	3.00
AO21BX4MA10TR	2.00	3.40
AO21BX6MA10TR	2.00	5.00



Pin	Power (uW/MHz)										
' '''	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M			
A0	0.0005	0.0006	0.0007	0.0010	0.0013	0.0021	0.0026	0.0040			
A1	0.0005	0.0006	0.0007	0.0010	0.0013	0.0021	0.0026	0.0038			
B0N	0.0007	0.0009	0.0011	0.0017	0.0022	0.0034	0.0045	0.0068			

## Pin Capacitance

Pin	Capacitance (pF)										
' '''	X0P5M	X0P7M	X1P0M	X1P4M X2P0M		X3P0M	X4P0M	X6P0M			
A0	0.0009	0.0010	0.0011	0.0014	0.0017	0.0027	0.0032	0.0050			
A1	0.0009	0.0010	0.0011	0.0014	0.0016	0.0028	0.0033	0.0047			
B0N	0.0013	0.0016	0.0020	0.0030	0.0037	0.0058	0.0075	0.0115			

## Delays at 25°C,1.0V, Typical Process

De	scrip	tion	l				Intrinsic I	Delay (ns)			
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
A0	$\rightarrow$	Υ	$\uparrow$	0.0426	0.0411	0.0379	0.0411	0.0377	0.0362	0.0358	0.0364
A0	$\rightarrow$	Υ	$\downarrow$	0.0371	0.0368	0.0349	0.0362	0.0338	0.0321	0.0319	0.0322
A1	$\rightarrow$	Υ	$\uparrow$	0.0440	0.0425	0.0393	0.0425	0.0390	0.0374	0.0370	0.0374
A1	$\rightarrow$	Υ	$\downarrow$	0.0384	0.0380	0.0362	0.0376	0.0351	0.0339	0.0337	0.0337
B0N	$\rightarrow$	Υ	$\uparrow$	0.0104	0.0100	0.0092	0.0092	0.0085	0.0086	0.0084	0.0084
B0N	$\rightarrow$	Υ	$\downarrow$	0.0115	0.0111	0.0100	0.0096	0.0088	0.0090	0.0087	0.0088

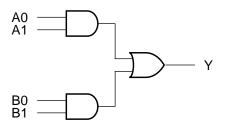
De	scrip	tion	1		K <sub>load</sub> (ns/pF)							
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	
A0	$\rightarrow$	Υ	$\uparrow$	4.4568	3.2540	2.3388	1.6116	1.1596	0.7805	0.5799	0.3822	
A0	$\rightarrow$	Υ	$\downarrow$	5.3365	3.8942	2.7685	1.7787	1.2587	0.8381	0.6282	0.4186	
A1	$\rightarrow$	Υ	$\uparrow$	4.4563	3.2537	2.3386	1.6115	1.1596	0.7805	0.5799	0.3822	
A1	$\rightarrow$	Υ	$\downarrow$	5.3361	3.8937	2.7683	1.7788	1.2586	0.8381	0.6282	0.4186	
B0N	$\rightarrow$	Υ	$\uparrow$	4.5351	3.3108	2.3788	1.6105	1.1617	0.7667	0.5740	0.3805	
B0N	$\rightarrow$	Υ	$\downarrow$	5.3274	3.8873	2.7639	1.7741	1.2555	0.8365	0.6269	0.4177	

### **Cell Description**

The AO22 cell provides the logical OR of two AND groups. The output (Y) is represented by the logic equation:

$$Y = (A0 \bullet A1) + (B0 \bullet B1)$$

## **Logic Symbol**

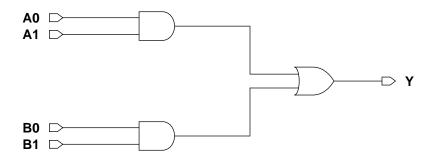


### **Function Table**

A0	<b>A</b> 1	В0	B1	Υ
0	х	0	Х	0
0	х	х	0	0
х	0	0	Х	0
Х	0	Х	0	0
х	х	1	1	1
1	1	х	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
AO22X0P5MA10TR	2.00	2.00
AO22X0P7MA10TR	2.00	2.00
AO22X1MA10TR	2.00	2.00
AO22X1P4MA10TR	2.00	3.20
AO22X2MA10TR	2.00	3.20
AO22X3MA10TR	2.00	4.40
AO22X4MA10TR	2.00	4.80
AO22X6MA10TR	2.00	7.40



Pin	Power (uW/MHz)											
' '''	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
A0	0.0006	0.0008	0.0010	0.0015	0.0020	0.0029	0.0037	0.0058				
A1	0.0007	0.0008	0.0010	0.0015	0.0019	0.0029	0.0037	0.0059				
В0	0.0002	0.0002	0.0003	0.0004	0.0006	0.0009	0.0012	0.0020				
B1	0.0002	0.0002	0.0003	0.0005	0.0006	0.0009	0.0012	0.0020				

## Pin Capacitance

Pin	Capacitance (pF)											
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
A0	0.0012	0.0014	0.0016	0.0024	0.0029	0.0043	0.0050	0.0080				
A1	0.0011	0.0013	0.0015	0.0025	0.0030	0.0043	0.0051	0.0080				
В0	0.0013	0.0014	0.0017	0.0023	0.0028	0.0043	0.0052	0.0082				
B1	0.0012	0.0014	0.0016	0.0026	0.0031	0.0042	0.0052	0.0082				

## Delays at 25°C,1.0V, Typical Process

Description				Intrinsic I	Delay (ns)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
$A0 \rightarrow Y \uparrow$	0.0430	0.0412	0.0382	0.0417	0.0384	0.0390	0.0377	0.0377
$A0 \rightarrow Y \downarrow$	0.0543	0.0529	0.0495	0.0510	0.0476	0.0510	0.0500	0.0492
A1 $\rightarrow$ Y $\uparrow$	0.0441	0.0424	0.0396	0.0428	0.0396	0.0412	0.0398	0.0399
A1 $\rightarrow$ Y $\downarrow$	0.0582	0.0569	0.0536	0.0544	0.0510	0.0549	0.0539	0.0532
B0 $\rightarrow$ Y $\uparrow$	0.0365	0.0353	0.0327	0.0330	0.0304	0.0321	0.0312	0.0312
B0 $\rightarrow$ Y $\downarrow$	0.0448	0.0442	0.0413	0.0426	0.0398	0.0431	0.0425	0.0419
B1 $\rightarrow$ Y $\uparrow$	0.0378	0.0367	0.0342	0.0347	0.0319	0.0344	0.0334	0.0334
B1 $\rightarrow$ Y $\downarrow$	0.0486	0.0480	0.0452	0.0464	0.0435	0.0475	0.0468	0.0463

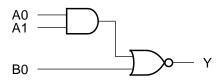
Description		K <sub>load</sub> (ns/pF)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	
A0 $\rightarrow$ Y $\uparrow$	4.5919	3.3481	2.4128	1.6553	1.1860	0.7920	0.5875	0.3900	
A0 $\rightarrow$ Y $\downarrow$	2.9034	2.0857	1.4650	1.0380	0.7295	0.4957	0.3659	0.2446	
A1 $\rightarrow$ Y $\uparrow$	4.5916	3.3480	2.4127	1.6554	1.1860	0.7920	0.5875	0.3900	
A1 $\rightarrow$ Y $\downarrow$	2.9139	2.0929	1.4699	1.0406	0.7314	0.4969	0.3669	0.2452	
B0 $\rightarrow$ Y $\uparrow$	4.5720	3.3353	2.4046	1.6463	1.1803	0.7887	0.5852	0.3884	
B0 $\rightarrow$ Y $\downarrow$	2.9055	2.0869	1.4658	1.0383	0.7297	0.4954	0.3657	0.2445	
B1 $\rightarrow$ Y $\uparrow$	4.5723	3.3352	2.4047	1.6463	1.1803	0.7887	0.5853	0.3885	
B1 $\rightarrow$ Y $\downarrow$	2.9138	2.0928	1.4699	1.0407	0.7314	0.4969	0.3669	0.2452	

### **Cell Description**

The AOI21 cell provides the logical inverted OR of one AND group and an additional input. The output (Y) is represented by the logic equation:

$$Y = \overline{(A0 \bullet A1) + B0}$$

## **Logic Symbol**

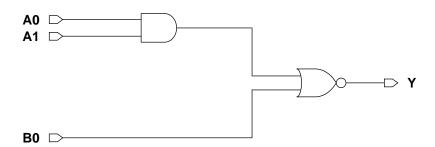


### **Function Table**

A0	<b>A</b> 1	В0	Υ
0	х	0	1
х	0	0	1
х	х	1	0
1	1	Х	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI21X0P5MA10TR	2.00	1.20
AOI21X0P7MA10TR	2.00	1.20
AOI21X1MA10TR	2.00	1.20
AOI21X1P4MA10TR	2.00	2.00
AOI21X2MA10TR	2.00	2.00
AOI21X3MA10TR	2.00	2.60
AOI21X4MA10TR	2.00	3.40
AOI21X6MA10TR	2.00	5.00
AOI21X8MA10TR	2.00	6.60



Pin		Power (uW/MHz)										
F 111	X0P5M	X0P7M	X1P0M	X3P0M	X4P0M	X6P0M	X8P0M					
Α0	0.0006	0.0007	0.0009	0.0014	0.0018	0.0027	0.0037	0.0055	0.0074			
A1	0.0006	0.0007	0.0009	0.0015	0.0019	0.0027	0.0037	0.0055	0.0074			
В0	0.0004	0.0005	0.0007	0.0011	0.0014	0.0019	0.0026	0.0039	0.0052			

## Pin Capacitance

Pin	Capacitance (pF)										
F 111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
A0	0.0013	0.0014	0.0017	0.0027	0.0034	0.0049	0.0064	0.0096	0.0127		
A1	0.0011	0.0014	0.0016	0.0029	0.0035	0.0049	0.0065	0.0097	0.0130		
В0	0.0012	0.0015	0.0017	0.0024	0.0030	0.0045	0.0059	0.0086	0.0117		

## Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A0 \rightarrow Y \uparrow$	0.0231	0.0207	0.0189	0.0188	0.0177	0.0172	0.0166	0.0164	0.0164
$A0 \rightarrow Y \downarrow$	0.0185	0.0166	0.0151	0.0151	0.0141	0.0132	0.0131	0.0129	0.0130
A1 $\rightarrow$ Y $\uparrow$	0.0254	0.0234	0.0218	0.0217	0.0205	0.0216	0.0212	0.0208	0.0208
A1 $\rightarrow$ Y $\downarrow$	0.0192	0.0177	0.0163	0.0165	0.0154	0.0154	0.0154	0.0152	0.0152
B0 → Y ↑	0.0196	0.0181	0.0165	0.0150	0.0145	0.0161	0.0153	0.0151	0.0153
$B0 \rightarrow Y \downarrow$	0.0106	0.0099	0.0091	0.0085	0.0083	0.0088	0.0084	0.0084	0.0085

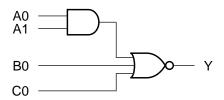
Description	K <sub>load</sub> (ns/pF)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 → Y ↑	8.7489	6.7387	4.8405	3.2760	2.3681	1.5688	1.1634	0.7718	0.5780
A0 $\rightarrow$ Y $\downarrow$	6.0713	4.6276	3.2714	2.2502	1.5870	1.0143	0.7715	0.5136	0.3861
A1 $\rightarrow$ Y $\uparrow$	8.7795	6.7719	4.8752	3.2743	2.3625	1.5896	1.1830	0.7836	0.5870
A1 $\rightarrow$ Y $\downarrow$	6.0711	4.6272	3.2712	2.2502	1.5869	1.0144	0.7714	0.5135	0.3862
B0 → Y ↑	8.7881	6.7774	4.8787	3.2760	2.3635	1.5903	1.1836	0.7840	0.5873
$B0 \rightarrow Y \downarrow$	4.4454	3.4740	2.5350	1.7228	1.2566	0.8845	0.6521	0.4408	0.3345

### **Cell Description**

The AOI211 cell provides the logical inverted OR of one AND group and two additional inputs. The output (Y) is represented by the logic equation:

$$Y = \overline{(A0 \bullet A1) + B0 + C0}$$

# Logic Symbol

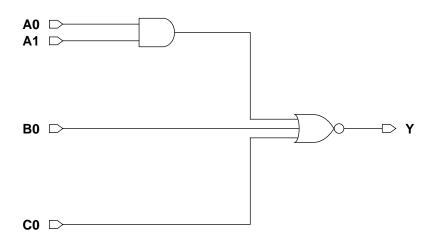


#### **Function Table**

A0	<b>A</b> 1	В0	C0	Υ
0	Х	0	0	1
Х	0	0	0	1
х	х	Х	1	0
х	х	1	х	0
1	1	Х	Х	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI211X0P5MA10TR	2.00	1.40
AOI211X0P7MA10TR	2.00	1.40
AOI211X1MA10TR	2.00	1.40
AOI211X1P4MA10TR	2.00	2.40
AOI211X2MA10TR	2.00	2.40
AOI211X3MA10TR	2.00	3.40
AOI211X4MA10TR	2.00	4.20



Pin		Power (uW/MHz)										
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M					
A0	0.0005	0.0006	0.0008	0.0012	0.0015	0.0023	0.0031					
A1	0.0004	0.0006	0.0008	0.0013	0.0017	0.0024	0.0033					
В0	0.0002	0.0002	0.0003	0.0005	0.0006	0.0009	0.0012					
C0	0.0001	0.0002	0.0003	0.0004	0.0006	0.0008	0.0011					

# Pin Capacitance

Pin		Capacitance (pF)										
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M					
A0	0.0011	0.0014	0.0016	0.0024	0.0030	0.0046	0.0062					
A1	0.0010	0.0012	0.0015	0.0026	0.0032	0.0045	0.0060					
В0	0.0011	0.0012	0.0014	0.0021	0.0028	0.0040	0.0055					
C0	0.0011	0.0013	0.0015	0.0021	0.0027	0.0043	0.0055					

# Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n	Intrinsic Delay (ns)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
A0	$\rightarrow$	Υ	$\uparrow$	0.0377	0.0332	0.0304	0.0291	0.0272	0.0266	0.0271		
A0	$\rightarrow$	Υ	$\downarrow$	0.0268	0.0249	0.0232	0.0227	0.0213	0.0216	0.0216		
A1	$\rightarrow$	Υ	$\uparrow$	0.0399	0.0358	0.0335	0.0319	0.0301	0.0293	0.0296		
A1	$\rightarrow$	Υ	$\downarrow$	0.0270	0.0255	0.0241	0.0239	0.0225	0.0228	0.0226		
В0	$\rightarrow$	Υ	$\uparrow$	0.0346	0.0300	0.0280	0.0257	0.0250	0.0242	0.0248		
В0	$\rightarrow$	Υ	$\downarrow$	0.0123	0.0144	0.0138	0.0148	0.0144	0.0132	0.0138		
C0	$\rightarrow$	Υ	$\uparrow$	0.0305	0.0258	0.0231	0.0198	0.0189	0.0192	0.0191		
C0	$\rightarrow$	Υ	$\downarrow$	0.0114	0.0130	0.0120	0.0114	0.0109	0.0111	0.0113		

**AOI211** 

# CLN65G+

De	escri	ptio	n	K <sub>load</sub> (ns/pF)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
A0	$\rightarrow$	Υ	$\uparrow$	14.2989	10.0562	7.4713	5.0750	3.6674	2.4325	1.8154			
A0	$\rightarrow$	Υ	$\downarrow$	8.1358	5.8851	4.4113	3.0594	2.1881	1.4983	1.1049			
A1	$\rightarrow$	Υ	$\uparrow$	14.4234	10.1145	7.5398	5.0627	3.6538	2.4246	1.8130			
A1	$\rightarrow$	Υ	$\downarrow$	8.1355	5.8857	4.4112	3.0594	2.1881	1.4982	1.1049			
В0	$\rightarrow$	Υ	$\uparrow$	14.4303	10.1174	7.5415	5.0633	3.6547	2.4251	1.8134			
В0	$\rightarrow$	Υ	$\downarrow$	4.3801	4.3386	3.3117	2.6203	1.8695	1.1575	0.8866			
C0	$\rightarrow$	Y	$\uparrow$	14.4380	10.1213	7.5434	5.0644	3.6551	2.4257	1.8138			
C0	$\rightarrow$	Υ	$\downarrow$	4.5113	4.5111	3.4366	2.5066	1.7938	1.2166	0.9251			

#### **Cell Description**

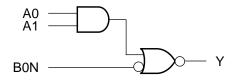
The AOI21B cell provides the logical inverted OR of one AND group and an additional input. The output (Y) is represented by the logic equation:

$$Y = \overline{(A0 \bullet A1) + \overline{B0N}}$$

#### **Function Table**

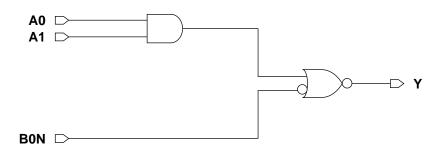
A0	<b>A</b> 1	B0N	Υ
Х	х	0	0
Х	0	1	1
0	х	1	1
1	1	Х	0

# **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI21BX0P5MA10TR	2.00	1.60
AOI21BX0P7MA10TR	2.00	1.60
AOI21BX1MA10TR	2.00	1.60
AOI21BX1P4MA10TR	2.00	2.40
AOI21BX2MA10TR	2.00	2.40
AOI21BX3MA10TR	2.00	3.20
AOI21BX4MA10TR	2.00	4.00
AOI21BX6MA10TR	2.00	5.80
AOI21BX8MA10TR	2.00	7.40



Pin		Power (uW/MHz)										
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0007	0.0008	0.0011	0.0015	0.0020	0.0030	0.0040	0.0061	0.0081			
A1	0.0006	0.0008	0.0010	0.0016	0.0021	0.0030	0.0040	0.0061	0.0081			
B0N	0.0017	0.0017	0.0019	0.0024	0.0030	0.0041	0.0052	0.0077	0.0099			

# Pin Capacitance

Pin		Capacitance (pF)										
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0013	0.0015	0.0018	0.0027	0.0034	0.0049	0.0064	0.0096	0.0127			
A1	0.0011	0.0013	0.0016	0.0028	0.0035	0.0049	0.0065	0.0097	0.0129			
B0N	0.0009	0.0009	0.0009	0.0011	0.0013	0.0016	0.0019	0.0031	0.0037			

# Delays at 25°C,1.0V, Typical Process

De	scrip	tion	l	Intrinsic Delay (ns)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
A0	$\rightarrow$	Υ	$\uparrow$	0.0240	0.0219	0.0205	0.0202	0.0192	0.0187	0.0182	0.0179	0.0180	
A0	$\rightarrow$	Υ	$\downarrow$	0.0188	0.0171	0.0154	0.0151	0.0140	0.0132	0.0131	0.0129	0.0129	
A1	$\rightarrow$	Υ	$\uparrow$	0.0261	0.0243	0.0232	0.0229	0.0220	0.0230	0.0227	0.0223	0.0224	
A1	$\rightarrow$	Υ	$\downarrow$	0.0192	0.0177	0.0163	0.0164	0.0153	0.0153	0.0153	0.0151	0.0152	
B0N	$\rightarrow$	Υ	$\uparrow$	0.0336	0.0328	0.0331	0.0306	0.0299	0.0306	0.0298	0.0284	0.0287	
B0N	$\rightarrow$	Υ	$\downarrow$	0.0347	0.0359	0.0386	0.0374	0.0364	0.0360	0.0360	0.0336	0.0342	

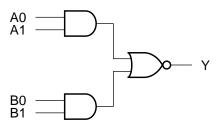
De	scrip	tion	)	K <sub>load</sub> (ns/pF)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
A0	$\rightarrow$	Υ	$\uparrow$	8.5350	6.5747	4.7234	3.2371	2.3437	1.5476	1.1515	0.7658	0.5749	
A0	$\rightarrow$	Υ	$\downarrow$	6.0593	4.6432	3.2656	2.2505	1.5875	1.0128	0.7695	0.5136	0.3865	
A1	$\rightarrow$	Υ	$\uparrow$	8.6353	6.6609	4.7961	3.2313	2.3385	1.5684	1.1704	0.7781	0.5842	
A1	$\rightarrow$	Υ	$\downarrow$	6.0582	4.6430	3.2658	2.2494	1.5870	1.0128	0.7695	0.5136	0.3865	
B0N	$\rightarrow$	Υ	$\uparrow$	8.6451	6.6677	4.8007	3.2334	2.3399	1.5692	1.1709	0.7784	0.5845	
B0N	$\rightarrow$	Υ	$\downarrow$	4.4308	3.4633	2.5314	1.7250	1.2567	0.8854	0.6649	0.4412	0.3352	

#### **Cell Description**

The AOI22 cell provides the logical inverted OR of two AND groups. The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (\overline{A0 \bullet A1) + (B0 \bullet B1)}$$

# **Logic Symbol**

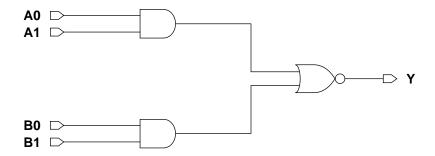


### **Function Table**

A0	<b>A</b> 1	В0	B1	Υ
0	х	0	Х	1
0	х	х	0	1
х	0	0	Х	1
Х	0	Х	0	1
х	х	1	1	0
1	1	х	Х	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI22X0P5MA10TR	2.00	1.40
AOI22X0P7MA10TR	2.00	1.40
AOI22X1MA10TR	2.00	1.40
AOI22X1P4MA10TR	2.00	2.40
AOI22X2MA10TR	2.00	2.40
AOI22X3MA10TR	2.00	3.40
AOI22X4MA10TR	2.00	4.80
AOI22X6MA10TR	2.00	6.80
AOI22X8MA10TR	2.00	9.00



Pin		Power (uW/MHz)											
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	0.0006	0.0007	0.0010	0.0015	0.0021	0.0031	0.0042	0.0063	0.0084				
A1	0.0006	0.0007	0.0010	0.0015	0.0021	0.0031	0.0041	0.0063	0.0084				
В0	0.0001	0.0002	0.0002	0.0003	0.0005	0.0007	0.0010	0.0015	0.0020				
B1	0.0001	0.0002	0.0002	0.0003	0.0005	0.0007	0.0010	0.0015	0.0020				

# Pin Capacitance

Pin		Capacitance (pF)											
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	0.0012	0.0014	0.0018	0.0026	0.0034	0.0050	0.0066	0.0099	0.0132				
A1	0.0011	0.0013	0.0016	0.0027	0.0034	0.0050	0.0066	0.0100	0.0133				
В0	0.0012	0.0015	0.0018	0.0027	0.0034	0.0052	0.0069	0.0104	0.0138				
B1	0.0012	0.0014	0.0017	0.0029	0.0036	0.0052	0.0069	0.0104	0.0139				

# Delays at 25°C,1.0V, Typical Process

Desc	crip	tior	1	Intrinsic Delay (ns)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
A0 -	$\rightarrow$	Υ	$\uparrow$	0.0303	0.0283	0.0261	0.0274	0.0253	0.0256	0.0249	0.0248	0.0247	
A0 -	$\rightarrow$	Υ	$\downarrow$	0.0229	0.0212	0.0193	0.0208	0.0189	0.0181	0.0173	0.0175	0.0175	
A1 -	$\rightarrow$	Υ	$\uparrow$	0.0326	0.0310	0.0289	0.0301	0.0279	0.0290	0.0297	0.0296	0.0295	
A1 -	$\rightarrow$	Υ	$\downarrow$	0.0236	0.0220	0.0204	0.0219	0.0201	0.0202	0.0199	0.0199	0.0198	
В0 -	$\rightarrow$	Υ	$\uparrow$	0.0203	0.0193	0.0177	0.0197	0.0180	0.0189	0.0193	0.0192	0.0192	
В0 -	$\rightarrow$	Υ	$\downarrow$	0.0136	0.0128	0.0115	0.0133	0.0119	0.0116	0.0111	0.0112	0.0112	
B1 -	$\rightarrow$	Υ	$\uparrow$	0.0238	0.0229	0.0213	0.0228	0.0210	0.0224	0.0233	0.0232	0.0233	
B1 -	$\rightarrow$	Υ	$\downarrow$	0.0151	0.0143	0.0131	0.0147	0.0133	0.0138	0.0135	0.0136	0.0136	

AOI22

CLN65G+

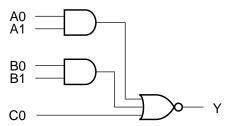
Description	K <sub>load</sub> (ns/pF)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
A0 $\rightarrow$ Y $\uparrow$	8.7012	6.7107	4.8192	3.2805	2.3591	1.5738	1.1617	0.7730	0.5797	
A0 $\rightarrow$ Y $\downarrow$	5.9658	4.5443	3.2088	2.2441	1.5823	1.0130	0.7503	0.5020	0.3781	
A1 $\rightarrow$ Y $\uparrow$	8.7487	6.7681	4.8630	3.2763	2.3555	1.5550	1.1734	0.7819	0.5867	
A1 $\rightarrow$ Y $\downarrow$	5.9642	4.5436	3.2088	2.2439	1.5821	1.0129	0.7502	0.5020	0.3781	
B0 $\rightarrow$ Y $\uparrow$	8.6395	6.6816	4.7978	3.2839	2.3689	1.5740	1.1819	0.7875	0.5910	
B0 $\rightarrow$ Y $\downarrow$	5.7070	4.3721	3.0982	2.2404	1.5857	1.0123	0.7622	0.5085	0.3821	
B1 $\rightarrow$ Y $\uparrow$	8.7524	6.7710	4.8639	3.2778	2.3530	1.5505	1.1680	0.7782	0.5844	
B1 $\rightarrow$ Y $\downarrow$	5.7063	4.3716	3.0979	2.2402	1.5856	1.0122	0.7620	0.5083	0.3820	

#### **Cell Description**

The AOI221 cell provides the logical inverted OR of two AND groups and a third input. The output (Y) is represented by the logic equation:

$$Y = \overline{(A0 \bullet A1) + (B0 \bullet B1) + C0}$$

# **Logic Symbol**

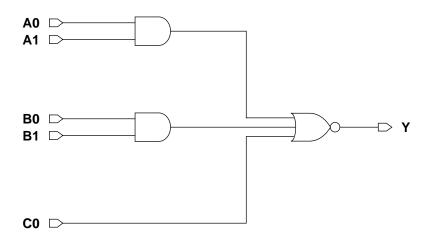


#### **Function Table**

A0	<b>A</b> 1	В0	B1	C0	Υ
0	х	0	Х	0	1
0	х	х	0	0	1
Х	0	0	Х	0	1
Х	0	х	0	0	1
Х	х	х	Х	1	0
Х	Х	1	1	Х	0
1	1	Х	Х	Х	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI221X0P5MA10TR	2.00	1.80
AOI221X0P7MA10TR	2.00	1.80
AOI221X1MA10TR	2.00	1.80
AOI221X1P4MA10TR	2.00	3.20
AOI221X2MA10TR	2.00	3.20
AOI221X3MA10TR	2.00	4.40
AOI221X4MA10TR	2.00	5.80



Pin	Power (uW/MHz)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M				
A0	0.0004	0.0006	0.0008	0.0013	0.0016	0.0025	0.0032				
A1	0.0004	0.0006	0.0008	0.0012	0.0017	0.0024	0.0034				
В0	0.0002	0.0002	0.0003	0.0005	0.0006	0.0009	0.0012				
B1	0.0002	0.0002	0.0003	0.0004	0.0006	0.0009	0.0012				
C0	0.0004	0.0005	0.0006	0.0009	0.0012	0.0016	0.0023				

# Pin Capacitance

Pin	Capacitance (pF)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M				
A0	0.0011	0.0013	0.0016	0.0026	0.0031	0.0046	0.0064				
A1	0.0010	0.0012	0.0015	0.0022	0.0031	0.0044	0.0062				
В0	0.0011	0.0013	0.0016	0.0025	0.0031	0.0047	0.0064				
B1	0.0010	0.0013	0.0015	0.0022	0.0031	0.0045	0.0062				
C0	0.0011	0.0013	0.0015	0.0021	0.0028	0.0041	0.0054				

# Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n			Intri	nsic Delay	(ns)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	0.0491	0.0432	0.0408	0.0385	0.0390	0.0367	0.0373
A0	$\rightarrow$	Υ	$\downarrow$	0.0331	0.0298	0.0285	0.0288	0.0277	0.0264	0.0267
A1	$\rightarrow$	Υ	$\uparrow$	0.0515	0.0461	0.0440	0.0408	0.0415	0.0393	0.0395
A1	$\rightarrow$	Υ	$\downarrow$	0.0335	0.0308	0.0294	0.0293	0.0288	0.0273	0.0275
В0	$\rightarrow$	Υ	<b>↑</b>	0.0419	0.0362	0.0338	0.0323	0.0325	0.0303	0.0310
В0	$\rightarrow$	Υ	$\downarrow$	0.0262	0.0230	0.0214	0.0218	0.0208	0.0199	0.0201
B1	$\rightarrow$	Υ	<b>↑</b>	0.0456	0.0397	0.0373	0.0345	0.0354	0.0328	0.0335
B1	$\rightarrow$	Υ	$\downarrow$	0.0276	0.0245	0.0228	0.0226	0.0219	0.0209	0.0209
C0	$\rightarrow$	Υ	$\uparrow$	0.0322	0.0272	0.0258	0.0210	0.0228	0.0218	0.0219
C0	$\rightarrow$	Υ	$\downarrow$	0.0120	0.0135	0.0130	0.0118	0.0122	0.0117	0.0117

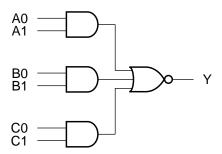
De	escri	ptio	n			ŀ	ເ <sub>load</sub> (ns/pF	)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	13.9374	9.8619	7.3653	4.9387	3.5741	2.3820	1.7688
A0	$\rightarrow$	Υ	$\downarrow$	8.3988	5.9992	4.4564	3.1672	2.2159	1.4585	1.0959
A1	$\rightarrow$	Υ	1	13.9996	9.8879	7.4157	4.9491	3.5659	2.3704	1.7663
A1	$\rightarrow$	Υ	$\downarrow$	8.3985	5.9992	4.4564	3.1671	2.2159	1.4585	1.0957
В0	$\rightarrow$	Υ	1	14.0043	9.8862	7.3911	4.9574	3.5745	2.3764	1.7694
В0	$\rightarrow$	Υ	$\downarrow$	8.2972	5.9280	4.4090	3.1412	2.1546	1.4531	1.0804
B1	$\rightarrow$	Υ	$\uparrow$	14.0018	9.8891	7.4164	4.9493	3.5660	2.3726	1.7662
B1	$\rightarrow$	Υ	$\downarrow$	8.2972	5.9279	4.4089	3.1410	2.1545	1.4531	1.0803
C0	$\rightarrow$	Υ	$\uparrow$	14.0112	9.8930	7.4190	4.9509	3.5672	2.3732	1.7668
C0	$\rightarrow$	Υ	$\downarrow$	4.6326	4.6318	3.5376	2.5754	1.7972	1.2061	0.8864

#### **Cell Description**

The AOI222 cell provides the logical inverted OR of three AND groups. The output (Y) is represented by the logic equation:

$$Y = (\overline{A0 {\bullet} A1) + (B0 {\bullet} B1) + (C0 {\bullet} C1)}$$

# **Logic Symbol**

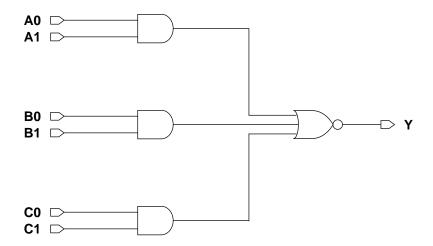


#### **Function Table**

A0	<b>A</b> 1	В0	B1	C0	C1	Υ
0	х	0	х	0	Х	1
0	х	0	х	Х	0	1
0	х	х	0	0	Х	1
0	х	х	0	Х	0	1
Х	0	0	х	0	Х	1
Х	0	0	х	Х	0	1
Х	0	х	0	0	Х	1
Х	0	Х	0	Х	0	1
Х	Х	Х	х	1	1	0
Х	х	1	1	Х	Х	0
1	1	Х	Х	Х	Х	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI222X0P5MA10TR	2.00	2.20
AOI222X0P7MA10TR	2.00	2.20
AOI222X1MA10TR	2.00	2.20
AOI222X1P4MA10TR	2.00	3.60
AOI222X2MA10TR	2.00	3.60
AOI222X3MA10TR	2.00	5.20
AOI222X4MA10TR	2.00	6.80



Pin	Power (uW/MHz)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M				
A0	0.0004	0.0006	0.0008	0.0013	0.0016	0.0025	0.0032				
A1	0.0004	0.0006	0.0008	0.0012	0.0017	0.0024	0.0034				
В0	0.0002	0.0002	0.0003	0.0005	0.0006	0.0009	0.0012				
B1	0.0002	0.0002	0.0003	0.0004	0.0006	0.0009	0.0012				
C0	0.0001	0.0001	0.0001	0.0002	0.0003	0.0004	0.0005				
C1	0.0001	0.0001	0.0001	0.0002	0.0003	0.0004	0.0005				

# Pin Capacitance

Pin		Capacitance (pF)										
' '''	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M					
Α0	0.0011	0.0013	0.0017	0.0025	0.0030	0.0046	0.0062					
A1	0.0010	0.0012	0.0015	0.0022	0.0032	0.0044	0.0063					
В0	0.0011	0.0013	0.0016	0.0025	0.0031	0.0045	0.0062					
B1	0.0010	0.0012	0.0015	0.0022	0.0032	0.0044	0.0062					
C0	0.0011	0.0013	0.0017	0.0025	0.0031	0.0048	0.0064					
C1	0.0011	0.0013	0.0016	0.0022	0.0034	0.0046	0.0066					

# Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n			Intri	nsic Delay	(ns)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	0.0586	0.0541	0.0513	0.0491	0.0481	0.0461	0.0468
A0	$\rightarrow$	Υ	$\downarrow$	0.0412	0.0391	0.0368	0.0343	0.0341	0.0338	0.0340
A1	$\rightarrow$	Υ	$\uparrow$	0.0612	0.0569	0.0542	0.0516	0.0510	0.0486	0.0494
A1	$\rightarrow$	Υ	$\downarrow$	0.0417	0.0398	0.0375	0.0351	0.0353	0.0347	0.0351
В0	$\rightarrow$	Υ	$\uparrow$	0.0512	0.0465	0.0440	0.0419	0.0414	0.0396	0.0402
В0	$\rightarrow$	Υ	$\downarrow$	0.0323	0.0300	0.0280	0.0264	0.0265	0.0261	0.0261
B1	$\rightarrow$	Υ	<b>↑</b>	0.0538	0.0493	0.0468	0.0448	0.0444	0.0422	0.0430
B1	$\rightarrow$	Υ	$\downarrow$	0.0332	0.0310	0.0290	0.0277	0.0277	0.0272	0.0271
C0	$\rightarrow$	Υ	$\uparrow$	0.0324	0.0288	0.0273	0.0260	0.0256	0.0247	0.0254
C0	$\rightarrow$	Υ	$\downarrow$	0.0205	0.0191	0.0176	0.0175	0.0163	0.0161	0.0162
C1	$\rightarrow$	Υ	$\uparrow$	0.0355	0.0319	0.0304	0.0274	0.0293	0.0273	0.0288

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description			Intri	nsic Delay	(ns)		
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
$C1 \rightarrow Y \downarrow$	0.0215	0.0200	0.0186	0.0180	0.0177	0.0171	0.0176

De	escri	ptio	n		K <sub>load</sub> (ns/pF)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
A0	$\rightarrow$	Υ	$\uparrow$	13.6955	10.0383	7.2746	4.9357	3.5777	2.3657	1.7629			
A0	$\rightarrow$	Υ	$\downarrow$	8.3637	6.2127	4.4386	2.8971	2.1532	1.4556	1.0853			
A1	$\rightarrow$	Υ	$\uparrow$	13.7555	10.0824	7.3222	4.9326	3.5699	2.3544	1.7595			
A1	$\rightarrow$	Υ	$\downarrow$	8.3635	6.2125	4.4384	2.8972	2.1536	1.4554	1.0854			
В0	$\rightarrow$	Υ	$\uparrow$	13.7725	10.0733	7.3058	4.9143	3.5814	2.3624	1.7636			
В0	$\rightarrow$	Υ	$\downarrow$	8.2225	6.1098	4.3720	2.8785	2.1566	1.4525	1.0777			
B1	$\rightarrow$	Υ	$\uparrow$	13.7546	10.0833	7.3222	4.9328	3.5700	2.3567	1.7596			
В1	$\rightarrow$	Υ	$\downarrow$	8.2221	6.1097	4.3719	2.8784	2.1565	1.4524	1.0777			
C0	$\rightarrow$	Υ	$\uparrow$	13.6511	10.0058	7.2475	4.9531	3.5495	2.3644	1.7573			
C0	$\rightarrow$	Υ	$\downarrow$	8.0549	6.2674	4.4681	3.2062	2.1713	1.4693	1.0902			
C1	$\rightarrow$	Υ	$\uparrow$	13.7589	10.0858	7.3236	4.9290	3.5709	2.3569	1.7599			
C1	$\rightarrow$	Υ	$\downarrow$	8.0536	6.2666	4.4675	3.2055	2.1712	1.4691	1.0901			

#### **Cell Description**

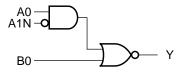
The AOI2XB1 cell provides the logical inverted OR of two AND group consisting of three inputs: (A0, A1N) and (B0). The output (Y) is represented by the logic equation:

$$Y = \overline{(A0 \bullet \overline{A1N}) + (B0)}$$

#### **Function Table**

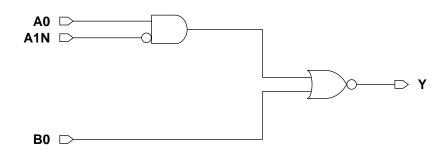
A0	A1N	В0	Υ
0	Х	0	1
Х	1	0	1
х	Х	1	0
1	0	Х	0

# **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI2XB1X0P5MA10TR	2.00	1.60
AOI2XB1X0P7MA10TR	2.00	1.60
AOI2XB1X1MA10TR	2.00	1.60
AOI2XB1X1P4MA10TR	2.00	2.40
AOI2XB1X2MA10TR	2.00	2.40
AOI2XB1X3MA10TR	2.00	3.20
AOI2XB1X4MA10TR	2.00	4.20
AOI2XB1X6MA10TR	2.00	5.80
AOI2XB1X8MA10TR	2.00	7.60



Pin		Power (uW/MHz)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0006	0.0007	0.0009	0.0014	0.0018	0.0028	0.0038	0.0057	0.0076			
A1N	0.0015	0.0016	0.0017	0.0025	0.0031	0.0042	0.0055	0.0080	0.0109			
В0	0.0007	0.0008	0.0010	0.0016	0.0021	0.0028	0.0037	0.0056	0.0074			

### Pin Capacitance

Pin		Capacitance (pF)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0013	0.0015	0.0017	0.0027	0.0034	0.0049	0.0064	0.0096	0.0128			
A1N	0.0009	0.0009	0.0009	0.0011	0.0013	0.0017	0.0025	0.0033	0.0045			
В0	0.0012	0.0014	0.0017	0.0024	0.0031	0.0045	0.0059	0.0087	0.0117			

### Delays at 25°C,1.0V, Typical Process

De	scrip	tion	)		Intrinsic Delay (ns)											
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	$\rightarrow$	Υ	1	0.0228	0.0209	0.0189	0.0187	0.0178	0.0173	0.0167	0.0164	0.0164				
A0	$\rightarrow$	Υ	$\downarrow$	0.0182	0.0167	0.0150	0.0149	0.0141	0.0133	0.0131	0.0129	0.0130				
A1N	$\rightarrow$	Υ	$\uparrow$	0.0397	0.0394	0.0392	0.0407	0.0393	0.0377	0.0368	0.0359	0.0368				
A1N	$\rightarrow$	Υ	$\downarrow$	0.0407	0.0415	0.0427	0.0447	0.0435	0.0416	0.0405	0.0397	0.0404				
В0	$\rightarrow$	Υ	$\uparrow$	0.0186	0.0175	0.0160	0.0149	0.0145	0.0160	0.0152	0.0150	0.0152				
В0	$\rightarrow$	Υ	$\downarrow$	0.0102	0.0098	0.0090	0.0085	0.0084	0.0088	0.0084	0.0084	0.0086				

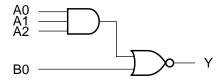
Description		K <sub>load</sub> (ns/pF)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
A0 $\rightarrow$ Y $\uparrow$	8.6737	6.6784	4.7972	3.2650	2.3628	1.5632	1.1636	0.7713	0.5779		
A0 $\rightarrow$ Y $\downarrow$	6.0476	4.6134	3.2593	2.2449	1.5836	1.0115	0.7705	0.5129	0.3856		
A1N $\rightarrow$ Y $\uparrow$	8.6628	6.6803	4.8102	3.2546	2.3516	1.5728	1.1709	0.7788	0.5841		
A1N $\rightarrow$ Y $\downarrow$	6.0503	4.6170	3.2624	2.2480	1.5857	1.0125	0.7712	0.5133	0.3860		
B0 $\rightarrow$ Y $\uparrow$	8.6712	6.6849	4.8126	3.2561	2.3524	1.5732	1.1713	0.7790	0.5843		
B0 $\rightarrow$ Y $\downarrow$	4.4381	3.4672	2.5342	1.7241	1.2555	0.8849	0.6514	0.4408	0.3346		

#### **Cell Description**

The AOI31 cell provides the logical inverted OR of one AND group and an additional input. The output (Y) is represented by the logic equation:

$$\mathsf{Y} = \overline{(A0 \bullet A1 \bullet A2) + B0}$$

# **Logic Symbol**

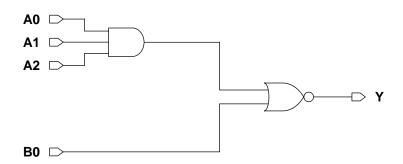


#### **Function Table**

Α0	<b>A</b> 1	A2	B0	Υ
0	х	х	0	1
Х	0	Х	0	1
Х	х	0	0	1
х	х	х	1	0
1	1	1	Х	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI31X0P5MA10TR	2.00	1.40
AOI31X0P7MA10TR	2.00	1.40
AOI31X1MA10TR	2.00	1.40
AOI31X1P4MA10TR	2.00	2.60
AOI31X2MA10TR	2.00	2.60
AOI31X3MA10TR	2.00	3.40
AOI31X4MA10TR	2.00	4.80
AOI31X6MA10TR	2.00	6.80



Pin		Power (uW/MHz)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
A0	0.0005	0.0006	0.0008	0.0013	0.0017	0.0027	0.0035	0.0053		
A1	0.0005	0.0006	0.0008	0.0013	0.0017	0.0027	0.0035	0.0054		
A2	0.0006	0.0007	0.0009	0.0013	0.0017	0.0027	0.0035	0.0053		
В0	0.0005	0.0006	0.0008	0.0013	0.0018	0.0024	0.0035	0.0051		

# Pin Capacitance

Pin		Capacitance (pF)								
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
A0	0.0013	0.0016	0.0019	0.0027	0.0035	0.0053	0.0070	0.0107		
A1	0.0012	0.0014	0.0017	0.0026	0.0034	0.0052	0.0068	0.0104		
A2	0.0012	0.0014	0.0017	0.0027	0.0035	0.0052	0.0070	0.0105		
В0	0.0012	0.0014	0.0017	0.0023	0.0029	0.0043	0.0056	0.0087		

# Delays at 25°C,1.0V, Typical Process

Description				Intrinsic I	Delay (ns)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
$A0 \rightarrow Y \uparrow$	0.0256	0.0239	0.0216	0.0225	0.0205	0.0196	0.0196	0.0198
$A0 \rightarrow Y \downarrow$	0.0216	0.0199	0.0175	0.0175	0.0160	0.0151	0.0152	0.0154
A1 $\rightarrow$ Y $\uparrow$	0.0285	0.0271	0.0253	0.0277	0.0256	0.0252	0.0252	0.0251
A1 $\rightarrow$ Y $\downarrow$	0.0232	0.0217	0.0196	0.0212	0.0195	0.0189	0.0191	0.0191
A2 $\rightarrow$ Y $\uparrow$	0.0328	0.0314	0.0296	0.0338	0.0313	0.0303	0.0303	0.0304
A2 $\rightarrow$ Y $\downarrow$	0.0246	0.0232	0.0211	0.0237	0.0219	0.0208	0.0211	0.0211
B0 $\rightarrow$ Y $\uparrow$	0.0260	0.0246	0.0231	0.0248	0.0230	0.0230	0.0225	0.0229
$B0 \rightarrow Y \downarrow$	0.0111	0.0104	0.0097	0.0098	0.0090	0.0093	0.0090	0.0092

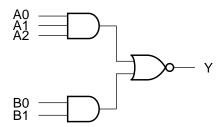
Description		K <sub>load</sub> (ns/pF)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
A0 $\rightarrow$ Y $\uparrow$	8.5637	6.9211	4.9714	3.4808	2.4847	1.6317	1.2198	0.8095
A0 $\rightarrow$ Y $\downarrow$	6.6249	5.2438	3.6398	2.5217	1.7931	1.1503	0.8734	0.5800
A1 $\rightarrow$ Y $\uparrow$	8.6357	6.9856	5.0289	3.4731	2.4865	1.6365	1.2219	0.8121
A1 $\rightarrow$ Y $\downarrow$	6.6237	5.2438	3.6395	2.5213	1.7932	1.1504	0.8732	0.5799
A2 $\rightarrow$ Y $\uparrow$	8.7181	7.0668	5.0898	3.5131	2.5195	1.6609	1.2354	0.8229
A2 $\rightarrow$ Y $\downarrow$	6.6235	5.2433	3.6393	2.5214	1.7932	1.1503	0.8732	0.5799
B0 $\rightarrow$ Y $\uparrow$	8.7269	7.0715	5.0929	3.5148	2.5204	1.6617	1.2360	0.8233
B0 $\rightarrow$ Y $\downarrow$	4.3572	3.5520	2.6149	1.9405	1.3585	0.9515	0.7054	0.4733

### **Cell Description**

The AOI32 cell provides the logical inverted OR of two AND groups. The output (Y) is represented by the logic equation:

$$\mathsf{Y} = \overline{(A0 \bullet A1 \bullet A2) + (B0 \bullet B1)}$$

# **Logic Symbol**

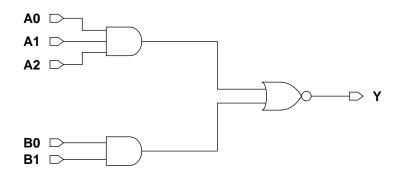


#### **Function Table**

A0	<b>A</b> 1	<b>A2</b>	В0	B1	Υ
0	х	х	0	Х	1
0	х	Х	х	0	1
Х	0	Х	0	х	1
х	0	х	х	0	1
Х	х	0	0	Х	1
Х	х	0	х	0	1
Х	Х	х	1	1	0
1	1	1	Х	Х	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
AOI32X0P5MA10TR	2.00	1.60
AOI32X0P7MA10TR	2.00	1.60
AOI32X1MA10TR	2.00	1.60
AOI32X1P4MA10TR	2.00	3.00
AOI32X2MA10TR	2.00	3.00
AOI32X3MA10TR	2.00	4.20
AOI32X4MA10TR	2.00	6.00
AOI32X6MA10TR	2.00	8.60



Pin		Power (uW/MHz)								
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
A0	0.0005	0.0007	0.0009	0.0014	0.0019	0.0030	0.0040	0.0060		
A1	0.0005	0.0007	0.0009	0.0014	0.0018	0.0028	0.0038	0.0057		
A2	0.0006	0.0007	0.0009	0.0015	0.0020	0.0029	0.0038	0.0058		
В0	0.0001	0.0002	0.0003	0.0004	0.0006	0.0009	0.0012	0.0018		
B1	0.0001	0.0002	0.0003	0.0004	0.0006	0.0009	0.0011	0.0018		

# Pin Capacitance

Pin	Capacitance (pF)									
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
A0	0.0012	0.0015	0.0018	0.0028	0.0036	0.0053	0.0070	0.0105		
A1	0.0012	0.0014	0.0017	0.0028	0.0035	0.0052	0.0069	0.0102		
A2	0.0011	0.0014	0.0017	0.0031	0.0038	0.0052	0.0070	0.0105		
В0	0.0012	0.0014	0.0017	0.0026	0.0033	0.0051	0.0068	0.0101		
B1	0.0011	0.0013	0.0016	0.0027	0.0033	0.0049	0.0066	0.0099		

# Delays at 25°C,1.0V, Typical Process

Description				Intrinsic I	Delay (ns)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
A0 → Y ↑	0.0330	0.0298	0.0278	0.0301	0.0280	0.0278	0.0291	0.0285
A0 $\rightarrow$ Y $\downarrow$	0.0271	0.0238	0.0216	0.0228	0.0206	0.0199	0.0208	0.0206
A1 $\rightarrow$ Y $\uparrow$	0.0364	0.0336	0.0317	0.0335	0.0316	0.0334	0.0347	0.0342
A1 $\rightarrow$ Y $\downarrow$	0.0294	0.0262	0.0241	0.0251	0.0230	0.0237	0.0247	0.0245
A2 → Y ↑	0.0405	0.0377	0.0359	0.0378	0.0357	0.0387	0.0403	0.0397
A2 $\rightarrow$ Y $\downarrow$	0.0307	0.0276	0.0255	0.0270	0.0249	0.0255	0.0267	0.0265
B0 → Y ↑	0.0265	0.0247	0.0234	0.0247	0.0237	0.0251	0.0263	0.0259
$B0 \rightarrow Y \downarrow$	0.0144	0.0131	0.0119	0.0131	0.0120	0.0113	0.0121	0.0119
$B1 \rightarrow Y \uparrow$	0.0301	0.0284	0.0270	0.0275	0.0263	0.0298	0.0315	0.0310
$B1 \rightarrow Y \downarrow$	0.0160	0.0146	0.0134	0.0145	0.0133	0.0135	0.0146	0.0143

Description				K <sub>load</sub> (	ns/pF)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
A0 $\rightarrow$ Y $\uparrow$	9.4995	7.0110	5.0645	3.4036	2.4599	1.6297	1.2321	0.8177
A0 $\rightarrow$ Y $\downarrow$	7.2848	5.2306	3.6652	2.4226	1.6964	1.1464	0.8744	0.5858
A1 $\rightarrow$ Y $\uparrow$	9.4650	7.0053	5.0488	3.3899	2.4406	1.6343	1.2347	0.8210
A1 $\rightarrow$ Y $\downarrow$	7.2839	5.2304	3.6652	2.4223	1.6962	1.1462	0.8743	0.5857
A2 $\rightarrow$ Y $\uparrow$	9.5177	7.0402	5.0701	3.3935	2.4459	1.6564	1.2504	0.8315
A2 $\rightarrow$ Y $\downarrow$	7.2840	5.2309	3.6651	2.4224	1.6963	1.1462	0.8743	0.5857
B0 → Y ↑	9.3663	6.9211	4.9773	3.4074	2.4595	1.6311	1.2252	0.8169
B0 $\rightarrow$ Y $\downarrow$	6.3522	4.7173	3.3291	2.3252	1.6380	1.0430	0.8041	0.5366
B1 → Y ↑	9.5222	7.0430	5.0717	3.3947	2.4418	1.6567	1.2508	0.8317
$B1 \rightarrow Y \downarrow$	6.3518	4.7169	3.3287	2.3251	1.6379	1.0428	0.8040	0.5365

### **Cell Description**

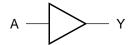
The BUF cell provides the logical buffer of a single input (A). The output (Y) is represented by the logic equation:

Y = A

### **Function Table**

Α	Υ
0	0
1	1

# **Logic Symbol**



### **Cell Size**

Drive Strength	Height (um)	Width (um)
BUFX0P7BA10TR	2.00	0.80
BUFX0P7MA10TR	2.00	0.80
BUFX0P8BA10TR	2.00	0.80
BUFX0P8MA10TR	2.00	0.80
BUFX1BA10TR	2.00	0.80
BUFX1MA10TR	2.00	0.80
BUFX1P2BA10TR	2.00	1.20
BUFX1P2MA10TR	2.00	1.20
BUFX1P4BA10TR	2.00	1.20
BUFX1P4MA10TR	2.00	1.20
BUFX1P7BA10TR	2.00	1.20
BUFX1P7MA10TR	2.00	1.20
BUFX2BA10TR	2.00	1.20
BUFX2MA10TR	2.00	1.20
BUFX2P5BA10TR	2.00	1.40
BUFX2P5MA10TR	2.00	1.40
BUFX3BA10TR	2.00	1.40
BUFX3MA10TR	2.00	1.40
BUFX3P5BA10TR	2.00	2.00
BUFX3P5MA10TR	2.00	2.00

# Cell Size (Cont'd.)

Drive Strength	Height (um)	Width (um)
BUFX4BA10TR	2.00	2.00
BUFX4MA10TR	2.00	2.00
BUFX5BA10TR	2.00	2.20
BUFX5MA10TR	2.00	2.20
BUFX6BA10TR	2.00	2.40
BUFX6MA10TR	2.00	2.40
BUFX7P5BA10TR	2.00	3.20
BUFX7P5MA10TR	2.00	3.20
BUFX9BA10TR	2.00	3.40
BUFX9MA10TR	2.00	3.40
BUFX11BA10TR	2.00	4.20
BUFX11MA10TR	2.00	4.20
BUFX13BA10TR	2.00	4.80
BUFX13MA10TR	2.00	4.80
BUFX16BA10TR	2.00	5.80
BUFX16MA10TR	2.00	5.80



#### **AC Power**

Pin				Power (u	ıW/MHz)			
· · · · ·	X0P7B	X0P7M	X0P8B	X0P8M	X1P0B	X1P0M	X1P2B	X1P2M
Α	0.0024	0.0025	0.0025	0.0026	0.0026	0.0028	0.0032	0.0035

# AC Power (Cont'd.)

	Pin				Power (u	ıW/MHz)			
		X1P4B	X1P4M	X1P7B	X1P7M	X2P0B	X2P0M	X2P5B	X2P5M
Ī	Α	0.0035	0.0039	0.0039	0.0045	0.0044	0.0049	0.0055	0.0065

### AC Power (Cont'd.)

Pin		Power (uW/MHz)							
' '''	X3P0B	X3P0M	X3P5B	X3P5M	X4P0B	X4P0M	X5P0B	X5P0M	
Α	0.0064	0.0073	0.0074	0.0086	0.0082	0.0094	0.0102	0.0119	

### AC Power (Cont'd.)

Pin	Power (uW/MHz)							
F	X6P0B	X6P0M	X7P5B	X7P5M	X9P0B	X9P0M	X11P0B	X11P0M
Α	0.0120	0.0139	0.0158	0.0183	0.0183	0.0215	0.0226	0.0263

# AC Power (Cont'd.)

Ī	Pin	Power (uW/MHz)							
	PIII	X13P0B	X13P0M	X16P0B	X16P0M				
Ī	Α	0.0267	0.0307	0.0325	0.0376				

# Pin Capacitance

Pin				Capacita	nce (pF)			
' '''	X0P7B	X0P7M	X0P8B	X0P8M	X1P0B	X1P0M	X1P2B	X1P2M
Α	0.0011	0.0010	0.0011	0.0010	0.0010	0.0009	0.0010	0.0011

# Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)								
FIII	X1P4B	X1P4M	X1P7B	X1P7M	X2P0B	X2P0M	X2P5B	X2P5M		
Α	0.0011	0.0012	0.0012	0.0013	0.0013	0.0014	0.0015	0.0017		

# Pin Capacitance (Cont'd.)

Pin				Capacita	nce (pF)			
' '''	X3P0B	X3P0M	X3P5B	X3P5M	X4P0B	X4P0M	X5P0B	X5P0M
Α	0.0017	0.0018	0.0022	0.0024	0.0024	0.0025	0.0027	0.0031

# Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)								
' '''	X6P0B	X6P0M	X7P5B	X7P5M	X9P0B	X9P0M	X11P0B	X11P0M		
Α	0.0030	0.0034	0.0040	0.0045	0.0045	0.0051	0.0057	0.0065		

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)							
' '''	X13P0B	X13P0M	X16P0B	X16P0M				
Α	0.0065	0.0072	0.0077	0.0087				

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)							
	X0P7B	X0P7M	X0P8B	X0P8M	X1P0B	X1P0M	X1P2B	X1P2M
$A \rightarrow Y \uparrow$	0.0245	0.0255	0.0246	0.0259	0.0253	0.0248	0.0285	0.0249
$A \rightarrow Y \downarrow$	0.0281	0.0340	0.0287	0.0353	0.0306	0.0341	0.0333	0.0342

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)							
	X1P4B	X1P4M	X1P7B	X1P7M	X2P0B	X2P0M	X2P5B	X2P5M
$A \rightarrow Y \uparrow$	0.0287	0.0246	0.0274	0.0245	0.0274	0.0235	0.0272	0.0241
$A \ \rightarrow \ Y \ \downarrow$	0.0331	0.0341	0.0321	0.0343	0.0316	0.0330	0.0309	0.0333

Description	Intrinsic Delay (ns)							
	X3P0B	X3P0M	X3P5B	X3P5M	X4P0B	X4P0M	X5P0B	X5P0M
$A \rightarrow Y \uparrow$	0.0272	0.0234	0.0252	0.0227	0.0255	0.0224	0.0255	0.0223
$A \rightarrow Y \downarrow$	0.0312	0.0327	0.0291	0.0312	0.0290	0.0305	0.0289	0.0306

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)							
	X6P0B	X6P0M	X7P5B	X7P5M	X9P0B	X9P0M	X11P0B	X11P0M
$A \rightarrow Y \uparrow$	0.0255	0.0221	0.0265	0.0232	0.0265	0.0231	0.0260	0.0225
$A \rightarrow Y \downarrow$	0.0289	0.0306	0.0296	0.0313	0.0291	0.0311	0.0289	0.0306

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	iptic	n	Intrinsic Delay (ns)						
				X13P0B	X13P0M	X16P0B	X16P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.0261	0.0224	0.0262	0.0227			
Α	$\rightarrow$	Υ	$\downarrow$	0.0292	0.0305	0.0293	0.0308			

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

De	scri	ptio	n	K <sub>load</sub> (ns/pF)							
				X0P7B	X0P7M	X0P8B	X0P8M	X1P0B	X1P0M	X1P2B	X1P2M
Α	$\rightarrow$	Υ	$\uparrow$	3.4444	3.4970	3.0413	3.0818	2.5067	2.5254	1.9133	1.9134
Α	$\rightarrow$	Υ	$\downarrow$	3.0310	2.1942	2.7217	1.9099	2.2322	1.5443	1.6896	1.1960

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)							
	X1P4B	X1P4M	X1P7B	X1P7M	X2P0B	X2P0M	X2P5B	X2P5M
$A \rightarrow Y \uparrow$	1.6547	1.6550	1.3780	1.3784	1.1896	1.1895	0.9320	0.9315
$A \rightarrow Y \downarrow$	1.4603	1.0331	1.2377	0.8462	1.0524	0.7210	0.8442	0.5772

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)							
	X3P0B	X3P0M	X3P5B	X3P5M	X4P0B	X4P0M	X5P0B	X5P0M
$A \rightarrow Y \uparrow$	0.7890	0.7885	0.6575	0.6575	0.5843	0.5842	0.4666	0.4663
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.7085	0.4846	0.6003	0.4087	0.5253	0.3613	0.4243	0.2898

Description	K <sub>load</sub> (ns/pF)							
	X6P0B	X6P0M	X7P5B	X7P5M	X9P0B	X9P0M	X11P0B	X11P0M
$A \rightarrow Y \uparrow$	0.3865	0.3862	0.3049	0.3046	0.2569	0.2568	0.2092	0.2091
$A \ \rightarrow \ Y \ \downarrow$	0.3485	0.2389	0.2781	0.1906	0.2340	0.1606	0.1920	0.1307

Process Technology:

CLN65G+

BUF

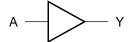
Description	K <sub>load</sub> (ns/pF)						
	X13P0B	X13P0M	X16P0B	X16P0M			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.1766	0.1764	0.1431	0.1430			
$A \rightarrow Y \downarrow$	0.1617	0.1103	0.1307	0.0915			

### **Cell Description**

The BUFH cell is a high-speed buffer of a single input (A). The output (Y) is represented by the logic equation:

Y = A

# **Logic Symbol**



### **Function Table**

Α	Υ
0	0
1	1

# **Cell Size**

Drive Strength	Height (um)	Width (um)
BUFHX0P7MA10TR	2.00	0.80
BUFHX0P8MA10TR	2.00	0.80
BUFHX1MA10TR	2.00	0.80
BUFHX1P2MA10TR	2.00	1.20
BUFHX1P4MA10TR	2.00	1.20
BUFHX1P7MA10TR	2.00	1.20
BUFHX2MA10TR	2.00	1.40
BUFHX2P5MA10TR	2.00	1.60
BUFHX3MA10TR	2.00	1.60
BUFHX3P5MA10TR	2.00	2.20
BUFHX4MA10TR	2.00	2.20
BUFHX5MA10TR	2.00	2.40
BUFHX6MA10TR	2.00	3.00
BUFHX7P5MA10TR	2.00	3.80
BUFHX9MA10TR	2.00	4.20
BUFHX11MA10TR	2.00	5.00
BUFHX13MA10TR	2.00	5.80
BUFHX16MA10TR	2.00	7.20



Pin		Power (uW/MHz)											
- ""	X0P7M	X1P7M	X2P0M	X2P5M									
Α	0.0028	0.0030	0.0033	0.0041	0.0045	0.0050	0.0057	0.0075					

# AC Power (Cont'd.)

Pin		Power (uW/MHz)										
	X3P0M	X3P5M	X4P0M	X5P0M	X6P0M	X7P5M	X9P0M	X11P0M				
Α	0.0084	0.0104	0.0113	0.0141	0.0166	0.0213	0.0252	0.0309				

# AC Power (Cont'd.)

Pin	Power (uW/MHz)					
F 1111	X13P0M	X16P0M				
Α	0.0362	0.0441				

# Pin Capacitance

Pin		Capacitance (pF)										
X0P7M X0P8M X1P0M X1P2M X1P4M X1P7M X2								X2P5M				
Α	0.0013	0.0014	0.0015	0.0017	0.0018	0.0019	0.0025	0.0031				

# Pin Capacitance (Cont'd.)

_	Pin		Capacitance (pF)											
•		X3P0M	X3P5M	X4P0M	X5P0M	X6P0M	X7P5M	X9P0M	X11P0M					
	Α	0.0035	0.0043	0.0047	0.0055	0.0067	0.0084	0.0101	0.0121					

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)					
	X13P0M	X16P0M				
Α	0.0143	0.0175				

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)										
	X0P7M	X0P8M	X1P0M	X1P2M	X1P4M	X1P7M	X2P0M	X2P5M			
$A \rightarrow Y \uparrow$	0.0209	0.0202	0.0193	0.0194	0.0191	0.0185	0.0170	0.0174			
$A \rightarrow Y \downarrow$	0.0267	0.0260	0.0248	0.0245	0.0244	0.0240	0.0218	0.0222			

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description			n	Intrinsic Delay (ns)										
				X3P0M	X3P5M	X4P0M	X5P0M	X6P0M	X7P5M	X9P0M	X11P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.0169	0.0176	0.0172	0.0172	0.0165	0.0172	0.0169	0.0171			
Α	$\rightarrow$	Υ	$\downarrow$	0.0218	0.0224	0.0219	0.0219	0.0212	0.0216	0.0213	0.0215			

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	ptic	n	Intrinsic Delay (ns)				
				X13P0M	X16P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.0167	0.0167			
Α	$\rightarrow$	Υ	$\downarrow$	0.0212	0.0212			

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)										
	X0P7M	X0P8M	X1P0M	X1P2M	X1P4M	X1P7M	X2P0M	X2P5M			
$A \rightarrow Y \uparrow$	3.4453	3.0763	2.5227	1.9035	1.6451	1.3694	1.1808	0.9266			
$A \ \rightarrow \ Y \ \downarrow$	2.1563	1.8859	1.5091	1.1576	1.0031	0.8295	0.7163	0.5716			

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)										
	X3P0M	X3P5M	X4P0M	X5P0M	X6P0M	X7P5M	X9P0M	X11P0M			
$A \rightarrow Y \uparrow$	0.7830	0.6536	0.5807	0.4642	0.3842	0.3034	0.2559	0.2084			
$A \ \rightarrow \ Y \ \downarrow$	0.4820	0.4035	0.3550	0.2846	0.2364	0.1881	0.1589	0.1292			

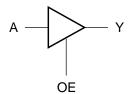
D	escri	iptic	n	K <sub>load</sub> (ns/pF)				
				X13P0M	X16P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.1761	0.1428			
Α	$\rightarrow$	Υ	$\downarrow$	0.1093	0.0908			

### **Cell Description**

The BUFZ cell provides the logical buffer of a single input (A) with an active-high output enable (OE). The output (Y) is tristated when the enable is low. When the enable is high, the output is represented by the logic equation:

$$Y = A$$

### **Logic Symbol**

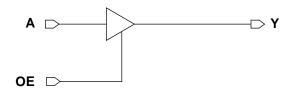


#### **Function Table**

OE	Α	Υ
0	Х	Ζ
1	0	0
1	1	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
BUFZX1MA10TR	2.00	2.20
BUFZX1P4MA10TR	2.00	2.20
BUFZX2MA10TR	2.00	3.00
BUFZX3MA10TR	2.00	3.20
BUFZX4MA10TR	2.00	3.80
BUFZX6MA10TR	2.00	5.40
BUFZX8MA10TR	2.00	7.00
BUFZX11MA10TR	2.00	8.80
BUFZX16MA10TR	2.00	12.00



Pin		Power (uW/MHz)											
-	X1P0M   X1P4M   X2P0M   X3P0M   X4P0M   X6P0M   X8P0M   X11P0M   X16								X16P0M				
Α	0.0008	0.0010	0.0015	0.0019	0.0025	0.0035	0.0046	0.0061	0.0087				
OE	0.0034	0.0044	0.0061	0.0083	0.0111	0.0153	0.0202	0.0269	0.0384				

# Pin Capacitance

Pin		Capacitance (pF)											
F 1111	X1P0M								X16P0M				
Α	0.0016	0.0019	0.0029	0.0037	0.0047	0.0064	0.0082	0.0106	0.0150				
OE	0.0018	0.0019	0.0022	0.0030	0.0036	0.0051	0.0066	0.0084	0.0109				
Υ	0.0013	0.0016	0.0026	0.0033	0.0042	0.0063	0.0085	0.0114	0.0166				

# Delays at 25°C,1.0V, Typical Process

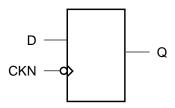
Description		Intrinsic Delay (ns)							
	X1P0M	X1P0M							X16P0M
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.0379	0.0353	0.0346	0.0332	0.0321	0.0342	0.0336	0.0343	0.0346
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.0459	0.0436	0.0421	0.0427	0.0411	0.0418	0.0415	0.0416	0.0414
$OE \rightarrow Y \uparrow$	0.0299	0.0282	0.0283	0.0262	0.0252	0.0278	0.0272	0.0280	0.0284
$OE \rightarrow Y \downarrow$	0.0410	0.0404	0.0401	0.0378	0.0381	0.0369	0.0366	0.0362	0.0359

Description	K <sub>load</sub> (ns/pF)								
	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	X11P0M	X16P0M
$A \rightarrow Y \uparrow$	2.2380	1.6300	1.1336	0.7554	0.5686	0.3746	0.2799	0.2043	0.1411
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	1.3663	0.9874	0.7043	0.4787	0.3528	0.2338	0.1756	0.1287	0.0887
$OE \rightarrow Y \uparrow$	2.2353	1.6282	1.1321	0.7546	0.5680	0.3743	0.2796	0.2041	0.1409
$OE \  o \ Y \ \downarrow$	1.3661	0.9873	0.7044	0.4787	0.3529	0.2338	0.1756	0.1286	0.0887

# **Cell Description**

The DFFNQ cell is a negative-edge triggered, static D-type flip-flop.

# **Logic Symbol**

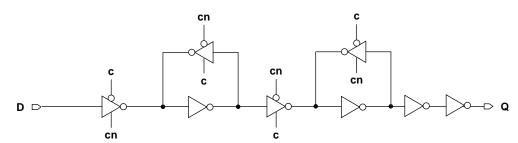


### **Function Table**

D	CKN	Q[n+1]
0	_	0
1	_	1
Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFNQX1MA10TR	2.00	4.20
DFFNQX2MA10TR	2.00	4.40
DFFNQX3MA10TR	2.00	4.80



Pin	Power (uW/MHz)							
F 1111	X1P0M	X2P0M	X3P0M					
D	0.0048	0.0059	0.0063					
CKN	0.0047	0.0053	0.0059					
Q	0.0047	0.0066	0.0083					

# Pin Capacitance

Pin	Capacitance (pF)							
F	X1P0M X2P0M X3P							
D	0.0013	0.0016	0.0016					
CKN	0.0010	0.0010	0.0011					

# Delays at 25°C,1.0V, Typical Process

Description	Intri	nsic Delay	(ns)	K <sub>load</sub> (ns/pF)			
	X1P0M X2P0M X3P0M			X1P0M	X2P0M	X3P0M	
$CKN \ \to \ Q \ \uparrow$	0.0906	0.0882	0.0878	2.3372	1.1657	0.7822	
$CKN \ \to \ Q \ \downarrow$	0.0847	0.0842	0.0862	1.4526	0.7226	0.4589	

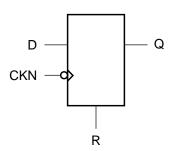
# Timing Constraints at 25°C,1.0V, Typical Process

Pin	Requirement				Interval (ns)			
F	INC.	quii	CIIIC	111	X1P0M	X2P0M	X3P0M	
	setup	$\uparrow$	$\rightarrow$	CKN	0.0039	0.0000	0.0000	
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0195	0.0195	0.0195	
	hold	$\uparrow$	$\rightarrow$	CKN	0.0156	0.0195	0.0156	
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0078	-0.0078	-0.0078	
CKN		min	pwl		0.8830	0.8830	0.8830	
CIXIV		min	pwh		0.8830	0.8830	0.8830	

#### **Cell Description**

The DFFNRPQ cell is a negative-edge triggered, static D-type flip-flop with asynchronous active-high reset (R).

# **Logic Symbol**

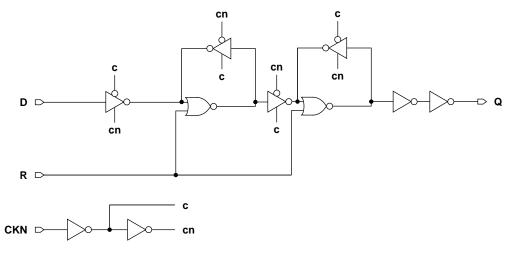


#### **Function Table**

R	D	CKN	Q[n+1]
1	Х	Х	0
0	0		0
0	1	_	1
0	Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFNRPQX1MA10TR	2.00	4.80
DFFNRPQX2MA10TR	2.00	5.20
DFFNRPQX3MA10TR	2.00	5.40



Pin	Power (uW/MHz)							
F 1111	X1P0M	X2P0M	X3P0M					
D	0.0050	0.0063	0.0065					
CKN	0.0049	0.0055	0.0060					
R	0.0014	0.0019	0.0022					
Q	0.0054	0.0070	0.0089					

# Pin Capacitance

Pin	Capacitance (pF)							
F	X1P0M	X2P0M	X3P0M					
D	0.0013	0.0016	0.0016					
CKN	0.0010	0.0010	0.0011					
R	0.0021	0.0024	0.0024					

# Delays at 25°C,1.0V, Typical Process

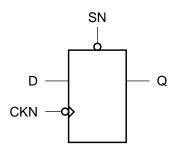
De	Description			Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)		
				X1P0M	X2P0M	X3P0M	X1P0M	X2P0M	X3P0M
CKN	$\rightarrow$	Q	$\uparrow$	0.1041	0.0964	0.0993	2.3369	1.1508	0.7850
CKN	$\rightarrow$	Q	$\downarrow$	0.0990	0.0948	0.0972	1.4577	0.7100	0.4615
R	$\rightarrow$	Q	$\downarrow$	0.0564	0.0590	0.0663	1.4551	0.7092	0.4610

Pin	Requirement			lı	nterval (ns	s)	
' '''	1	quii	CITIC		X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CKN	0.0117	0.0078	0.0078
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0234	0.0195	0.0195
	hold	$\uparrow$	$\rightarrow$	CKN	0.0156	0.0195	0.0195
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0117	-0.0078	-0.0078
CKN		mir	pwl		0.8830	0.8830	0.8830
CKIN		min	pwh		0.8830	0.8830	0.8830
		min	pwh		0.8830	0.8830	0.8830
R		reco	very		-0.0273	-0.0273	-0.0273
		rem	oval		0.0664	0.0742	0.0703

### **Cell Description**

The DFFNSQ cell is a negative-edge triggered, static D-type flip-flop with asynchronous active-low set (SN).

# **Logic Symbol**

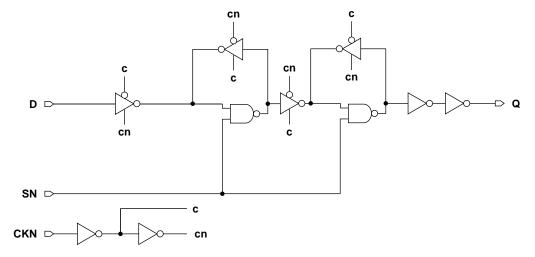


### **Function Table**

SN	D	CKN	Q[n+1]
0	Х	Х	1
1	0	_	0
1	1	_	1
1	Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFNSQX1MA10TR	2.00	4.80
DFFNSQX2MA10TR	2.00	5.20
DFFNSQX3MA10TR	2.00	5.80



Pin	Power (uW/MHz)							
F 1111	X1P0M	X2P0M	X3P0M					
D	0.0054	0.0064	0.0068					
CKN	0.0049	0.0056	0.0062					
SN	0.0016	0.0019	0.0022					
Q	0.0052	0.0067	0.0090					

# Pin Capacitance

Pin	Capacitance (pF)							
F 1111	X1P0M	X2P0M	X3P0M					
D	0.0013	0.0016	0.0016					
CKN	0.0010	0.0010	0.0011					
SN	0.0017	0.0018	0.0018					

# Delays at 25°C,1.0V, Typical Process

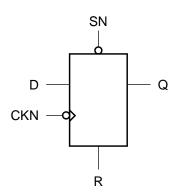
De	scrip	tion		Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)		
				X1P0M	X2P0M	X3P0M	X1P0M	X2P0M	X3P0M
CKN	$\rightarrow$	Q	<b>↑</b>	0.0939	0.0929	0.0956	2.3793	1.1635	0.7819
CKN	$\rightarrow$	Q	$\downarrow$	0.0931	0.0934	0.0974	1.4677	0.7263	0.4612
SN	$\rightarrow$	Q	$\uparrow$	0.0580	0.0620	0.0698	2.3771	1.1631	0.7816

Pin	Ro	Requirement				nterval (ns	s)
' '''	110	quii	CITIC		X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CKN	0.0078	0.0039	0.0078
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0195	0.0156	0.0156
	hold	$\uparrow$	$\rightarrow$	CKN	0.0117	0.0195	0.0156
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0078	-0.0039	-0.0039
CKN		mir	pwl		0.8830	0.8830	0.8830
CKIN		min	pwh		0.8830	0.8830	0.8830
		mir	pwl		0.8830	0.8830	0.8830
SN		reco	very		-0.0195	-0.0234	-0.0195
		rem	oval		0.0469	0.0508	0.0469

#### **Cell Description**

The DFFNSRPQ cell is a negative-edge triggered, static D-type flip-flop with asynchronous active-high reset (R) and asynchronous active-low set (SN). Set is dominant over reset if both are asserted.

# **Logic Symbol**

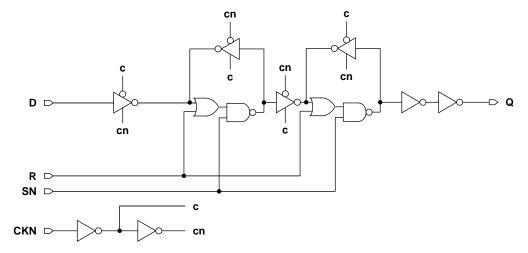


#### **Function Table**

R	SN	D	CKN	Q
1	1	Х	Х	0
0	0	Х	Х	1
1	0	Х	Х	1
0	1	0	_	0
0	1	1	_	1
0	1	Х		Q

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFNSRPQX1MA10TR	2.00	6.00
DFFNSRPQX2MA10TR	2.00	6.20
DFFNSRPQX3MA10TR	2.00	6.40



Pin	Power (uW/MHz)						
FIII	X1P0M	X2P0M	X3P0M				
D	0.0052	0.0065	0.0067				
CKN	0.0047	0.0054	0.0059				
SN	0.0017	0.0021	0.0023				
R	0.0018	0.0024	0.0026				
Q	0.0053	0.0069	0.0090				

# Pin Capacitance

Pin	Capacitance (pF)						
FIII	X1P0M	X2P0M	X3P0M				
D	0.0013	0.0016	0.0016				
CKN	0.0010	0.0010	0.0011				
SN	0.0026	0.0030	0.0029				
R	0.0021	0.0025	0.0024				

# Delays at 25°C,1.0V, Typical Process

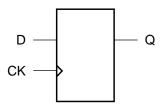
De	scrip	tion		Intri	nsic Delay	sic Delay (ns)		K <sub>load</sub> (ns/pF)		
				X1P0M	X2P0M	X3P0M	X1P0M	X2P0M	X3P0M	
CKN	$\rightarrow$	Q	$\uparrow$	0.1136	0.1154	0.1102	2.3368	1.1549	0.7861	
CKN	$\rightarrow$	Q	$\downarrow$	0.1100	0.1145	0.1088	1.4593	0.7215	0.4638	
SN	$\rightarrow$	Q	$\uparrow$	0.0645	0.0688	0.0745	2.3336	1.1542	0.7857	
SN	$\rightarrow$	Q	$\downarrow$	0.0774	0.0835	0.0897	1.4577	0.7212	0.4637	
R	$\rightarrow$	Q	$\downarrow$	0.0755	0.0819	0.0881	1.4577	0.7212	0.4636	

Pin	Po	au i	eme	nt	Interval (ns)				
F	ive.	quii	CITIC	111	X1P0M	X2P0M	X3P0M		
	setup	$\uparrow$	$\rightarrow$	CKN	0.0195	0.0039	0.0156		
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0273	0.0195	0.0234		
	hold	$\uparrow$	$\rightarrow$	CKN	0.0156	0.0273	0.0195		
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0078	-0.0039	-0.0039		
CKN	minpwl				0.8830	0.8830	0.8830		
CIXIV	minpwh				0.8830	0.8830	0.8830		
		min	pwl		0.8830	0.8830	0.8830		
SN		reco	very		0.0000	-0.0078	-0.0039		
	removal				0.0195	0.0312	0.0234		
	minpwh				0.8830	0.8830	0.8830		
R	recovery		-0.0078	-0.0273	-0.0117				
		rem	oval		0.0430	0.0586	0.0430		

### **Cell Description**

The DFFQ cell is a positive-edge triggered, static D-type flip-flop. The cell has a single output  $(\mathbf{Q})$ .

# **Logic Symbol**

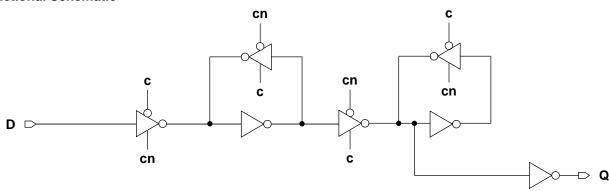


#### **Function Table**

D	CK	Q[n+1]
0		0
1		1
Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFQX0P5MA10TR	2.00	4.00
DFFQX1MA10TR	2.00	4.20
DFFQX2MA10TR	2.00	4.40
DFFQX3MA10TR	2.00	4.80
DFFQX4MA10TR	2.00	5.00



Pin	Power (uW/MHz)								
F III	X0P5M	(OP5M X1P0M X2F		X3P0M	X4P0M				
D	0.0037	0.0048	0.0060	0.0065	0.0066				
CK	0.0036	0.0041	0.0047	0.0053	0.0055				
Q	0.0031	0.0040	0.0057	0.0080	0.0106				

# Pin Capacitance

Pin	Capacitance (pF)									
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
D	0.0011	0.0014	0.0017	0.0018	0.0017					
CK	0.0009	0.0009	0.0010	0.0011	0.0012					

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)					
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
$CK \ \to \ Q \ \uparrow$	0.0925	0.0784	0.0752	0.0754	0.0736	
$CK \ \to \ Q \ \downarrow$	0.1016	0.0854	0.0821	0.0825	0.0767	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

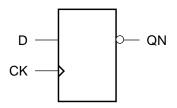
Description		ŀ	< <sub>load</sub> (ns/pF	)	
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
$CK \to Q \uparrow$	4.1883	2.3336	1.1633	0.7833	0.5862
$CK \to Q \downarrow$	2.4669	1.3332	0.6623	0.4568	0.3342

Pin	n Requirement Interval (ns)						5)		
F 111	1/60	Requirement		X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
	setup	$\uparrow$	$\rightarrow$	CK	0.0195	0.0156	0.0117	0.0156	0.0156
D	setup	$\downarrow$	$\rightarrow$	CK	0.0156	0.0117	0.0117	0.0156	0.0156
	hold	$\uparrow$	$\rightarrow$	CK	-0.0078	-0.0039	0.0000	-0.0039	-0.0039
	hold	$\downarrow$	$\rightarrow$	CK	0.0039	0.0039	0.0039	0.0000	0.0039
СК	minpwh		0.8830	0.8830	0.8830	0.8830	0.8830		
OIX		minpwl			0.8830	0.8830	0.8830	0.8830	0.8830

### **Cell Description**

The DFFQN cell is a positive-edge triggered, static D-type flip-flop. The cell has a single output (QN).

# **Logic Symbol**

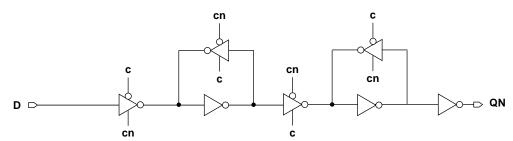


# **Function Table**

D	CK	QN[n+1]
0		1
1		0
Х		QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFQNX0P5MA10TR	2.00	4.00
DFFQNX1MA10TR	2.00	4.20
DFFQNX2MA10TR	2.00	4.40
DFFQNX3MA10TR	2.00	4.80



Pin		Power (u	ıW/MHz)	
	X0P5M	X1P0M	X2P0M	X3P0M
D	0.0037	0.0049	0.0060	0.0067
CK	0.0036	0.0040	0.0046	0.0055
QN	0.0032	0.0038	0.0056	0.0080

# Pin Capacitance

Pin	Capacitance (pF)							
F 111	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0011	0.0014	0.0017	0.0018				
CK	0.0009	0.0009	0.0010	0.0012				

### Delays at 25°C,1.0V, Typical Process

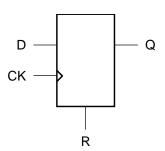
Description		K <sub>load</sub> (	ns/pF)					
X0P5M X1P0M X2P0M X3P0M					X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0886	0.0734	0.0720	0.0660	4.2553	2.3600	1.1728	0.7875
$CK \ \to \ QN \ \downarrow$	0.0867	0.0733	0.0758	0.0736	2.9083	1.5358	0.7639	0.5181

Pin	Por	auir.	emer	<b>.</b> +	Interval (ns)			
FIII	Vec	quii	emei	11.	X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0195	0.0156	0.0156	0.0156
D	setup	$\downarrow$	$\rightarrow$	CK	0.0156	0.0156	0.0156	0.0195
	hold	$\uparrow$	$\rightarrow$	CK	-0.0039	-0.0039	0.0000	0.0000
	hold	$\downarrow$	$\rightarrow$	CK	0.0078	0.0078	0.0039	0.0039
СК	minpwh				0.8830	0.8830	0.8830	0.8830
CIX		min	owl		0.8830	0.8830	0.8830	0.8830

### **Cell Description**

The DFFRPQ cell is a positive-edge triggered, static D-type flip-flop with asynchronous active-high reset (R). The cell has a single output (Q).

# **Logic Symbol**

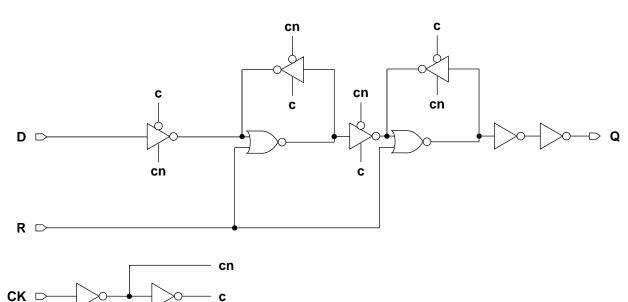


#### **Function Table**

R	D	CK	Q[n+1]
1	Х	Х	0
0	0		0
0	1		1
0	Х	_	Q[n]

### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFRPQX0P5MA10TR	2.00	4.80
DFFRPQX1MA10TR	2.00	4.80
DFFRPQX2MA10TR	2.00	5.20
DFFRPQX3MA10TR	2.00	5.60
DFFRPQX4MA10TR	2.00	6.20



Pin		Pov	ver (uW/N	IHz)	
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
D	0.0041	0.0052	0.0064	0.0069	0.0070
CK	0.0039	0.0043	0.0050	0.0055	0.0060
R	0.0014	0.0015	0.0019	0.0023	0.0026
Q	0.0035	0.0048	0.0061	0.0082	0.0112

# Pin Capacitance

Pin		Сар	acitance	(pF)	
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
D	0.0011	0.0014	0.0018	0.0018	0.0016
CK	0.0009	0.0010	0.0010	0.0011	0.0012
R	0.0018	0.0023	0.0026	0.0026	0.0027

# Delays at 25°C,1.0V, Typical Process

De	escri	otior	1		Intri	nsic Delay	(ns)		
				X0P5M X1P0M X2P0M X3P0M X4P0M					
CK	$\rightarrow$	Q	$\uparrow$	0.1050	0.0908	0.0815	0.0813	0.0838	
CK	$\rightarrow$	Q	$\downarrow$	0.1122	0.0930	0.0881	0.0878	0.0861	
R	$\rightarrow$	Q	$\downarrow$	0.0566	0.0525	0.0567	0.0629	0.0706	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

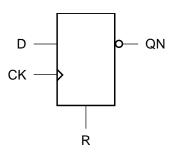
De	escri	otior	1		ŀ	ເ <sub>load</sub> (ns/pF	)		
				X0P5M X1P0M X2P0M X3P0M X					
CK	$\rightarrow$	Q	$\uparrow$	4.2125	2.3987	1.1527	0.7794	0.5803	
CK	$\rightarrow$	Q	$\downarrow$	2.6008	1.3218	0.7210	0.4596	0.3341	
R	$\rightarrow$	Q	$\downarrow$	2.5891	1.3204	0.7207	0.4595	0.3342	

Pin	Requi	romor	nt .		Interval (ns)				
	Requi	Cilici	11.	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
	setup ↑	$\rightarrow$	CK	0.0352	0.0195	0.0195	0.0195	0.0195	
D	setup ↓	$\rightarrow$	CK	0.0195	0.0156	0.0156	0.0195	0.0195	
	hold ↑	$\rightarrow$	CK	-0.0078	-0.0039	-0.0039	-0.0039	0.0000	
	hold ↓	$\rightarrow$	CK	0.0039	0.0039	0.0039	0.0000	0.0000	
СК	min	pwh		0.8830	0.8830	0.8830	0.8830	0.8830	
CK	mir	npwl		0.8830	0.8830	0.8830	0.8830	0.8830	
	minpwh			0.8830	0.8830	0.8830	0.8830	0.8830	
R	recovery			0.0156	0.0000	0.0039	0.0039	0.0000	
	rem	ioval		0.0117	0.0391	0.0430	0.0430	0.0352	

#### **Cell Description**

The DFFRPQN cell is a high-speed, positive-edge triggered, static D-type flip-flop with asynchronous active-high reset (R). The cell has a single inverted output (QN).

# **Logic Symbol**

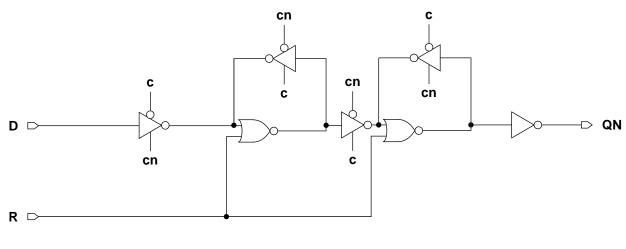


#### **Function Table**

R	D	CK	QN[n+1]
1	Х	Х	1
0	0		1
0	1		0
0	Х	_	QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFRPQNX0P5MA10TR	2.00	4.80
DFFRPQNX1MA10TR	2.00	4.80
DFFRPQNX2MA10TR	2.00	5.20
DFFRPQNX3MA10TR	2.00	5.60



Pin	Power (uW/MHz)							
' '''	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0042	0.0053	0.0066	0.0069				
CK	0.0038	0.0044	0.0048	0.0057				
R	0.0015	0.0014	0.0018	0.0020				
QN	0.0035	0.0044	0.0066	0.0096				

# Pin Capacitance

Pin	Capacitance (pF)							
FIII	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0011	0.0014	0.0019	0.0018				
CK	0.0009	0.0009	0.0010	0.0012				
R	0.0019	0.0024	0.0026	0.0026				

# Delays at 25°C,1.0V, Typical Process

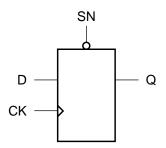
Description	Intrinsic Delay (ns)				K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
CK → QN ↑	0.0927	0.0801	0.0755	0.0747	4.3042	2.3596	1.1874	0.8001
$CK \to QN \downarrow$	0.0930	0.0847	0.0842	0.0887	3.1235	1.5824	0.7592	0.5240
$R \rightarrow QN \uparrow$	0.0349	0.0382	0.0494	0.0607	4.2418	2.3539	1.1861	0.7991

Pin	Poquiror	Requirement		Interval (ns)				
F 1111	Nequirei	Hent	X0P5M	X1P0M	X2P0M	X3P0M		
	setup ↑	→ CK	0.0312	0.0234	0.0195	0.0195		
D	setup ↓	→ CK	0.0234	0.0156	0.0156	0.0234		
	hold ↑	→ CK	-0.0078	-0.0039	-0.0039	0.0000		
	hold ↓	→ CK	0.0039	0.0039	0.0039	0.0000		
СК	minpw	vh	0.8830	0.8830	0.8830	0.8830		
CIX	minpv	νl	0.8830	0.8830	0.8830	0.8830		
	minpwh		0.8830	0.8830	0.8830	0.8830		
R	recove	ery	0.0117	0.0039	0.0000	0.0039		
	remov	al	0.0156	0.0391	0.0352	0.0312		

#### **Cell Description**

The DFFSQ cell is a high-speed, positive-edge triggered, static D-type flip-flop with asynchronous active-low set (SN). The cell has a single output (Q).

# **Logic Symbol**

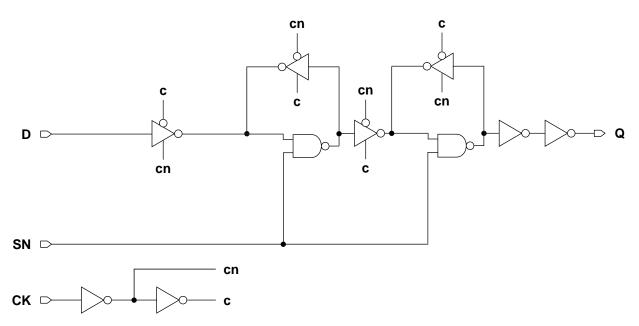


#### **Function Table**

SN	D	CK	Q[n+1]
0	Х	Х	1
1	0		0
1	1		1
1	Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFSQX0P5MA10TR	2.00	5.00
DFFSQX1MA10TR	2.00	5.00
DFFSQX2MA10TR	2.00	5.40
DFFSQX3MA10TR	2.00	5.60
DFFSQX4MA10TR	2.00	5.80



Pin	Power (uW/MHz)									
-	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
D	0.0042	0.0052	0.0066	0.0068	0.0070					
CK	0.0037	0.0043	0.0050	0.0054	0.0058					
SN	0.0014	0.0018	0.0022	0.0024	0.0027					
Q	0.0033	0.0045	0.0063	0.0081	0.0112					

# Pin Capacitance

Pin	Capacitance (pF)									
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
D	0.0012	0.0013	0.0018	0.0018	0.0017					
CK	0.0009	0.0010	0.0010	0.0011	0.0012					
SN	0.0018	0.0022	0.0027	0.0027	0.0027					

# Delays at 25°C,1.0V, Typical Process

Description			1	Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
CK	$\rightarrow$	Q	$\uparrow$	0.0967	0.0859	0.0793	0.0796	0.0779	
CK	$\rightarrow$	Q	$\downarrow$	0.1109	0.0946	0.0887	0.0908	0.0872	
SN	$\rightarrow$	Q	$\uparrow$	0.0665	0.0640	0.0687	0.0731	0.0795	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

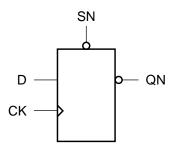
Description	K <sub>load</sub> (ns/pF)					
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
$CK \to Q \uparrow$	4.1893	2.3343	1.1600	0.7831	0.5838	
$CK \to Q \downarrow$	2.4784	1.3350	0.6619	0.4584	0.3323	
$SN \  o \ Q \  \uparrow$	4.1924	2.3355	1.1603	0.7834	0.5837	

Pin	Regu	Requirement			Interval (ns)					
	Requirement			X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
	setup ´	$\uparrow$ $\rightarrow$	CK	0.0234	0.0156	0.0156	0.0156	0.0195		
D	setup	$\downarrow$ $\rightarrow$	CK	0.0195	0.0117	0.0117	0.0156	0.0156		
	hold ´	$\uparrow$ $\rightarrow$	CK	-0.0078	-0.0039	-0.0039	-0.0039	-0.0039		
	hold	$\downarrow$ $\rightarrow$	CK	0.0039	0.0078	0.0039	0.0039	0.0039		
СК	mi	npwh		0.8830	0.8830	0.8830	0.8830	0.8830		
OIX	m	inpwl		0.8830	0.8830	0.8830	0.8830	0.8830		
	minpwl			0.8830	0.8830	0.8830	0.8830	0.8830		
SN	recovery			-0.0273	-0.0312	-0.0312	-0.0312	-0.0234		
	rer	moval		0.0508	0.0625	0.0625	0.0625	0.0508		

#### **Cell Description**

The DFFSQN cell is a positive-edge triggered, static D-type flip-flop with asynchronous active-low set (SN). The cell has a single inverted output (QN).

# **Logic Symbol**

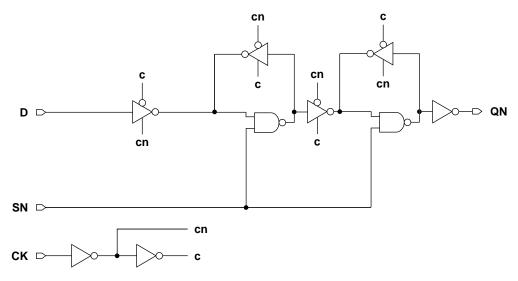


#### **Function Table**

SN	D	СК	QN
0	Х	Х	0
1	0		1
1	1		0
1	Х		QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFSQNX0P5MA10TR	2.00	5.00
DFFSQNX1MA10TR	2.00	5.00
DFFSQNX2MA10TR	2.00	5.40
DFFSQNX3MA10TR	2.00	5.60



Pin	Power (uW/MHz)							
	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0043	0.0054	0.0066	0.0068				
CK	0.0036	0.0041	0.0048	0.0055				
SN	0.0014	0.0018	0.0022	0.0024				
QN	0.0035	0.0044	0.0062	0.0089				

# Pin Capacitance

Pin	Capacitance (pF)							
F	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0012	0.0013	0.0018	0.0018				
CK	0.0009	0.0009	0.0010	0.0012				
SN	0.0019	0.0024	0.0026	0.0025				

# Delays at 25°C,1.0V, Typical Process

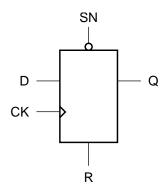
Description	Intrinsic Delay (ns)				K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0961	0.0807	0.0790	0.0776	4.2816	2.3581	1.1748	0.7956
$CK \to QN \downarrow$	0.0869	0.0797	0.0788	0.0824	2.9117	1.5399	0.7923	0.5319
$SN \  o \ QN \ \downarrow$	0.0539	0.0560	0.0699	0.0850	2.7502	1.4958	0.7802	0.5241

Pin	Requirement			Interval (ns)				
	Requii	CITICI		X0P5M	X1P0M	X2P0M	X3P0M	
	setup ↑	$\rightarrow$	CK	0.0234	0.0234	0.0156	0.0195	
D	setup ↓	$\rightarrow$	CK	0.0195	0.0117	0.0156	0.0195	
	hold ↑	$\rightarrow$	CK	-0.0078	-0.0078	-0.0039	-0.0039	
	hold ↓	$\rightarrow$	CK	0.0078	0.0078	0.0078	0.0039	
СК	min	owh		0.8830	0.8830	0.8830	0.8830	
Cit	min	pwl		0.8830	0.8830	0.8830	0.8830	
	minpwl			0.8830	0.8830	0.8830	0.8830	
SN	reco	recovery			-0.0352	-0.0312	-0.0234	
	rem	oval		0.0508	0.0664	0.0625	0.0547	

### **Cell Description**

The DFFSRPQ cell is a positive-edge triggered, static D-type flip-flop with asynchronous active-low reset (R) and set (SN), and set dominating reset.

# **Logic Symbol**

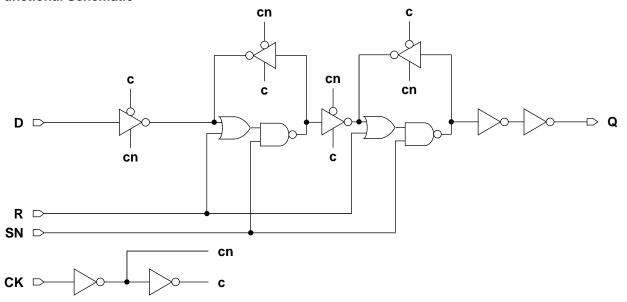


### **Function Table**

R	SN	D	СК	Q[n+1]
1	1	Х	Х	0
1	0	Х	Х	1
0	0	Х	Х	1
0	1	0		0
0	1	1		1
0	1	Х		Q[n]

### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFSRPQX0P5MA10TR	2.00	6.00
DFFSRPQX1MA10TR	2.00	6.00
DFFSRPQX2MA10TR	2.00	6.20
DFFSRPQX3MA10TR	2.00	6.40
DFFSRPQX4MA10TR	2.00	7.00



Pin	Power (uW/MHz)								
F 1111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
D	0.0041	0.0053	0.0065	0.0068	0.0070				
CK	0.0050	0.0055	0.0064	0.0067	0.0072				
SN	0.0014	0.0019	0.0022	0.0024	0.0027				
R	0.0014	0.0020	0.0024	0.0027	0.0030				
Q	0.0040	0.0052	0.0071	0.0090	0.0118				

# Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
D	0.0011	0.0013	0.0017	0.0017	0.0017				
CK	0.0009	0.0009	0.0010	0.0011	0.0012				
SN	0.0025	0.0029	0.0031	0.0031	0.0031				
R	0.0016	0.0020	0.0021	0.0022	0.0022				

# Delays at 25°C,1.0V, Typical Process

Description			1	Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
CK	$\rightarrow$	Q	$\uparrow$	0.1170	0.0964	0.0933	0.0937	0.0953	
CK	$\rightarrow$	Q	$\downarrow$	0.1280	0.1018	0.0989	0.1024	0.1003	
SN	$\rightarrow$	Q	$\uparrow$	0.0707	0.0692	0.0765	0.0781	0.0804	
SN	$\rightarrow$	Q	$\downarrow$	0.0735	0.0667	0.0760	0.0835	0.0904	
R	$\rightarrow$	Q	$\downarrow$	0.0718	0.0648	0.0743	0.0817	0.0884	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

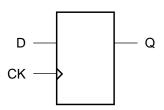
Descript	ion	K <sub>load</sub> (ns/pF)						
		X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
CK → C	ງ ↑	4.2057	2.3338	1.1539	0.7790	0.5857		
CK → C	Q ↓	2.6228	1.3346	0.6711	0.4628	0.3345		
SN → C	⊋ ↑	4.2036	2.3345	1.1538	0.7791	0.5855		
SN → C	Q ↓	2.6062	1.3322	0.6710	0.4627	0.3346		
$R \rightarrow 0$	Q ↓	2.6062	1.3321	0.6710	0.4626	0.3346		

D:	D		- 4		lı	nterval (ns	s)	
Pin	Require	Requirement –		X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
	setup ↑	$\rightarrow$	CK	0.0391	0.0273	0.0234	0.0234	0.0234
D	setup ↓	$\rightarrow$	CK	0.0234	0.0234	0.0195	0.0234	0.0273
	hold ↑	$\rightarrow$	CK	-0.0078	-0.0039	0.0000	0.0000	0.0000
	hold ↓	$\rightarrow$	CK	0.0039	0.0039	0.0039	0.0039	0.0000
СК	minp	owh		0.8830	0.8830	0.8830	0.8830	0.8830
CIX	minpwl		0.8830	0.8830	0.8830	0.8830	0.8830	
	minpwl		0.8830	0.8830	0.8830	0.8830	0.8830	
SN	recovery		-0.0156	-0.0156	-0.0156	-0.0117	-0.0039	
	removal		0.0352	0.0352	0.0352	0.0312	0.0273	
	minpwh		0.8830	0.8830	0.8830	0.8830	0.8830	
R	recovery		0.0195	0.0117	0.0156	0.0156	0.0117	
	remo	oval		0.0156	0.0234	0.0195	0.0195	0.0156

#### **Cell Description**

The DFFYQ cell is a positive-edge triggered, static D-type flip-flop to be used in synchronizing circuitry between asynchronous systems. The cell has a single output (Q) and overdriven feedback loops to increase MTBF due to metastability.

# **Logic Symbol**

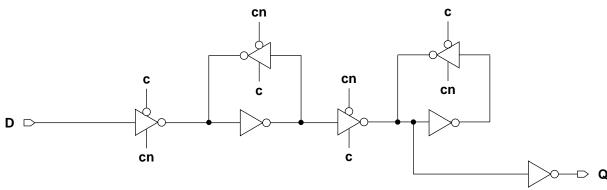


#### **Function Table**

D	CK	Q[n+1]
0		0
1		1
Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
DFFYQX1MA10TR	2.00	4.20
DFFYQX2MA10TR	2.00	4.60
DFFYQX3MA10TR	2.00	4.80
DFFYQX4MA10TR	2.00	5.40



Pin	Power (uW/MHz)							
' '''	X1P0M	X2P0M	X3P0M	X4P0M				
D	0.0055	0.0068	0.0067	0.0073				
CK	0.0055	0.0065	0.0062	0.0074				
Q	0.0047	0.0063	0.0091	0.0120				

# Pin Capacitance

Pin	Capacitance (pF)							
F	X1P0M	X2P0M	X3P0M	X4P0M				
D	0.0014	0.0017	0.0017	0.0018				
CK	0.0013	0.0016	0.0012	0.0015				

# Delays at 25°C,1.0V, Typical Process

Description		Intrinsic I	Delay (ns)			K <sub>load</sub> (	ns/pF)	
	X1P0M	X2P0M	X3P0M	X4P0M	X1P0M	X2P0M	X3P0M	X4P0M
CK → Q ↑	0.0751	0.0676	0.0763	0.0711	2.3326	1.1637	0.7847	0.5869
$CK \ \to \ Q \ \downarrow$	0.0802	0.0734	0.0852	0.0760	1.4505	0.7216	0.4591	0.3341

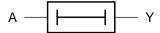
Pin	Po	Requirement			Interval (ns)				
FIII	I.e.				X1P0M	X2P0M	X3P0M	X4P0M	
	setup	<b>↑</b>	$\rightarrow$	CK	0.0195	0.0156	0.0156	0.0156	
D	setup	$\downarrow$	$\rightarrow$	CK	0.0234	0.0234	0.0195	0.0273	
	hold	$\uparrow$	$\rightarrow$	CK	-0.0078	-0.0039	-0.0039	-0.0039	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0039	-0.0039	0.0000	-0.0039	
СК	minpwh		0.8830	0.8830	0.8830	0.8830			
		minpwl			0.8830	0.8830	0.8830	0.8830	

### **Cell Description**

The DLY2 cell provides the logical delay of a single input (A). The output (Y) is represented by the logic equation:

Y = A

# **Logic Symbol**



### **Function Table**

Α	Υ
0	0
1	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)	
DLY2X0P5MA10TR	2.00	1.20	



Pin	Power (uW/MHz)
	X0P5M
Α	0.0028

# Pin Capacitance

Pin	Capacitance (pF)
-	X0P5M
Α	0.0014

# Delays at 25°C,1.0V, Typical Process

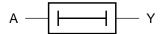
Description	Intrinsic Delay (ns)	K <sub>load</sub> (ns/pF)		
	X0P5M	X0P5M		
$A \rightarrow Y$	0.0450	4.7442		
$A \rightarrow Y$	0.0634	2.9678		

### **Cell Description**

The DLY4 cell provides the logical delay of a single input (A). The output (Y) is represented by the logic equation:

Y = A

# **Logic Symbol**



### **Function Table**

Α	Υ
0	0
1	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)	
DLY4X0P5MA10TR	2.00	2.20	



Pin	Power (uW/MHz)
F 1111	X0P5M
Α	0.0053

# Pin Capacitance

Pin	Capacitance (pF)
F III	X0P5M
Α	0.0014

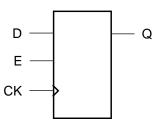
# Delays at 25°C,1.0V, Typical Process

Description			n	Intrinsic Delay (ns)	K <sub>load</sub> (ns/pF)		
				X0P5M	X0P5M		
Α	$\rightarrow$	Υ	$\uparrow$	0.1308	4.7047		
Α	$\rightarrow$	Υ	$\downarrow$	0.1481	2.9586		

### **Cell Description**

The EDFFQ cell is a positive-edge triggered, static D-type flip-flop with a synchronous, active-high enable (E). The cell has a single output (Q).

# **Logic Symbol**

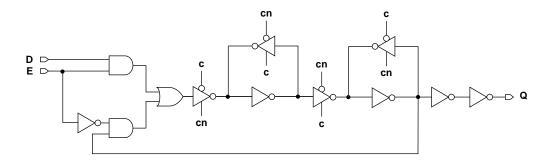


### **Function Table**

Е	D	CK	Q[n+1]
0	Х	Х	Q[n]
1	0		0
1	1		1
Х	Х		Q[n]

### **Cell Size**

Drive Strength	Height (um)	Width (um)
EDFFQX0P5MA10TR	2.00	6.20
EDFFQX1MA10TR	2.00	6.20
EDFFQX2MA10TR	2.00	6.60
EDFFQX3MA10TR	2.00	6.60



Pin	Power (uW/MHz)						
	X0P5M	X1P0M	X2P0M	X3P0M			
D	0.0061	0.0069	0.0086	0.0095			
CK	0.0038	0.0044	0.0050	0.0058			
Е	0.0060	0.0070	0.0086	0.0094			
Q	0.0052	0.0060	0.0082	0.0107			

# Pin Capacitance

Pin	Capacitance (pF)							
F 111	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0012	0.0011	0.0013	0.0014				
CK	0.0009	0.0010	0.0010	0.0012				
Е	0.0022	0.0023	0.0028	0.0028				

# Delays at 25°C,1.0V, Typical Process

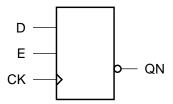
Description		Intrinsic I	Delay (ns)			K <sub>load</sub> (	ns/pF)	
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
CK → Q ↑	0.0935	0.0783	0.0739	0.0711	4.2855	2.3344	1.1614	0.7855
$CK \ \to \ Q \ \downarrow$	0.0860	0.0724	0.0728	0.0739	3.0069	1.5219	0.7553	0.5148

Pin	Requirement			Interval (ns)				
· · · ·	Requirement				X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0430	0.0391	0.0430
D	setup	$\downarrow$	$\rightarrow$	CK	0.0586	0.0508	0.0508	0.0508
	hold	$\uparrow$	$\rightarrow$	CK	-0.0195	-0.0195	-0.0156	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0391	-0.0352	-0.0352	-0.0312
СК	minpwh			0.8830	0.8830	0.8830	0.8830	
CIX		minp	owl		0.8830	0.8830	0.8830	0.8830
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0547	0.0508	0.0508
E	setup	$\downarrow$	$\rightarrow$	CK	0.0469	0.0391	0.0391	0.0391
	hold	$\uparrow$	$\rightarrow$	CK	-0.0312	-0.0273	-0.0234	-0.0273
	hold	$\downarrow$	$\rightarrow$	CK	-0.0312	-0.0273	-0.0234	-0.0273

### **Cell Description**

The EDFFQN cell is a positive-edge triggered, static D-type flip-flop with synchronous active-high enable (E). The cell has a single inverted output (QN).

# **Logic Symbol**

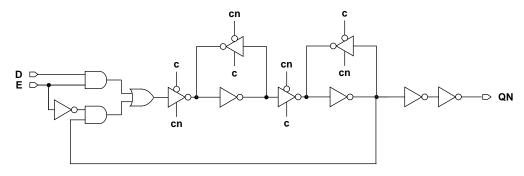


#### **Function Table**

Е	D	CK	QN[n+1]
0	Х	Х	QN[n]
1	0		1
1	1		0
Х	Х		QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
EDFFQNX0P5MA10TR	2.00	6.20
EDFFQNX1MA10TR	2.00	6.20
EDFFQNX2MA10TR	2.00	6.60
EDFFQNX3MA10TR	2.00	7.00



Pin	Power (uW/MHz)								
	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0056	0.0068	0.0086	0.0097					
CK	0.0038	0.0043	0.0050	0.0057					
Е	0.0056	0.0067	0.0082	0.0087					
QN	0.0061	0.0068	0.0087	0.0108					

# Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0011	0.0012	0.0015	0.0015					
CK	0.0009	0.0010	0.0010	0.0011					
Е	0.0022	0.0025	0.0030	0.0034					

# Delays at 25°C,1.0V, Typical Process

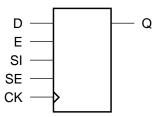
Description		Intrinsic I	Delay (ns)		K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0941	0.0788	0.0741	0.0699	4.2978	2.3352	1.1654	0.7854
$CK \to QN \downarrow$	0.0868	0.0731	0.0729	0.0728	3.0219	1.6301	0.7613	0.5196

Pin	Requirement			Interval (ns)				
· · · ·	Requirement				X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0430	0.0391	0.0430
D	setup	$\downarrow$	$\rightarrow$	CK	0.0508	0.0469	0.0430	0.0469
	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0234	-0.0195	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0117	-0.0117	-0.0078	-0.0117
СК	minpwh			0.8830	0.8830	0.8830	0.8830	
CIX		minpwl			0.8830	0.8830	0.8830	0.8830
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0469	0.0391	0.0430
E	setup	$\downarrow$	$\rightarrow$	CK	0.0391	0.0352	0.0312	0.0352
	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0234	-0.0234	-0.0234
	hold	$\downarrow$	$\rightarrow$	CK	-0.0078	-0.0117	-0.0078	-0.0078

#### **Cell Description**

The ESDFFQ cell is a positive-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and synchronous active-high enable (E). The cell has a single output (Q).

# **Logic Symbol**

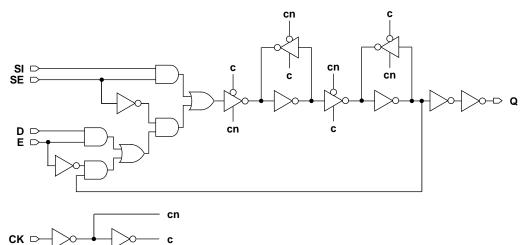


#### **Function Table**

D	Ε	SI	SE	CK	Q[n+1]
Х	Х	1	1		1
Х	Х	0	1		0
Х	0	Х	0		Q[n]
0	1	Х	0		0
1	1	Х	0		1
Х	Х	Х	Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
ESDFFQX0P5MA10TR	2.00	7.60
ESDFFQX1MA10TR	2.00	7.60
ESDFFQX2MA10TR	2.00	7.80
ESDFFQX3MA10TR	2.00	8.00



Pin	Power (uW/MHz)									
• •••	X0P5M	X1P0M	X2P0M	X3P0M						
SI	0.0053	0.0064	0.0075	0.0082						
SE	0.0058 0.0069		0.0081	0.0087						
D	0.0072	0.0085	0.0103	0.0109						
CK	0.0039	0.0044	0.0052	0.0059						
Е	0.0070	0.0086	0.0099	0.0106						
Q	0.0052	0.0061	0.0086	0.0106						

# Pin Capacitance

Pin	Capacitance (pF)								
FIII	X0P5M	X1P0M	X2P0M	X3P0M					
SI	0.0008	0.0007	0.0007	0.0007					
SE	0.0017	0.0017	0.0019	0.0018					
D	0.0012	0.0012	0.0014	0.0014					
CK	0.0009 0.0009		0.0011	0.0012					
Е	0.0015 0.0019		0.0019	0.0019					

# Delays at 25°C,1.0V, Typical Process

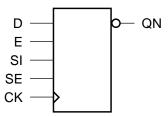
Description	on Intrinsic Delay (ns)					K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M	
CK → Q ↑	0.0933	0.0770	0.0769	0.0714	4.2777	2.3242	1.1619	0.7861	
$CK \ \to \ Q \ \downarrow$	0.0851	0.0713	0.0752	0.0731	2.8651	1.5005	0.7514	0.5221	

	Tilling Constraints at 25 C, 1.0 V, Typical F10Cess								
Pin	Red	nuira	amar	n#		Interval (ns)			
' '''	Requirement				X0P5M	X1P0M	X2P0M	X3P0M	
	setup	$\uparrow$	$\rightarrow$	CK	0.0586	0.0586	0.0586	0.0625	
SI	setup	$\downarrow$	$\rightarrow$	CK	0.0781	0.0820	0.0820	0.0898	
Si	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0312	-0.0312	-0.0391	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0547	-0.0625	-0.0664	-0.0703	
	setup	$\uparrow$	$\rightarrow$	CK	0.0898	0.0977	0.0977	0.1055	
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0664	0.0625	0.0547	0.0625	
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0234	-0.0273	-0.0312	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0352	-0.0391	-0.0273	-0.0312	
	setup	$\uparrow$	$\rightarrow$	CK	0.0742	0.0703	0.0625	0.0664	
D	setup	$\downarrow$	$\rightarrow$	CK	0.0938	0.0820	0.0742	0.0742	
	hold	$\uparrow$	$\rightarrow$	CK	-0.0430	-0.0430	-0.0352	-0.0391	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0703	-0.0664	-0.0547	-0.0586	
СК	ı	minp	wh		0.8830	0.8830	0.8830	0.8830	
CK		minp	owl		0.8830	0.8830	0.8830	0.8830	
	setup	$\uparrow$	$\rightarrow$	CK	0.0938	0.0820	0.0742	0.0781	
E	setup	$\downarrow$	$\rightarrow$	CK	0.0742	0.0664	0.0586	0.0625	
	hold	$\uparrow$	$\rightarrow$	CK	-0.0547	-0.0547	-0.0430	-0.0508	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0508	-0.0508	-0.0469	-0.0508	

### **Cell Description**

The ESDFFQN cell is a positive-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and synchronous active-high enable (E). The cell has a single output (QN).

## **Logic Symbol**

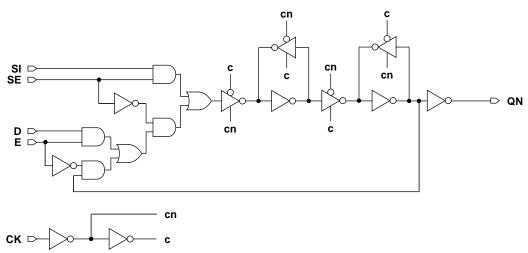


#### **Function Table**

D	Е	SI	SE	СК	QN[n+1]
Х	Х	1	1		0
Х	Х	0	1		1
Х	0	Х	0		QN[n]
0	1	Х	0		1
1	1	Х	0		0
Х	Х	Х	Х		QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
ESDFFQNX0P5MA10TR	2.00	7.60
ESDFFQNX1MA10TR	2.00	7.60
ESDFFQNX2MA10TR	2.00	7.80
ESDFFQNX3MA10TR	2.00	8.00



Pin	Power (uW/MHz)								
' '''	X0P5M	X1P0M	X2P0M	X3P0M					
SI	0.0051	0.0065	0.0077	0.0085					
SE	0.0057	0.0070	0.0081	0.0088					
D	0.0071	0.0085	0.0105	0.0113					
CK	0.0039	0.0044	0.0052	0.0057					
Е	0.0068	0.0085	0.0101	0.0108					
QN	0.0052	0.0066	0.0086	0.0102					

## Pin Capacitance

Pin	Capacitance (pF)								
F III	X0P5M	X1P0M	X2P0M	X3P0M					
SI	0.0007	0.0007	0.0007	0.0007					
SE	0.0018	0.0017	0.0019	0.0019					
D	0.0012	0.0011	0.0014	0.0014					
CK	0.0009	0.0010	0.0011	0.0011					
Е	0.0014	0.0018	0.0020	0.0020					

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns) K <sub>load</sub> (ns/pF)							
	X0P5M X1P0M X2P0M X3P0M			X0P5M	X1P0M	X2P0M	X3P0M	
$CK \to QN \uparrow$	0.0973	0.0837	0.0847	0.0796	4.2429	2.3204	1.1585	0.7814
$CK \to QN \downarrow$	0.1075	0.0907	0.0883	0.0903	2.4469	1.3327	0.7205	0.4603

Pin	Por	vi ir	emer			Interv	al (ns)	
FIII	Ket	<sub>4</sub> uire	eme	11.	X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0508	0.0547	0.0586
SI	setup	$\downarrow$	$\rightarrow$	CK	0.0859	0.0781	0.0820	0.0859
Si	hold	$\uparrow$	$\rightarrow$	CK	-0.0312	-0.0312	-0.0352	-0.0391
	hold	$\downarrow$	$\rightarrow$	CK	-0.0625	-0.0625	-0.0664	-0.0703
	setup	$\uparrow$	$\rightarrow$	CK	0.0977	0.0938	0.0938	0.1016
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0586	0.0508	0.0547
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0234	-0.0312	-0.0312
	hold	$\downarrow$	$\rightarrow$	CK	-0.0391	-0.0391	-0.0312	-0.0352
	setup	$\uparrow$	$\rightarrow$	CK	0.0781	0.0703	0.0586	0.0625
D	setup	$\downarrow$	$\rightarrow$	CK	0.0938	0.0820	0.0703	0.0742
	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0469	-0.0391	-0.0430
	hold	$\downarrow$	$\rightarrow$	CK	-0.0703	-0.0703	-0.0547	-0.0586
СК	r	ninp	wh		0.8830	0.8830	0.8830	0.8830
CIX		minp	owl		0.8830	0.8830	0.8830	0.8830
	setup	$\uparrow$	$\rightarrow$	CK	0.0938	0.0820	0.0703	0.0742
E	setup	$\downarrow$	$\rightarrow$	CK	0.0781	0.0703	0.0586	0.0586
	hold	$\uparrow$	$\rightarrow$	CK	-0.0586	-0.0547	-0.0430	-0.0469
	hold	$\downarrow$	$\rightarrow$	CK	-0.0625	-0.0547	-0.0469	-0.0508

#### **Cell Description**

The FRICG cell is a free running integrated latch clock gate, There are no enable signals since the ECK always reflects the value of (CK). The purpose of this cell is to match the delay of the POSTICG and PREICG cells across PVT.

## **Logic Symbol**



#### **Function Table**

СК	ECK
1	1
0	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
FRICGX0P5BA10TR	2.00	1.60
FRICGX0P6BA10TR	2.00	1.60
FRICGX0P7BA10TR	2.00	1.60
FRICGX0P8BA10TR	2.00	1.60
FRICGX1BA10TR	2.00	1.60
FRICGX1P2BA10TR	2.00	2.00
FRICGX1P4BA10TR	2.00	2.00
FRICGX1P7BA10TR	2.00	2.00
FRICGX2BA10TR	2.00	2.00
FRICGX2P5BA10TR	2.00	2.20
FRICGX3BA10TR	2.00	2.20
FRICGX3P5BA10TR	2.00	3.00
FRICGX4BA10TR	2.00	3.00
FRICGX5BA10TR	2.00	3.20
FRICGX6BA10TR	2.00	3.40
FRICGX7P5BA10TR	2.00	4.00
FRICGX9BA10TR	2.00	4.40
FRICGX11BA10TR	2.00	5.20
FRICGX13BA10TR	2.00	5.60
FRICGX16BA10TR	2.00	6.80

#### **AC Power**

Pin		Power (uW/MHz)									
' '''	X0P5B	X0P5B   X0P6B   X0P7B   X0P8B   X1P0B   X1P2B   X1P4B   X1P7B									
CK	0.0021	0.0022	0.0023	0.0024	0.0027	0.0035	0.0037	0.0041			

# AC Power (Cont'd.)

Pin		Power (uW/MHz)									
F	X2P0B	X2P0B   X2P5B   X3P0B   X3P5B   X4P0B   X5P0B   X6P0B   X7P5B									
CK	0.0047	0.0058	0.0065	0.0080	0.0088	0.0110	0.0128	0.0166			

# AC Power (Cont'd.)

Pin	Power (uW/MHz)					
F 1111	X9P0B	X11P0B	X13P0B	X16P0B		
CK	0.0195	0.0240	0.0274	0.0337		

# Pin Capacitance

Pin		Capacitance (pF)									
	X0P5B	X0P5B									
CK	0.0009	0.0009	0.0010	0.0010	0.0010	0.0011	0.0012	0.0013			

## Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)								
	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B	
CK	0.0014	0.0017	0.0018	0.0023	0.0026	0.0030	0.0034	0.0048	

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)							
F 1111	X9P0B	X11P0B X13P0B X16P0E						
CK	0.0053	0.0066	0.0074	0.0092				

## Delays at 25°C,1.0V, Typical Process

Description				Intrinsic I	Delay (ns)			
	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B
CK → ECK ↑	0.0366	0.0375	0.0389	0.0393	0.0383	0.0382	0.0374	0.0360
$CK \  o \ ECK \ \downarrow$	0.0328	0.0335	0.0347	0.0352	0.0341	0.0348	0.0341	0.0333

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description				Intrinsic I	Delay (ns)			
	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B
CK → ECK ↑	0.0361	0.0341	0.0325	0.0339	0.0334	0.0330	0.0326	0.0322
$CK \to ECK \downarrow$	0.0339	0.0321	0.0318	0.0322	0.0325	0.0319	0.0318	0.0307

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)				
		X9P0B	X11P0B	X13P0B	X16P0B
CK → ECK	$\uparrow$	0.0315	0.0316	0.0304	0.0308
CK → ECK	$\downarrow$	0.0308	0.0308	0.0305	0.0301

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description				K <sub>load</sub> (	ns/pF)			
	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B
CK → ECK ↑	4.7835	4.0971	3.5531	3.0632	2.4902	1.9016	1.6491	1.3828
$CK \ \to \ ECK \ \downarrow$	3.9687	3.3981	2.9286	2.6127	2.1270	1.6806	1.4446	1.2294

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description				K <sub>load</sub> (	ns/pF)			
	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B
CK → ECK ↑	1.1887	0.9308	0.7844	0.6624	0.5848	0.4679	0.3882	0.3099
$CK \to ECK \downarrow$	1.0461	0.8342	0.7002	0.6024	0.5294	0.4169	0.3505	0.2795

Description	K <sub>load</sub> (ns/pF)					
	X9P0B	X11P0B	X13P0B	X16P0B		
CK → ECK ↑	0.2581	0.2101	0.1788	0.1446		
CK → ECK ↓	0.2322	0.1882	0.1642	0.1345		

Process Technology:	FRIC
CLN65G+	
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### **Cell Description**

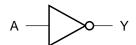
The INV cell provides the logical inversion of a single input (A). The output (Y) is represented by the logic equation:

 $Y = \overline{A}$ 

#### **Function Table**

Α	Υ
0	1
1	0

## **Logic Symbol**

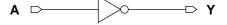


#### **Cell Size**

Drive Strength	Height (um)	Width (um)
INVX0P5BA10TR	2.00	0.60
INVX0P5MA10TR	2.00	0.60
INVX0P6BA10TR	2.00	0.60
INVX0P6MA10TR	2.00	0.60
INVX0P7BA10TR	2.00	0.60
INVX0P7MA10TR	2.00	0.60
INVX0P8BA10TR	2.00	0.60
INVX0P8MA10TR	2.00	0.60
INVX1BA10TR	2.00	0.60
INVX1MA10TR	2.00	0.60
INVX1P2BA10TR	2.00	0.80
INVX1P2MA10TR	2.00	0.80
INVX1P4BA10TR	2.00	0.80
INVX1P4MA10TR	2.00	0.80
INVX1P7BA10TR	2.00	0.80
INVX1P7MA10TR	2.00	0.80
INVX2BA10TR	2.00	0.80
INVX2MA10TR	2.00	0.80
INVX2P5BA10TR	2.00	1.20
INVX2P5MA10TR	2.00	1.20

# Cell Size (Cont'd.)

Drive Strength	Height (um)	Width (um)
INVX3BA10TR	2.00	1.20
INVX3MA10TR	2.00	1.20
INVX3P5BA10TR	2.00	1.40
INVX3P5MA10TR	2.00	1.40
INVX4BA10TR	2.00	1.40
INVX4MA10TR	2.00	1.40
INVX5BA10TR	2.00	1.60
INVX5MA10TR	2.00	1.60
INVX6BA10TR	2.00	2.00
INVX6MA10TR	2.00	2.00
INVX7P5BA10TR	2.00	2.40
INVX7P5MA10TR	2.00	2.40
INVX9BA10TR	2.00	2.60
INVX9MA10TR	2.00	2.60
INVX11BA10TR	2.00	3.20
INVX11MA10TR	2.00	3.20
INVX13BA10TR	2.00	3.80
INVX13MA10TR	2.00	3.80
INVX16BA10TR	2.00	4.60
INVX16MA10TR	2.00	4.60



#### **AC Power**

Pin		Power (uW/MHz)										
F 111	X0P5B	X0P5M	X0P6B	X0P6M	X0P7B	X0P7M	X0P8B	X0P8M				
Α	0.0011	0.0012	0.0012	0.0014	0.0014	0.0015	0.0015	0.0017				

## AC Power (Cont'd.)

Pin		Power (uW/MHz)										
' '''	X1P0B	X1P0M	X1P2B	X1P2M	X1P4B	X1P4M	X1P7B	X1P7M				
Α	0.0017	0.0019	0.0021	0.0023	0.0024	0.0027	0.0027	0.0030				

### AC Power (Cont'd.)

Pin		Power (uW/MHz)										
	FIII	X2P0B	X2P0M	X2P5B	X2P5M	X3P0B	X3P0M	X3P5B	X3P5M			
	Α	0.0031	0.0034	0.0041	0.0046	0.0048	0.0052	0.0054	0.0062			

## AC Power (Cont'd.)

Pin		Power (uW/MHz)										
	X4P0B	X4P0M	X5P0B	X5P0M	X6P0B	X6P0M	X7P5B	X7P5M				
Α	0.0062	0.0068	0.0079	0.0087	0.0094	0.0102	0.0114	0.0130				

## AC Power (Cont'd.)

Pin		Power (uW/MHz)										
	X9P0B	X9P0M	X11P0B	X11P0M	X13P0B	X13P0M	X16P0B	X16P0M				
Α	0.0143	0.0157	0.0175	0.0192	0.0207	0.0227	0.0252	0.0277				

## Pin Capacitance

Pin		Capacitance (pF)										
	X0P5B	X0P5M	X0P6B	X0P6M	X0P7B	X0P7M	X0P8B	X0P8M				
Α	0.0012	0.0012	0.0013	0.0015	0.0014	0.0016	0.0015	0.0017				

# Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
	X1P0B	X1P0M	X1P2B	X1P2M	X1P4B	X1P4M	X1P7B	X1P7M				
Α	0.0017	0.0019	0.0023	0.0026	0.0026	0.0030	0.0029	0.0033				

# Process Technology:

## CLN65G+

## Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
	X2P0B	X2P0M	X2P5B	X2P5M	X3P0B	X3P0M	X3P5B	X3P5M				
Α	0.0033	0.0037	0.0042	0.0048	0.0049	0.0055	0.0058	0.0067				

## Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
' '''	X4P0B	X4P0M	X5P0B	X5P0M	X6P0B	X6P0M	X7P5B	X7P5M				
Α	0.0066	0.0073	0.0082	0.0092	0.0099	0.0111	0.0122	0.0140				

## Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
	FIII	X9P0B	X9P0M	X11P0B	X11P0M	X13P0B	X13P0M	X16P0B	X16P0M			
	Α	0.0150	0.0168	0.0183	0.0205	0.0216	0.0242	0.0266	0.0295			

## Delays at 25°C,1.0V, Typical Process

D	escri	iptio	n	Intrinsic Delay (ns)									
				X0P5B	X0P5M	X0P6B	X0P6M	X0P7B	X0P7M	X0P8B	X0P8M		
Α	$\rightarrow$	Υ	$\uparrow$	0.0091	0.0096	0.0086	0.0095	0.0083	0.0090	0.0080	0.0087		
Α	$\rightarrow$	Υ	$\downarrow$	0.0084	0.0071	0.0080	0.0070	0.0077	0.0068	0.0075	0.0065		

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)									
	X1P0B	X1P0M	X1P2B	X1P2M	X1P4B	X1P4M	X1P7B	X1P7M		
$A \rightarrow Y \uparrow$	0.0079	0.0083	0.0075	0.0079	0.0073	0.0079	0.0069	0.0076		
$A \ \rightarrow \ Y \ \downarrow$	0.0074	0.0063	0.0073	0.0061	0.0068	0.0061	0.0066	0.0059		

Description	ion Intrinsic Delay (ns)							
	X2P0B	X2P0M	X2P5B	X2P5M	X3P0B	X3P0M	X3P5B	X3P5M
$A \rightarrow Y \uparrow$	0.0070	0.0073	0.0071	0.0077	0.0070	0.0075	0.0068	0.0073
$A \rightarrow Y \downarrow$	0.0066	0.0057	0.0069	0.0061	0.0068	0.0059	0.0066	0.0058

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)							
	X4P0B	X4P0M	X5P0B	X5P0M	X6P0B	X6P0M	X7P5B	X7P5M
$A \rightarrow Y \uparrow$	0.0068	0.0072	0.0069	0.0073	0.0068	0.0071	0.0066	0.0072
$A \rightarrow Y \downarrow$	0.0066	0.0057	0.0067	0.0058	0.0066	0.0057	0.0065	0.0058

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	iptic	n	n Intrinsic Delay (ns)							
				X9P0B	X9P0M	X11P0B	X11P0M	X13P0B	X13P0M	X16P0B	X16P0M
Α	$\rightarrow$	Υ	$\uparrow$	0.0069	0.0072	0.0068	0.0072	0.0068	0.0072	0.0068	0.0072
Α	$\rightarrow$	Υ	$\downarrow$	0.0067	0.0057	0.0067	0.0057	0.0066	0.0057	0.0066	0.0058

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)							
	X0P5B	X0P5M	X0P6B	X0P6M	X0P7B	X0P7M	X0P8B	X0P8M
$A \rightarrow Y \uparrow$	4.7642	4.7662	4.0146	4.0166	3.4643	3.4595	3.0494	3.0509
$A \rightarrow Y \downarrow$	3.9911	2.8360	3.4175	2.3580	2.9347	2.0468	2.6170	1.7864

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)							
	X1P0B	X1P0M	X1P2B	X1P2M	X1P4B	X1P4M	X1P7B	X1P7M
$A \rightarrow Y \uparrow$	2.4858	2.4868	1.9550	1.9545	1.6898	1.6905	1.4106	1.4112
$A \rightarrow Y \downarrow$	2.1023	1.4401	1.7599	1.1725	1.4465	1.0129	1.2290	0.8359

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	iption K <sub>load</sub> (ns/pF)								
		X2P0B	X2P0M	X2P5B	X2P5M	X3P0B	X3P0M	X3P5B	X3P5M
$A \rightarrow Y$	$\uparrow$	1.2176	1.2180	0.9444	0.9449	0.7973	0.7976	0.6687	0.6687
$A \ \rightarrow \ Y$	$\downarrow$	1.0394	0.7077	0.8471	0.5816	0.7092	0.4797	0.5976	0.4043

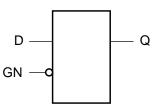
Description	n K <sub>load</sub> (ns/pF)							
	X4P0B	X4P0M	X5P0B	X5P0M	X6P0B	X6P0M	X7P5B	X7P5M
$A \rightarrow Y \uparrow$	0.5916	0.5919	0.4725	0.4726	0.3892	0.3893	0.3078	0.3080
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.5232	0.3545	0.4236	0.2864	0.3489	0.2359	0.2808	0.1920

Description K <sub>load</sub> (ns/pF)								
	X9P0B	X9P0M	X11P0B	X11P0M	X13P0B	X13P0M	X16P0B	X16P0M
$A \rightarrow Y \uparrow$	0.2587	0.2588	0.2104	0.2105	0.1773	0.1774	0.1435	0.1436
$A \rightarrow Y \downarrow$	0.2343	0.1582	0.1911	0.1291	0.1615	0.1091	0.1305	0.0904

### **Cell Description**

The LATNQ cell is a D-type active-low transparent latch. When the enable (GN) is low, data is transferred to the output (Q).

## **Logic Symbol**

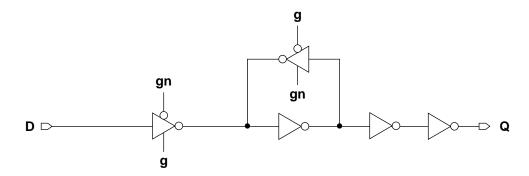


#### **Function Table**

GN	D	Q[n+1]
0	0	0
0	1	1
1	Х	Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATNQX0P5MA10TR	2.00	2.40
LATNQX1MA10TR	2.00	2.40
LATNQX2MA10TR	2.00	2.60
LATNQX3MA10TR	2.00	3.00



#### **AC Power**

Pin	Power (uW/MHz)							
	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0014	0.0019	0.0025	0.0030				
GN	0.0016	0.0018	0.0021	0.0025				
Q	0.0032	0.0040	0.0060	0.0084				

## Pin Capacitance

Pin	Capacitance (pF)							
	X0P5M	X1P0M	X2P0M	X3P0M				
D	0.0010	0.0014	0.0018	0.0019				
GN	0.0018	0.0018	0.0019	0.0021				

### Delays at 25°C,1.0V, Typical Process

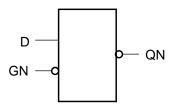
Description			Intrinsic Delay (ns)				K <sub>load</sub> (ns/pF)			
		X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M	
$D \rightarrow Q$	1	0.0505	0.0393	0.0387	0.0406	4.7285	2.4563	1.2028	0.7973	
$D \to Q$	$\downarrow$	0.0608	0.0502	0.0496	0.0555	2.8750	1.4938	0.7170	0.4826	
GN → Q	1	0.0550	0.0475	0.0478	0.0480	4.7279	2.4561	1.2026	0.7972	
$GN \to Q$	$\downarrow$	0.0608	0.0525	0.0534	0.0566	2.8746	1.4933	0.7168	0.4825	

Pin	Por	nuir/	emer	\ <b>+</b>	Interval (ns)			
· · · ·	ive.	<sub>4</sub> uii (	CIIICI	11	X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	GN	0.0508	0.0352	0.0352	0.0352
D	setup	$\downarrow$	$\rightarrow$	GN	0.0547	0.0469	0.0469	0.0508
	hold	$\uparrow$	$\rightarrow$	GN	-0.0352	-0.0234	-0.0234	-0.0234
	hold	$\downarrow$	$\rightarrow$	GN	-0.0469	-0.0352	-0.0352	-0.0430
GN	minpwl			0.8830	0.8830	0.8830	0.8830	

### **Cell Description**

The LATNQN cell is a D-type active-low transparent latch. When the enable (GN) is low, data is transferred to the output (QN).

## **Logic Symbol**

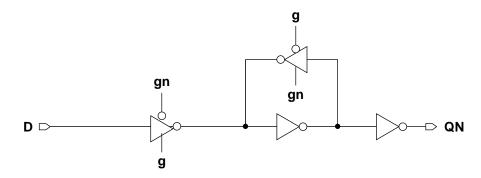


#### **Function Table**

GN	D	QN[n+1]
0	0	1
0	1	0
1	Х	QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATNQNX0P5MA10TR	2.00	2.60
LATNQNX1MA10TR	2.00	2.60
LATNQNX2MA10TR	2.00	2.80
LATNQNX3MA10TR	2.00	3.00
LATNQNX4MA10TR	2.00	3.40



Pin	Power (uW/MHz)									
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
D	0.0013	0.0019	0.0024	0.0027	0.0031					
GN	0.0015	0.0018	0.0021	0.0024	0.0028					
QN	0.0032	0.0042	0.0061	0.0082	0.0098					

## Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M X1P0M X2P0M X3P0M X4P0M								
D	0.0010	0.0014	0.0016	0.0017	0.0019				
GN	0.0017	0.0018	0.0019	0.0019	0.0021				

# Delays at 25°C,1.0V, Typical Process

Description				Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
D	$\rightarrow$	QN	$\uparrow$	0.0675	0.0572	0.0539	0.0558	0.0591	
D	$\rightarrow$	QN	$\downarrow$	0.0639	0.0537	0.0521	0.0559	0.0568	
GN	$\rightarrow$	QN	$\uparrow$	0.0663	0.0560	0.0525	0.0544	0.0555	
GN	$\rightarrow$	QN	$\downarrow$	0.0688	0.0621	0.0609	0.0644	0.0652	

Description				K <sub>load</sub> (ns/pF)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
D	$\rightarrow$	QN	$\uparrow$	4.6193	2.3825	1.1767	0.7859	0.5817	
D	$\rightarrow$	QN	$\downarrow$	2.8247	1.4441	0.7131	0.4885	0.3622	
GN	$\rightarrow$	QN	$\uparrow$	4.6196	2.3824	1.1766	0.7860	0.5817	
GN	$\rightarrow$	QN	$\downarrow$	2.8248	1.4443	0.7130	0.4885	0.3622	

Process Technology:

CLN65G+

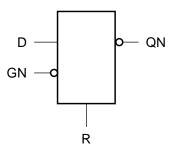
LATNQN

Pin	Requirement				Interval (ns)					
	ive.	quiit	SIIICI	11	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
	setup	$\uparrow$	$\rightarrow$	GN	0.0430	0.0273	0.0273	0.0273	0.0234	
D	setup	$\downarrow$	$\rightarrow$	GN	0.0469	0.0391	0.0391	0.0391	0.0391	
	hold	$\uparrow$	$\rightarrow$	GN	-0.0273	-0.0156	-0.0156	-0.0156	-0.0156	
	hold	$\downarrow$	$\rightarrow$	GN	-0.0430	-0.0312	-0.0312	-0.0312	-0.0312	
GN	minpwl			0.8830	0.8830	0.8830	0.8830	0.8830		

#### **Cell Description**

The LATNRPQN cell is a D-type active-low transparent latch with asynchronous active-high reset (R). When the enable (GN) is low, data is transferred to the output (QN).

## **Logic Symbol**

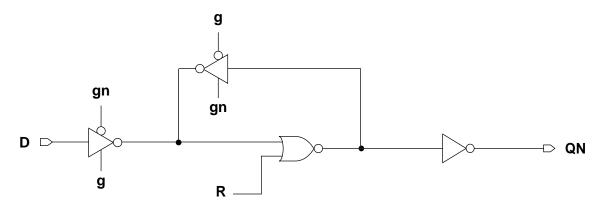


#### **Function Table**

R	GN	D	QN[n+1]
1	Х	Х	1
0	0	0	1
0	0	1	0
0	1	Х	QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATNRPQNX0P5MA10TR	2.00	2.80
LATNRPQNX1MA10TR	2.00	2.80
LATNRPQNX2MA10TR	2.00	3.00
LATNRPQNX3MA10TR	2.00	3.20
LATNRPQNX4MA10TR	2.00	3.60



Pin	Power (uW/MHz)									
' '''	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
D	0.0014	0.0021	0.0026	0.0028	0.0032					
GN	0.0016	0.0019	0.0023	0.0025	0.0029					
R	0.0009	0.0012	0.0015	0.0016	0.0018					
QN	0.0035	0.0047	0.0065	0.0089	0.0118					

## Pin Capacitance

Pin	Capacitance (pF)								
' '''	X0P5M	X1P0M	X3P0M	X4P0M					
D	0.0010	0.0014	0.0017	0.0017	0.0019				
GN	0.0017	0.0018	0.0019	0.0019	0.0021				
R	0.0012	0.0016	0.0017	0.0016	0.0016				

## Delays at 25°C,1.0V, Typical Process

Description				Intrinsic Delay (ns)						
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
D	$\rightarrow$	QN	$\uparrow$	0.0717	0.0568	0.0572	0.0647	0.0698		
D	$\rightarrow$	QN	$\downarrow$	0.0735	0.0625	0.0663	0.0770	0.0834		
GN	$\rightarrow$	QN	$\uparrow$	0.0710	0.0566	0.0552	0.0627	0.0659		
GN	$\rightarrow$	QN	$\downarrow$	0.0783	0.0701	0.0752	0.0850	0.0918		
R	$\rightarrow$	QN	<b>↑</b>	0.0294	0.0251	0.0294	0.0395	0.0436		
R	$\rightarrow$	QN	$\downarrow$	0.0455	0.0428	0.0505	0.0603	0.0692		

Description				K <sub>load</sub> (ns/pF)						
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
D	$\rightarrow$	QN	$\uparrow$	4.6441	2.3803	1.1765	0.7873	0.5840		
D	$\rightarrow$	QN	$\downarrow$	2.7768	1.3110	0.6643	0.4638	0.3503		
GN	$\rightarrow$	QN	$\uparrow$	4.6440	2.3803	1.1765	0.7873	0.5840		
GN	$\rightarrow$	QN	$\downarrow$	2.7772	1.3111	0.6644	0.4638	0.3504		
R	$\rightarrow$	QN	$\uparrow$	4.6576	2.3861	1.1794	0.7890	0.5850		
R	$\rightarrow$	QN	$\downarrow$	2.7751	1.3105	0.6642	0.4637	0.3503		

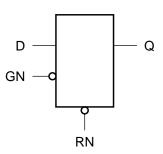
**LATNRPQN** 

<b>.</b>				_	Interval (ns)						
Pin	Red	Requirement				X1P0M	X2P0M	X3P0M	X4P0M		
	setup	$\uparrow$	$\rightarrow$	GN	0.0430	0.0312	0.0273	0.0273	0.0273		
D	setup	$\downarrow$	$\rightarrow$	GN	0.0508	0.0430	0.0391	0.0430	0.0430		
	hold	$\uparrow$	$\rightarrow$	GN	-0.0273	-0.0195	-0.0156	-0.0156	-0.0156		
	hold	$\downarrow$	$\rightarrow$	GN	-0.0430	-0.0352	-0.0312	-0.0352	-0.0352		
GN		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830		
	minpwh		0.8830	0.8830	0.8830	0.8830	0.8830				
R	r	ecov	ery		-0.0039	-0.0156	-0.0156	-0.0117	-0.0078		
	r	removal			0.0078	0.0195	0.0195	0.0156	0.0117		

### **Cell Description**

The LATNRQ cell is a D-type active-low transparent latch with asynchronous active-low reset (RN). When the enable (GN) is low, data is transferred to the output (Q).

## **Logic Symbol**

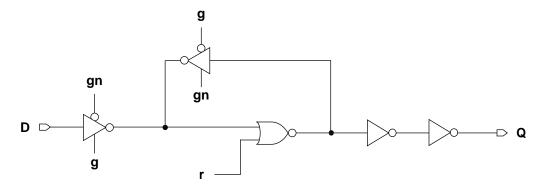


#### **Function Table**

RN	GN	D	Q[n+1]
0	Х	Х	0
1	0	0	0
1	0	1	1
1	1	Х	Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATNRQX0P5MA10TR	2.00	3.00
LATNRQX1MA10TR	2.00	3.00
LATNRQX2MA10TR	2.00	3.20
LATNRQX3MA10TR	2.00	3.40



Pin	Power (uW/MHz)								
F 111	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0016	0.0022	0.0027	0.0030					
GN	0.0017	0.0019	0.0022	0.0026					
RN	0.0011	0.0013	0.0015	0.0017					
Q	0.0034	0.0042	0.0063	0.0087					

## Pin Capacitance

Pin	Capacitance (pF)							
• •••	X0P5M	X3P0M						
D	0.0011	0.0015	0.0017	0.0017				
GN	0.0017	0.0019	0.0020	0.0022				
RN	0.0020	0.0023	0.0024	0.0024				

## Delays at 25°C,1.0V, Typical Process

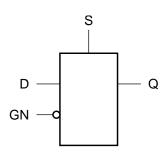
Description	Intrinsic Delay (ns) K <sub>load</sub> (ns/pF)							
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$D \to Q \uparrow$	0.0542	0.0464	0.0491	0.0553	4.8346	2.4719	1.2058	0.8088
$D \;\;  o \;\; Q \;\; \downarrow$	0.0641	0.0547	0.0563	0.0618	3.0481	1.6518	0.7898	0.5349
$GN \  o \ Q \ \uparrow$	0.0578	0.0517	0.0540	0.0572	4.8339	2.4718	1.2056	0.8086
$GN \  o \ Q \ \downarrow$	0.0649	0.0564	0.0587	0.0621	3.0482	1.6515	0.7896	0.5348
$RN \ \to \ Q \ \uparrow$	0.0573	0.0491	0.0515	0.0577	4.8340	2.4717	1.2059	0.8088
$RN \  o \ Q \ \downarrow$	0.0307	0.0405	0.0490	0.0585	2.8101	1.6025	0.7693	0.5244

Pin	Requirement			Interval (ns)				
F	ive.	quii	cilici	11.	X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	GN	0.0508	0.0430	0.0430	0.0508
D	setup	$\downarrow$	$\rightarrow$	GN	0.0586	0.0508	0.0547	0.0586
	hold	$\uparrow$	$\rightarrow$	GN	-0.0352	-0.0273	-0.0312	-0.0352
	hold	$\downarrow$	$\rightarrow$	GN	-0.0508	-0.0430	-0.0430	-0.0469
GN		min	owl		0.8830	0.8830	0.8830	0.8830
		min	owl		0.8830	0.8830	0.8830	0.8830
RN	r	ecov	ery/		0.0469	0.0391	0.0391	0.0430
	ı	emo	oval		-0.0430	-0.0352	-0.0352	-0.0391

#### **Cell Description**

The LATNSPQ cell is a D-type active-low transparent latch with asynchronous active-high set (S). When the enable (GN) is low, data is transferred to the output (Q).

## **Logic Symbol**

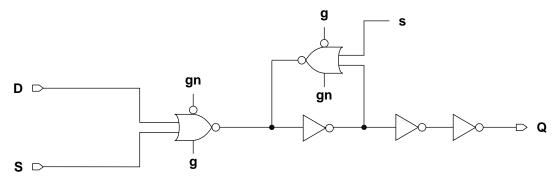


#### **Function Table**

S	GN	D	Q[n+1]
1	Х	Х	1
0	0	0	0
0	0	1	1
0	1	Х	Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATNSPQX0P5MA10TR	2.00	3.00
LATNSPQX1MA10TR	2.00	3.00
LATNSPQX2MA10TR	2.00	3.20
LATNSPQX3MA10TR	2.00	4.20



Pin	Power (uW/MHz)								
' '''	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0016	0.0022	0.0025	0.0045					
GN	0.0017	0.0020	0.0022	0.0030					
S	0.0012	0.0016	0.0017	0.0028					
Q	0.0036	0.0045	0.0071	0.0086					

# Pin Capacitance

Pin	Capacitance (pF)								
• •••	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0011	0.0015	0.0016	0.0029					
GN	0.0017	0.0018	0.0019	0.0021					
S	0.0015	0.0018	0.0018	0.0027					

## Delays at 25°C,1.0V, Typical Process

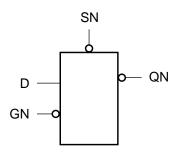
De	escri	otior	1		Intrinsic I	Delay (ns)		K <sub>load</sub> (ns/pF)			
				X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
D	$\rightarrow$	Q	$\uparrow$	0.0529	0.0426	0.0470	0.0438	4.7242	2.4277	1.2066	0.7973
D	$\rightarrow$	Q	$\downarrow$	0.0749	0.0659	0.0766	0.0634	2.9747	1.5360	0.7620	0.4931
GN	$\rightarrow$	Q	$\uparrow$	0.0565	0.0493	0.0529	0.0542	4.7240	2.4274	1.2063	0.7971
GN	$\rightarrow$	Q	$\downarrow$	0.0693	0.0611	0.0704	0.0588	2.9739	1.5349	0.7615	0.4920
S	$\rightarrow$	Q	<b>↑</b>	0.0357	0.0440	0.0537	0.0703	4.6960	2.4397	1.2156	0.8138
S	$\rightarrow$	Q	$\downarrow$	0.0778	0.0686	0.0792	0.0662	2.9747	1.5360	0.7620	0.4931

Pin	Requirement				Interval (ns)				
FIII					X0P5M	X1P0M	X2P0M	X3P0M	
	setup	$\uparrow$	$\rightarrow$	GN	0.0508	0.0391	0.0430	0.0352	
D	setup	$\downarrow$	$\rightarrow$	GN	0.0703	0.0625	0.0703	0.0586	
	hold $\uparrow$ $\rightarrow$ GN		-0.0352	-0.0273	-0.0273	-0.0234			
	hold	$\downarrow$	$\rightarrow$	GN	-0.0625	-0.0547	-0.0625	-0.0508	
GN		min	owl		0.8830	0.8830	0.8830	0.8830	
	minpwh			0.8830	0.8830	0.8830	0.8830		
S	recovery		0.0703	0.0625	0.0703	0.0586			
	removal				-0.0664	-0.0586	-0.0664	-0.0547	

### **Cell Description**

The LATNSQN cell is a D-type active-low transparent latch with asynchronous active-low set (SN). When the enable (GN) is low, data is transferred to the output (QN).

## **Logic Symbol**

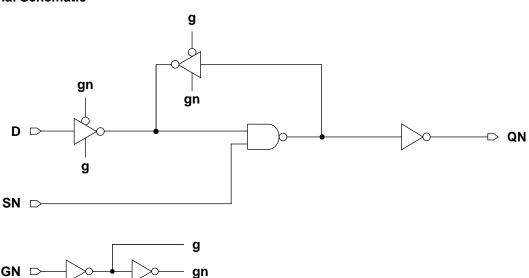


### **Function Table**

SN	GN	D	QN[n+1]
0	Х	Х	0
1	0	0	1
1	0	1	0
1	1	Х	QN[n]

### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATNSQNX0P5MA10TR	2.00	2.80
LATNSQNX1MA10TR	2.00	2.80
LATNSQNX2MA10TR	2.00	3.00
LATNSQNX3MA10TR	2.00	3.20
LATNSQNX4MA10TR	2.00	3.40



Pin	Power (uW/MHz)									
F 111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
D	0.0014	0.0020	0.0026	0.0028	0.0031					
GN	0.0015	0.0018	0.0022	0.0024	0.0028					
SN	0.0007	0.0009	0.0014	0.0016	0.0018					
QN	0.0034	0.0044	0.0063	0.0082	0.0102					

# Pin Capacitance

Pin	Capacitance (pF)									
F 1111	X0P5M	(OP5M X1P0M X2P		X3P0M	X4P0M					
D	0.0010	0.0014	0.0017	0.0017	0.0019					
GN	0.0020	0.0022	0.0023	0.0024	0.0026					
SN	0.0011	0.0013	0.0017	0.0017	0.0017					

## Delays at 25°C,1.0V, Typical Process

D	Description			Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
D	$\rightarrow$	QN	$\uparrow$	0.0766	0.0645	0.0609	0.0674	0.0737	
D	$\rightarrow$	QN	$\downarrow$	0.0672	0.0568	0.0564	0.0616	0.0653	
GN	$\rightarrow$	QN	$\uparrow$	0.0754	0.0634	0.0603	0.0658	0.0702	
GN	$\rightarrow$	QN	$\downarrow$	0.0718	0.0646	0.0644	0.0701	0.0737	
SN	$\rightarrow$	QN	<b>↑</b>	0.0355	0.0350	0.0353	0.0416	0.0472	
SN	$\rightarrow$	QN	$\downarrow$	0.0371	0.0376	0.0370	0.0435	0.0497	

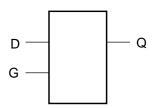
D	Description			K <sub>load</sub> (ns/pF)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
D	$\rightarrow$	QN	$\uparrow$	4.5741	2.3658	1.1666	0.7847	0.5861	
D	$\rightarrow$	QN	$\downarrow$	2.8072	1.4490	0.7162	0.4920	0.3696	
GN	$\rightarrow$	QN	$\uparrow$	4.5740	2.3658	1.1666	0.7847	0.5861	
GN	$\rightarrow$	QN	$\downarrow$	2.8078	1.4492	0.7163	0.4921	0.3696	
SN	$\rightarrow$	QN	$\uparrow$	4.5699	2.3649	1.1663	0.7847	0.5861	
SN	$\rightarrow$	QN	$\downarrow$	2.8215	1.4582	0.7192	0.4928	0.3699	

Pin	Po	auir	amor	<b>.</b> +	Interval (ns)					
F III	Ve	Requirement				X1P0M	X2P0M	X3P0M	X4P0M	
	setup	$\uparrow$	$\rightarrow$	GN	0.0430	0.0312	0.0273	0.0273	0.0234	
D	setup	$\downarrow$	$\rightarrow$	GN	0.0547	0.0430	0.0391	0.0430	0.0430	
	hold	$\uparrow$	$\rightarrow$	GN	-0.0273	-0.0156	-0.0156	-0.0156	-0.0156	
	hold	$\downarrow$	$\rightarrow$	GN	-0.0469	-0.0352	-0.0312	-0.0352	-0.0352	
GN		minpwl			0.8830	0.8830	0.8830	0.8830	0.8830	
	minpwl			0.8830	0.8830	0.8830	0.8830	0.8830		
SN	recovery				0.0039	0.0039	0.0039	0.0078	0.0078	
	ı	remo	oval		0.0000	0.0000	0.0000	-0.0039	-0.0039	

### **Cell Description**

The LATQ cell is a D-type active-high transparent latch. When the enable (G) is high, data is transferred to the output (Q).

## **Logic Symbol**

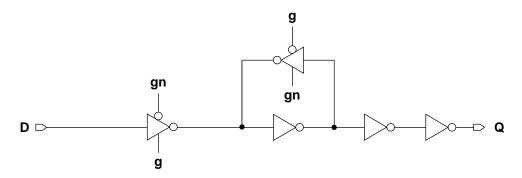


#### **Function Table**

G	۵	Q[n+1]
1	0	0
1	1	1
0	Х	Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATQX0P5MA10TR	2.00	2.40
LATQX1MA10TR	2.00	2.40
LATQX2MA10TR	2.00	2.60
LATQX3MA10TR	2.00	3.00



Pin	Power (uW/MHz)								
	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0012	0.0018	0.0024	0.0028					
G	0.0020	0.0022	0.0025	0.0028					
Q	0.0036	0.0047	0.0068	0.0092					

## Pin Capacitance

Pin	Capacitance (pF)									
F III	X0P5M	X1P0M	X2P0M	X3P0M						
D	0.0010	0.0014	0.0018	0.0019						
G	0.0014	0.0017	0.0016	0.0017						

## Delays at 25°C,1.0V, Typical Process

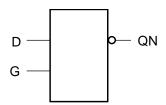
Description	Intrinsic Delay (ns)					K <sub>load</sub> (	ns/pF)	
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$D \;  o \; Q \; \uparrow$	0.0488	0.0375	0.0367	0.0383	4.7257	2.4486	1.1995	0.7963
$D \;  o \; Q \; \downarrow$	0.0618	0.0519	0.0519	0.0574	2.8491	1.4841	0.7164	0.4849
$G \to Q \uparrow$	0.0400	0.0312	0.0317	0.0334	4.7260	2.4484	1.1995	0.7964
$G \;  o \; Q \; \downarrow$	0.0607	0.0520	0.0516	0.0539	2.8489	1.4841	0.7164	0.4848

Pin	Pog	Requirement			Interval (ns)				
	Requirement			X0P5M	X1P0M	X2P0M	X3P0M		
	setup	$\uparrow$	$\rightarrow$	G	0.0508	0.0391	0.0391	0.0391	
D	setup	$\downarrow$	$\rightarrow$	G	0.0508	0.0430	0.0391	0.0469	
	hold	$\uparrow$	$\rightarrow$	G	-0.0391	-0.0312	-0.0312	-0.0312	
	hold	$\downarrow$	$\rightarrow$	G	-0.0391	-0.0273	-0.0273	-0.0312	
G	minpwh			0.8830	0.8830	0.8830	0.8830		

### **Cell Description**

The LATQN cell is a D-type active-high transparent latch. When the enable (G) is high, data is transferred to the outputs (QN).

## **Logic Symbol**

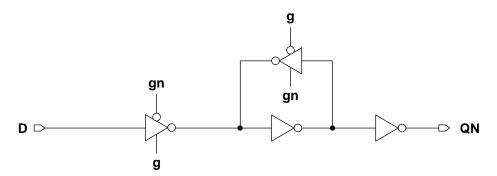


#### **Function Table**

G	D	QN[n+1]
1	0	1
1	1	0
0	Х	QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATQNX0P5MA10TR	2.00	2.40
LATQNX1MA10TR	2.00	2.40
LATQNX2MA10TR	2.00	2.80
LATQNX3MA10TR	2.00	3.00
LATQNX4MA10TR	2.00	3.40



Pin	Power (uW/MHz)									
F 1111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
D	0.0012	0.0017	0.0022	0.0026	0.0029					
G	0.0020	0.0022	0.0025	0.0026	0.0029					
QN	0.0037	0.0049	0.0069	0.0090	0.0106					

### Pin Capacitance

Pin	Capacitance (pF)								
F	X0P5M	X0P5M X1P0M		X3P0M	X4P0M				
D	0.0009	0.0013	0.0016	0.0017	0.0019				
G	0.0014	0.0015	0.0015	0.0015	0.0016				

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)				
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
$D \rightarrow QN \uparrow$	0.0692	0.0591	0.0552	0.0582	0.0599
$D \rightarrow QN \downarrow$	0.0638	0.0532	0.0507	0.0546	0.0548
$G \rightarrow QN \uparrow$	0.0689	0.0603	0.0563	0.0592	0.0591
$G \to QN \downarrow$	0.0557	0.0472	0.0447	0.0486	0.0494

	)esci	ription		K <sub>load</sub> (ns/pF)							
			X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
D	$\rightarrow$	QN ↑	4.6752	2.4076	1.1801	0.7856	0.5834				
D	$\rightarrow$	QN ↓	2.8543	1.4639	0.7147	0.4893	0.3625				
G	$\rightarrow$	QN ↑	4.6753	2.4077	1.1801	0.7856	0.5834				
G	$\rightarrow$	QN ↓	2.8542	1.4637	0.7147	0.4893	0.3625				

Process Technology:

CLN65G+

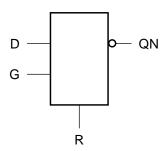
LATQN

Pin	Requirement			Interval (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
	setup	$\uparrow$	$\rightarrow$	G	0.0430	0.0312	0.0312	0.0312	0.0273
D	setup	$\downarrow$	$\rightarrow$	G	0.0430	0.0352	0.0312	0.0312	0.0312
	hold	$\uparrow$	$\rightarrow$	G	-0.0312	-0.0234	-0.0234	-0.0234	-0.0195
	hold	$\downarrow$	$\rightarrow$	G	-0.0312	-0.0234	-0.0234	-0.0234	-0.0234
G	minpwh			0.8830	0.8830	0.8830	0.8830	0.8830	

### **Cell Description**

The LATRPQN cell is a D-type active-high transparent latch with asynchronous active-high reset (R). When the enable (G) is high, data is transferred to the output (QN).

## **Logic Symbol**

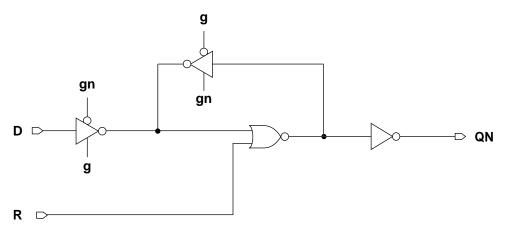


#### **Function Table**

R	G	D	QN[n+1]
1	Х	Х	1
0	1	0	1
0	1	1	0
0	0	Х	QN[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATRPQNX0P5MA10TR	2.00	2.60
LATRPQNX1MA10TR	2.00	2.60
LATRPQNX2MA10TR	2.00	3.00
LATRPQNX3MA10TR	2.00	3.20
LATRPQNX4MA10TR	2.00	3.60



Pin	Power (uW/MHz)						
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
D	0.0013	0.0019	0.0024	0.0026	0.0030		
G	0.0021	0.0023	0.0026	0.0027	0.0030		
R	0.0009	0.0012	0.0014	0.0016	0.0018		
QN	0.0041	0.0054	0.0071	0.0091	0.0113		

# Pin Capacitance

Pin	Capacitance (pF)						
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
D	0.0009	0.0014	0.0017	0.0017	0.0019		
G	0.0014	0.0014	0.0015	0.0014	0.0016		
R	0.0013	0.0016	0.0017	0.0016	0.0016		

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)					
		X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
$D \rightarrow$	QN ↑	0.0735	0.0584	0.0590	0.0672	0.0719	
$D  \to $	QN ↓	0.0721	0.0610	0.0649	0.0764	0.0823	
$G \rightarrow$	QN ↑	0.0731	0.0593	0.0600	0.0692	0.0713	
$G \rightarrow$	QN ↓	0.0638	0.0551	0.0601	0.0706	0.0775	
$R \rightarrow$	QN ↑	0.0292	0.0242	0.0283	0.0395	0.0438	
$R \rightarrow$	QN ↓	0.0452	0.0427	0.0508	0.0614	0.0695	

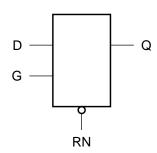
Description		K <sub>load</sub> (ns/pF)						
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
D	$\rightarrow$	QN	$\uparrow$	4.7041	2.4154	1.1799	0.7880	0.5841
D	$\rightarrow$	QN	$\downarrow$	2.7505	1.3462	0.6665	0.4645	0.3506
G	$\rightarrow$	QN	$\uparrow$	4.7039	2.4154	1.1799	0.7880	0.5841
G	$\rightarrow$	QN	$\leftarrow$	2.7506	1.3463	0.6665	0.4645	0.3505
R	$\rightarrow$	QN	1	4.7178	2.4216	1.1824	0.7896	0.5852
R	$\rightarrow$	QN	$\downarrow$	2.7488	1.3459	0.6664	0.4644	0.3505

Pin	Requirement			Interval (ns)						
F III	Requi	emen		X0P5M	(OP5M X1P0M X2P0M X3P0	X3P0M	X4P0M			
	setup 1	$\rightarrow$	G	0.0430	0.0352	0.0312	0.0352	0.0391		
D	setup \	$\rightarrow$	G	0.0469	0.0352	0.0312	0.0352	0.0352		
	hold $\uparrow$ $\rightarrow$		G	-0.0352	-0.0273	-0.0234	-0.0234	-0.0234		
	hold	$\rightarrow$	G	-0.0352	-0.0234	-0.0234	-0.0234	-0.0234		
G	min	pwh		0.8830	0.8830	0.8830	0.8830	0.8830		
	minpwh			0.8830	0.8830	0.8830	0.8830	0.8830		
R	reco	very		0.0078	0.0078	0.0078	0.0117	0.0117		
	rem	oval	•	-0.0039	-0.0039	-0.0039	-0.0078	-0.0078		

## **Cell Description**

The LATRQ cell is a D-type active-high transparent latch with asynchronous active-low reset (RN). When the enable (G) is high, data is transferred to the output (Q).

## **Logic Symbol**

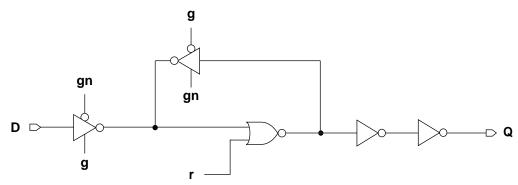


#### **Function Table**

RN	G	G D Q[n+1]	
0	Х	Х	0
1	1	0	0
1	1	1	1
1	0	Х	Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
LATRQX0P5MA10TR	2.00	3.00
LATRQX1MA10TR	2.00	3.00
LATRQX2MA10TR	2.00	3.20
LATRQX3MA10TR	2.00	3.40



Pin	Power (uW/MHz)								
	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0015	0.0020	0.0025	0.0028					
G	0.0021	0.0024	0.0026	0.0030					
RN	0.0008	0.0010	0.0012	0.0015					
Q	0.0039	0.0048	0.0069	0.0095					

# Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0011	0.0015	0.0017	0.0018					
G	0.0016	0.0017	0.0018	0.0019					
RN	0.0018	0.0020	0.0021	0.0022					

## Delays at 25°C,1.0V, Typical Process

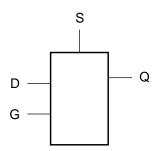
Description					Intrinsic I	Delay (ns)		K <sub>load</sub> (ns/pF)			
				X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
D	$\rightarrow$	Q	$\uparrow$	0.0530	0.0430	0.0461	0.0524	4.8272	2.4822	1.2235	0.8113
D	$\rightarrow$	Q	$\downarrow$	0.0641	0.0544	0.0568	0.0627	3.0304	1.5246	0.7732	0.5292
G	$\rightarrow$	Q	$\uparrow$	0.0432	0.0343	0.0373	0.0422	4.8284	2.4824	1.2237	0.8115
G	$\rightarrow$	Q	$\leftarrow$	0.0617	0.0529	0.0545	0.0575	3.0297	1.5243	0.7730	0.5290
RN	$\rightarrow$	Q	$\uparrow$	0.0556	0.0451	0.0480	0.0546	4.8277	2.4823	1.2234	0.8114
RN	$\rightarrow$	Q	$\downarrow$	0.0437	0.0544	0.0679	0.0821	2.8740	1.5153	0.7813	0.5427

Pin	Requirement			Interval (ns)				
F 1111	Requirement		X0P5M	X1P0M	X2P0M	X3P0M		
	setup	$\uparrow$	$\rightarrow$	G	0.0547	0.0430	0.0469	0.0508
D	setup	$\downarrow$	$\rightarrow$	G	0.0547	0.0430	0.0430	0.0508
	hold	$\uparrow$	$\rightarrow$	G	-0.0430	-0.0352	-0.0391	-0.0430
	hold	$\downarrow$	$\rightarrow$	G	-0.0391	-0.0312	-0.0312	-0.0352
G	n	ninp	wh		0.8830	0.8830	0.8830	0.8830
	minpwl				0.8830	0.8830	0.8830	0.8830
RN	recovery				0.0508	0.0430	0.0430	0.0508
	re	emo	val		-0.0469	-0.0391	-0.0391	-0.0469

#### **Cell Description**

The LATSPQ cell is a D-type active-high transparent latch with asynchronous active-high set (S). When the enable (G) is high, data is transferred to the output (Q).

## **Logic Symbol**

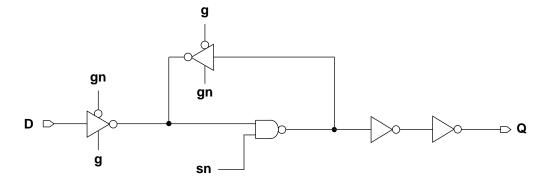


#### **Function Table**

S	G	D	Q[n+1]
1	Х	Х	1
0	1	0	0
0	1	1	1
0	0	Х	Q[n]

## **Cell Size**

Drive Strength	Height (um)	Width (um)
LATSPQX0P5MA10TR	2.00	3.00
LATSPQX1MA10TR	2.00	3.00
LATSPQX2MA10TR	2.00	3.20
LATSPQX3MA10TR	2.00	4.20



Pin	Power (uW/MHz)								
	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0015	0.0021	0.0024	0.0043					
G	0.0021	0.0024	0.0026	0.0031					
S	0.0010	0.0014	0.0015	0.0025					
Q	0.0042	0.0052	0.0080	0.0096					

# Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M	X1P0M	X2P0M	X3P0M					
D	0.0007	0.0009	0.0009	0.0017					
G	0.0014	0.0014	0.0015	0.0018					
S	0.0015	0.0017	0.0017	0.0027					

## Delays at 25°C,1.0V, Typical Process

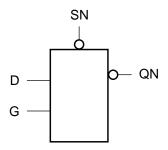
Description		Intrinsic I	Delay (ns)		K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$D \;  o \; Q \; \uparrow$	0.0516	0.0412	0.0456	0.0416	4.7200	2.3922	1.1937	0.7974
$D \;  o \; Q \; \downarrow$	0.0762	0.0673	0.0779	0.0657	2.9785	1.4841	0.7587	0.4930
$G \to Q \uparrow$	0.0420	0.0336	0.0376	0.0347	4.7203	2.3922	1.1937	0.7974
$G \;  o \; Q \; \downarrow$	0.0686	0.0595	0.0672	0.0561	2.9780	1.4835	0.7584	0.4928
$S \rightarrow Q \uparrow$	0.0364	0.0450	0.0547	0.0709	4.6923	2.4046	1.2026	0.8126
$S \rightarrow Q \downarrow$	0.0791	0.0701	0.0806	0.0683	2.9783	1.4840	0.7587	0.4930

Pin	Peguirement				Pin Requirement Interval (ns)					
F 1111	ixeq	une	IIICII		X0P5M	X1P0M	X2P0M	X3P0M		
	setup	$\uparrow$	$\rightarrow$	G	0.0508	0.0430	0.0469	0.0430		
D	setup	$\downarrow$	$\rightarrow$	G	0.0664	0.0547	0.0664	0.0547		
	hold	$\uparrow$	$\rightarrow$	G	-0.0430	-0.0352	-0.0391	-0.0312		
	hold	$\downarrow$	$\rightarrow$	G	-0.0508	-0.0430	-0.0547	-0.0430		
G	n	ninp	wh		0.8830	0.8830	0.8830	0.8830		
	minpwh		0.8830	0.8830	0.8830	0.8830				
S	re	cov	ery		0.0625	0.0508	0.0625	0.0508		
	re	emo	val		-0.0586	-0.0469	-0.0586	-0.0469		

## **Cell Description**

The LATSQN cell is a D-type active-high transparent latch with asynchronous active-low set (SN). When the enable (G) is high, data is transferred to the output (QN).

## **Logic Symbol**

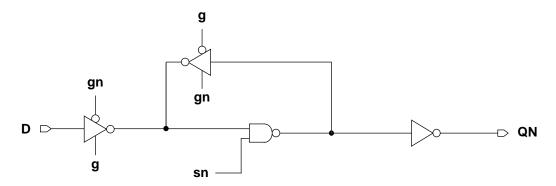


#### **Function Table**

SN	G	D	QN[n+1]
0	Х	Х	0
1	1	0	1
1	1	1	0
1	0	Х	QN[n]

## **Cell Size**

Drive Strength	Height (um)	Width (um)
LATSQNX0P5MA10TR	2.00	2.80
LATSQNX1MA10TR	2.00	2.80
LATSQNX2MA10TR	2.00	3.00
LATSQNX3MA10TR	2.00	3.20
LATSQNX4MA10TR	2.00	3.40



Pin	Power (uW/MHz)								
F III	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
D	0.0013	0.0018	0.0024	0.0026	0.0030				
G	0.0020	0.0022	0.0025	0.0027	0.0030				
SN	0.0006	0.0009	0.0013	0.0015	0.0017				
QN	0.0040	0.0052	0.0071	0.0092	0.0111				

# Pin Capacitance

Pin	Capacitance (pF)								
F 111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
D	0.0009	0.0013	0.0016	0.0017	0.0019				
G	0.0012	0.0013	0.0013	0.0013	0.0014				
SN	0.0011	0.0013	0.0017	0.0017	0.0016				

## Delays at 25°C,1.0V, Typical Process

Description				Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
D	$\rightarrow$	QN	$\uparrow$	0.0783	0.0667	0.0626	0.0700	0.0757	
D	$\rightarrow$	QN	$\downarrow$	0.0660	0.0556	0.0544	0.0601	0.0643	
G	$\rightarrow$	QN	$\uparrow$	0.0776	0.0676	0.0643	0.0714	0.0749	
G	$\rightarrow$	QN	$\downarrow$	0.0579	0.0496	0.0481	0.0543	0.0586	
SN	$\rightarrow$	QN	$\uparrow$	0.0355	0.0351	0.0351	0.0421	0.0475	
SN	$\rightarrow$	QN	$\downarrow$	0.0372	0.0377	0.0386	0.0458	0.0522	

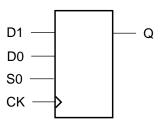
Description				K <sub>load</sub> (ns/pF)				
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
D	$\rightarrow$	QN	$\uparrow$	4.5746	2.3575	1.1676	0.7841	0.5860
D	$\rightarrow$	QN	$\downarrow$	2.8081	1.4497	0.7161	0.4928	0.3701
G	$\rightarrow$	QN	$\uparrow$	4.5745	2.3576	1.1675	0.7841	0.5860
G	$\rightarrow$	QN	$\rightarrow$	2.8078	1.4497	0.7162	0.4928	0.3701
SN	$\rightarrow$	QN	<b>↑</b>	4.5701	2.3567	1.1674	0.7840	0.5860
SN	$\rightarrow$	QN	$\downarrow$	2.8233	1.4600	0.7209	0.4946	0.3716

Pin	Pog	Requirement			Interval (ns)					
	Nequilement				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
	setup	$\uparrow$	$\rightarrow$	G	0.0430	0.0312	0.0312	0.0312	0.0312	
D	setup	$\downarrow$	$\rightarrow$	G	0.0469	0.0352	0.0312	0.0352	0.0352	
	hold	$\uparrow$	$\rightarrow$	G	-0.0352	-0.0234	-0.0234	-0.0234	-0.0234	
	hold	$\downarrow$	$\rightarrow$	G	-0.0352	-0.0234	-0.0195	-0.0234	-0.0234	
G	n	ninp	wh		0.8830	0.8830	0.8830	0.8830	0.8830	
	r	minpwl			0.8830	0.8830	0.8830	0.8830	0.8830	
SN	re	recovery			-0.0117	-0.0156	-0.0195	-0.0156	-0.0156	
	re	emo	val		0.0156	0.0195	0.0234	0.0195	0.0195	

#### **Cell Description**

The M2DFFQ cell is a positive-edge triggered, static D-type flip-flop with a 2-to-1 data select control (S0) for the data inputs (D1, D0). The cell has a single output (Q).

## **Logic Symbol**

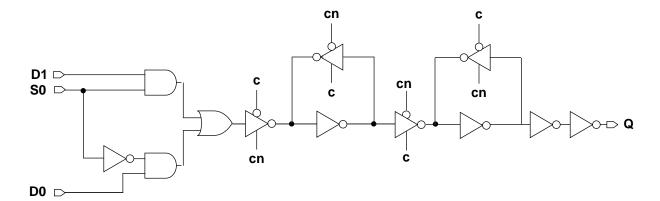


#### **Function Table**

S0	D1	D0	CK	Q[n+1]
0	х	0		0
0	х	1		1
1	0	Х		0
1	1	Х		1
Х	Х	Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
M2DFFQX0P5MA10TR	2.00	5.80
M2DFFQX1MA10TR	2.00	5.80
M2DFFQX2MA10TR	2.00	6.20
M2DFFQX3MA10TR	2.00	6.40
M2DFFQX4MA10TR	2.00	7.20



## **AC Power**

Pin	Power (uW/MHz)								
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
D0	0.0051	0.0065	0.0081	0.0088	0.0094				
D1	0.0055	0.0068	0.0086	0.0093	0.0099				
S0	0.0056	0.0072	0.0086	0.0093	0.0088				
CK	0.0038	0.0043	0.0051	0.0060	0.0059				
Q	0.0033	0.0039	0.0056	0.0082	0.0103				

## Pin Capacitance

Pin	Capacitance (pF)								
F 111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
D0	0.0012	0.0012	0.0015	0.0015	0.0019				
D1	0.0012	0.0011	0.0014	0.0014	0.0018				
S0	0.0018	0.0021	0.0022	0.0022	0.0026				
CK	0.0009	0.0010	0.0010	0.0012	0.0011				

## Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)				
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
CK → Q ↑	0.0895	0.0733	0.0708	0.0664	0.0727
$CK \ \to \ Q \ \downarrow$	0.0866	0.0740	0.0732	0.0750	0.0766

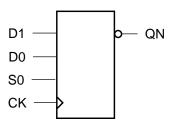
Description	K <sub>load</sub> (ns/pF)						
	X0P5M X1P0M X2P0M X3P0M X4P0						
CK → Q ↑	4.3141	2.3951	1.1691	0.7864	0.5836		
$CK \ \to \ Q \ \downarrow$	2.9337	1.5901	0.7652	0.5023	0.3611		

					Пот, тур.	Interval (ns)						
Pin	Red	quire	emer	nt	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M			
	setup	$\uparrow$	$\rightarrow$	CK	0.0508	0.0430	0.0430	0.0469	0.0352			
DO	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0547	0.0469	0.0508	0.0430			
D0	hold	$\uparrow$	$\rightarrow$	CK	-0.0195	-0.0195	-0.0195	-0.0195	-0.0195			
	hold	$\downarrow$	$\rightarrow$	CK	-0.0391	-0.0391	-0.0312	-0.0312	-0.0117			
	setup	$\uparrow$	$\rightarrow$	CK	0.0508	0.0430	0.0391	0.0430	0.0352			
D1	setup	$\downarrow$	$\rightarrow$	CK	0.0664	0.0547	0.0508	0.0508	0.0430			
וטו	hold	$\uparrow$	$\rightarrow$	CK	-0.0195	-0.0195	-0.0156	-0.0195	-0.0195			
	hold	$\downarrow$	$\rightarrow$	CK	-0.0430	-0.0391	-0.0352	-0.0352	-0.0117			
	setup	$\uparrow$	$\rightarrow$	CK	0.0664	0.0547	0.0508	0.0547	0.0430			
S0	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0508	0.0508	0.0508	0.0469			
30	hold	$\uparrow$	$\rightarrow$	CK	-0.0117	-0.0117	-0.0117	-0.0117	-0.0117			
	hold	$\downarrow$	$\rightarrow$	CK	-0.0312	-0.0273	-0.0273	-0.0273	-0.0117			
СК	r	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830			
CK		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830			

## **Cell Description**

The M2DFFQN cell is a positive-edge triggered, static D-type flip-flop with a 2-to-1 data select control (S0) for the data inputs (D1, D0). The cell has a single output (QN).

## **Logic Symbol**

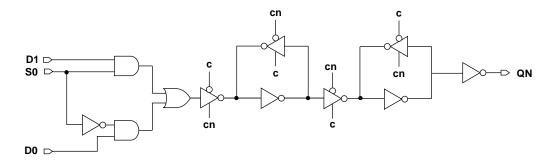


## **Function Table**

S0	D1	D0	CK	QN[n+1]
0	Х	0		1
0	Х	1		0
1	0	Х		1
1	1	х		0
Х	Х	Х		QN[n]

## **Cell Size**

Drive Strength	Height (um)	Width (um)
M2DFFQNX0P5MA10TR	2.00	5.60
M2DFFQNX1MA10TR	2.00	5.80
M2DFFQNX2MA10TR	2.00	6.20
M2DFFQNX3MA10TR	2.00	6.60



Pin	Power (uW/MHz)									
	X0P5M	X1P0M	X2P0M	X3P0M						
D0	0.0051	0.0064	0.0078	0.0091						
D1	0.0057	0.0068	0.0083	0.0096						
S0	0.0057	0.0067	0.0080	0.0087						
CK	0.0038	0.0043	0.0050	0.0059						
QN	0.0035	0.0040	0.0058	0.0084						

# Pin Capacitance

Pin	Capacitance (pF)									
F III	X0P5M	X1P0M	X2P0M	X3P0M						
D0	0.0012	0.0014	0.0016	0.0018						
D1	0.0012	0.0013	0.0014	0.0017						
S0	0.0020	0.0022	0.0023	0.0028						
CK	0.0009	0.0010	0.0010	0.0012						

## Delays at 25°C,1.0V, Typical Process

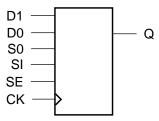
Description		Intrinsic I	Delay (ns)		K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0888	0.0733	0.0708	0.0667	4.2721	2.3951	1.1692	0.7872
$CK \ \to \ QN \ \downarrow$	0.0870	0.0739	0.0731	0.0745	2.9512	1.5901	0.7653	0.5032

Din	Pin Requirement			\ <b>+</b>		Interv	al (ns)	
F 1111				X0P5M	X1P0M	X2P0M	X3P0M	
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0430	0.0391	0.0391
D0	setup	$\downarrow$	$\rightarrow$	CK	0.0469	0.0391	0.0469	0.0430
00	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0234	-0.0195	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0117	-0.0078	-0.0117	-0.0078
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0430	0.0391	0.0391
D1	setup	$\downarrow$	$\rightarrow$	CK	0.0508	0.0430	0.0469	0.0469
וטו	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0234	-0.0195	-0.0156
	hold	$\downarrow$	$\rightarrow$	CK	-0.0117	-0.0078	-0.0117	-0.0117
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0391	0.0469	0.0430
S0	setup	$\downarrow$	$\rightarrow$	CK	0.0547	0.0508	0.0508	0.0469
30	hold	$\uparrow$	$\rightarrow$	CK	-0.0078	-0.0078	-0.0078	-0.0078
	hold	$\downarrow$	$\rightarrow$	CK	-0.0039	-0.0078	-0.0078	-0.0078
СК	r	minpwh			0.8830	0.8830	0.8830	0.8830
		min	owl		0.8830	0.8830	0.8830	0.8830

#### **Cell Description**

The M2SDFFQ cell is a positive-edge triggered, static D-type flip-flop with a 2-to-1 data select control (S0) for the data inputs (D1, D0), scan input (SI), and active-high scan enable (SE). The cell has a single output (Q).

## **Logic Symbol**

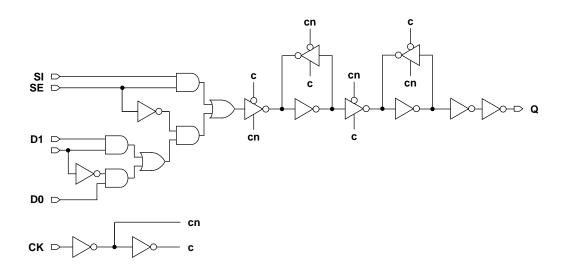


#### **Function Table**

SE	SI	S0	D1	D0	CK	Q[n+1]
0	Х	0	Х	0		0
0	Х	0	х	1		1
0	Х	1	0	Х		0
0	Х	1	1	х		1
1	0	Х	Х	х		0
1	1	Х	Х	Х		1
Х	Х	Х	Х	Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
M2SDFFQX0P5MA10TR	2.00	7.60
M2SDFFQX1MA10TR	2.00	7.60
M2SDFFQX2MA10TR	2.00	8.00
M2SDFFQX3MA10TR	2.00	8.00
M2SDFFQX4MA10TR	2.00	8.60



Pin		Power (uW/MHz)										
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M							
SI	0.0049	0.0062	0.0073	0.0080	0.0082							
SE	0.0056	0.0068	0.0080	0.0086	0.0088							
D0	0.0064	0.0079	0.0096	0.0102	0.0104							
D1	0.0068	0.0084	0.0101	0.0107	0.0109							
S0	0.0069	0.0087	0.0102	0.0108	0.0110							
CK	0.0038	0.0044	0.0051	0.0060	0.0060							
Q	0.0033	0.0038	0.0056	0.0081	0.0116							

# Pin Capacitance

Pin	Capacitance (pF)									
F 111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
SI	0.0007	0.0007	0.0007	0.0007	0.0007					
SE	0.0017	0.0017	0.0018	0.0018	0.0018					
D0	0.0012	0.0012	0.0015	0.0015	0.0015					
D1	0.0011	0.0012	0.0014	0.0014	0.0014					
S0	0.0018	0.0022	0.0023	0.0023	0.0023					
CK	0.0009	0.0009	0.0010	0.0012	0.0011					

# Delays at 25°C,1.0V, Typical Process

Description		Intri	nsic Delay	(ns)	
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
$CK \ \to \ Q \ \uparrow$	0.0885	0.0734	0.0708	0.0699	0.0702
$CK \  o \ Q \ \downarrow$	0.0846	0.0705	0.0722	0.0781	0.0850

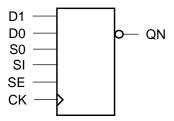
Description		ŀ	ััั <sub>load</sub> (ns/pF	)	
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M
CK → Q ↑	4.3073	2.3532	1.1646	0.7887	0.5870
$CK \ \to \ Q \ \downarrow$	2.9232	1.5243	0.7584	0.5313	0.3932

Pin	Do.	Requirement			Interval (ns)					
Pin	Requirement		X0P5M	X1P0M	X2P0M	X3P0M	X4P0M			
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0586	0.0586	0.0664	0.0664	
SI	setup	$\downarrow$	$\rightarrow$	CK	0.0859	0.0820	0.0859	0.0859	0.0859	
SI	hold	$\uparrow$	$\rightarrow$	CK	-0.0312	-0.0312	-0.0352	-0.0391	-0.0391	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0625	-0.0625	-0.0664	-0.0664	-0.0664	
	setup	$\uparrow$	$\rightarrow$	CK	0.0977	0.0938	0.0977	0.1016	0.1016	
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0625	0.0547	0.0625	0.0625	
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0273	-0.0273	-0.0352	-0.0352	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0352	-0.0352	-0.0312	-0.0352	-0.0352	
	setup	$\uparrow$	$\rightarrow$	CK	0.0820	0.0742	0.0664	0.0703	0.0742	
D0	setup	$\downarrow$	$\rightarrow$	CK	0.0938	0.0820	0.0742	0.0742	0.0742	
DU	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0469	-0.0430	-0.0469	-0.0469	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0703	-0.0625	-0.0547	-0.0586	-0.0547	
	setup	$\uparrow$	$\rightarrow$	CK	0.0781	0.0703	0.0625	0.0703	0.0703	
D1	setup	$\downarrow$	$\rightarrow$	CK	0.0977	0.0820	0.0742	0.0742	0.0742	
וטו	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0430	-0.0391	-0.0430	-0.0430	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0703	-0.0625	-0.0586	-0.0586	-0.0586	
	setup	$\uparrow$	$\rightarrow$	CK	0.0977	0.0820	0.0742	0.0781	0.0781	
S0	setup	$\downarrow$	$\rightarrow$	CK	0.0938	0.0781	0.0742	0.0781	0.0781	
30	hold	$\uparrow$	$\rightarrow$	CK	-0.0391	-0.0391	-0.0312	-0.0391	-0.0391	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0547	-0.0508	-0.0469	-0.0508	-0.0547	
СК	r	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830	
5		minpwl		0.8830	0.8830	0.8830	0.8830	0.8830		

## **Cell Description**

The M2SDFFQN cell is a positive-edge triggered, static D-type flip-flop with a 2-to-1 data select control (S0) for the data inputs (D1,D0), scan input (SI), and active-high scan enable (SE). The cell has a single output (QN).

## **Logic Symbol**

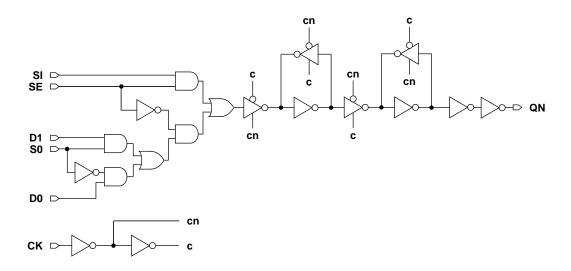


## **Function Table**

SE	SI	S0	D1	D0	CK	QN[n+1]
0	Х	0	Х	0		1
0	Х	0	Х	1		0
0	Х	1	0	х		1
0	Х	1	1	х		0
1	0	Х	Х	Х		1
1	1	Х	Х	Х		0
Х	Х	Х	Х	Х		QN[n]

## **Cell Size**

Drive Strength	Height (um)	Width (um)
M2SDFFQNX0P5MA10TR	2.00	7.60
M2SDFFQNX1MA10TR	2.00	7.60
M2SDFFQNX2MA10TR	2.00	8.00
M2SDFFQNX3MA10TR	2.00	8.20



Pin	Power (uW/MHz)									
F 1111	X0P5M	X1P0M	X2P0M	X3P0M						
SI	0.0050	0.0063	0.0076	0.0082						
SE	0.0056	0.0069	0.0083	0.0088						
D0	0.0064	0.0079	0.0099	0.0104						
D1	0.0068	0.0083	0.0104	0.0109						
S0	0.0070	0.0087	0.0105	0.0110						
CK	0.0039	0.0045	0.0051	0.0057						
QN	0.0033	0.0041	0.0062	0.0079						

# Pin Capacitance

Pin		nce (pF)		
F III	X0P5M	X1P0M	X2P0M	X3P0M
SI	0.0007	0.0007	0.0007	0.0007
SE	0.0017	0.0017	0.0018	0.0018
D0	0.0012	0.0012	0.0015	0.0016
D1	0.0011	0.0011	0.0014	0.0014
S0	0.0018	0.0021	0.0023	0.0023
CK	0.0009	0.0009	0.0010	0.0011

# Delays at 25°C,1.0V, Typical Process

Description		Intrinsic I		K <sub>load</sub> (	ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0902	0.0788	0.0731	0.0732	4.2468	2.3426	1.1555	0.7823
$CK \to QN \downarrow$	0.1001	0.0876	0.0814	0.0813	2.4649	1.3648	0.6584	0.4563

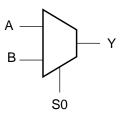
Pin	Dag		ame:	.4		Interv	al (ns)	
Pin	Requirement		X0P5M	X1P0M	X2P0M	X3P0M		
	setup	$\uparrow$	$\rightarrow$	CK	0.0586	0.0547	0.0586	0.0586
SI	setup	$\downarrow$	$\rightarrow$	CK	0.0859	0.0781	0.0859	0.0859
Si	hold	$\uparrow$	$\rightarrow$	CK	-0.0312	-0.0312	-0.0391	-0.0391
	hold	$\downarrow$	$\rightarrow$	CK	-0.0625	-0.0625	-0.0703	-0.0703
	setup	$\uparrow$	$\rightarrow$	CK	0.0977	0.0898	0.0977	0.0977
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0625	0.0547	0.0547
36	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0273	-0.0312	-0.0352
	hold	$\downarrow$	$\rightarrow$	CK	-0.0391	-0.0391	-0.0352	-0.0352
	setup	$\uparrow$	$\rightarrow$	CK	0.0781	0.0742	0.0664	0.0664
D0	setup	$\downarrow$	$\rightarrow$	CK	0.0938	0.0820	0.0742	0.0742
00	hold	$\uparrow$	$\rightarrow$	CK	-0.0508	-0.0508	-0.0469	-0.0469
	hold	$\downarrow$	$\rightarrow$	CK	-0.0703	-0.0664	-0.0586	-0.0586
	setup	$\uparrow$	$\rightarrow$	CK	0.0781	0.0703	0.0625	0.0625
D1	setup	$\downarrow$	$\rightarrow$	CK	0.0938	0.0820	0.0742	0.0742
וטו	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0469	-0.0430	-0.0430
	hold	$\downarrow$	$\rightarrow$	CK	-0.0703	-0.0664	-0.0586	-0.0586
	setup	$\uparrow$	$\rightarrow$	CK	0.0938	0.0820	0.0742	0.0742
S0	setup	$\downarrow$	$\rightarrow$	CK	0.0898	0.0781	0.0742	0.0703
30	hold	$\uparrow$	$\rightarrow$	CK	-0.0430	-0.0430	-0.0352	-0.0391
	hold	$\downarrow$	$\rightarrow$	CK	-0.0586	-0.0547	-0.0508	-0.0508
СК	r	ninp	wh		0.8830	0.8830	0.8830	0.8830
		minp	owl		0.8830	0.8830	0.8830	0.8830

## **Cell Description**

The MX2 cell is a 2-to-1 multiplexer. The state of the select input (S0) determines which data input (A, B) is presented to the output (Y). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (\overline{\mathsf{S}0} {\bullet} \mathsf{A}) + (\mathsf{S}0 {\bullet} \mathsf{B})$$

## **Logic Symbol**

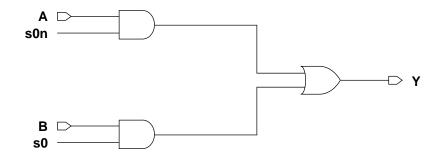


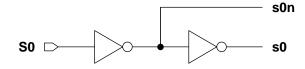
## **Function Table**

S0	Α	В	Υ
0	0	Х	0
0	1	Х	1
1	Х	0	0
1	Х	1	1

## **Cell Size**

Drive Strength	Height (um)	Width (um)
MX2X0P5BA10TR	2.00	2.60
MX2X0P5MA10TR	2.00	2.40
MX2X0P7BA10TR	2.00	2.60
MX2X0P7MA10TR	2.00	2.40
MX2X1BA10TR	2.00	2.60
MX2X1MA10TR	2.00	2.40
MX2X1P4BA10TR	2.00	3.20
MX2X1P4MA10TR	2.00	3.80
MX2X2BA10TR	2.00	3.20
MX2X2MA10TR	2.00	4.00
MX2X3BA10TR	2.00	4.60
MX2X3MA10TR	2.00	5.60
MX2X4BA10TR	2.00	5.00
MX2X4MA10TR	2.00	5.60
MX2X6BA10TR	2.00	7.80
MX2X6MA10TR	2.00	8.40
MX2X8BA10TR	2.00	9.80





Pin		Power (uW/MHz)										
-	X0P5B	X0P5M	X0P7B	X0P7M	X1P0B	X1P0M	X1P4B	X1P4M				
S0	0.0024	0.0025	0.0026	0.0028	0.0030	0.0032	0.0035	0.0048				
В	0.0007	0.0008	0.0008	0.0009	0.0010	0.0012	0.0013	0.0017				
Α	0.0006	0.0002	0.0007	0.0003	0.0008	0.0004	0.0012	0.0005				

## AC Power (Cont'd.)

Pin		Power (uW/MHz)										
-	X2P0B	X2P0M	X3P0B	X3P0M	X4P0B	X4P0M	X6P0B	X6P0M	X8P0B			
S0	0.0042	0.0060	0.0066	0.0081	0.0081	0.0097	0.0121	0.0153	0.0161			
В	0.0016	0.0023	0.0025	0.0033	0.0033	0.0042	0.0050	0.0066	0.0067			
Α	0.0014	0.0007	0.0022	0.0011	0.0028	0.0015	0.0042	0.0023	0.0056			

# Pin Capacitance

Pin		Capacitance (pF)										
F 111	X0P5B	X0P5M	X0P7B	X0P7M	X1P0B	X1P0M	X1P4B	X1P4M				
S0	0.0026	0.0023	0.0027	0.0025	0.0029	0.0028	0.0029	0.0044				
В	0.0009	0.0012	0.0009	0.0013	0.0011	0.0016	0.0014	0.0024				
Α	0.0010	0.0013	0.0010	0.0014	0.0012	0.0016	0.0015	0.0024				

# Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
FIII	X2P0B	X2P0M	X3P0B	X3P0M	X4P0B	X4P0M	X6P0B	X6P0M	X8P0B			
S0	0.0033	0.0058	0.0055	0.0076	0.0066	0.0088	0.0096	0.0137	0.0129			
В	0.0017	0.0030	0.0025	0.0042	0.0031	0.0051	0.0049	0.0080	0.0064			
Α	0.0018	0.0031	0.0027	0.0043	0.0032	0.0053	0.0050	0.0083	0.0065			

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)									
	X0P5B	X0P5M	X0P7B	X0P7M	X1P0B	X1P0M	X1P4B	X1P4M			
$S0 \rightarrow Y \uparrow$	0.0559	0.0532	0.0533	0.0511	0.0514	0.0478	0.0535	0.0490			
$S0 \rightarrow Y \downarrow$	0.0474	0.0565	0.0452	0.0550	0.0437	0.0525	0.0464	0.0527			
$B \to Y \uparrow$	0.0422	0.0457	0.0400	0.0436	0.0377	0.0404	0.0384	0.0418			
$B \to Y \downarrow$	0.0371	0.0557	0.0355	0.0540	0.0344	0.0508	0.0340	0.0519			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.0414	0.0371	0.0387	0.0353	0.0364	0.0325	0.0394	0.0342			
$A \rightarrow Y \downarrow$	0.0368	0.0450	0.0346	0.0437	0.0327	0.0409	0.0361	0.0429			

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	ptior	1		Intrinsic Delay (ns)										
				X2P0B	X2P0M	X3P0B	X3P0M	X4P0B	X4P0M	X6P0B	X6P0M	X8P0B			
S0	$\rightarrow$	Υ	$\uparrow$	0.0511	0.0458	0.0487	0.0480	0.0466	0.0455	0.0476	0.0462	0.0461			
S0	$\rightarrow$	Υ	$\downarrow$	0.0438	0.0497	0.0422	0.0537	0.0404	0.0514	0.0419	0.0513	0.0405			
В	$\rightarrow$	Υ	$\uparrow$	0.0365	0.0396	0.0337	0.0404	0.0338	0.0373	0.0342	0.0372	0.0338			
В	$\rightarrow$	Υ	$\downarrow$	0.0327	0.0495	0.0307	0.0528	0.0315	0.0505	0.0317	0.0495	0.0316			
Α	$\rightarrow$	Υ	$\uparrow$	0.0369	0.0323	0.0360	0.0345	0.0342	0.0316	0.0351	0.0316	0.0341			
Α	$\rightarrow$	Υ	$\downarrow$	0.0335	0.0407	0.0331	0.0454	0.0319	0.0430	0.0324	0.0422	0.0318			

Description	K <sub>load</sub> (ns/pF)										
	X0P5B	X0P5M	X0P7B	X0P7M	X1P0B	X1P0M	X1P4B	X1P4M			
S0 → Y ↑	4.3852	4.5878	3.2055	3.3499	2.3036	2.3983	1.6411	1.6479			
$SO \rightarrow Y \downarrow$	5.0343	2.8996	3.6418	2.0929	2.5346	1.4695	1.8029	1.0377			
$B \ \to \ Y \ \uparrow$	4.3863	4.6218	3.2351	3.3732	2.3088	2.4132	1.6139	1.6593			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	5.0272	2.8995	3.6390	2.0928	2.5338	1.4694	1.8009	1.0377			
$A  \rightarrow  Y  \uparrow$	4.3809	4.5955	3.2033	3.3557	2.3024	2.4021	1.6411	1.6512			
$A  \rightarrow  Y  \downarrow$	5.0255	2.8988	3.6372	2.0922	2.5322	1.4693	1.8020	1.0377			

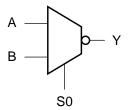
Description				·)					
	X2P0B	X2P0M	X3P0B	X3P0M	X4P0B	X4P0M	X6P0B	X6P0M	X8P0B
$SO \rightarrow Y \uparrow$	1.1642	1.1747	0.7731	0.7846	0.5762	0.5821	0.3829	0.3876	0.2878
S0 $\rightarrow$ Y $\downarrow$	1.2670	0.7238	0.8434	0.4945	0.6267	0.3655	0.4195	0.2448	0.3146
$B \ \to \ Y \ \uparrow$	1.1569	1.1823	0.7686	0.7896	0.5740	0.5856	0.3816	0.3900	0.2870
$B \ \to \ Y \ \downarrow$	1.2663	0.7239	0.8429	0.4945	0.6266	0.3655	0.4194	0.2448	0.3145
$A  \rightarrow  Y  \uparrow$	1.1642	1.1771	0.7730	0.7869	0.5762	0.5836	0.3829	0.3887	0.2879
$A  \rightarrow  Y  \downarrow$	1.2665	0.7237	0.8428	0.4949	0.6265	0.3657	0.4193	0.2449	0.3144

## **Cell Description**

The MXIT2 cell is a 2-to-1 multiplexer with inverted output. The state of the select input (S0) determines which data input (A, B) is presented to the output (Y). The output (Y) is represented by the logic equation:

$$Y = (\overline{\overline{S0} \bullet A}) + (S0 \bullet B)$$

## **Logic Symbol**

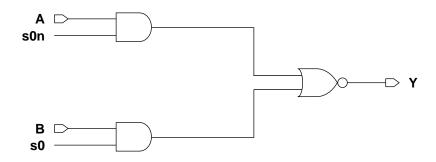


## **Function Table**

S0	Α	В	Υ
0	0	Х	1
0	1	Х	0
1	Х	0	1
1	Х	1	0

## **Cell Size**

Drive Strength	Height (um)	Width (um)
MXIT2X0P5MA10TR	2.00	2.00
MXIT2X0P7MA10TR	2.00	2.00
MXIT2X1MA10TR	2.00	2.00
MXIT2X1P4MA10TR	2.00	3.40
MXIT2X2MA10TR	2.00	3.60
MXIT2X3MA10TR	2.00	4.00
MXIT2X4MA10TR	2.00	6.00



Pin		Power (uW/MHz)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M					
S0	0.0022	0.0024	0.0029	0.0041	0.0055	0.0073	0.0101					
В	0.0015	0.0018	0.0023	0.0035	0.0045	0.0067	0.0095					
Α	0.0015	0.0020	0.0025	0.0037	0.0047	0.0069	0.0097					

## Pin Capacitance

Pin		Capacitance (pF)										
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M					
S0	0.0028	0.0032	0.0036	0.0044	0.0061	0.0080	0.0110					
В	0.0012	0.0014	0.0018	0.0027	0.0035	0.0052	0.0070					
Α	0.0011	0.0014	0.0018	0.0026	0.0033	0.0049	0.0064					

## Delays at 25°C,1.0V, Typical Process

De	Description			Intrinsic Delay (ns)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
S0	$\rightarrow$	Υ	$\uparrow$	0.0180	0.0171	0.0163	0.0185	0.0165	0.0147	0.0153		
S0	$\rightarrow$	Υ	$\downarrow$	0.0178	0.0171	0.0169	0.0203	0.0177	0.0164	0.0173		
В	$\rightarrow$	Υ	$\uparrow$	0.0203	0.0186	0.0171	0.0192	0.0177	0.0161	0.0168		
В	$\rightarrow$	Υ	$\downarrow$	0.0149	0.0136	0.0124	0.0144	0.0132	0.0121	0.0127		
Α	$\rightarrow$	Υ	$\uparrow$	0.0193	0.0183	0.0165	0.0170	0.0160	0.0142	0.0150		
Α	$\rightarrow$	Υ	$\downarrow$	0.0154	0.0148	0.0136	0.0150	0.0140	0.0128	0.0136		

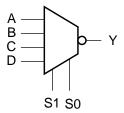
De	Description		K <sub>load</sub> (ns/pF)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	
S0	$\rightarrow$	Υ	$\uparrow$	6.7057	4.9530	3.5696	2.4856	1.8189	1.1901	0.8987	
S0	$\rightarrow$	Υ	$\downarrow$	4.5335	3.3086	2.3439	1.7486	1.2926	0.8371	0.6361	
В	$\rightarrow$	Υ	$\uparrow$	6.5864	4.8783	3.5313	2.5084	1.8086	1.1933	0.9013	
В	$\rightarrow$	Υ	$\downarrow$	4.5373	3.3270	2.3674	1.7938	1.2658	0.8251	0.6228	
Α	$\rightarrow$	Υ	$\uparrow$	6.6910	4.9445	3.5644	2.4850	1.8183	1.1897	0.8986	
Α	$\rightarrow$	Υ	$\downarrow$	4.6001	3.3528	2.3745	1.7696	1.3052	0.8455	0.6429	

## **Cell Description**

The MXIT4 cell is a 4-to-1 multiplexer with inverted output. The state of the select inputs (S1, S0) determines which data input (A, B, C, D) is presented to the output (Y). The output (Y) is represented by the logic equation:

$$Y = (\overline{S0} \bullet \overline{S1} \bullet A) + (S0 \bullet \overline{S1} \bullet B) + (\overline{S0} \bullet S1 \bullet C) + (S0 \bullet S1 \bullet D)$$

## **Logic Symbol**

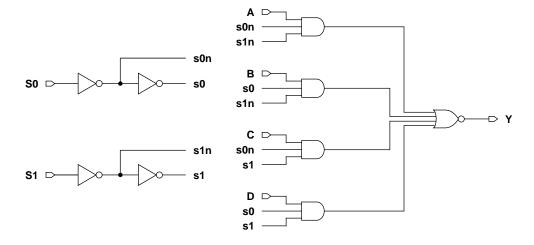


#### **Function Table**

S1	S0	Α	В	С	D	Υ
0	0	0	Х	Х	Х	1
0	0	1	Х	Х	Х	0
0	1	Х	0	Х	Х	1
0	1	Х	1	Х	Х	0
1	0	Х	Х	0	Х	1
1	0	Х	Х	1	Х	0
1	1	Х	Х	Х	0	1
1	1	Х	Х	Х	1	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
MXIT4X0P5MA10TR	2.00	5.60
MXIT4X0P7MA10TR	2.00	5.60
MXIT4X1MA10TR	2.00	6.00
MXIT4X1P4MA10TR	2.00	6.20
MXIT4X2MA10TR	2.00	6.20
MXIT4X3MA10TR	2.00	6.60



Pin		Power (uW/MHz)									
- 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M					
S1	0.0022	0.0024	0.0027	0.0032	0.0036	0.0044					
S0	0.0036	0.0040	0.0044	0.0050	0.0054	0.0062					
D	0.0015	0.0017	0.0020	0.0025	0.0028	0.0033					
С	0.0015	0.0018	0.0021	0.0026	0.0030	0.0035					
В	0.0014	0.0017	0.0020	0.0025	0.0028	0.0032					
Α	0.0016	0.0019	0.0022	0.0027	0.0031	0.0036					

## Pin Capacitance

Pin		Capacitance (pF)									
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M					
S1	0.0015	0.0015	0.0017	0.0019	0.0021	0.0024					
S0	0.0036	0.0039	0.0043	0.0051	0.0054	0.0061					
D	0.0009	0.0010	0.0012	0.0014	0.0015	0.0017					
С	0.0010	0.0011	0.0012	0.0014	0.0016	0.0018					
В	0.0009	0.0011	0.0012	0.0014	0.0016	0.0017					
Α	0.0009	0.0011	0.0012	0.0014	0.0016	0.0018					

## Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n	Intrinsic Delay (ns)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M			
S1	$\rightarrow$	Υ	$\uparrow$	0.0473	0.0461	0.0443	0.0444	0.0449	0.0462			
S1	$\rightarrow$	Υ	$\downarrow$	0.0518	0.0516	0.0508	0.0526	0.0548	0.0589			
S0	$\rightarrow$	Υ	$\uparrow$	0.0948	0.0874	0.0830	0.0786	0.0792	0.0792			
S0	$\rightarrow$	Υ	$\downarrow$	0.0989	0.0940	0.0899	0.0866	0.0888	0.0901			
D	$\rightarrow$	Υ	$\uparrow$	0.0835	0.0788	0.0735	0.0714	0.0715	0.0734			
D	$\rightarrow$	Υ	$\downarrow$	0.0876	0.0838	0.0796	0.0795	0.0808	0.0843			
С	$\rightarrow$	Υ	$\uparrow$	0.0816	0.0771	0.0720	0.0702	0.0708	0.0729			
С	$\rightarrow$	Υ	$\downarrow$	0.0857	0.0828	0.0789	0.0788	0.0805	0.0839			
В	$\rightarrow$	Υ	$\uparrow$	0.0905	0.0836	0.0790	0.0765	0.0771	0.0783			
В	$\rightarrow$	Υ	$\downarrow$	0.0930	0.0874	0.0832	0.0817	0.0837	0.0868			
Α	$\rightarrow$	Υ	$\uparrow$	0.0931	0.0859	0.0810	0.0780	0.0788	0.0800			

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	ptio	n	Intrinsic Delay (ns)						
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	
Α	$\rightarrow$	Υ	$\downarrow$	0.0937	0.0886	0.0843	0.0826	0.0848	0.0877	

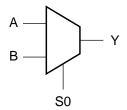
De	escri	ptio	n	K <sub>load</sub> (ns/pF)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M			
S1	$\rightarrow$	Υ	$\uparrow$	4.5925	3.3552	2.3839	1.6919	1.2018	0.7873			
S1	$\rightarrow$	Υ	$\downarrow$	2.9114	2.0204	1.3907	1.0406	0.7269	0.4808			
S0	$\rightarrow$	Υ	$\uparrow$	4.5959	3.3575	2.3852	1.6926	1.2023	0.7876			
S0	$\rightarrow$	Υ	$\downarrow$	2.9132	2.0176	1.3896	1.0392	0.7261	0.4801			
D	$\rightarrow$	Υ	$\uparrow$	4.5951	3.3575	2.3853	1.6924	1.2024	0.7877			
D	$\rightarrow$	Υ	$\downarrow$	2.9133	2.0214	1.3912	1.0409	0.7271	0.4809			
С	$\rightarrow$	Υ	$\uparrow$	4.5948	3.3572	2.3853	1.6926	1.2024	0.7877			
С	$\rightarrow$	Υ	$\downarrow$	2.9130	2.0213	1.3911	1.0409	0.7270	0.4809			
В	$\rightarrow$	Υ	$\uparrow$	4.5952	3.3573	2.3852	1.6927	1.2023	0.7876			
В	$\rightarrow$	Υ	$\downarrow$	2.9131	2.0174	1.3896	1.0393	0.7261	0.4802			
Α	$\rightarrow$	Υ	$\uparrow$	4.5961	3.3574	2.3853	1.6927	1.2023	0.7876			
Α	$A \rightarrow Y \downarrow 2.9127 2.01$		2.0174	1.3895	1.0392	0.7261	0.4802					

## **Cell Description**

The MXT2 cell is a 2-to-1 multiplexer. The state of the select input (S0) determines which data input (A, B) is presented to the output (Y). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (\overline{\mathsf{S}0} {\bullet} \mathsf{A}) + (\mathsf{S}0 {\bullet} \mathsf{B})$$

## **Logic Symbol**

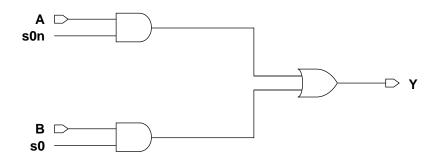


## **Function Table**

S0	Α	В	Υ
0	0	Х	0
0	1	Х	1
1	Х	0	0
1	Х	1	1

## **Cell Size**

Drive Strength	Height (um)	Width (um)
MXT2X0P5MA10TR	2.00	2.20
MXT2X0P7MA10TR	2.00	2.20
MXT2X1MA10TR	2.00	2.20
MXT2X1P4MA10TR	2.00	2.60
MXT2X2MA10TR	2.00	2.60
MXT2X3MA10TR	2.00	4.40
MXT2X4MA10TR	2.00	4.60
MXT2X6MA10TR	2.00	5.60



Pin		Power (uW/MHz)										
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
S0	0.0020	0.0023	0.0025	0.0027	0.0032	0.0052	0.0060	0.0085				
В	0.0014	0.0016	0.0019	0.0022	0.0027	0.0043	0.0052	0.0077				
Α	0.0015	0.0017	0.0021	0.0024	0.0029	0.0045	0.0054	0.0081				

## Pin Capacitance

Pin	Capacitance (pF)								
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	
S0	0.0026	0.0029	0.0031	0.0032	0.0037	0.0052	0.0059	0.0082	
В	0.0010	0.0012	0.0014	0.0015	0.0017	0.0030	0.0035	0.0050	
Α	0.0011	0.0012	0.0014	0.0015	0.0019	0.0027	0.0032	0.0048	

## Delays at 25°C,1.0V, Typical Process

De	Description			Intrinsic Delay (ns)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	
S0	$\rightarrow$	Υ	$\uparrow$	0.0427	0.0412	0.0390	0.0418	0.0395	0.0431	0.0410	0.0387	
S0	$\rightarrow$	Υ	$\downarrow$	0.0468	0.0460	0.0443	0.0463	0.0439	0.0465	0.0459	0.0425	
В	$\rightarrow$	Υ	<b>↑</b>	0.0382	0.0364	0.0339	0.0356	0.0333	0.0351	0.0343	0.0324	
В	$\rightarrow$	Υ	$\downarrow$	0.0503	0.0490	0.0465	0.0488	0.0461	0.0481	0.0474	0.0445	
Α	$\rightarrow$	Υ	$\uparrow$	0.0383	0.0362	0.0340	0.0359	0.0340	0.0380	0.0370	0.0346	
Α	$\rightarrow$	Υ	$\downarrow$	0.0485	0.0472	0.0446	0.0470	0.0447	0.0478	0.0471	0.0436	

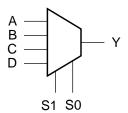
Description	K <sub>load</sub> (ns/pF)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
$SO \rightarrow Y \uparrow$	4.5143	3.3146	2.3778	1.6089	1.1649	0.7955	0.5860	0.3878		
$SO \rightarrow Y \downarrow$	2.6748	1.9349	1.3781	0.9448	0.6646	0.4770	0.3487	0.2281		
$B \to Y \uparrow$	4.5164	3.3162	2.3787	1.6096	1.1653	0.7945	0.5854	0.3875		
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	2.6746	1.9350	1.3780	0.9448	0.6649	0.4764	0.3483	0.2281		
$A  \rightarrow  Y  \uparrow$	4.5109	3.3119	2.3757	1.6086	1.1647	0.7956	0.5861	0.3878		
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	2.6685	1.9306	1.3753	0.9430	0.6641	0.4774	0.3489	0.2282		

## **Cell Description**

The MXT4 cell is a 4-to-1 multiplexer. The state of the select inputs (S1, S0) determines which data input (A, B, C, D) is presented to the output (Y). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (\overline{S0} \bullet \overline{S1} \bullet A) + (S0 \bullet \overline{S1} \bullet B) + (\overline{S0} \bullet S1 \bullet C) + (S0 \bullet S1 \bullet D)$$

## **Logic Symbol**

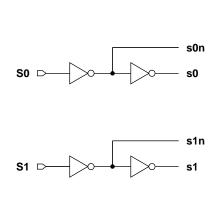


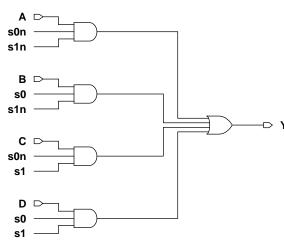
## **Function Table**

S1	S0	Α	В	С	D	Υ
0	0	0	Х	Х	Х	0
0	0	1	Х	Х	Х	1
0	1	Х	0	Х	Х	0
0	1	Х	1	Х	Х	1
1	0	Х	Х	0	Х	0
1	0	Х	Х	1	Х	1
1	1	Х	Х	Х	0	0
1	1	Х	Х	Х	1	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
MXT4X0P5MA10TR	2.00	5.60
MXT4X0P7MA10TR	2.00	5.60
MXT4X1MA10TR	2.00	5.60
MXT4X1P4MA10TR	2.00	5.80
MXT4X2MA10TR	2.00	5.80
MXT4X3MA10TR	2.00	11.00





Pin	Power (uW/MHz)									
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M				
S1	0.0023	0.0026	0.0029	0.0034	0.0038	0.0060				
S0	0.0039	0.0044	0.0048	0.0053	0.0056	0.0117				
D	0.0016	0.0019	0.0023	0.0025	0.0030	0.0055				
С	0.0017	0.0020	0.0023	0.0025	0.0030	0.0061				
В	0.0016	0.0019	0.0022	0.0025	0.0029	0.0055				
Α	0.0017	0.0020	0.0024	0.0027	0.0031	0.0059				

## Pin Capacitance

Pin		Capacitance (pF)									
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M					
S1	0.0020	0.0022	0.0024	0.0028	0.0030	0.0053					
S0	0.0039	0.0044	0.0050	0.0054	0.0056	0.0116					
D	0.0010	0.0012	0.0014	0.0015	0.0017	0.0031					
С	0.0011	0.0013	0.0015	0.0015	0.0018	0.0033					
В	0.0011	0.0013	0.0014	0.0015	0.0017	0.0031					
Α	0.0010	0.0012	0.0014	0.0015	0.0017	0.0033					

# Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n			Intrinsic I	Delay (ns)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M
S1	$\rightarrow$	Υ	$\uparrow$	0.0499	0.0470	0.0472	0.0480	0.0488	0.0443
S1	$\rightarrow$	Υ	$\downarrow$	0.0601	0.0578	0.0582	0.0624	0.0635	0.0546
S0	$\rightarrow$	Υ	$\uparrow$	0.0705	0.0655	0.0633	0.0641	0.0648	0.0619
S0	$\rightarrow$	Υ	$\downarrow$	0.0884	0.0824	0.0799	0.0847	0.0842	0.0766
D	$\rightarrow$	Υ	$\uparrow$	0.0633	0.0586	0.0561	0.0569	0.0576	0.0553
D	$\rightarrow$	Υ	$\downarrow$	0.0816	0.0767	0.0754	0.0798	0.0793	0.0726
С	$\rightarrow$	Υ	$\uparrow$	0.0634	0.0587	0.0579	0.0584	0.0593	0.0566
С	$\rightarrow$	Υ	$\downarrow$	0.0797	0.0744	0.0742	0.0786	0.0779	0.0732
В	$\rightarrow$	Υ	$\uparrow$	0.0655	0.0603	0.0585	0.0596	0.0606	0.0564
В	$\rightarrow$	Υ	$\downarrow$	0.0826	0.0771	0.0758	0.0811	0.0804	0.0719
Α	$\rightarrow$	Υ	$\uparrow$	0.0659	0.0607	0.0588	0.0601	0.0605	0.0573

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	ptio	n	Intrinsic Delay (ns)					
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M
Α	$\rightarrow$	Υ	$\downarrow$	0.0842	0.0780	0.0766	0.0827	0.0810	0.0725

De	escri	ptio	n			K <sub>load</sub> (	ns/pF)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M
S1	$\rightarrow$	Υ	$\uparrow$	4.6043	3.3414	2.4118	1.6695	1.1920	0.7821
S1	$\rightarrow$	Υ	$\downarrow$	2.9317	2.0769	1.4555	1.0437	0.7321	0.4915
S0	$\rightarrow$	Υ	$\uparrow$	4.6092	3.3434	2.4135	1.6699	1.1919	0.7821
S0	$\rightarrow$	Υ	$\downarrow$	2.9699	2.0928	1.4652	1.0523	0.7361	0.4922
D	$\rightarrow$	Υ	$\uparrow$	4.6025	3.3404	2.4099	1.6674	1.1903	0.7817
D	$\rightarrow$	Υ	$\downarrow$	2.9412	2.0812	1.4586	1.0447	0.7330	0.4915
С	$\rightarrow$	Υ	$\uparrow$	4.6046	3.3415	2.4124	1.6695	1.1917	0.7821
С	$\rightarrow$	Υ	$\downarrow$	2.9348	2.0728	1.4568	1.0446	0.7322	0.4922
В	$\rightarrow$	Υ	$\uparrow$	4.6074	3.3431	2.4123	1.6696	1.1921	0.7821
В	$\rightarrow$	Υ	$\downarrow$	2.9599	2.0895	1.4634	1.0499	0.7354	0.4919
Α	$\rightarrow$	Υ	$\uparrow$	4.6024	3.3403	2.4101	1.6678	1.1904	0.7819
Α	$\rightarrow$	Υ	$\downarrow$	2.9703	2.0931	1.4654	1.0523	0.7361	0.4926

## **Cell Description**

The NAND2 cell provides the logical NAND of two inputs (A,B). The output (Y) is represented by the logic equation:

 $Y = \overline{(A \bullet B)}$ 

#### **Function Table**

Α	В	Υ
0	Х	1
Х	0	1
1	1	0

## **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND2X0P5AA10TR	2.00	0.80
NAND2X0P5BA10TR	2.00	0.80
NAND2X0P5MA10TR	2.00	0.80
NAND2X0P7AA10TR	2.00	0.80
NAND2X0P7BA10TR	2.00	0.80
NAND2X0P7MA10TR	2.00	0.80
NAND2X1AA10TR	2.00	0.80
NAND2X1BA10TR	2.00	0.80
NAND2X1MA10TR	2.00	0.80
NAND2X1P4AA10TR	2.00	1.40
NAND2X1P4BA10TR	2.00	1.40
NAND2X1P4MA10TR	2.00	1.40
NAND2X2AA10TR	2.00	1.40
NAND2X2BA10TR	2.00	1.40
NAND2X2MA10TR	2.00	1.40
NAND2X3AA10TR	2.00	2.00
NAND2X3BA10TR	2.00	2.00
NAND2X3MA10TR	2.00	2.00
NAND2X4AA10TR	2.00	2.40
NAND2X4BA10TR	2.00	2.40

# Cell Size (Cont'd.)

Drive Strength	Height (um)	Width (um)
NAND2X4MA10TR	2.00	2.40
NAND2X6AA10TR	2.00	3.40
NAND2X6BA10TR	2.00	3.40
NAND2X6MA10TR	2.00	3.40
NAND2X8AA10TR	2.00	4.60
NAND2X8BA10TR	2.00	4.60
NAND2X8MA10TR	2.00	4.60



#### **AC Power**

Pin		Power (uW/MHz)										
F	X0P5A	X0P5B	X0P5M	X0P7A	X0P7B	X0P7M	X1P0A	X1P0B				
Α	0.0006	0.0006	0.0005	0.0008	0.0008	0.0007	0.0009	0.0011				
В	0.0005	0.0006	0.0004	0.0007	0.0007	0.0006	0.0008	0.0009				

### AC Power (Cont'd.)

Pin		Power (uW/MHz)									
' '''	X1P0M	X1P4A	X1P4B	X1P4M	X2P0A	X2P0B	X2P0M	X3P0A			
Α	0.0008	0.0014	0.0016	0.0013	0.0018	0.0020	0.0017	0.0029			
В	0.0007	0.0014	0.0015	0.0012	0.0018	0.0020	0.0016	0.0026			

### AC Power (Cont'd.)

Pin		Power (uW/MHz)										
F 111	X3P0B											
Α	0.0032	0.0026	0.0037	0.0041	0.0034	0.0057	0.0063	0.0051				
В	0.0029	0.0023	0.0036	0.0040	0.0032	0.0054	0.0060	0.0048				

### AC Power (Cont'd.)

Pin	Power (uW/MHz)							
FIII	X8P0A	X8P0B	X8P0M					
Α	0.0076	0.0084	0.0068					
В	0.0073	0.0080	0.0064					

### Pin Capacitance

Pin		Capacitance (pF)									
' '''	X0P5A	X0P5B	X0P7B	X0P7M	X1P0A	X1P0B					
Α	0.0012	0.0013	0.0012	0.0015	0.0016	0.0015	0.0019	0.0020			
В	0.0011	0.0012	0.0010	0.0014	0.0015	0.0013	0.0017	0.0018			

## Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
' '''	X1P0M	X1P4A	X1P4B	X1P4M	X2P0A	X2P0B	X2P0M	X3P0A				
Α	0.0018	0.0028	0.0029	0.0027	0.0035	0.0037	0.0033	0.0056				
В	0.0016	0.0028	0.0029	0.0026	0.0035	0.0038	0.0033	0.0051				

### Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
FIII												
Α	0.0058	0.0052	0.0071	0.0075	0.0068	0.0108	0.0115	0.0103				
В	0.0054	0.0054										

## Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)							
• •••	X8P0A	X8P0B	X8P0M					
Α	0.0146	0.0154	0.0138					
В	0.0141	0.0149	0.0132					

### Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)								
		X0P5A	X0P5B	X0P5M	X0P7A	X0P7B	X0P7M	X1P0A	X1P0B	
$A \rightarrow Y$	$\uparrow$	0.0115	0.0111	0.0129	0.0111	0.0103	0.0124	0.0101	0.0095	
$A \rightarrow Y$	$\downarrow$	0.0108	0.0119	0.0106	0.0104	0.0108	0.0100	0.0093	0.0097	
$B \to Y$	$\uparrow$	0.0129	0.0122	0.0144	0.0124	0.0114	0.0141	0.0117	0.0108	
$B \to Y$	$\downarrow$	0.0113	0.0123	0.0109	0.0109	0.0113	0.0105	0.0101	0.0105	

D	escr	iptic	n	Intrinsic Delay (ns)										
				X1P0M	X1P4A	X1P4B	X1P4M	X2P0A	X2P0B	X2P0M	X3P0A			
Α	$\rightarrow$	Υ	$\uparrow$	0.0112	0.0100	0.0093	0.0111	0.0092	0.0086	0.0101	0.0093			
Α	$\rightarrow$	Υ	$\downarrow$	0.0088	0.0094	0.0098	0.0090	0.0085	0.0089	0.0081	0.0087			
В	$\rightarrow$	Υ	$\uparrow$	0.0132	0.0120	0.0110	0.0135	0.0113	0.0104	0.0127	0.0112			
В	$\rightarrow$	Υ	$\downarrow$	0.0097	0.0105	0.0110	0.0101	0.0097	0.0103	0.0093	0.0098			

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	iptic	n	Intrinsic Delay (ns)								
				X3P0B	X3P0M	X4P0A	X4P0B	X4P0M	X6P0A	X6P0B	X6P0M	
Α	$\rightarrow$	Υ	<b>↑</b>	0.0088	0.0102	0.0092	0.0086	0.0100	0.0091	0.0086	0.0100	
Α	$\rightarrow$	Υ	$\downarrow$	0.0091	0.0083	0.0084	0.0088	0.0080	0.0083	0.0089	0.0080	
В	$\rightarrow$	Υ	$\uparrow$	0.0103	0.0125	0.0112	0.0103	0.0125	0.0111	0.0102	0.0124	
В	$\rightarrow$	Υ	$\downarrow$	0.0102	0.0094	0.0097	0.0101	0.0093	0.0096	0.0101	0.0092	

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escr	iptic	n	Intri	nsic Delay	(ns)
				X8P0A	X8P0B	X8P0M
Α	$\rightarrow$	Υ	$\uparrow$	0.0091	0.0085	0.0100
Α	$\rightarrow$	Υ	$\downarrow$	0.0084	0.0088	0.0079
В	$\rightarrow$	Υ	$\uparrow$	0.0110	0.0102	0.0123
В	$\rightarrow$	Υ	$\downarrow$	0.0096	0.0100	0.0091

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)								
	X0P5A	X0P5B	X0P5M	X0P7A	X0P7B	X0P7M	X1P0A	X1P0B	
$A \rightarrow Y \uparrow$	5.4422	4.6623	6.4523	3.9669	3.4073	4.7620	2.8594	2.4550	
$A \rightarrow Y \downarrow$	5.1410	5.1488	5.1441	3.6920	3.6922	3.6468	2.5926	2.5930	
$B \to Y \uparrow$	5.4388	4.6363	6.4472	3.9415	3.3822	4.7356	2.8349	2.4310	
$B \to Y \downarrow$	5.1389	5.1464	5.1420	3.6908	3.6912	3.6463	2.5914	2.5920	

Description	K <sub>load</sub> (ns/pF)								
	X1P0M	X1P4A	X1P4B	X1P4M	X2P0A	X2P0B	X2P0M	X3P0A	
$A \rightarrow Y \uparrow$	3.4673	1.9361	1.6579	2.3220	1.3956	1.1779	1.6725	0.9081	
$A \rightarrow Y \downarrow$	2.5923	1.8087	1.8090	1.7864	1.2677	1.2671	1.2615	0.8496	
$B \to Y \uparrow$	3.4424	1.9315	1.6509	2.3206	1.3861	1.1824	1.6812	0.9060	
$B \to Y \downarrow$	2.5911	1.8084	1.8085	1.7860	1.2674	1.2669	1.2614	0.8494	

NAND2

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description		K <sub>load</sub> (ns/pF)								
	X3P0B	X3P0M	X4P0A	X4P0B	X4P0M	X6P0A	X6P0B	X6P0M		
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	0.7769	1.1015	0.6757	0.5791	0.8186	0.4475	0.3838	0.5411		
$A \rightarrow Y \downarrow$	0.8440	0.8476	0.6201	0.6204	0.6294	0.4085	0.4180	0.4085		
$B \to Y \uparrow$	0.7765	1.0988	0.6777	0.5810	0.8208	0.4485	0.3844	0.5425		
$B \to Y \downarrow$	0.8438	0.8474	0.6199	0.6202	0.6291	0.4085	0.4178	0.4084		

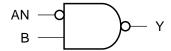
Description			n	K <sub>load</sub> (ns/pF)					
				X8P0A	X8P0B	X8P0M			
Α	$\rightarrow$	Υ	$\rightarrow$	0.3339	0.2860	0.4031			
Α	$\rightarrow$	Υ	$\downarrow$	0.3064	0.3103	0.3057			
В	$\rightarrow$	Υ	$\rightarrow$	0.3341	0.2862	0.4035			
В	$\rightarrow$	Υ	$\downarrow$	0.3065	0.3102	0.3057			

### **Cell Description**

The NAND2B cell provides the logical NAND of one inverted input (AN) and one non-inverted input (B). The output (Y) is represented by the logic equation:

$$Y = \overline{(\overline{AN} \bullet B)}$$

### **Logic Symbol**



#### **Function Table**

AN	В	Υ
1	Х	1
Х	0	1
0	1	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND2BX0P5MA10TR	2.00	1.20
NAND2BX0P7MA10TR	2.00	1.20
NAND2BX1MA10TR	2.00	1.20
NAND2BX1P4MA10TR	2.00	1.60
NAND2BX2MA10TR	2.00	1.60
NAND2BX3MA10TR	2.00	2.20
NAND2BX4MA10TR	2.00	2.60
NAND2BX6MA10TR	2.00	4.00
NAND2BX8MA10TR	2.00	5.00



Process Technology: NAND2B

## **AC Power**

CLN65G+

Pin	Power (uW/MHz)									
-	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
AN	0.0014	0.0015	0.0016	0.0021	0.0026	0.0039	0.0048	0.0072	0.0091	
В	0.0004	0.0005	0.0007	0.0012	0.0016	0.0023	0.0032	0.0049	0.0066	

### Pin Capacitance

Pin	Capacitance (pF)									
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
AN	0.0009	0.0009	0.0008	0.0011	0.0013	0.0017	0.0019	0.0031	0.0036	
В	0.0010	0.0012	0.0016	0.0026	0.0034	0.0048	0.0066	0.0099	0.0133	

### Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$AN \rightarrow Y \uparrow$	0.0280	0.0277	0.0289	0.0291	0.0274	0.0273	0.0272	0.0261	0.0265
$AN \rightarrow Y \downarrow$	0.0342	0.0344	0.0364	0.0366	0.0350	0.0352	0.0371	0.0329	0.0344
$B \to Y \uparrow$	0.0137	0.0129	0.0123	0.0130	0.0122	0.0121	0.0120	0.0119	0.0118
$B \to Y \downarrow$	0.0113	0.0108	0.0108	0.0114	0.0108	0.0109	0.0110	0.0108	0.0109

Description		K <sub>load</sub> (ns/pF)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
$AN \rightarrow Y \uparrow$	6.3300	4.6870	3.4098	2.3055	1.6582	1.0936	0.8154	0.5378	0.4021	
$AN \rightarrow Y \downarrow$	5.0856	3.6891	2.6628	1.7816	1.2585	0.8395	0.6289	0.4080	0.3060	
$B  \rightarrow  Y  \uparrow$	6.2137	4.6096	3.3352	2.2988	1.6588	1.0858	0.8147	0.5367	0.4014	
$B \to Y \downarrow$	5.0763	3.6820	2.6582	1.7781	1.2560	0.8379	0.6275	0.4074	0.3055	

### **Cell Description**

The NAND2XB cell provides the logical NAND of one non-inverted input (A) and one inverted input (BN). The output (Y) is represented by the logic equation:

$$Y = \overline{(A \bullet \overline{BN})}$$

## **Logic Symbol**



#### **Function Table**

Α	BN	Υ
0	Х	1
Х	1	1
1	0	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND2XBX0P5MA10TR	2.00	1.20
NAND2XBX0P7MA10TR	2.00	1.20
NAND2XBX1MA10TR	2.00	1.20
NAND2XBX1P4MA10TR	2.00	1.60
NAND2XBX2MA10TR	2.00	1.60
NAND2XBX3MA10TR	2.00	2.20
NAND2XBX4MA10TR	2.00	2.80
NAND2XBX6MA10TR	2.00	4.00
NAND2XBX8MA10TR	2.00	5.00



NAND2XB

Process Technology: CLN65G+

#### **AC Power**

Pin		Power (uW/MHz)											
-	X0P5M	X0P5M         X0P7M         X1P0M         X1P4M         X2P0M         X3P0M         X4P0M         X6P0M         X8P0M											
Α	0.0006	0.0007	0.0009	0.0013	0.0017	0.0027	0.0035	0.0052	0.0070				
BN	0.0016	0.0017	0.0019	0.0025	0.0032	0.0046	0.0058	0.0085	0.0109				

### Pin Capacitance

Pin		Capacitance (pF)									
F 111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
Α	0.0012	0.0015	0.0017	0.0026	0.0033	0.0052	0.0068	0.0103	0.0139		
BN	0.0010	0.0010	0.0009	0.0011	0.0013	0.0017	0.0019	0.0031	0.0036		

### Delays at 25°C,1.0V, Typical Process

Description	scription Intrinsic Delay (ns)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A  \rightarrow  Y  \uparrow$	0.0128	0.0119	0.0108	0.0110	0.0100	0.0102	0.0098	0.0099	0.0100
$A  \rightarrow  Y  \downarrow$	0.0104	0.0095	0.0085	0.0088	0.0078	0.0081	0.0078	0.0078	0.0078
$BN \to Y \uparrow$	0.0284	0.0287	0.0300	0.0318	0.0305	0.0291	0.0296	0.0284	0.0286
$BN \to Y \downarrow$	0.0322	0.0332	0.0357	0.0375	0.0367	0.0350	0.0361	0.0336	0.0349

Description	on K <sub>load</sub> (ns/pF)								
	X0P5M	X0P5M         X0P7M         X1P0M         X1P4M         X2P0M         X3P0M         X4P0M							X8P0M
$A  \rightarrow  Y  \uparrow$	6.3259	4.6891	3.4070	2.3034	1.6572	1.0931	0.8127	0.5370	0.4019
$A  \rightarrow  Y  \downarrow$	5.0682	3.6736	2.6223	1.7864	1.2449	0.8408	0.6246	0.4067	0.3048
$BN \to Y \uparrow$	6.2102	4.6121	3.3339	2.2981	1.6674	1.0866	0.8110	0.5363	0.4014
$BN \to Y \downarrow$	5.0729	3.6789	2.6282	1.7913	1.2488	0.8432	0.6266	0.4078	0.3059

### **Cell Description**

The NAND3 cell provides the logical NAND of three inputs (A,B,C). The output (Y) is represented by the logic equation:

 $Y = \overline{(A \bullet B \bullet C)}$ 

# Logic Symbol

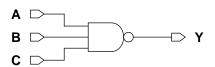


#### **Function Table**

Α	В	С	Υ
0	Х	Х	1
Х	0	Х	1
Х	Х	0	1
1	1	1	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND3X0P5MA10TR	2.00	1.20
NAND3X0P5AA10TR	2.00	1.20
NAND3X0P7MA10TR	2.00	1.20
NAND3X0P7AA10TR	2.00	1.20
NAND3X1MA10TR	2.00	1.20
NAND3X1AA10TR	2.00	1.20
NAND3X1P4MA10TR	2.00	1.80
NAND3X1P4AA10TR	2.00	2.00
NAND3X2MA10TR	2.00	2.00
NAND3X2AA10TR	2.00	2.00
NAND3X3MA10TR	2.00	2.60
NAND3X3AA10TR	2.00	2.60
NAND3X4MA10TR	2.00	3.80
NAND3X4AA10TR	2.00	3.80
NAND3X6MA10TR	2.00	4.80
NAND3X6AA10TR	2.00	5.20



### **AC Power**

Pin	Power (uW/MHz)										
F	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A			
Α	0.0005	0.0005	0.0006	0.0007	0.0007	0.0009	0.0009	0.0014			
В	0.0003	0.0004	0.0004	0.0005	0.0005	0.0007	0.0007	0.0012			
С	0.0003	0.0004	0.0004	0.0006	0.0006	0.0007	0.0008	0.0013			

### AC Power (Cont'd.)

Pin		Power (uW/MHz)										
FIII	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A				
Α	0.0013	0.0017	0.0021	0.0027	0.0029	0.0036	0.0041	0.0054				
В	0.0011	0.0015	0.0016	0.0022	0.0022	0.0030	0.0032	0.0045				
С	0.0012	0.0015	0.0017	0.0023	0.0022	0.0030	0.0032	0.0045				

## Pin Capacitance

Pin		Capacitance (pF)											
- 1111	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A					
Α	0.0011	0.0012	0.0013	0.0015	0.0017	0.0018	0.0023	0.0028					
В	0.0010	0.0010	0.0012	0.0013	0.0015	0.0017	0.0022	0.0028					
С	0.0009	0.0010	0.0012	0.0014	0.0015	0.0017	0.0024	0.0029					

## Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
FIII	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A				
Α	0.0030	0.0034	0.0046	0.0052	0.0061	0.0069	0.0087	0.0103				
В	0.0030	0.0034	0.0045	0.0051	0.0059	0.0067	0.0083	0.0100				
С	0.0032	0.0035	0.0045	0.0050	0.0060	0.0068	0.0083	0.0099				

### Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)								
	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A	
$A \rightarrow Y \uparrow$	0.0167	0.0134	0.0158	0.0133	0.0148	0.0120	0.0140	0.0117	
$A \ \rightarrow \ Y \ \downarrow$	0.0147	0.0155	0.0129	0.0151	0.0118	0.0132	0.0107	0.0135	
$B \ \to \ Y \ \uparrow$	0.0189	0.0152	0.0183	0.0150	0.0178	0.0139	0.0176	0.0142	
$B \to Y \downarrow$	0.0167	0.0178	0.0150	0.0172	0.0143	0.0156	0.0135	0.0164	
$C \rightarrow Y \uparrow$	0.0220	0.0173	0.0217	0.0171	0.0210	0.0160	0.0219	0.0166	
$C \rightarrow Y \downarrow$	0.0178	0.0189	0.0162	0.0184	0.0154	0.0168	0.0151	0.0178	

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description		Intrinsic Delay (ns)								
	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A		
$A \ \rightarrow \ Y \ \uparrow$	0.0130	0.0107	0.0134	0.0110	0.0131	0.0107	0.0126	0.0106		
$A \rightarrow Y \downarrow$	0.0105	0.0118	0.0099	0.0112	0.0097	0.0109	0.0092	0.0108		
$B \to Y \uparrow$	0.0165	0.0130	0.0179	0.0139	0.0178	0.0138	0.0171	0.0136		
$B \to Y \downarrow$	0.0134	0.0147	0.0136	0.0149	0.0137	0.0150	0.0127	0.0149		
$C \rightarrow Y \uparrow$	0.0202	0.0155	0.0223	0.0167	0.0223	0.0167	0.0212	0.0163		
$C \rightarrow Y \downarrow$	0.0149	0.0162	0.0155	0.0168	0.0157	0.0170	0.0145	0.0167		

Description		K <sub>load</sub> (ns/pF)									
	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A			
$A \rightarrow Y \uparrow$	7.9308	5.7165	6.1062	4.2068	4.4168	3.0395	3.2014	2.0222			
$A \rightarrow Y \downarrow$	7.4579	7.3300	5.2805	5.2816	3.7410	3.7417	2.6435	2.6418			
$B \rightarrow Y \uparrow$	7.7737	5.6311	5.9834	4.1438	4.3507	2.9779	3.2128	2.0390			
$B \to Y \downarrow$	7.4557	7.3280	5.2794	5.2804	3.7411	3.7417	2.6432	2.6412			
$C \rightarrow Y \uparrow$	7.9140	5.7237	6.0931	4.1777	4.3863	3.0137	3.2628	2.0673			
$C \rightarrow Y \downarrow$	7.4570	7.3288	5.2797	5.2806	3.7411	3.7408	2.6439	2.6416			

Process Technology: NAND3
CLN65G+

Description	K <sub>load</sub> (ns.							
	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	2.1357	1.4709	1.4576	0.9893	1.0841	0.7371	0.7314	0.4859
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	1.8748	1.8753	1.1467	1.1470	0.8648	0.8650	0.5724	0.5793
$B \to Y \uparrow$	2.1533	1.4788	1.4215	0.9679	1.0599	0.7223	0.7221	0.4773
$B \to Y \downarrow$	1.8746	1.8751	1.1466	1.1470	0.8647	0.8649	0.5723	0.5793
$C \rightarrow Y \uparrow$	2.1770	1.5011	1.4555	0.9904	1.0756	0.7328	0.7304	0.4871
$C \rightarrow Y \downarrow$	1.8751	1.8754	1.1466	1.1470	0.8648	0.8651	0.5725	0.5794

### **Cell Description**

The NAND3B cell provides the logical NAND of one inverted input (AN) and two non-inverted inputs (B,C). The output (Y) is represented by the logic equation:

$$Y = \overline{(\overline{AN} \bullet B \bullet C)}$$

### **Logic Symbol**

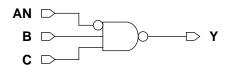


### **Function Table**

AN	В	С	Υ
1	Х	Х	1
Х	0	Х	1
Х	Х	0	1
0	1	1	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND3BX0P5MA10TR	2.00	1.40
NAND3BX0P7MA10TR	2.00	1.40
NAND3BX1MA10TR	2.00	1.40
NAND3BX1P4MA10TR	2.00	2.20
NAND3BX2MA10TR	2.00	2.20
NAND3BX3MA10TR	2.00	3.00
NAND3BX4MA10TR	2.00	4.20
NAND3BX6MA10TR	2.00	5.00



#### **AC Power**

Pin		Power (uW/MHz)										
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
AN	0.0015	0.0016	0.0017	0.0023	0.0027	0.0040	0.0055	0.0074				
В	0.0004	0.0004	0.0006	0.0009	0.0012	0.0017	0.0023	0.0033				
С	0.0004	0.0004	0.0006	0.0009	0.0012	0.0017	0.0023	0.0033				

### Pin Capacitance

Pin		Capacitance (pF)											
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M					
AN	0.0009	0.0010	0.0009	0.0010	0.0012	0.0015	0.0018	0.0029					
В	0.0010	0.0012	0.0015	0.0024	0.0031	0.0045	0.0060	0.0084					
С	0.0010	0.0012	0.0015	0.0025	0.0032	0.0045	0.0060	0.0083					

### Delays at 25°C,1.0V, Typical Process

Description				Intrinsic Delay (ns)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
AN	$\rightarrow$	Υ	$\uparrow$	0.0313	0.0305	0.0317	0.0327	0.0311	0.0312	0.0320	0.0289		
AN	$\rightarrow$	Υ	$\downarrow$	0.0367	0.0358	0.0370	0.0398	0.0376	0.0371	0.0380	0.0339		
В	$\rightarrow$	Υ	$\uparrow$	0.0189	0.0178	0.0175	0.0167	0.0161	0.0174	0.0175	0.0167		
В	$\rightarrow$	Υ	$\downarrow$	0.0173	0.0156	0.0157	0.0151	0.0147	0.0160	0.0162	0.0151		
С	$\rightarrow$	Υ	$\uparrow$	0.0215	0.0210	0.0208	0.0203	0.0198	0.0217	0.0220	0.0210		
С	$\rightarrow$	Υ	$\downarrow$	0.0188	0.0172	0.0175	0.0168	0.0164	0.0182	0.0187	0.0172		

Descrip	tion	K <sub>load</sub> (ns/pF)								
		X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	
$AN \rightarrow$	Y ↑	7.9799	6.1306	4.4556	2.9365	2.1305	1.4557	1.0847	0.7317	
$AN \rightarrow$	Y ↓	7.4282	5.3489	3.8740	2.6335	1.8643	1.1573	0.8663	0.5788	
$B  \rightarrow $	Y ↑	7.8301	6.0173	4.3738	2.9538	2.1443	1.4175	1.0592	0.7220	
$B  \rightarrow $	Y ↓	7.4246	5.3468	3.8736	2.6321	1.8636	1.1569	0.8660	0.5787	
$C \rightarrow$	Y ↑	7.6993	6.0172	4.3593	2.9727	2.1607	1.4215	1.0650	0.7257	
$C \rightarrow$	Y ↓	7.4249	5.3481	3.8732	2.6323	1.8638	1.1571	0.8661	0.5788	

### **Cell Description**

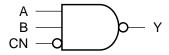
The NAND3XXB cell provides the logical NAND of two non-inverted inputs (A, B) and one inverted input (CN). The output (Y) is represented by the logic equation:

$$Y = \overline{(A \bullet B \bullet \overline{CN})}$$

### **Function Table**

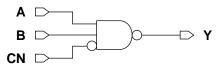
Α	В	CN	Υ
Х	Х	1	1
Х	0	Х	1
0	Х	Х	1
1	1	0	0

### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND3XXBX0P5MA10TR	2.00	1.40
NAND3XXBX0P7MA10TR	2.00	1.40
NAND3XXBX1MA10TR	2.00	1.40
NAND3XXBX1P4MA10TR	2.00	2.20
NAND3XXBX2MA10TR	2.00	2.20
NAND3XXBX3MA10TR	2.00	3.00
NAND3XXBX4MA10TR	2.00	4.20
NAND3XXBX6MA10TR	2.00	5.00



#### **AC Power**

Pin		Power (uW/MHz)										
F III	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
Α	0.0005	0.0006	0.0008	0.0011	0.0014	0.0022	0.0030	0.0042				
В	0.0004	0.0004	0.0006	0.0008	0.0012	0.0017	0.0023	0.0033				
CN	0.0015	0.0017	0.0018	0.0026	0.0030	0.0042	0.0053	0.0076				

### Pin Capacitance

Pin		Capacitance (pF)											
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M					
Α	0.0011	0.0013	0.0016	0.0024	0.0031	0.0046	0.0061	0.0087					
В	0.0010	0.0012	0.0015	0.0024	0.0030	0.0045	0.0059	0.0083					
CN	0.0010	0.0010	0.0009	0.0011	0.0012	0.0016	0.0019	0.0030					

### Delays at 25°C,1.0V, Typical Process

De	Description			Intrinsic Delay (ns)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
Α	$\rightarrow$	Υ	$\uparrow$	0.0170	0.0155	0.0149	0.0134	0.0129	0.0134	0.0131	0.0126		
Α	$\rightarrow$	Υ	$\downarrow$	0.0149	0.0127	0.0119	0.0111	0.0105	0.0100	0.0097	0.0092		
В	$\rightarrow$	Υ	$\uparrow$	0.0189	0.0181	0.0177	0.0168	0.0165	0.0178	0.0178	0.0170		
В	$\rightarrow$	Υ	$\downarrow$	0.0165	0.0147	0.0140	0.0137	0.0133	0.0136	0.0136	0.0128		
CN	$\rightarrow$	Υ	$\uparrow$	0.0344	0.0354	0.0377	0.0406	0.0386	0.0386	0.0395	0.0364		
CN	$\rightarrow$	Υ	$\downarrow$	0.0366	0.0369	0.0388	0.0437	0.0413	0.0415	0.0424	0.0381		

De	Description			K <sub>load</sub> (ns/pF)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
Α	$\rightarrow$	Υ	1	8.0380	6.1476	4.4546	2.9368	2.1282	1.4548	1.0859	0.7312		
Α	$\rightarrow$	Υ	$\downarrow$	7.4057	5.3338	3.7409	2.6299	1.8680	1.1556	0.8652	0.5769		
В	$\rightarrow$	Υ	$\uparrow$	7.7941	5.9945	4.3722	2.9539	2.1420	1.4166	1.0586	0.7215		
В	$\rightarrow$	Υ	$\downarrow$	7.4037	5.3321	3.7410	2.6293	1.8678	1.1556	0.8652	0.5769		
CN	$\rightarrow$	Υ	$\uparrow$	7.6824	6.0202	4.4223	2.9751	2.1598	1.4218	1.0647	0.7258		
CN	$\rightarrow$	Υ	$\downarrow$	7.4054	5.3341	3.7422	2.6329	1.8704	1.1569	0.8660	0.5774		

### **Cell Description**

The NAND4 cell provides a logical NAND of four inputs (A,B,C,D). The output (Y) is represented by the logic equation:

 $Y = \overline{(A \bullet B \bullet C \bullet D)}$ 

## **Logic Symbol**

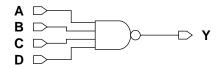


#### **Function Table**

Α	В	С	D	Υ
0	Х	Х	Х	1
Х	0	Х	Х	1
Х	Х	0	Х	1
Х	Х	Х	0	1
1	1	1	1	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND4X0P5MA10TR	2.00	1.40
NAND4X0P5AA10TR	2.00	1.40
NAND4X0P7MA10TR	2.00	1.40
NAND4X0P7AA10TR	2.00	1.40
NAND4X1MA10TR	2.00	1.40
NAND4X1AA10TR	2.00	1.40
NAND4X1P4MA10TR	2.00	2.40
NAND4X1P4AA10TR	2.00	2.40
NAND4X2MA10TR	2.00	2.40
NAND4X2AA10TR	2.00	2.40
NAND4X3MA10TR	2.00	3.40
NAND4X3AA10TR	2.00	3.40
NAND4X4MA10TR	2.00	4.40
NAND4X4AA10TR	2.00	5.00



### **AC Power**

Pin		Power (uW/MHz)												
FIII	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A						
Α	0.0005	0.0005	0.0005	0.0007	0.0007	0.0009	0.0009	0.0012						
В	0.0003	0.0004	0.0003	0.0005	0.0004	0.0006	0.0007	0.0009						
С	0.0003	0.0004	0.0003	0.0005	0.0004	0.0007	0.0007	0.0010						
D	0.0003	0.0004	0.0003	0.0005	0.0004	0.0007	0.0009	0.0011						

## AC Power (Cont'd.)

Pin		Power (uW/MHz)											
F 111	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A							
Α	0.0011	0.0015	0.0019	0.0025	0.0025	0.0033							
В	0.0008	0.0012	0.0013	0.0020	0.0017	0.0026							
С	0.0009	0.0013	0.0013	0.0020	0.0017	0.0026							
D	0.0010	0.0015	0.0013	0.0020	0.0017	0.0026							

## Pin Capacitance

Pin		Capacitance (pF)											
FIII	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A					
Α	0.0011	0.0012	0.0013	0.0015	0.0016	0.0018	0.0023	0.0026					
В	0.0010	0.0010	0.0011	0.0013	0.0014	0.0016	0.0022	0.0025					
С	0.0010	0.0011	0.0012	0.0013	0.0014	0.0017	0.0025	0.0027					
D	0.0010	0.0010	0.0011	0.0013	0.0014	0.0016	0.0027	0.0029					

## Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)										
FIII	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A						
Α	0.0028	0.0032	0.0042	0.0050	0.0056	0.0066						
В	0.0028	0.0031	0.0041	0.0049	0.0051	0.0064						
С	0.0030	0.0033	0.0041	0.0049	0.0051	0.0064						
D	0.0031	0.0036	0.0041	0.0049	0.0051	0.0064						

### Delays at 25°C,1.0V, Typical Process

D	escr	iptio	n				Intrinsic I	Delay (ns)			
				X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A
Α	$\rightarrow$	Υ	$\uparrow$	0.0208	0.0161	0.0193	0.0153	0.0174	0.0137	0.0167	0.0130
Α	$\rightarrow$	Υ	$\downarrow$	0.0183	0.0213	0.0159	0.0193	0.0134	0.0166	0.0131	0.0152
В	$\rightarrow$	Υ	$\uparrow$	0.0235	0.0177	0.0223	0.0171	0.0209	0.0157	0.0207	0.0155
В	$\rightarrow$	Υ	$\downarrow$	0.0211	0.0240	0.0188	0.0223	0.0166	0.0198	0.0167	0.0188
С	$\rightarrow$	Υ	$\uparrow$	0.0281	0.0206	0.0271	0.0201	0.0259	0.0187	0.0257	0.0186
С	$\rightarrow$	Υ	$\downarrow$	0.0245	0.0274	0.0221	0.0256	0.0199	0.0232	0.0200	0.0221
D	$\rightarrow$	Υ	$\uparrow$	0.0315	0.0226	0.0309	0.0222	0.0297	0.0208	0.0308	0.0217
D	$\rightarrow$	Υ	$\downarrow$	0.0254	0.0283	0.0233	0.0267	0.0211	0.0243	0.0223	0.0245

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Descri	ption			Intrinsic I	Delay (ns)		
		X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A
$A  \rightarrow $	Y ↑	0.0151	0.0117	0.0156	0.0127	0.0165	0.0126
$A  \rightarrow $	Y ↓	0.0111	0.0133	0.0107	0.0138	0.0110	0.0136
$B \ \rightarrow$	Y ↑	0.0194	0.0143	0.0214	0.0160	0.0228	0.0162
$B \ \rightarrow$	Y ↓	0.0148	0.0170	0.0162	0.0194	0.0164	0.0196
$C \rightarrow$	Y ↑	0.0245	0.0173	0.0266	0.0190	0.0283	0.0195
$C \rightarrow$	Y ↓	0.0179	0.0201	0.0197	0.0228	0.0199	0.0235
$D \rightarrow$	Y ↑	0.0294	0.0201	0.0318	0.0220	0.0339	0.0224
$D  \rightarrow $	Y ↓	0.0200	0.0223	0.0215	0.0246	0.0219	0.0254

D	escri	iptio	n	K <sub>load</sub> (ns/pF)										
				X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A			
Α	$\rightarrow$	Υ	$\uparrow$	9.0125	6.2432	7.2388	4.6253	5.4297	3.3376	3.5183	2.2818			
Α	$\rightarrow$	Υ	$\downarrow$	9.0459	9.6357	6.8377	6.8404	4.8467	4.8467	3.2031	3.2033			
В	$\rightarrow$	Υ	$\uparrow$	8.9233	6.1746	7.1614	4.5706	5.3669	3.2969	3.5127	2.2710			
В	$\rightarrow$	Υ	$\downarrow$	9.0433	9.6321	6.8378	6.8385	4.8452	4.8456	3.2019	3.2023			
С	$\rightarrow$	Υ	$\uparrow$	8.9917	6.2219	7.2147	4.6048	5.4054	3.3217	3.5622	2.3037			
С	$\rightarrow$	Υ	$\downarrow$	9.0444	9.6330	6.8381	6.8390	4.8463	4.8465	3.2035	3.2031			
D	$\rightarrow$	Υ	$\uparrow$	9.1118	6.3160	7.3173	4.6500	5.4807	3.3725	3.6244	2.3481			
D	$\rightarrow$	Υ	$\downarrow$	9.0464	9.6327	6.8369	6.8388	4.8462	4.8462	3.2034	3.2034			

Process Technology: NAND4
CLN65G+

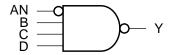
Description			K <sub>load</sub> (	ns/pF)		
	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A
$A \ \rightarrow \ Y \ \uparrow$	2.6379	1.6410	1.7852	1.0981	1.3774	0.8301
$A \ \rightarrow \ Y \ \downarrow$	2.2713	2.2717	1.4954	1.4958	1.1245	1.1340
$B \ \to \ Y \ \uparrow$	2.6287	1.6277	1.7474	1.0710	1.3895	0.8118
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	2.2706	2.2709	1.4952	1.4953	1.1245	1.1340
$C \rightarrow Y \uparrow$	2.6654	1.6510	1.7498	1.0732	1.3910	0.8137
$C \rightarrow Y \downarrow$	2.2706	2.2709	1.4953	1.4957	1.1247	1.1344
$D \rightarrow Y \uparrow$	2.7145	1.6787	1.7918	1.1040	1.4150	0.8342
$D \rightarrow Y \downarrow$	2.2712	2.2716	1.4954	1.4960	1.1249	1.1340

### **Cell Description**

The NAND4B cell provides a logical NAND of one inverted input (AN) and three non-inverted inputs (B,C,D). The output (Y) is represented by the logic equation:

$$Y = (\overline{AN} \bullet B \bullet C \bullet D)$$

### **Logic Symbol**

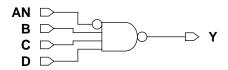


#### **Function Table**

AN	В	С	D	Υ
1	Х	Х	Х	1
Х	0	Х	Х	1
Х	Х	0	Х	1
х	Х	Х	0	1
0	1	1	1	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND4BX0P5MA10TR	2.00	1.60
NAND4BX0P7MA10TR	2.00	1.60
NAND4BX1MA10TR	2.00	1.60
NAND4BX1P4MA10TR	2.00	2.60
NAND4BX2MA10TR	2.00	2.60
NAND4BX3MA10TR	2.00	3.80
NAND4BX4MA10TR	2.00	4.80



### **AC Power**

Pin	Power (uW/MHz)									
F III	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
AN	0.0015	0.0016	0.0016	0.0022	0.0027	0.0039	0.0051			
В	0.0003	0.0004	0.0005	0.0006	0.0009	0.0014	0.0018			
С	0.0003	0.0004	0.0005	0.0006	0.0009	0.0014	0.0018			
D	0.0003	0.0003	0.0004	0.0007	0.0011	0.0013	0.0017			

### Pin Capacitance

Pin	Capacitance (pF)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
AN	0.0010	0.0010	0.0009	0.0011	0.0012	0.0015	0.0018			
В	0.0010	0.0012	0.0014	0.0020	0.0027	0.0041	0.0051			
С	0.0010	0.0011	0.0014	0.0022	0.0030	0.0041	0.0051			
D	0.0010	0.0011	0.0014	0.0023	0.0032	0.0041	0.0051			

## Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n	Intrinsic Delay (ns)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
AN	$\rightarrow$	Υ	$\uparrow$	0.0345	0.0343	0.0335	0.0328	0.0323	0.0328	0.0343		
AN	$\rightarrow$	Υ	$\downarrow$	0.0406	0.0394	0.0375	0.0368	0.0373	0.0363	0.0363		
В	$\rightarrow$	Υ	$\uparrow$	0.0228	0.0216	0.0204	0.0198	0.0192	0.0210	0.0221		
В	$\rightarrow$	Υ	$\downarrow$	0.0219	0.0199	0.0184	0.0155	0.0161	0.0181	0.0185		
С	$\rightarrow$	Υ	$\uparrow$	0.0270	0.0260	0.0249	0.0257	0.0245	0.0265	0.0278		
С	$\rightarrow$	Υ	$\downarrow$	0.0253	0.0235	0.0218	0.0194	0.0198	0.0219	0.0222		
D	$\rightarrow$	Υ	$\uparrow$	0.0296	0.0296	0.0297	0.0306	0.0293	0.0313	0.0333		
D	$\rightarrow$	Υ	$\downarrow$	0.0262	0.0245	0.0230	0.0211	0.0218	0.0238	0.0244		

Process Technology:

CLN65G+

NAND4B

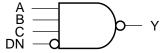
Description				K <sub>load</sub> (ns/pF)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
AN	$\rightarrow$	Υ	$\uparrow$	9.0757	7.2671	5.4285	3.8423	2.6329	1.7875	1.3800		
AN	$\rightarrow$	Υ	$\downarrow$	9.3605	7.1764	5.1383	3.1954	2.2771	1.4922	1.1286		
В	$\rightarrow$	Υ	$\uparrow$	8.9340	7.1820	5.3638	3.8665	2.6212	1.7485	1.3734		
В	$\rightarrow$	Υ	$\downarrow$	9.3581	7.1754	5.1381	3.1958	2.2765	1.4922	1.1287		
С	$\rightarrow$	Υ	1	8.9339	7.1439	5.3382	3.9149	2.6494	1.7460	1.3726		
С	$\rightarrow$	Υ	$\downarrow$	9.3576	7.1749	5.1387	3.1954	2.2772	1.4921	1.1287		
D	$\rightarrow$	Υ	1	8.8069	7.2163	5.5750	3.9715	2.6771	1.7524	1.3868		
D	$\rightarrow$	Υ	$\downarrow$	9.3585	7.1745	5.1376	3.1952	2.2772	1.4920	1.1290		

### **Cell Description**

The NAND4XXXB cell provides a logical NAND of three non-inverted inputs (A, B, C) and one inverted input (DN). The output (Y) is represented by the logic equation:

$$Y = \overline{(A \bullet B \bullet C \bullet \overline{DN})}$$

### **Logic Symbol**

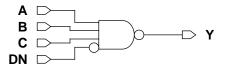


#### **Function Table**

Α	В	С	DN	Υ
Х	Х	Х	1	1
Х	Х	0	Х	1
Х	0	Х	Х	1
0	Х	Х	Х	1
1	1	1	0	0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NAND4XXXBX0P5MA10TR	2.00	1.60
NAND4XXXBX0P7MA10TR	2.00	1.60
NAND4XXXBX1MA10TR	2.00	1.60
NAND4XXXBX1P4MA10TR	2.00	2.60
NAND4XXXBX2MA10TR	2.00	2.60
NAND4XXXBX3MA10TR	2.00	3.80
NAND4XXXBX4MA10TR	2.00	4.80



### **AC Power**

Pin	Power (uW/MHz)									
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
Α	0.0005	0.0006	0.0007	0.0008	0.0012	0.0019	0.0025			
В	0.0003	0.0004	0.0005	0.0006	0.0009	0.0013	0.0018			
С	0.0003	0.0004	0.0004	0.0006	0.0009	0.0013	0.0017			
DN	0.0016	0.0018	0.0019	0.0026	0.0030	0.0043	0.0050			

### Pin Capacitance

Pin	Capacitance (pF)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
Α	0.0012	0.0013	0.0016	0.0021	0.0028	0.0042	0.0056			
В	0.0010	0.0011	0.0014	0.0020	0.0028	0.0041	0.0051			
С	0.0010	0.0011	0.0014	0.0022	0.0030	0.0041	0.0051			
DN	0.0010	0.0010	0.0010	0.0011	0.0012	0.0016	0.0018			

### Delays at 25°C,1.0V, Typical Process

De	escri	ptio	า	Intrinsic Delay (ns)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
Α	$\rightarrow$	Υ	$\uparrow$	0.0206	0.0185	0.0175	0.0157	0.0152	0.0153	0.0165		
Α	$\rightarrow$	Υ	$\downarrow$	0.0187	0.0157	0.0137	0.0110	0.0112	0.0103	0.0110		
В	$\rightarrow$	Υ	$\uparrow$	0.0231	0.0217	0.0212	0.0200	0.0195	0.0209	0.0225		
В	$\rightarrow$	Υ	$\downarrow$	0.0214	0.0191	0.0174	0.0144	0.0149	0.0158	0.0164		
С	$\rightarrow$	Υ	<b>↑</b>	0.0270	0.0259	0.0255	0.0259	0.0245	0.0261	0.0279		
С	$\rightarrow$	Υ	$\downarrow$	0.0243	0.0219	0.0202	0.0178	0.0179	0.0192	0.0198		
DN	$\rightarrow$	Υ	<b>↑</b>	0.0431	0.0436	0.0458	0.0487	0.0468	0.0462	0.0486		
DN	$\rightarrow$	Υ	$\downarrow$	0.0450	0.0439	0.0435	0.0460	0.0465	0.0451	0.0446		

Process Technology:

CLN65G+

NAND4XXXB

De	escri	ptio	n	K <sub>load</sub> (ns/pF)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
Α	$\rightarrow$	Υ	$\uparrow$	9.1022	7.2758	5.5121	3.8417	2.6321	1.7858	1.3821		
Α	$\rightarrow$	Υ	$\downarrow$	9.3965	7.1550	5.1000	3.1669	2.2665	1.4911	1.1256		
В	$\rightarrow$	Υ	$\uparrow$	8.9673	7.1552	5.4522	3.8661	2.6203	1.7411	1.3729		
В	$\rightarrow$	Υ	$\downarrow$	9.3942	7.1541	5.0995	3.1671	2.2666	1.4911	1.1256		
С	$\rightarrow$	Υ	$\uparrow$	8.9084	7.1564	5.4195	3.9180	2.6492	1.7393	1.3724		
С	$\rightarrow$	Υ	$\downarrow$	9.3948	7.1566	5.1002	3.1668	2.2664	1.4910	1.1257		
DN	$\rightarrow$	Υ	$\uparrow$	8.8281	7.1932	5.6908	3.9834	2.6773	1.7511	1.3863		
DN	$\rightarrow$	Υ	$\downarrow$	9.3963	7.1565	5.1012	3.1690	2.2684	1.4915	1.1264		

## Process Technology:

### CLN65G+

#### **Cell Description**

The NOR2 cell provides a logical NOR of two inputs (A,B). The output (Y) is represented by the logic equation:

$$\mathsf{Y}=\overline{(A+B)}$$

#### **Function Table**

Α	В	Υ		
0	0	1		
Х	1	0		
1	Х	0		

### **Logic Symbol**



### **Cell Size**

Drive Strength	Height (um)	Width (um)
NOR2X0P5MA10TR	2.00	0.80
NOR2X0P5AA10TR	2.00	0.80
NOR2X0P7MA10TR	2.00	0.80
NOR2X0P7AA10TR	2.00	0.80
NOR2X1MA10TR	2.00	0.80
NOR2X1AA10TR	2.00	0.80
NOR2X1P4MA10TR	2.00	1.40
NOR2X1P4AA10TR	2.00	1.40
NOR2X2MA10TR	2.00	1.40
NOR2X2AA10TR	2.00	1.40
NOR2X3MA10TR	2.00	2.00
NOR2X3AA10TR	2.00	2.00
NOR2X4MA10TR	2.00	2.40
NOR2X4AA10TR	2.00	2.40
NOR2X6MA10TR	2.00	3.40
NOR2X6AA10TR	2.00	3.40
NOR2X8MA10TR	2.00	4.60
NOR2X8AA10TR	2.00	4.60



### **AC Power**

Pin		Power (uW/MHz)											
' '''	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A					
Α	0.0002	0.0002	0.0002	0.0002	0.0003	0.0003	0.0005	0.0005					
В	0.0005	0.0005	0.0006	0.0006	0.0008	0.0008	0.0012	0.0012					

### AC Power (Cont'd.)

Pin		Power (uW/MHz)											
FIII	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A					
Α	0.0007	0.0007	0.0010	0.0010	0.0014	0.0014	0.0021	0.0021					
В	0.0016	0.0016	0.0025	0.0025	0.0033	0.0032	0.0049	0.0049					

## AC Power (Cont'd.)

Pin	Power (uW/MHz)						
	X8P0M	X8P0A					
Α	0.0028	0.0028					
В	0.0065	0.0065					

### Pin Capacitance

Pin		Capacitance (pF)											
F	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A					
Α	0.0012	0.0013	0.0014	0.0015	0.0016	0.0019	0.0025	0.0028					
В	0.0010	0.0011	0.0012	0.0014	0.0014	0.0017	0.0024	0.0028					

### Pin Capacitance (Cont'd.)

Pin		Capacitance (pF)											
F	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A					
Α	0.0030	0.0035	0.0047	0.0055	0.0062	0.0071	0.0094	0.0108					
В	0.0031	0.0036	0.0044	0.0051	0.0060	0.0070	0.0090	0.0105					

## Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)						
' '''	X8P0M	X8P0A					
Α	0.0126	0.0145					
В	0.0119	0.0139					

## Delays at 25°C,1.0V, Typical Process

D	escri	ptic	n		Intrinsic Delay (ns)									
				X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A			
Α	$\rightarrow$	Υ	$\uparrow$	0.0170	0.0182	0.0151	0.0175	0.0134	0.0156	0.0131	0.0154			
Α	$\rightarrow$	Υ	$\downarrow$	0.0104	0.0082	0.0096	0.0077	0.0088	0.0071	0.0089	0.0072			
В	$\rightarrow$	Υ	$\uparrow$	0.0178	0.0192	0.0164	0.0188	0.0151	0.0174	0.0152	0.0175			
В	$\rightarrow$	Υ	$\downarrow$	0.0113	0.0087	0.0107	0.0082	0.0102	0.0078	0.0103	0.0080			

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escr	ptio	n	Intrinsic Delay (ns)									
				X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A		
Α	$\rightarrow$	Υ	$\uparrow$	0.0115	0.0137	0.0119	0.0139	0.0114	0.0134	0.0114	0.0134		
Α	$\rightarrow$	Υ	$\downarrow$	0.0081	0.0066	0.0083	0.0068	0.0082	0.0068	0.0082	0.0067		
В	$\rightarrow$	Υ	$\uparrow$	0.0141	0.0164	0.0138	0.0159	0.0138	0.0159	0.0136	0.0157		
В	$\rightarrow$	Υ	$\downarrow$	0.0098	0.0076	0.0099	0.0076	0.0099	0.0076	0.0099	0.0076		

### Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	iptic	n	Intrinsic Delay (ns)			
				X8P0M	X8P0A		
Α	$\rightarrow$	Υ	$\uparrow$	0.0113	0.0133		
Α	$\rightarrow$	Υ	$\downarrow$	0.0082	0.0067		
В	$\rightarrow$	Υ	$\uparrow$	0.0135	0.0156		
В	$\rightarrow$	Υ	$\downarrow$	0.0098	0.0076		

Description	1	K <sub>load</sub> (ns/pF)									
		X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A		
$A \rightarrow Y$	$\uparrow$	9.5176	9.5228	7.3027	7.3075	5.2675	5.2704	3.5163	3.5183		
$A \rightarrow Y$	$\downarrow$	4.5836	2.9842	3.5694	2.1726	2.6058	1.5237	1.8248	1.1151		
$B \rightarrow Y$	$\uparrow$	9.5107	9.5136	7.2986	7.3018	5.2652	5.2675	3.5150	3.5166		
$B \rightarrow Y$	$\downarrow$	4.5861	2.9874	3.5713	2.1528	2.6071	1.5254	1.7646	1.0695		

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description			n	K <sub>load</sub> (ns/pF)									
				X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A	X6P0M	X6P0A		
Α	$\rightarrow$	Υ	$\uparrow$	2.5203	2.5216	1.6617	1.6634	1.2215	1.2220	0.8097	0.8102		
Α	$\rightarrow$	Υ	$\downarrow$	1.3328	0.7755	0.8705	0.5190	0.6579	0.3943	0.4365	0.2614		
В	$\rightarrow$	Υ	$\uparrow$	2.5197	2.5206	1.6611	1.6626	1.2212	1.2217	0.8095	0.8099		
В	$\rightarrow$	Υ	$\downarrow$	1.2874	0.7515	0.8695	0.5166	0.6467	0.3847	0.4318	0.2574		

D	escr	iptic	n	K <sub>load</sub> (ns/pF)			
				X8P0M	X8P0A		
Α	$\rightarrow$	Υ	$\uparrow$	0.6034	0.6037		
Α	$\rightarrow$	Υ	$\downarrow$	0.3264	0.1959		
В	$\rightarrow$	Υ	$\uparrow$	0.6032	0.6035		
В	$\rightarrow$	Υ	$\downarrow$	0.3238	0.1936		

#### **Cell Description**

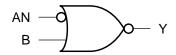
The NOR2B cell provides a logical NOR of one inverted input (AN) and one non-inverted input (B). The output (Y) is represented by the logic equation:

$$Y = \overline{(\overline{AN} + B)}$$

### **Function Table**

AN	В	Υ
1	0	1
х	1	0
0	Х	0

### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NOR2BX0P5MA10TR	2.00	1.20
NOR2BX0P7MA10TR	2.00	1.20
NOR2BX1MA10TR	2.00	1.20
NOR2BX1P4MA10TR	2.00	1.60
NOR2BX2MA10TR	2.00	1.60
NOR2BX3MA10TR	2.00	2.20
NOR2BX4MA10TR	2.00	2.60
NOR2BX6MA10TR	2.00	4.00
NOR2BX8MA10TR	2.00	5.00



#### **AC Power**

Pin		Power (uW/MHz)											
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
AN	0.0017	0.0018	0.0019	0.0025	0.0029	0.0044	0.0056	0.0080	0.0105				
В	0.0006	0.0008	0.0010	0.0015	0.0020	0.0030	0.0041	0.0061	0.0081				

### Pin Capacitance

Pin		Capacitance (pF)											
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
AN	0.0009	0.0009	0.0009	0.0010	0.0012	0.0016	0.0019	0.0030	0.0035				
В	0.0010	0.0012	0.0015	0.0024	0.0030	0.0043	0.0060	0.0090	0.0121				

### Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
$AN \rightarrow Y \uparrow$	0.0310	0.0299	0.0291	0.0297	0.0271	0.0279	0.0289	0.0262	0.0266		
$AN \rightarrow Y \downarrow$	0.0348	0.0356	0.0375	0.0391	0.0372	0.0370	0.0369	0.0345	0.0350		
$B \to Y \uparrow$	0.0182	0.0169	0.0158	0.0161	0.0149	0.0149	0.0149	0.0148	0.0149		
$B \to Y \downarrow$	0.0110	0.0104	0.0099	0.0099	0.0095	0.0096	0.0095	0.0095	0.0095		

Description		K <sub>load</sub> (ns/pF)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
$AN \rightarrow Y \uparrow$	9.2557	7.1268	5.1346	3.4937	2.4968	1.6421	1.2241	0.8085	0.6038			
$AN \rightarrow Y \downarrow$	4.5632	3.5564	2.5977	1.8244	1.3311	0.8716	0.6599	0.4370	0.3279			
$B \to Y \uparrow$	9.2477	7.1220	5.1322	3.4922	2.4958	1.6415	1.2237	0.8082	0.6036			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	4.4623	3.4841	2.5516	1.7409	1.2759	0.8620	0.6405	0.4283	0.3225			

#### **Cell Description**

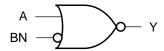
The NOR2XB cell provides a logical NOR of one non-inverted input (A) and one inverted input (BN). The output (Y) is represented by the logic equation:

$$Y = \overline{(A + \overline{BN})}$$

### **Function Table**

Α	BN	Υ
0	1	1
Х	0	0
1	Х	0

### **Logic Symbol**



### **Cell Size**

Drive Strength	Height (um)	Width (um)
NOR2XBX0P5MA10TR	2.00	1.20
NOR2XBX0P7MA10TR	2.00	1.20
NOR2XBX1MA10TR	2.00	1.20
NOR2XBX1P4MA10TR	2.00	1.60
NOR2XBX2MA10TR	2.00	1.60
NOR2XBX3MA10TR	2.00	2.20
NOR2XBX4MA10TR	2.00	2.60
NOR2XBX6MA10TR	2.00	4.00
NOR2XBX8MA10TR	2.00	5.00



### **AC Power**

Pin		Power (uW/MHz)											
' '''	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
Α	0.0004	0.0005	0.0006	0.0009	0.0013	0.0019	0.0026	0.0039	0.0053				
BN	0.0016	0.0017	0.0018	0.0024	0.0028	0.0039	0.0051	0.0075	0.0098				

### Pin Capacitance

Pin		Capacitance (pF)											
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
Α	0.0012	0.0014	0.0016	0.0024	0.0030	0.0048	0.0063	0.0092	0.0126				
BN	0.0010	0.0010	0.0010	0.0011	0.0012	0.0016	0.0019	0.0030	0.0036				

### Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A  \rightarrow  Y  \uparrow$	0.0169	0.0149	0.0131	0.0128	0.0113	0.0116	0.0112	0.0109	0.0111
$A  \rightarrow  Y  \downarrow$	0.0105	0.0096	0.0088	0.0088	0.0082	0.0083	0.0081	0.0081	0.0082
$BN \ \to \ Y \ \uparrow$	0.0313	0.0306	0.0308	0.0328	0.0306	0.0294	0.0316	0.0290	0.0293
$BN \ \to \ Y \ \downarrow$	0.0347	0.0358	0.0383	0.0416	0.0396	0.0377	0.0387	0.0365	0.0367

Description	K <sub>load</sub> (ns/pF)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A  \rightarrow  Y  \uparrow$	9.2530	7.1158	5.1337	3.4812	2.5001	1.6415	1.2178	0.8033	0.6011
$A  \rightarrow  Y  \downarrow$	4.5434	3.5417	2.5848	1.8133	1.3240	0.8671	0.6561	0.4348	0.3257
$BN \ \to \ Y \ \uparrow$	9.2448	7.1107	5.1312	3.4805	2.4997	1.6410	1.2176	0.8032	0.6010
$BN \  o \ Y \ \downarrow$	4.4713	3.4956	2.5594	1.7520	1.2766	0.8632	0.6428	0.4297	0.3232

#### **Cell Description**

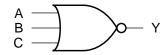
The NOR3 cell provides a logical NOR of three inputs (A,B,C). The output (Y) is represented by the logic equation:

$$Y = \overline{(A + B + C)}$$

### **Function Table**

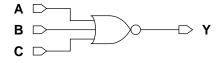
Α	В	С	Υ
0	0	0	1
Х	Х	1	0
Х	1	Х	0
1	Х	Х	0

### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
NOR3X0P5MA10TR	2.00	1.20
NOR3X0P5AA10TR	2.00	1.20
NOR3X0P7MA10TR	2.00	1.20
NOR3X0P7AA10TR	2.00	1.20
NOR3X1MA10TR	2.00	1.20
NOR3X1AA10TR	2.00	1.20
NOR3X1P4MA10TR	2.00	1.80
NOR3X1P4AA10TR	2.00	2.00
NOR3X2MA10TR	2.00	2.00
NOR3X2AA10TR	2.00	2.00
NOR3X3MA10TR	2.00	2.60
NOR3X3AA10TR	2.00	2.60
NOR3X4MA10TR	2.00	3.80
NOR3X4AA10TR	2.00	3.80



Pin		Power (uW/MHz)										
	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A				
Α	0.0001	0.0001	0.0002	0.0002	0.0003	0.0003	0.0004	0.0004				
В	0.0001	0.0001	0.0002	0.0002	0.0003	0.0003	0.0004	0.0004				
С	0.0004	0.0004	0.0005	0.0005	0.0007	0.0007	0.0010	0.0010				

# AC Power (Cont'd.)

Pin	Power (uW/MHz)									
F 111	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A				
Α	0.0005	0.0005	0.0010	0.0010	0.0016	0.0016				
В	0.0005	0.0005	0.0009	0.0009	0.0013	0.0013				
С	0.0014	0.0014	0.0023	0.0023	0.0031	0.0031				

# Pin Capacitance

Pin	Capacitance (pF)											
• •••	X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A				
Α	0.0012	0.0012	0.0013	0.0014	0.0016	0.0018	0.0021	0.0026				
В	0.0010	0.0010	0.0011	0.0013	0.0014	0.0016	0.0021	0.0025				
С	0.0010	0.0011	0.0012	0.0013	0.0014	0.0016	0.0022	0.0027				

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)									
• •••	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A				
Α	0.0029	0.0032	0.0043	0.0050	0.0058	0.0067				
В	0.0028	0.0032	0.0042	0.0048	0.0055	0.0064				
С	0.0030	0.0033	0.0041	0.0048	0.0055	0.0064				

## Delays at 25°C,1.0V, Typical Process

De	escri	ption	Intrinsic Delay (ns)								
			X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A	
Α	$\rightarrow$	Y ↑	0.0288	0.0300	0.0228	0.0255	0.0193	0.0234	0.0165	0.0211	
Α	$\rightarrow$	Y ↓	0.0119	0.0105	0.0128	0.0094	0.0118	0.0089	0.0112	0.0084	
В	$\rightarrow$	Y ↑	0.0317	0.0330	0.0266	0.0294	0.0238	0.0280	0.0220	0.0269	
В	$\rightarrow$	Y ↓	0.0127	0.0111	0.0144	0.0102	0.0139	0.0099	0.0139	0.0099	
С	$\rightarrow$	Y ↑	0.0344	0.0357	0.0292	0.0320	0.0265	0.0307	0.0247	0.0294	
С	$\rightarrow$	Y ↓	0.0142	0.0122	0.0165	0.0113	0.0161	0.0110	0.0161	0.0107	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description			Intrinsic I	Delay (ns)		
	X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A
$A \ \rightarrow \ Y \ \uparrow$	0.0158	0.0186	0.0151	0.0190	0.0144	0.0181
$A \ \rightarrow \ Y \ \downarrow$	0.0103	0.0077	0.0108	0.0084	0.0105	0.0081
$B \ \to \ Y \ \uparrow$	0.0217	0.0246	0.0225	0.0265	0.0225	0.0262
$B \ \to \ Y \ \downarrow$	0.0132	0.0092	0.0143	0.0102	0.0142	0.0099
$C \rightarrow Y \uparrow$	0.0242	0.0271	0.0256	0.0295	0.0259	0.0296
$C \rightarrow Y \downarrow$	0.0151	0.0101	0.0168	0.0112	0.0169	0.0110

Description				K <sub>load</sub> (ns/pF)								
				X0P5M	X0P5A	X0P7M	X0P7A	X1P0M	X1P0A	X1P4M	X1P4A	
Α	$\rightarrow$	Υ	$\uparrow$	14.6818	14.6849	10.7376	10.7413	7.7385	7.7411	5.3817	5.3510	
Α	$\rightarrow$	Υ	$\downarrow$	4.5448	3.6979	4.5441	2.7095	3.4612	1.9567	2.6063	1.3862	
В	$\rightarrow$	Υ	$\uparrow$	14.6726	14.6737	10.7331	10.7359	7.7352	7.7376	5.3797	5.3497	
В	$\rightarrow$	Υ	$\downarrow$	4.5103	3.6674	4.5091	2.6794	3.4265	1.9344	2.5920	1.3921	
С	$\rightarrow$	Υ	<b>↑</b>	14.6728	14.6748	10.7330	10.7357	7.7357	7.7383	5.3804	5.3499	
С	$\rightarrow$	Y	$\downarrow$	4.5572	3.7105	4.5533	2.7175	3.4677	1.9613	2.5421	1.3701	

Process Technology: NOR3

# CLN65G+

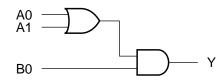
D	escri	iptio	n	K <sub>load</sub> (ns/pF)								
				X2P0M	X2P0A	X3P0M	X3P0A	X4P0M	X4P0A			
Α	$\rightarrow$	Υ	$\uparrow$	3.8309	3.8323	2.3905	2.3916	1.7847	1.7855			
Α	$\rightarrow$	Υ	$\downarrow$	1.7453	0.9852	1.1817	0.6710	0.8736	0.4878			
В	$\rightarrow$	Υ	$\uparrow$	3.8301	3.8313	2.3896	2.3904	1.7841	1.7847			
В	$\rightarrow$	Υ	$\downarrow$	1.7524	0.9886	1.1659	0.6619	0.8696	0.4851			
С	$\rightarrow$	Υ	$\uparrow$	3.8299	3.8311	2.3896	2.3903	1.7842	1.7846			
С	$\rightarrow$	Υ	$\downarrow$	1.7200	0.9752	1.1735	0.6659	0.8766	0.4900			

### **Cell Description**

The OA21 cell provides the logical AND of one OR group and an additional input. The output (Y) is represented by the logic equation:

$$Y = (A0 + A1) \bullet B0$$

## **Logic Symbol**

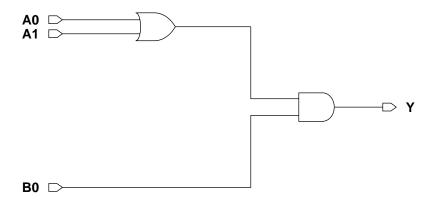


## **Function Table**

A0	<b>A</b> 1	В0	Υ
Х	Х	0	0
0	0	х	0
Х	1	1	1
1	Х	1	1

## **Cell Size**

Drive Strength	Height (um)	Width (um)
OA21X0P5MA10TR	2.00	1.60
OA21X0P7MA10TR	2.00	1.60
OA21X1MA10TR	2.00	1.60
OA21X1P4MA10TR	2.00	2.60
OA21X2MA10TR	2.00	2.60
OA21X3MA10TR	2.00	3.40
OA21X4MA10TR	2.00	4.00
OA21X6MA10TR	2.00	5.60
OA21X8MA10TR	2.00	7.00



Pin		Power (uW/MHz)										
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0002	0.0003	0.0004	0.0006	0.0008	0.0013	0.0017	0.0031	0.0040			
A1	0.0005	0.0007	0.0008	0.0012	0.0016	0.0023	0.0031	0.0050	0.0068			
В0	0.0006	0.0007	0.0008	0.0011	0.0014	0.0021	0.0028	0.0042	0.0055			

## Pin Capacitance

Pin		Capacitance (pF)										
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0012	0.0013	0.0016	0.0022	0.0027	0.0041	0.0050	0.0073	0.0100			
A1	0.0011	0.0012	0.0015	0.0024	0.0028	0.0039	0.0048	0.0070	0.0096			
В0	0.0011	0.0012	0.0014	0.0017	0.0021	0.0029	0.0037	0.0054	0.0069			

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 → Y ↑	0.0358	0.0346	0.0327	0.0336	0.0310	0.0312	0.0306	0.0300	0.0301
A0 → Y ↓	0.0491	0.0472	0.0456	0.0459	0.0420	0.0421	0.0415	0.0388	0.0391
A1 $\rightarrow$ Y $\uparrow$	0.0383	0.0375	0.0356	0.0361	0.0335	0.0336	0.0333	0.0343	0.0345
A1 $\rightarrow$ Y $\downarrow$	0.0510	0.0494	0.0479	0.0481	0.0444	0.0442	0.0436	0.0425	0.0428
B0 → Y ↑	0.0348	0.0339	0.0318	0.0317	0.0295	0.0296	0.0299	0.0301	0.0304
B0 → Y ↓	0.0380	0.0376	0.0370	0.0391	0.0361	0.0350	0.0353	0.0352	0.0358

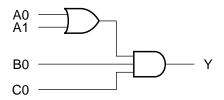
Description		K <sub>load</sub> (ns/pF)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 → Y ↑	4.6981	3.3651	2.4062	1.6539	1.1790	0.7855	0.5837	0.3855	0.2871
A0 → Y ↓	2.9121	2.0965	1.4716	1.0381	0.7236	0.4912	0.3637	0.2421	0.1824
A1 $\rightarrow$ Y $\uparrow$	4.7044	3.3697	2.4091	1.6558	1.1804	0.7864	0.5845	0.3864	0.2878
A1 $\rightarrow$ Y $\downarrow$	2.9121	2.0965	1.4717	1.0381	0.7236	0.4912	0.3637	0.2421	0.1824
B0 → Y ↑	4.7042	3.3697	2.4091	1.6558	1.1804	0.7864	0.5845	0.3864	0.2878
B0 → Y ↓	2.8888	2.0843	1.4658	1.0382	0.7244	0.4909	0.3638	0.2440	0.1840

### **Cell Description**

The OA211 cell provides the logical OR of one OR group and two additional inputs. The output (Y) is represented by the logic equation:

$$Y = (A0 + A1) \bullet B0 \bullet C0$$

## **Logic Symbol**

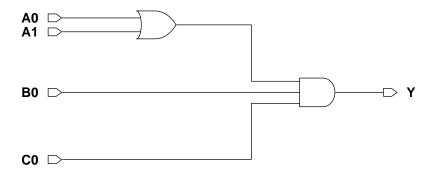


### **Function Table**

A0	<b>A1</b>	В0	C0	Υ
0	0	х	х	0
Х	Х	0	Х	0
х	х	х	0	0
х	1	1	1	1
1	х	1	1	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OA211X0P5MA10TR	2.00	1.80
OA211X0P7MA10TR	2.00	1.80
OA211X1MA10TR	2.00	2.40
OA211X1P4MA10TR	2.00	3.00
OA211X2MA10TR	2.00	3.20
OA211X3MA10TR	2.00	4.40
OA211X4MA10TR	2.00	5.60
OA211X6MA10TR	2.00	8.20



Pin		Power (uW/MHz)										
F	X0P5M X0		X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
A0	0.0004	0.0004	0.0006	0.0009	0.0011	0.0016	0.0021	0.0032				
A1	0.0007	0.0008	0.0011	0.0015	0.0018	0.0026	0.0034	0.0051				
В0	0.0006	0.0007	0.0008	0.0012	0.0016	0.0022	0.0030	0.0044				
C0	0.0007	0.0008	0.0010	0.0012	0.0016	0.0023	0.0031	0.0046				

## Pin Capacitance

Pin	Capacitance (pF)											
· · · ·	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
A0	0.0015	0.0017	0.0023	0.0030	0.0033	0.0050	0.0066	0.0102				
A1	0.0014	0.0016	0.0024	0.0030	0.0034	0.0048	0.0064	0.0097				
В0	0.0013	0.0014	0.0016	0.0024	0.0029	0.0038	0.0054	0.0078				
C0	0.0013	0.0015	0.0018	0.0023	0.0028	0.0040	0.0053	0.0079				

## Delays at 25°C,1.0V, Typical Process

Description				Intrinsic I	Delay (ns)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
$A0 \rightarrow Y \uparrow$	0.0405	0.0388	0.0377	0.0368	0.0369	0.0378	0.0367	0.0369
$A0 \rightarrow Y \downarrow$	0.0520	0.0503	0.0483	0.0465	0.0480	0.0480	0.0466	0.0472
A1 $\rightarrow$ Y $\uparrow$	0.0441	0.0426	0.0401	0.0394	0.0393	0.0407	0.0393	0.0397
A1 $\rightarrow$ Y $\downarrow$	0.0542	0.0526	0.0503	0.0487	0.0504	0.0500	0.0487	0.0492
B0 $\rightarrow$ Y $\uparrow$	0.0407	0.0392	0.0361	0.0358	0.0360	0.0373	0.0361	0.0362
$B0 \rightarrow Y \downarrow$	0.0429	0.0422	0.0421	0.0407	0.0402	0.0419	0.0408	0.0415
$C0 \rightarrow Y \uparrow$	0.0384	0.0367	0.0339	0.0329	0.0333	0.0347	0.0333	0.0335
$C0 \rightarrow Y \downarrow$	0.0396	0.0387	0.0385	0.0364	0.0365	0.0381	0.0365	0.0373

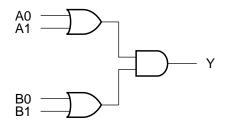
Description		K <sub>load</sub> (ns/pF)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
A0 → Y ↑	4.5836	3.3532	2.4006	1.6535	1.1807	0.7874	0.5853	0.3885
A0 → Y ↓	2.9097	2.1237	1.4986	1.0372	0.7282	0.5041	0.3728	0.2456
A1 $\rightarrow$ Y $\uparrow$	4.5917	3.3593	2.4037	1.6559	1.1821	0.7886	0.5862	0.3892
A1 $\rightarrow$ Y $\downarrow$	2.9099	2.1237	1.4985	1.0371	0.7282	0.5041	0.3728	0.2456
B0 $\rightarrow$ Y $\uparrow$	4.5917	3.3593	2.4036	1.6558	1.1821	0.7886	0.5862	0.3892
$B0 \rightarrow Y \downarrow$	2.8914	2.1133	1.4976	1.0366	0.7255	0.5037	0.3726	0.2456
$C0 \rightarrow Y \uparrow$	4.5917	3.3594	2.4036	1.6559	1.1821	0.7887	0.5862	0.3892
C0 → Y ↓	2.8848	2.1089	1.4936	1.0337	0.7239	0.5025	0.3715	0.2449

### **Cell Description**

The OA22 cell provides the logical AND of two OR groups. The output (Y) is represented by the logic equation:

$$Y = (A0 + A1) \bullet (B0 + B1)$$

## **Logic Symbol**

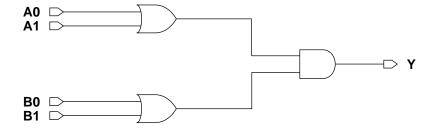


### **Function Table**

A0	<b>A</b> 1	В0	B1	Υ
х	х	0	0	0
0	0	х	х	0
Х	1	Х	1	1
х	1	1	х	1
1	х	х	1	1
1	Х	1	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OA22X0P5MA10TR	2.00	2.00
OA22X0P7MA10TR	2.00	2.00
OA22X1MA10TR	2.00	2.00
OA22X1P4MA10TR	2.00	3.20
OA22X2MA10TR	2.00	3.20
OA22X3MA10TR	2.00	4.40
OA22X4MA10TR	2.00	4.80
OA22X6MA10TR	2.00	7.40
OA22X8MA10TR	2.00	9.20



## **AC Power**

Pin		Power (uW/MHz)											
' '''	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	0.0002	0.0003	0.0004	0.0006	0.0008	0.0013	0.0018	0.0027	0.0038				
A1	0.0005	0.0006	0.0008	0.0012	0.0016	0.0025	0.0033	0.0051	0.0068				
В0	0.0002	0.0003	0.0004	0.0006	0.0008	0.0014	0.0018	0.0027	0.0039				
B1	0.0005	0.0006	0.0008	0.0011	0.0016	0.0026	0.0033	0.0051	0.0068				

# Pin Capacitance

Pin		Capacitance (pF)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0012	0.0013	0.0016	0.0024	0.0030	0.0043	0.0052	0.0080	0.0106			
A1	0.0011	0.0012	0.0015	0.0023	0.0029	0.0042	0.0051	0.0078	0.0101			
В0	0.0012	0.0014	0.0016	0.0024	0.0030	0.0043	0.0051	0.0079	0.0104			
B1	0.0012	0.0013	0.0015	0.0024	0.0030	0.0041	0.0050	0.0078	0.0101			

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A0 \rightarrow Y \uparrow$	0.0410	0.0396	0.0373	0.0391	0.0362	0.0390	0.0369	0.0375	0.0361
A0 $\rightarrow$ Y $\downarrow$	0.0596	0.0574	0.0553	0.0573	0.0537	0.0539	0.0511	0.0511	0.0501
A1 $\rightarrow$ Y $\uparrow$	0.0430	0.0418	0.0396	0.0410	0.0382	0.0421	0.0399	0.0406	0.0399
A1 $\rightarrow$ Y $\downarrow$	0.0614	0.0593	0.0573	0.0591	0.0556	0.0572	0.0543	0.0543	0.0537
B0 → Y ↑	0.0355	0.0344	0.0319	0.0343	0.0314	0.0340	0.0325	0.0330	0.0323
$B0 \rightarrow Y \downarrow$	0.0469	0.0455	0.0431	0.0462	0.0425	0.0433	0.0415	0.0415	0.0409
B1 $\rightarrow$ Y $\uparrow$	0.0378	0.0370	0.0346	0.0362	0.0335	0.0373	0.0356	0.0362	0.0358
B1 $\rightarrow$ Y $\downarrow$	0.0493	0.0482	0.0458	0.0482	0.0448	0.0468	0.0448	0.0449	0.0445

Description		K <sub>load</sub> (ns/pF)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 $\rightarrow$ Y $\uparrow$	4.6940	3.3624	2.4041	1.6460	1.1800	0.7887	0.5851	0.3885	0.2906
A0 $\rightarrow$ Y $\downarrow$	2.9788	2.1413	1.5015	1.0628	0.7401	0.5068	0.3732	0.2497	0.1880
A1 $\rightarrow$ Y $\uparrow$	4.6984	3.3655	2.4063	1.6474	1.1810	0.7900	0.5861	0.3891	0.2912
A1 $\rightarrow$ Y $\downarrow$	2.9784	2.1413	1.5013	1.0627	0.7400	0.5068	0.3731	0.2497	0.1879
B0 $\rightarrow$ Y $\uparrow$	4.6937	3.3621	2.4039	1.6459	1.1799	0.7887	0.5851	0.3884	0.2907
B0 $\rightarrow$ Y $\downarrow$	2.9436	2.1181	1.4848	1.0526	0.7328	0.5025	0.3702	0.2477	0.1865
B1 $\rightarrow$ Y $\uparrow$	4.6982	3.3654	2.4063	1.6474	1.1810	0.7900	0.5860	0.3890	0.2912
B1 $\rightarrow$ Y $\downarrow$	2.9435	2.1180	1.4848	1.0526	0.7328	0.5024	0.3702	0.2477	0.1865

### **Cell Description**

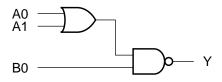
The OAI21 cell provides the logical inverted AND of one OR group and an additional input. The output (Y) is represented by the logic equation:

$$Y = \overline{(A0 + A1) \bullet B0}$$

# Function Table

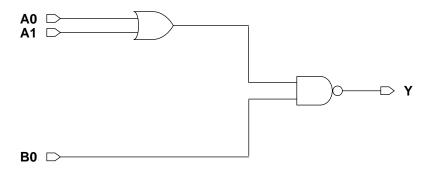
Α0	<b>A</b> 1	В0	Υ
0	0	Х	1
х	Х	0	1
Х	1	1	0
1	Х	1	0

## **Logic Symbol**



## **Cell Size**

Drive Strength	Height (um)	Width (um)
OAI21X0P5MA10TR	2.00	1.20
OAI21X0P7MA10TR	2.00	1.20
OAI21X1MA10TR	2.00	1.20
OAI21X1P4MA10TR	2.00	2.00
OAI21X2MA10TR	2.00	2.00
OAI21X3MA10TR	2.00	2.60
OAI21X4MA10TR	2.00	3.40
OAI21X6MA10TR	2.00	5.00
OAI21X8MA10TR	2.00	6.60



Pin	Power (uW/MHz)										
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
Α0	0.0002	0.0003	0.0004	0.0005	0.0007	0.0011	0.0020	0.0030	0.0040		
A1	0.0005	0.0006	0.0008	0.0012	0.0016	0.0024	0.0035	0.0052	0.0070		
В0	0.0005	0.0006	0.0008	0.0011	0.0015	0.0022	0.0029	0.0043	0.0058		

## Pin Capacitance

Pin		Capacitance (pF)											
F 111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	0.0012	0.0014	0.0018	0.0027	0.0034	0.0053	0.0069	0.0103	0.0138				
A1	0.0011	0.0013	0.0016	0.0027	0.0034	0.0050	0.0065	0.0098	0.0131				
В0	0.0011	0.0013	0.0016	0.0021	0.0027	0.0039	0.0052	0.0077	0.0102				

## Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)							
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 → Y ↑	0.0250	0.0222	0.0217	0.0210	0.0193	0.0196	0.0180	0.0177	0.0178
A0 $\rightarrow$ Y $\downarrow$	0.0153	0.0139	0.0135	0.0135	0.0125	0.0127	0.0125	0.0123	0.0123
A1 $\rightarrow$ Y $\uparrow$	0.0267	0.0241	0.0237	0.0233	0.0217	0.0216	0.0216	0.0212	0.0212
A1 $\rightarrow$ Y $\downarrow$	0.0171	0.0159	0.0155	0.0155	0.0146	0.0147	0.0156	0.0154	0.0155
B0 → Y ↑	0.0147	0.0136	0.0131	0.0123	0.0116	0.0118	0.0115	0.0110	0.0111
B0 → Y ↓	0.0138	0.0128	0.0122	0.0112	0.0105	0.0112	0.0116	0.0114	0.0115

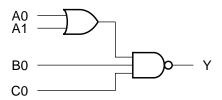
Description	K <sub>load</sub> (ns/pF)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 $\rightarrow$ Y $\uparrow$	9.7774	7.1445	5.1387	3.4458	2.4717	1.6398	1.1698	0.7755	0.5805
A0 $\rightarrow$ Y $\downarrow$	5.8418	4.3169	3.0550	2.1345	1.5197	1.0170	0.7626	0.5098	0.3833
A1 $\rightarrow$ Y $\uparrow$	9.7744	7.1427	5.1374	3.4452	2.4710	1.6395	1.1695	0.7753	0.5804
A1 $\rightarrow$ Y $\downarrow$	5.8421	4.3363	3.0582	2.1116	1.4989	1.0160	0.7690	0.5155	0.3890
B0 $\rightarrow$ Y $\uparrow$	7.5334	5.7589	4.1868	2.8996	2.0837	1.3809	1.0611	0.6958	0.5226
$B0 \rightarrow Y \downarrow$	5.8446	4.3385	3.0591	2.1213	1.5104	1.0161	0.7692	0.5156	0.3891

## **Cell Description**

The OAI211 cell provides the logical inverted OR of one OR group and two additional inputs. The output (Y) is represented by the logic equation:

 $Y = \overline{(A0 + A1) \bullet B0 \bullet C0}$ 

## **Logic Symbol**

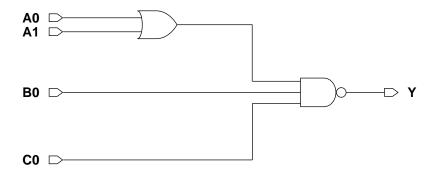


### **Function Table**

A0	<b>A</b> 1	В0	C0	Υ
0	0	х	х	1
Х	Х	0	Х	1
Х	х	х	0	1
Х	1	1	1	0
1	Х	1	1	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OAI211X0P5MA10TR	2.00	1.40
OAI211X0P7MA10TR	2.00	1.40
OAI211X1MA10TR	2.00	1.40
OAI211X1P4MA10TR	2.00	2.40
OAI211X2MA10TR	2.00	2.40
OAI211X3MA10TR	2.00	3.40
OAI211X4MA10TR	2.00	4.40



Pin		Power (uW/MHz)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M					
A0	0.0002	0.0003	0.0004	0.0006	0.0008	0.0013	0.0017					
A1	0.0004	0.0006	0.0007	0.0011	0.0014	0.0021	0.0028					
В0	0.0004	0.0005	0.0006	0.0009	0.0013	0.0018	0.0026					
C0	0.0005	0.0006	0.0007	0.0010	0.0014	0.0021	0.0028					

## Pin Capacitance

Pin		Capacitance (pF)										
-	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M					
A0	0.0011	0.0014	0.0018	0.0029	0.0035	0.0054	0.0072					
A1	0.0011	0.0014	0.0017	0.0028	0.0035	0.0052	0.0069					
В0	0.0010	0.0012	0.0015	0.0023	0.0031	0.0042	0.0059					
C0	0.0011	0.0014	0.0017	0.0022	0.0030	0.0045	0.0061					

## Delays at 25°C,1.0V, Typical Process

De	scri	otio	n			Intri	nsic Delay	(ns)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	0.0342	0.0328	0.0304	0.0298	0.0289	0.0281	0.0277
A0	$\rightarrow$	Υ	$\downarrow$	0.0214	0.0199	0.0182	0.0184	0.0175	0.0175	0.0171
A1	$\rightarrow$	Υ	$\uparrow$	0.0359	0.0348	0.0326	0.0315	0.0312	0.0299	0.0296
A1	$\rightarrow$	Υ	$\rightarrow$	0.0236	0.0222	0.0206	0.0202	0.0195	0.0194	0.0191
В0	$\rightarrow$	Υ	$\uparrow$	0.0199	0.0194	0.0182	0.0184	0.0177	0.0177	0.0175
В0	$\rightarrow$	Υ	$\downarrow$	0.0199	0.0182	0.0169	0.0161	0.0155	0.0162	0.0158
C0	$\rightarrow$	Υ	$\uparrow$	0.0180	0.0173	0.0156	0.0147	0.0142	0.0146	0.0139
C0	$\rightarrow$	Υ	$\rightarrow$	0.0182	0.0164	0.0147	0.0132	0.0128	0.0138	0.0131

De	escri	ptio	n			ŀ	ເ <sub>load</sub> (ns/pF	)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	10.1188	7.3870	5.3594	3.6008	2.6269	1.7066	1.2736
A0	$\rightarrow$	Υ	$\downarrow$	7.1755	5.1065	3.6008	2.5215	1.7802	1.1829	0.8820
A1	$\rightarrow$	Υ	$\uparrow$	10.1173	7.3857	5.3591	3.5998	2.6265	1.7063	1.2733
A1	$\rightarrow$	Υ	$\downarrow$	7.1851	5.0985	3.6084	2.4918	1.7483	1.1816	0.8751
В0	$\rightarrow$	Υ	$\uparrow$	7.7525	5.9581	4.3208	3.0837	2.1441	1.4332	1.0644
В0	$\rightarrow$	Υ	$\downarrow$	7.1850	5.0991	3.6094	2.5060	1.7705	1.1818	0.8768
C0	$\rightarrow$	Y	$\uparrow$	8.0195	6.1724	4.4777	3.1265	2.1693	1.4531	1.0716
C0	$\rightarrow$	Υ	$\downarrow$	7.1866	5.1000	3.6093	2.5059	1.7702	1.1819	0.8768

## **Cell Description**

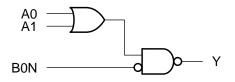
The OAl21B cell provides the logical inverted AND of one OR group and an additional input. The output (Y) is represented by the logic equation:

$$Y = \overline{(A0 + A1) \bullet \overline{B0N}}$$

### **Function Table**

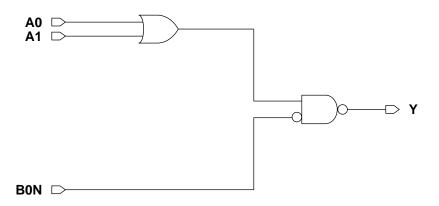
A0	<b>A</b> 1	B0N	Υ
0	0	Х	1
х	х	1	1
Х	1	0	0
1	Х	0	0

## **Logic Symbol**



### **Cell Size**

Drive Strength	Height (um)	Width (um)
OAI21BX0P5MA10TR	2.00	1.60
OAI21BX0P7MA10TR	2.00	1.60
OAI21BX1MA10TR	2.00	1.60
OAI21BX1P4MA10TR	2.00	2.40
OAI21BX2MA10TR	2.00	2.40
OAI21BX3MA10TR	2.00	3.20
OAI21BX4MA10TR	2.00	4.00
OAI21BX6MA10TR	2.00	5.80
OAI21BX8MA10TR	2.00	7.40



Pin		Power (uW/MHz)										
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0003	0.0004	0.0005	0.0009	0.0013	0.0016	0.0021	0.0033	0.0044			
A1	0.0004	0.0006	0.0008	0.0014	0.0018	0.0026	0.0036	0.0054	0.0072			
B0N	0.0016	0.0018	0.0020	0.0027	0.0035	0.0049	0.0063	0.0093	0.0122			

## Pin Capacitance

Pin		Capacitance (pF)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0012	0.0015	0.0019	0.0027	0.0035	0.0052	0.0069	0.0102	0.0135			
A1	0.0010	0.0013	0.0017	0.0027	0.0034	0.0050	0.0067	0.0099	0.0133			
B0N	0.0009	0.0009	0.0009	0.0009	0.0011	0.0015	0.0018	0.0028	0.0035			

## Delays at 25°C,1.0V, Typical Process

De	scrip	tion		Intrinsic Delay (ns)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
A0	$\rightarrow$	Υ	$\uparrow$	0.0255	0.0236	0.0218	0.0198	0.0187	0.0185	0.0184	0.0181	0.0177	
A0	$\rightarrow$	Υ	$\downarrow$	0.0170	0.0164	0.0158	0.0164	0.0155	0.0153	0.0152	0.0150	0.0149	
A1	$\rightarrow$	Υ	$\uparrow$	0.0268	0.0252	0.0236	0.0243	0.0229	0.0219	0.0219	0.0215	0.0212	
A1	$\rightarrow$	Υ	$\downarrow$	0.0187	0.0184	0.0178	0.0202	0.0190	0.0184	0.0185	0.0182	0.0181	
B0N	$\rightarrow$	Υ	$\uparrow$	0.0289	0.0288	0.0300	0.0292	0.0293	0.0285	0.0273	0.0264	0.0257	
B0N	$\rightarrow$	Υ	$\downarrow$	0.0353	0.0355	0.0378	0.0381	0.0392	0.0374	0.0366	0.0345	0.0343	

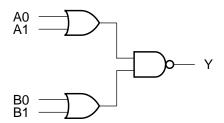
De	scrip	tion		K <sub>load</sub> (ns/pF)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
A0	$\rightarrow$	Υ	$\uparrow$	9.7292	7.0941	5.1062	3.2787	2.3664	1.5656	1.1747	0.7790	0.5830	
A0	$\rightarrow$	Υ	$\downarrow$	5.8112	4.2961	3.0176	2.1325	1.4927	1.0004	0.7386	0.4944	0.3723	
A1	$\rightarrow$	Υ	$\uparrow$	9.7247	7.0916	5.1045	3.2777	2.3657	1.5651	1.1743	0.7788	0.5829	
A1	$\rightarrow$	Υ	$\downarrow$	5.8179	4.2903	3.0237	2.1428	1.5030	1.0084	0.7527	0.5038	0.3804	
B0N	$\rightarrow$	Υ	$\uparrow$	7.3611	5.6233	4.0686	3.0156	2.0517	1.3884	1.0263	0.6882	0.5130	
B0N	$\rightarrow$	Υ	$\downarrow$	5.8223	4.2915	3.0245	2.1433	1.5034	1.0087	0.7531	0.5037	0.3804	

### **Cell Description**

The OAI22 cell provides the logical inverted AND of two OR groups. The output (Y) is represented by the logic equation:

$$\mathsf{Y} = \overline{(A0 + A1) \bullet (B0 + B1)}$$

## **Logic Symbol**

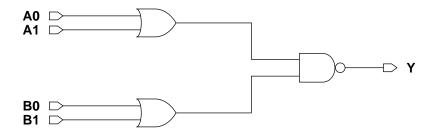


### **Function Table**

A0	<b>A</b> 1	В0	B1	Υ
0	0	х	Х	1
х	х	0	0	1
Х	1	Х	1	0
х	1	1	х	0
1	х	х	1	0
1	Х	1	Х	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OAI22X0P5MA10TR	2.00	1.40
OAI22X0P7MA10TR	2.00	1.40
OAI22X1MA10TR	2.00	1.40
OAI22X1P4MA10TR	2.00	2.40
OAI22X2MA10TR	2.00	2.40
OAI22X3MA10TR	2.00	3.40
OAI22X4MA10TR	2.00	4.80
OAI22X6MA10TR	2.00	6.80
OAI22X8MA10TR	2.00	9.00



## **AC Power**

Pin		Power (uW/MHz)											
F 111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	0.0002	0.0002	0.0003	0.0005	0.0007	0.0012	0.0018	0.0027	0.0035				
A1	0.0005	0.0006	0.0008	0.0012	0.0016	0.0028	0.0038	0.0057	0.0077				
В0	0.0002	0.0002	0.0003	0.0005	0.0007	0.0012	0.0019	0.0027	0.0035				
B1	0.0004	0.0006	0.0008	0.0011	0.0016	0.0028	0.0037	0.0056	0.0075				

# Pin Capacitance

Pin		Capacitance (pF)										
-	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
A0	0.0012	0.0014	0.0018	0.0027	0.0034	0.0052	0.0070	0.0105	0.0140			
A1	0.0011	0.0013	0.0017	0.0027	0.0034	0.0051	0.0067	0.0100	0.0133			
В0	0.0012	0.0014	0.0018	0.0027	0.0034	0.0052	0.0070	0.0103	0.0139			
B1	0.0011	0.0014	0.0017	0.0027	0.0035	0.0051	0.0067	0.0100	0.0135			

## Delays at 25°C,1.0V, Typical Process

Description				Intri	nsic Delay	(ns)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 → Y ↑	0.0326	0.0291	0.0270	0.0282	0.0260	0.0252	0.0242	0.0239	0.0241
A0 $\rightarrow$ Y $\downarrow$	0.0214	0.0195	0.0183	0.0190	0.0177	0.0188	0.0183	0.0182	0.0181
A1 $\rightarrow$ Y $\uparrow$	0.0339	0.0311	0.0289	0.0302	0.0283	0.0284	0.0279	0.0275	0.0275
A1 $\rightarrow$ Y $\downarrow$	0.0228	0.0215	0.0202	0.0207	0.0195	0.0212	0.0215	0.0214	0.0213
B0 → Y ↑	0.0205	0.0173	0.0163	0.0181	0.0164	0.0163	0.0155	0.0155	0.0155
B0 → Y ↓	0.0156	0.0137	0.0132	0.0143	0.0130	0.0143	0.0143	0.0144	0.0144
B1 → Y ↑	0.0229	0.0205	0.0190	0.0203	0.0190	0.0195	0.0191	0.0190	0.0189
$B1 \rightarrow Y \downarrow$	0.0175	0.0164	0.0154	0.0161	0.0149	0.0170	0.0172	0.0173	0.0172

Process Technology: OAI22

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

CLN65G+

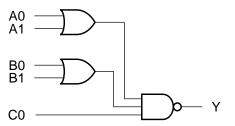
Description				ı	ζ <sub>load</sub> (ns/pF	·)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0 $\rightarrow$ Y $\uparrow$	9.5980	7.0148	5.0338	3.4321	2.4760	1.5658	1.1686	0.7778	0.5832
$A0 \rightarrow Y \downarrow$	5.7959	4.2836	3.0245	2.1279	1.4945	0.9982	0.7484	0.5038	0.3773
A1 $\rightarrow$ Y $\uparrow$	9.5945	7.0132	5.0325	3.4314	2.4756	1.5655	1.1680	0.7775	0.5830
A1 $\rightarrow$ Y $\downarrow$	5.7439	4.2498	3.0023	2.1125	1.4810	0.9951	0.7526	0.5086	0.3827
B0 $\rightarrow$ Y $\uparrow$	9.3820	6.8669	4.9141	3.4348	2.4764	1.5662	1.1723	0.7783	0.5827
$B0 \rightarrow Y \downarrow$	5.7541	4.2376	2.9849	2.1281	1.4942	1.0024	0.7560	0.5125	0.3856
$ B1 \rightarrow Y \uparrow $	9.3788	6.8661	4.9126	3.4339	2.4760	1.5657	1.1717	0.7779	0.5825
$B1 \rightarrow Y \downarrow$	5.7592	4.2576	3.0064	2.1065	1.4852	0.9916	0.7526	0.5085	0.3819

## **Cell Description**

The OAI221 cell provides the logical inverted AND of two OR groups and an additional input. The output (Y) is represented by the logic equation:

 $Y = \overline{(A0 + A1) \bullet (B0 + B1) \bullet C0}$ 

## **Logic Symbol**

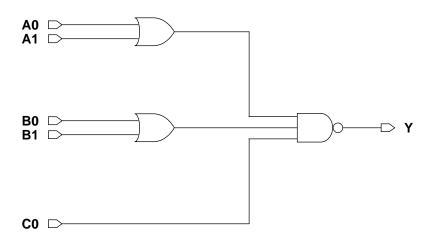


### **Function Table**

A0	<b>A</b> 1	В0	B1	C0	Υ
0	0	х	Х	Х	1
Х	х	0	0	Х	1
Х	Х	Х	Х	0	1
Х	1	х	1	1	0
Х	1	1	Х	1	0
1	Х	Х	1	1	0
1	Х	1	Х	1	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OAI221X0P5MA10TR	2.00	2.00
OAI221X0P7MA10TR	2.00	2.00
OAI221X1MA10TR	2.00	2.00
OAI221X1P4MA10TR	2.00	3.20
OAI221X2MA10TR	2.00	3.20
OAI221X3MA10TR	2.00	4.60
OAI221X4MA10TR	2.00	5.80



Pin	Power (uW/MHz)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M				
A0	0.0002	0.0002	0.0003	0.0005	0.0007	0.0011	0.0015				
A1	0.0004	0.0006	0.0008	0.0012	0.0016	0.0023	0.0033				
В0	0.0002	0.0003	0.0004	0.0005	0.0007	0.0011	0.0015				
B1	0.0004	0.0006	0.0008	0.0012	0.0017	0.0024	0.0033				
C0	0.0005	0.0006	0.0008	0.0011	0.0015	0.0022	0.0030				

## Pin Capacitance

Pin	Capacitance (pF)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M				
A0	0.0012	0.0015	0.0018	0.0029	0.0036	0.0055	0.0072				
A1	0.0011	0.0014	0.0017	0.0029	0.0036	0.0051	0.0070				
В0	0.0012	0.0014	0.0018	0.0027	0.0035	0.0054	0.0070				
B1	0.0011	0.0014	0.0017	0.0029	0.0036	0.0051	0.0070				
C0	0.0010	0.0012	0.0015	0.0023	0.0029	0.0042	0.0057				

# Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n			Intri	nsic Delay	(ns)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	0.0425	0.0395	0.0378	0.0383	0.0358	0.0349	0.0348
A0	$\rightarrow$	Υ	$\downarrow$	0.0282	0.0258	0.0247	0.0250	0.0232	0.0236	0.0236
A1	$\rightarrow$	Υ	$\uparrow$	0.0444	0.0417	0.0400	0.0403	0.0379	0.0368	0.0369
A1	$\rightarrow$	Υ	$\downarrow$	0.0306	0.0283	0.0272	0.0268	0.0250	0.0258	0.0256
В0	$\rightarrow$	Υ	$\uparrow$	0.0316	0.0283	0.0273	0.0275	0.0257	0.0248	0.0250
В0	$\rightarrow$	Υ	$\downarrow$	0.0238	0.0213	0.0205	0.0204	0.0190	0.0196	0.0192
B1	$\rightarrow$	Υ	$\uparrow$	0.0343	0.0309	0.0296	0.0301	0.0283	0.0270	0.0275
B1	$\rightarrow$	Υ	$\downarrow$	0.0268	0.0242	0.0232	0.0229	0.0213	0.0220	0.0216
C0	$\rightarrow$	Υ	$\uparrow$	0.0190	0.0178	0.0171	0.0163	0.0153	0.0156	0.0156
C0	$\rightarrow$	Υ	$\downarrow$	0.0195	0.0177	0.0172	0.0158	0.0146	0.0164	0.0157

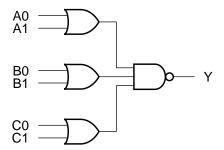
De	escri	ptio	n	K <sub>load</sub> (ns/pF)								
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
A0	$\rightarrow$	Υ	$\uparrow$	9.9093	7.2358	5.2330	3.6272	2.5982	1.7108	1.2819		
A0	$\rightarrow$	Υ	$\downarrow$	6.7974	4.8643	3.4757	2.4531	1.7386	1.1808	0.8832		
A1	$\rightarrow$	Υ	$\uparrow$	9.9081	7.2350	5.2324	3.6268	2.5979	1.7106	1.2818		
A1	$\rightarrow$	Υ	$\downarrow$	6.8408	4.8963	3.4989	2.4110	1.7067	1.1781	0.8709		
В0	$\rightarrow$	Υ	$\uparrow$	9.7982	7.1447	5.1762	3.5413	2.5553	1.6836	1.2611		
В0	$\rightarrow$	Υ	$\downarrow$	6.7955	4.8405	3.4520	2.4544	1.7394	1.1783	0.8831		
B1	$\rightarrow$	Υ	$\uparrow$	9.7972	7.1438	5.1753	3.5410	2.5551	1.6833	1.2609		
B1	$\rightarrow$	Υ	$\downarrow$	6.8411	4.8964	3.4991	2.4289	1.7151	1.1782	0.8771		
C0	$\rightarrow$	Υ	$\uparrow$	8.1276	6.2099	4.4943	2.9968	2.1730	1.4683	1.0874		
C0	$\rightarrow$	Υ	$\downarrow$	6.8423	4.8963	3.4996	2.4388	1.7289	1.1784	0.8779		

### **Cell Description**

The OAI222 cell provides the logical inverted AND of three OR groups. The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (\overline{\mathsf{A}0 + \mathsf{A}1}) \bullet (B0 + B1) \bullet (C0 + C1)$$

## **Logic Symbol**

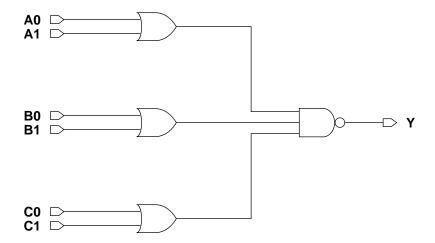


### **Function Table**

A0	<b>A</b> 1	В0	B1	C0	C1	Υ
0	0	Х	Х	Х	Х	1
Х	х	0	0	Х	Х	1
Х	х	х	Х	0	0	1
Х	1	Х	1	1	Х	0
Х	1	х	1	Х	1	0
Х	1	1	х	1	Х	0
Х	1	1	Х	Х	1	0
1	х	х	1	1	Х	0
1	Х	х	1	х	1	0
1	Х	1	Х	1	Х	0
1	х	1	Х	Х	1	0

## Cell Size

Drive Strength	Height (um)	Width (um)
OAI222X0P5MA10TR	2.00	2.20
OAI222X0P7MA10TR	2.00	2.20
OAI222X1MA10TR	2.00	2.20
OAI222X1P4MA10TR	2.00	3.80
OAI222X2MA10TR	2.00	3.80
OAI222X3MA10TR	2.00	5.40
OAI222X4MA10TR	2.00	6.80



Pin	Power (uW/MHz)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M				
A0	0.0002	0.0002	0.0003	0.0005	0.0006	0.0010	0.0013				
A1	0.0005	0.0006	0.0008	0.0011	0.0016	0.0024	0.0031				
В0	0.0002	0.0002	0.0003	0.0005	0.0007	0.0010	0.0013				
B1	0.0004	0.0006	0.0008	0.0011	0.0016	0.0024	0.0032				
C0	0.0002	0.0002	0.0003	0.0005	0.0006	0.0010	0.0013				
C1	0.0004	0.0006	0.0008	0.0012	0.0016	0.0024	0.0032				

## Pin Capacitance

Pin	Capacitance (pF)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M				
A0	0.0013	0.0016	0.0019	0.0029	0.0036	0.0055	0.0072				
A1	0.0011	0.0014	0.0017	0.0029	0.0036	0.0051	0.0070				
В0	0.0012	0.0015	0.0019	0.0027	0.0035	0.0054	0.0070				
B1	0.0011	0.0014	0.0017	0.0028	0.0035	0.0051	0.0070				
C0	0.0013	0.0015	0.0019	0.0029	0.0037	0.0056	0.0073				
C1	0.0012	0.0014	0.0018	0.0029	0.0037	0.0052	0.0071				

# Delays at 25°C,1.0V, Typical Process

De	escri	ptio	n			Intri	nsic Delay	(ns)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	0.0552	0.0519	0.0478	0.0474	0.0442	0.0437	0.0427
A0	$\rightarrow$	Υ	$\downarrow$	0.0372	0.0340	0.0318	0.0317	0.0294	0.0303	0.0296
A1	$\rightarrow$	Υ	$\uparrow$	0.0562	0.0534	0.0496	0.0494	0.0464	0.0455	0.0448
A1	$\rightarrow$	Υ	$\downarrow$	0.0385	0.0357	0.0338	0.0335	0.0312	0.0325	0.0316
В0	$\rightarrow$	Υ	$\uparrow$	0.0422	0.0390	0.0361	0.0357	0.0332	0.0326	0.0321
В0	$\rightarrow$	Υ	$\downarrow$	0.0325	0.0293	0.0275	0.0279	0.0260	0.0263	0.0261
B1	$\rightarrow$	Υ	$\uparrow$	0.0438	0.0408	0.0381	0.0380	0.0356	0.0348	0.0344
B1	$\rightarrow$	Υ	$\downarrow$	0.0340	0.0310	0.0295	0.0297	0.0277	0.0286	0.0282
C0	$\rightarrow$	Υ	$\uparrow$	0.0287	0.0257	0.0237	0.0239	0.0223	0.0223	0.0217
C0	$\rightarrow$	Υ	$\downarrow$	0.0229	0.0204	0.0194	0.0192	0.0178	0.0195	0.0188
C1	$\rightarrow$	Υ	<b>↑</b>	0.0300	0.0274	0.0258	0.0260	0.0246	0.0241	0.0238

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
C1 → Y ↓	0.0246	0.0223	0.0216	0.0213	0.0201	0.0215	0.0210		

De	escri	ptio	n			ŀ	ເ <sub>load</sub> (ns/pF	)		
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
A0	$\rightarrow$	Υ	$\uparrow$	9.9662	7.3323	5.2486	3.5849	2.5713	1.7073	1.2743
A0	$\rightarrow$	Υ	$\downarrow$	6.8046	4.8393	3.4647	2.4544	1.7456	1.1708	0.8798
A1	$\rightarrow$	Υ	$\uparrow$	9.9642	7.3311	5.2480	3.5845	2.5711	1.7072	1.2741
A1	$\rightarrow$	Υ	$\downarrow$	6.7647	4.7960	3.4348	2.4347	1.7290	1.1682	0.8755
В0	$\rightarrow$	Υ	$\uparrow$	9.7796	7.1954	5.1688	3.5351	2.5319	1.6812	1.2560
В0	$\rightarrow$	Υ	$\downarrow$	6.8077	4.8185	3.4429	2.4544	1.7447	1.1709	0.8809
B1	$\rightarrow$	Υ	$\uparrow$	9.7772	7.1939	5.1678	3.5347	2.5316	1.6809	1.2558
B1	$\rightarrow$	Υ	$\downarrow$	6.7625	4.8099	3.4440	2.4208	1.7153	1.1682	0.8721
C0	$\rightarrow$	Υ	$\uparrow$	10.0103	7.3669	5.2739	3.6247	2.6013	1.7192	1.2811
C0	$\rightarrow$	Υ	$\downarrow$	6.7418	4.7927	3.4307	2.4452	1.7406	1.1680	0.8790
C1	$\rightarrow$	Υ	$\uparrow$	10.0050	7.3636	5.2722	3.6235	2.6007	1.7186	1.2807
C1	$\rightarrow$	Υ	$\downarrow$	6.7650	4.8093	3.4437	2.4400	1.7355	1.1682	0.8754

**Logic Symbol** 

# CLN65G+

## **Cell Description**

The OAI2XB1 cell provides the logical inverted AND of one OR group and an additional input. The output (Y) is represented by the logic equation:

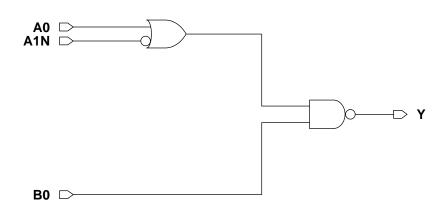
$$Y = (\overline{A0 + \overline{A1N}}) \bullet B0$$

# Function Table Cell Size

A0	A1N	В0	Υ
0	1	х	1
х	Х	0	1
Х	0	1	0
1	Х	1	0

A0 A1N	

Drive Strength	Height (um)	Width (um)
OAI2XB1X0P5MA10TR	2.00	1.60
OAI2XB1X0P7MA10TR	2.00	1.60
OAI2XB1X1MA10TR	2.00	1.60
OAI2XB1X1P4MA10TR	2.00	2.40
OAI2XB1X2MA10TR	2.00	2.40
OAI2XB1X3MA10TR	2.00	3.20
OAI2XB1X4MA10TR	2.00	4.20
OAI2XB1X6MA10TR	2.00	5.80
OAI2XB1X8MA10TR	2.00	7.60



Pin		Power (uW/MHz)											
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	0.0004	0.0005	0.0007	0.0010	0.0014	0.0021	0.0031	0.0046	0.0061				
A1N	0.0016	0.0017	0.0018	0.0026	0.0032	0.0044	0.0054	0.0078	0.0106				
В0	0.0005	0.0007	0.0008	0.0012	0.0015	0.0023	0.0030	0.0045	0.0060				

## Pin Capacitance

Pin		Capacitance (pF)											
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
A0	0.0012	0.0014	0.0018	0.0027	0.0034	0.0051	0.0068	0.0103	0.0137				
A1N	0.0009	0.0009	0.0009	0.0011	0.0013	0.0017	0.0025	0.0033	0.0045				
В0	0.0011	0.0013	0.0016	0.0021	0.0026	0.0039	0.0052	0.0077	0.0102				

## Delays at 25°C,1.0V, Typical Process

De	Description		Intrinsic Delay (ns)										
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M	
A0	$\rightarrow$	Υ	<b>↑</b>	0.0247	0.0233	0.0215	0.0208	0.0193	0.0188	0.0179	0.0176	0.0177	
A0	$\rightarrow$	Υ	$\downarrow$	0.0153	0.0146	0.0136	0.0135	0.0125	0.0125	0.0125	0.0122	0.0123	
A1N	$\rightarrow$	Υ	$\uparrow$	0.0408	0.0412	0.0408	0.0411	0.0393	0.0373	0.0373	0.0364	0.0372	
A1N	$\rightarrow$	Υ	$\downarrow$	0.0400	0.0426	0.0444	0.0456	0.0439	0.0413	0.0407	0.0400	0.0407	
В0	$\rightarrow$	Υ	$\uparrow$	0.0145	0.0139	0.0130	0.0123	0.0113	0.0119	0.0115	0.0110	0.0111	
В0	$\rightarrow$	Υ	$\downarrow$	0.0136	0.0128	0.0120	0.0110	0.0102	0.0114	0.0116	0.0114	0.0115	

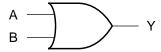
Des	Description		K <sub>load</sub> (ns/pF)									
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
A0	$\rightarrow$	Υ	$\uparrow$	9.6392	7.0395	5.0509	3.4100	2.4531	1.6211	1.1582	0.7701	0.5773
A0	$\rightarrow$	Υ	$\downarrow$	5.8385	4.3129	3.0534	2.1340	1.5199	1.0253	0.7622	0.5100	0.3834
A1N	$\rightarrow$	Υ	$\uparrow$	9.6373	7.0392	5.0504	3.4102	2.4530	1.6210	1.1579	0.7700	0.5772
A1N	$\rightarrow$	Υ	$\downarrow$	5.8329	4.3014	3.0570	2.1111	1.5021	1.0232	0.7691	0.5156	0.3890
В0	$\rightarrow$	Υ	1	7.5238	5.7803	4.1740	2.8946	2.0845	1.3788	1.0600	0.6964	0.5228
В0	$\rightarrow$	Υ	$\downarrow$	5.8321	4.2984	3.0534	2.1209	1.5108	1.0219	0.7683	0.5152	0.3886

### **Cell Description**

The OR2 cell provides the logical OR of two inputs (A,B). The output (Y) is represented by the logic equation:

$$Y = (A + B)$$

## **Logic Symbol**



### **Function Table**

Α	В	Υ		
0	0	0		
Х	1	1		
1	Х	1		

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OR2X0P5MA10TR	2.00	1.20
OR2X0P7MA10TR	2.00	1.20
OR2X1MA10TR	2.00	1.20
OR2X1P4MA10TR	2.00	2.00
OR2X2MA10TR	2.00	2.00
OR2X3MA10TR	2.00	2.60
OR2X4MA10TR	2.00	3.00
OR2X6MA10TR	2.00	4.60
OR2X8MA10TR	2.00	5.60
OR2X11MA10TR	2.00	7.40



Pin				Power (u	ıW/MHz)			
F 111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
Α	0.0002	0.0003	0.0004	0.0005	0.0007	0.0011	0.0015	0.0023
В	0.0005	0.0005	0.0007	0.0011	0.0014	0.0022	0.0028	0.0042

# AC Power (Cont'd.)

Pin	Power (uW/MHz)						
F 1111	X8P0M	X11P0M					
Α	0.0030	0.0043					
В	0.0057	0.0080					

## Pin Capacitance

Pin		Capacitance (pF)										
F 111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M				
Α	0.0012	0.0012	0.0013	0.0021	0.0024	0.0038	0.0044	0.0070				
В	0.0012	0.0012	0.0013	0.0021	0.0025	0.0037	0.0043	0.0067				

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)					
• •••	X8P0M	M X11P0M				
Α	0.0088	0.0121				
В	0.0087	0.0118				

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M		
$A \rightarrow Y \uparrow$	0.0277	0.0275	0.0256	0.0257	0.0243	0.0247	0.0237	0.0238		
$A \rightarrow Y \downarrow$	0.0409	0.0415	0.0381	0.0378	0.0357	0.0361	0.0346	0.0343		
$B \to Y \uparrow$	0.0297	0.0294	0.0277	0.0269	0.0256	0.0266	0.0258	0.0260		
$B \to Y \downarrow$	0.0439	0.0445	0.0410	0.0400	0.0381	0.0385	0.0371	0.0367		

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escri	iptic	n	Intrinsic Delay (ns)			
				X8P0M	X11P0M		
Α	$\rightarrow$	Υ	$\uparrow$	0.0234	0.0236		
Α	$\rightarrow$	Υ	$\downarrow$	0.0334	0.0335		
В	$\rightarrow$	Υ	$\uparrow$	0.0255	0.0258		
В	$\rightarrow$	Υ	$\downarrow$	0.0359	0.0360		

## Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description		K <sub>load</sub> (ns/pF)									
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M			
$A \rightarrow Y \uparrow$	4.5630	3.3536	2.3951	1.6519	1.1913	0.7809	0.5788	0.3841			
$A \rightarrow Y \downarrow$	3.0820	2.3242	1.6005	1.0832	0.7668	0.5107	0.3692	0.2448			
$B \to Y \uparrow$	4.5655	3.3549	2.3962	1.6526	1.1918	0.7815	0.5793	0.3844			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	3.0816	2.3239	1.6003	1.0831	0.7667	0.5107	0.3692	0.2448			

D	escr	iptic	n	K <sub>load</sub> (ns/pF)			
				X8P0M	X11P0M		
Α	$\rightarrow$	Υ	$\uparrow$	0.2872	0.2090		
Α	$\rightarrow$	Υ	$\rightarrow$	0.1862	0.1331		
В	$\rightarrow$	Υ	$\uparrow$	0.2875	0.2092		
В	$\rightarrow$	Υ	$\downarrow$	0.1862	0.1331		

## **Cell Description**

The OR3 cell provides the logical OR of three inputs (A,B,C). The output (Y) is represented by the logic equation:

$$Y = (A + B + C)$$

# Logic Symbol

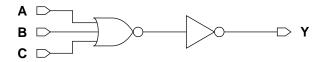


### **Function Table**

Α	В	С	Υ
0	0	0	0
Х	Х	1	1
Х	1	Х	1
1	Х	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OR3X0P5MA10TR	2.00	1.40
OR3X0P7MA10TR	2.00	2.00
OR3X1MA10TR	2.00	2.00
OR3X1P4MA10TR	2.00	2.40
OR3X2MA10TR	2.00	3.40
OR3X3MA10TR	2.00	4.80
OR3X4MA10TR	2.00	6.60
OR3X6MA10TR	2.00	8.60
OR3X8MA10TR	2.00	11.20



Pin		Power (uW/MHz)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
Α	0.0003	0.0004	0.0005	0.0007	0.0011	0.0020	0.0026	0.0038	0.0048			
В	0.0003	0.0004	0.0005	0.0007	0.0011	0.0017	0.0022	0.0033	0.0044			
С	0.0007	0.0009	0.0012	0.0016	0.0024	0.0036	0.0049	0.0072	0.0097			

## Pin Capacitance

Pin		Capacitance (pF)											
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M				
Α	0.0015	0.0019	0.0022	0.0029	0.0041	0.0058	0.0080	0.0115	0.0157				
В	0.0014	0.0019	0.0022	0.0029	0.0039	0.0056	0.0077	0.0110	0.0150				
С	0.0014	0.0019	0.0022	0.0030	0.0039	0.0056	0.0077	0.0111	0.0150				

## Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A \rightarrow Y \uparrow$	0.0273	0.0253	0.0238	0.0231	0.0237	0.0226	0.0229	0.0225	0.0227
$A \ \rightarrow \ Y \ \downarrow$	0.0455	0.0415	0.0395	0.0395	0.0380	0.0364	0.0365	0.0360	0.0365
$B \to Y \uparrow$	0.0300	0.0282	0.0268	0.0261	0.0277	0.0269	0.0272	0.0267	0.0268
$B \ \to \ Y \ \downarrow$	0.0512	0.0470	0.0452	0.0455	0.0459	0.0450	0.0449	0.0441	0.0441
$C \rightarrow Y \uparrow$	0.0313	0.0298	0.0284	0.0276	0.0306	0.0298	0.0302	0.0297	0.0300
$C \rightarrow Y \downarrow$	0.0540	0.0492	0.0474	0.0481	0.0490	0.0485	0.0483	0.0474	0.0473

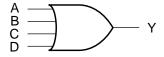
Description	K <sub>load</sub> (ns/pF)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A \rightarrow Y \uparrow$	4.5399	3.3093	2.3678	1.6268	1.1757	0.7834	0.5826	0.3869	0.2900
$A \rightarrow Y \downarrow$	2.8614	2.0838	1.5251	1.0752	0.7286	0.4945	0.3728	0.2494	0.1851
$B \to Y \uparrow$	4.5463	3.3140	2.3710	1.6287	1.1780	0.7852	0.5839	0.3877	0.2906
$B \to Y \downarrow$	2.8609	2.0836	1.5250	1.0751	0.7286	0.4945	0.3728	0.2494	0.1851
$C \rightarrow Y \uparrow$	4.5502	3.3172	2.3732	1.6309	1.1814	0.7876	0.5858	0.3890	0.2916
$C \rightarrow Y \downarrow$	2.8605	2.0834	1.5249	1.0751	0.7286	0.4945	0.3728	0.2494	0.1851

### **Cell Description**

The OR4 cell provides the logical OR of four inputs (A,B,C,D). The output (Y) is represented by the logic equation:

$$Y = (A + B + C + D)$$

## **Logic Symbol**

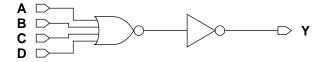


### **Function Table**

Α	В	С	D	Υ
0	0	0	0	0
Х	Х	Х	1	1
Х	Х	1	Х	1
Х	1	Х	Х	1
1	Х	Х	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
OR4X0P5MA10TR	2.00	2.20
OR4X0P7MA10TR	2.00	2.20
OR4X1MA10TR	2.00	2.20
OR4X1P4MA10TR	2.00	3.00
OR4X2MA10TR	2.00	3.40
OR4X3MA10TR	2.00	3.80
OR4X4MA10TR	2.00	5.40
OR4X6MA10TR	2.00	7.20
OR4X8MA10TR	2.00	9.20



Pin	Power (uW/MHz)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
Α	0.0002	0.0002	0.0003	0.0004	0.0006	0.0009	0.0012	0.0018	0.0024		
В	0.0005	0.0005	0.0006	0.0009	0.0013	0.0018	0.0024	0.0037	0.0049		
С	0.0002	0.0002	0.0003	0.0004	0.0006	0.0009	0.0012	0.0018	0.0024		
D	0.0005	0.0005	0.0006	0.0009	0.0013	0.0018	0.0025	0.0037	0.0049		

# Pin Capacitance

Pin	Capacitance (pF)										
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M		
Α	0.0012	0.0012	0.0013	0.0015	0.0023	0.0028	0.0041	0.0059	0.0078		
В	0.0010	0.0010	0.0011	0.0013	0.0022	0.0028	0.0038	0.0057	0.0074		
С	0.0011	0.0011	0.0012	0.0015	0.0022	0.0028	0.0040	0.0059	0.0078		
D	0.0012	0.0012	0.0013	0.0013	0.0022	0.0028	0.0038	0.0057	0.0074		

# Delays at 25°C,1.0V, Typical Process

Descripti	on				Intri	nsic Delay	(ns)			
		X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M
$A \rightarrow Y$	1	0.0303	0.0304	0.0295	0.0291	0.0268	0.0253	0.0262	0.0256	0.0257
$A \rightarrow Y$	$\downarrow$	0.0432	0.0442	0.0430	0.0411	0.0366	0.0344	0.0351	0.0346	0.0351
$B \rightarrow Y$	1	0.0319	0.0320	0.0312	0.0310	0.0292	0.0278	0.0285	0.0280	0.0282
$B \rightarrow Y$	$\downarrow$	0.0444	0.0454	0.0445	0.0427	0.0389	0.0369	0.0373	0.0370	0.0375
$C \rightarrow Y$	1	0.0315	0.0317	0.0311	0.0334	0.0302	0.0288	0.0298	0.0293	0.0293
$C \rightarrow Y$	$\downarrow$	0.0436	0.0448	0.0442	0.0462	0.0404	0.0386	0.0395	0.0388	0.0391
$D \rightarrow Y$	<b>↑</b>	0.0334	0.0334	0.0326	0.0354	0.0328	0.0313	0.0322	0.0317	0.0319
$D \rightarrow Y$	$\downarrow$	0.0470	0.0480	0.0472	0.0478	0.0429	0.0412	0.0417	0.0411	0.0415

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

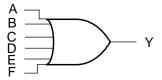
Description		K <sub>load</sub> (ns/pF)										
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M	X8P0M			
$A \ \rightarrow \ Y \ \uparrow$	6.0505	4.4820	3.2537	2.2434	1.5949	1.0620	0.7931	0.5289	0.3967			
$A \ \rightarrow \ Y \ \downarrow$	5.3105	3.8826	2.7821	1.6980	1.1828	0.8025	0.5945	0.4043	0.3042			
$B \ \to \ Y \ \uparrow$	6.0553	4.4853	3.2559	2.2449	1.5960	1.0627	0.7937	0.5293	0.3970			
$B \ \to \ Y \ \downarrow$	5.3115	3.8827	2.7821	1.6979	1.1828	0.8024	0.5947	0.4042	0.3042			
$C \rightarrow Y \uparrow$	5.9963	4.4554	3.2704	2.2437	1.5956	1.0623	0.7936	0.5292	0.3969			
$C \rightarrow Y \downarrow$	5.3117	3.8841	2.7840	1.7018	1.1850	0.8039	0.5957	0.4049	0.3047			
$D \rightarrow Y \uparrow$	5.9988	4.4572	3.2714	2.2450	1.5966	1.0629	0.7941	0.5295	0.3972			
$D \rightarrow Y \downarrow$	5.3113	3.8836	2.7838	1.7018	1.1850	0.8038	0.5957	0.4049	0.3047			

#### **Cell Description**

The OR6 cell provides the logical OR of six inputs (A,B,C,D,E,F). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (A+B+C+D+E+F)$$

# **Logic Symbol**

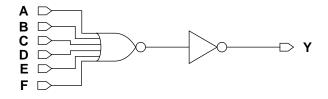


#### **Function Table**

Α	В	С	D	Е	F	Υ
0	0	0	0	0	0	0
Х	Х	Х	Х	Х	1	1
Х	Х	Х	Х	1	Х	1
Х	Х	Х	1	Х	Х	1
Х	Х	1	Х	Х	Х	1
Х	1	Х	Х	Х	Х	1
1	Х	Х	Х	Х	Х	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
OR6X0P5MA10TR	2.00	2.60
OR6X0P7MA10TR	2.00	2.60
OR6X1MA10TR	2.00	2.60
OR6X1P4MA10TR	2.00	4.20
OR6X2MA10TR	2.00	4.20
OR6X3MA10TR	2.00	6.60
OR6X4MA10TR	2.00	9.20
OR6X6MA10TR	2.00	13.40



Pin				Power (u	ıW/MHz)			
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
Α	0.0002	0.0003	0.0004	0.0005	0.0007	0.0012	0.0019	0.0027
В	0.0002	0.0003	0.0004	0.0005	0.0007	0.0012	0.0016	0.0023
С	0.0006	0.0006	0.0008	0.0012	0.0015	0.0025	0.0034	0.0050
D	0.0003	0.0003	0.0004	0.0005	0.0007	0.0012	0.0019	0.0027
Е	0.0002	0.0003	0.0004	0.0005	0.0007	0.0012	0.0016	0.0023
F	0.0005	0.0006	0.0008	0.0012	0.0015	0.0025	0.0033	0.0050

# Pin Capacitance

Pin		Capacitance (pF)											
' '''	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M					
Α	0.0014	0.0014	0.0016	0.0022	0.0026	0.0040	0.0052	0.0078					
В	0.0011	0.0012	0.0014	0.0022	0.0026	0.0038	0.0050	0.0076					
С	0.0012	0.0012	0.0014	0.0023	0.0027	0.0038	0.0050	0.0076					
D	0.0013	0.0013	0.0015	0.0022	0.0026	0.0040	0.0052	0.0079					
Е	0.0012	0.0013	0.0014	0.0022	0.0026	0.0038	0.0050	0.0076					
F	0.0013	0.0013	0.0015	0.0022	0.0026	0.0038	0.0050	0.0076					

#### Delays at 25°C,1.0V, Typical Process

D	escri	iptio	n	Intrinsic Delay (ns)										
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M			
Α	$\rightarrow$	Υ	$\uparrow$	0.0348	0.0340	0.0317	0.0297	0.0276	0.0278	0.0281	0.0285			
Α	$\rightarrow$	Υ	$\downarrow$	0.0540	0.0532	0.0492	0.0423	0.0397	0.0389	0.0380	0.0389			
В	$\rightarrow$	Υ	$\uparrow$	0.0373	0.0366	0.0346	0.0334	0.0314	0.0317	0.0332	0.0335			
В	$\rightarrow$	Υ	$\downarrow$	0.0580	0.0572	0.0538	0.0482	0.0456	0.0464	0.0466	0.0472			
С	$\rightarrow$	Υ	$\uparrow$	0.0392	0.0385	0.0366	0.0358	0.0338	0.0352	0.0363	0.0367			
С	$\rightarrow$	Υ	$\downarrow$	0.0603	0.0596	0.0562	0.0506	0.0481	0.0494	0.0496	0.0503			
D	$\rightarrow$	Υ	$\uparrow$	0.0363	0.0358	0.0338	0.0340	0.0317	0.0308	0.0317	0.0321			
D	$\rightarrow$	Υ	$\downarrow$	0.0533	0.0534	0.0503	0.0469	0.0443	0.0417	0.0416	0.0423			
Е	$\rightarrow$	Υ	$\uparrow$	0.0393	0.0388	0.0369	0.0378	0.0355	0.0348	0.0369	0.0370			
Е	$\rightarrow$	Υ	$\downarrow$	0.0585	0.0586	0.0557	0.0528	0.0502	0.0492	0.0502	0.0506			
F	$\rightarrow$	Υ	$\uparrow$	0.0406	0.0398	0.0377	0.0402	0.0379	0.0384	0.0401	0.0404			

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description Intrinsic Delay (ns)								
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
$F \to Y \downarrow$	0.0618	0.0618	0.0585	0.0551	0.0526	0.0523	0.0533	0.0537

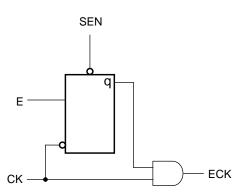
# Delays at 25°C,1.0V, Typical Process (Cont'd.)

D	escr	iptic	n				K <sub>load</sub> (	ns/pF)			
				X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	X6P0M
Α	$\rightarrow$	Υ	$\uparrow$	6.0602	4.4750	3.2487	2.1841	1.5834	1.0544	0.7916	0.5281
Α	$\rightarrow$	Υ	$\downarrow$	5.3424	3.8837	2.7688	1.6915	1.2142	0.7973	0.5971	0.3995
В	$\rightarrow$	Υ	$\uparrow$	6.0667	4.4802	3.2522	2.1866	1.5852	1.0558	0.7929	0.5290
В	$\rightarrow$	Υ	$\downarrow$	5.3424	3.8836	2.7690	1.6912	1.2141	0.7973	0.5971	0.3995
С	$\rightarrow$	Υ	$\uparrow$	6.0734	4.4848	3.2557	2.1894	1.5871	1.0579	0.7944	0.5299
С	$\rightarrow$	Υ	$\downarrow$	5.3424	3.8837	2.7688	1.6911	1.2141	0.7972	0.5971	0.3995
D	$\rightarrow$	Υ	$\uparrow$	5.9410	4.4075	3.1822	2.1851	1.5840	1.0545	0.7918	0.5284
D	$\rightarrow$	Υ	$\downarrow$	5.3345	3.8808	2.7683	1.6934	1.2161	0.7980	0.5977	0.3999
Е	$\rightarrow$	Υ	$\uparrow$	5.9464	4.4116	3.1850	2.1871	1.5855	1.0557	0.7929	0.5291
Е	$\rightarrow$	Υ	$\downarrow$	5.3341	3.8805	2.7685	1.6933	1.2159	0.7980	0.5978	0.3999
F	$\rightarrow$	Υ	$\uparrow$	5.9505	4.4145	3.1870	2.1893	1.5872	1.0576	0.7942	0.5300
F	$\rightarrow$	Υ	$\downarrow$	5.3336	3.8793	2.7683	1.6933	1.2160	0.7980	0.5977	0.3999

#### **Cell Description**

The POSTICG cell is a transparent low integrated latch clock gate. It is therefore compatible for use with positive-edge triggered flops. The high phase of the clock input (CK) is qualified by the latched enable signal (E) and the active-low asynchronous enable (SEN) to create the gated clock (ECK).

#### **Logic Symbol**



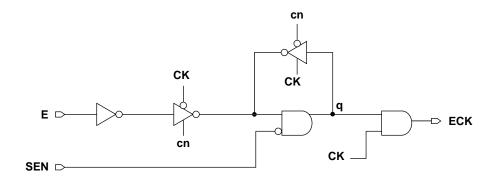
#### **Function Table**

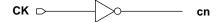
CK	SEN	Е	q[n+1]	ECK[n+1]
0	1	1	1	0
0	0	0	1	0
0	0	1	1	0
0	1	0	0	0
1	Х	Х	q[n]	q[n]

<sup>-</sup> Note: q is an internal node and is not accessible.

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
POSTICGX0P5BA10TR	2.00	3.40
POSTICGX0P6BA10TR	2.00	3.40
POSTICGX0P7BA10TR	2.00	3.40
POSTICGX0P8BA10TR	2.00	3.40
POSTICGX1BA10TR	2.00	3.40
POSTICGX1P2BA10TR	2.00	3.80
POSTICGX1P4BA10TR	2.00	3.80
POSTICGX1P7BA10TR	2.00	3.80
POSTICGX2BA10TR	2.00	3.80
POSTICGX2P5BA10TR	2.00	4.00
POSTICGX3BA10TR	2.00	4.00
POSTICGX3P5BA10TR	2.00	4.60
POSTICGX4BA10TR	2.00	4.60
POSTICGX5BA10TR	2.00	4.80
POSTICGX6BA10TR	2.00	5.20
POSTICGX7P5BA10TR	2.00	6.20
POSTICGX9BA10TR	2.00	6.60
POSTICGX11BA10TR	2.00	7.40
POSTICGX13BA10TR	2.00	7.60
POSTICGX16BA10TR	2.00	8.80





Pin	Power (uW/MHz)										
' ""	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B			
E	0.0015	0.0015	0.0015	0.0016	0.0016	0.0016	0.0017	0.0017			
SEN	0.0007	0.0007	0.0008	0.0008	0.0008	0.0008	0.0009	0.0009			
CK	0.0023	0.0023	0.0023	0.0024	0.0024	0.0025	0.0026	0.0027			
ECK	0.0041	0.0042	0.0043	0.0044	0.0046	0.0051	0.0053	0.0057			

# AC Power (Cont'd.)

Pin	Power (uW/MHz)										
F 1111	X2P0B	X2P5B	X3P0B X3P5B X4P0		X4P0B	X5P0B	X6P0B	X7P5B			
Е	0.0018	0.0019	0.0019	0.0021	0.0022	0.0024	0.0027	0.0031			
SEN	0.0010	0.0011	0.0012	0.0013	0.0014	0.0017	0.0019	0.0024			
CK	0.0029	0.0031	0.0033	0.0036	0.0038	0.0044	0.0048	0.0059			
ECK	0.0062	0.0072	0.0078	0.0090	0.0095	0.0115	0.0131	0.0163			

# AC Power (Cont'd.)

Pin	Power (uW/MHz)							
FIII	X9P0B	X11P0B	X13P0B	X16P0B				
Е	0.0035	0.0040	0.0045	0.0053				
SEN	0.0028	0.0033	0.0037	0.0045				
CK	0.0067	0.0079	0.0088	0.0107				
ECK	0.0188	0.0227	0.0255	0.0306				

# Pin Capacitance

Pin	Capacitance (pF)										
' '''	X0P5B	X0P6B	X0P7B	7B X0P8B X1P0B		X1P2B	X1P4B	X1P7B			
E	0.0010	0.0010	0.0010	0.0010	0.0010	0.0010	0.0010	0.0010			
SEN	0.0010	0.0010	0.0010	0.0010	0.0010	0.0011	0.0011	0.0011			
CK	0.0030	0.0030	0.0030	0.0030	0.0030	0.0031	0.0032	0.0033			

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)										
	X2P0B	X2P5B	X3P0B	X3P0B   X3P5B   X4P		X5P0B	X6P0B	X7P5B			
E	0.0010	0.0010	0.0010	0.0011	0.0011	0.0011	0.0012	0.0012			
SEN	0.0011	0.0012	0.0012	0.0013	0.0013	0.0015	0.0016	0.0022			
CK	0.0034	0.0038	0.0039	0.0044	0.0045	0.0051	0.0055	0.0070			

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)								
F	X9P0B	X11P0B	X13P0B	X16P0B					
Е	0.0013	0.0014	0.0016	0.0018					
SEN	0.0024	0.0026	0.0029	0.0033					
CK	0.0076	0.0090	0.0097	0.0118					

# Delays at 25°C,1.0V, Typical Process

Description	n Intrinsic Delay (ns)							
	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B
CK → ECK ↑	0.0392	0.0400	0.0410	0.0411	0.0400	0.0374	0.0367	0.0365
$CK \to ECK \downarrow$	0.0354	0.0364	0.0373	0.0378	0.0369	0.0354	0.0349	0.0343

#### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description Intrinsic Delay (ns)								
	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B
CK → ECK ↑	0.0360	0.0328	0.0319	0.0336	0.0327	0.0322	0.0319	0.0319
$CK \to ECK \downarrow$	0.0341	0.0330	0.0325	0.0324	0.0323	0.0316	0.0317	0.0303

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)					
	X9P0B	X11P0B	X13P0B	X16P0B		
CK → ECK ↑	0.0313	0.0312	0.0300	0.0304		
$CK \to ECK \downarrow$	0.0304	0.0305	0.0301	0.0297		

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)							
	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B
CK → ECK ↑	4.5966	3.9204	3.4971	3.1267	2.5381	1.9020	1.6540	1.3686
$CK \to ECK \downarrow$	4.0616	3.5664	3.1284	2.8166	2.2999	1.7893	1.5030	1.2063

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)							
	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B
CK → ECK ↑	1.1874	0.9334	0.7887	0.6659	0.5874	0.4703	0.3886	0.3101
$CK \to ECK \downarrow$	1.0242	0.8197	0.6837	0.6037	0.5301	0.4177	0.3503	0.2787

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)					
	X9P0B	X11P0B	X13P0B	X16P0B		
CK → ECK ↑	0.2585	0.2105	0.1796	0.1455		
$CK \  o \ ECK \ \downarrow$	0.2326	0.1888	0.1646	0.1351		

#### Timing Constraints at 25°C,1.0V, Typical Process

Pin	Requirement			Interval (ns)							
			X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B	
	setup $\uparrow$ $\rightarrow$	CK	0.0586	0.0586	0.0586	0.0586	0.0586	0.0586	0.0586	0.0586	
Е	setup $\downarrow$ $\rightarrow$	CK	0.0469	0.0469	0.0469	0.0469	0.0469	0.0469	0.0469	0.0469	
L	hold $\uparrow$ $\rightarrow$	CK	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273	
	hold $\downarrow$ $\rightarrow$	CK	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	
CK	minpwl		0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	

Pin	Poguiromoni	Poquiroment		Interval (ns)							
- 111	Requirement		X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B	
	setup $\uparrow$ $\rightarrow$	CK	0.0586	0.0586	0.0586	0.0586	0.0586	0.0547	0.0547	0.0508	
E	setup $\downarrow$ $\rightarrow$	CK	0.0469	0.0469	0.0469	0.0469	0.0469	0.0430	0.0430	0.0469	
	hold $\uparrow$ $\rightarrow$	CK	-0.0273	-0.0273	-0.0273	-0.0273	-0.0234	-0.0234	-0.0234	-0.0195	
	hold $\downarrow$ $\rightarrow$	CK	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	
CK	minpwl		0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	

**POSTICG** 

Pin	Por	Requirement			Interval (ns)					
F III	Requirement			ıı	X9P0B	X11P0B	X13P0B	X16P0B		
	setup	$\uparrow$	$\rightarrow$	CK	0.0508	0.0469	0.0469	0.0469		
E	setup	$\downarrow$	$\rightarrow$	CK	0.0430	0.0430	0.0430	0.0391		
_	hold	$\uparrow$	$\rightarrow$	CK	-0.0195	-0.0195	-0.0195	-0.0156		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0312	-0.0312	-0.0312	-0.0273		
CK	minpwl			0.8830	0.8830	0.8830	0.8830			

#### **Cell Description**

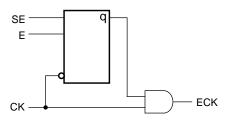
The PREICG cell is a transparent low integrated latch clock gate. It is therefore compatible for use with positive-edge triggered flops. The high phase of the clock input (CK) is qualified by the latched enable signal (E) and the active-high scan enable (SE) to create the gated clock (ECK).

# **Function Table**

СК	SE	Е	q[n+1]	ECK[n+1]
1	Х	Х	q[n]	q[n]
0	0	0	0	0
0	0	1	1	0
0	1	0	1	0
0	1	1	1	0

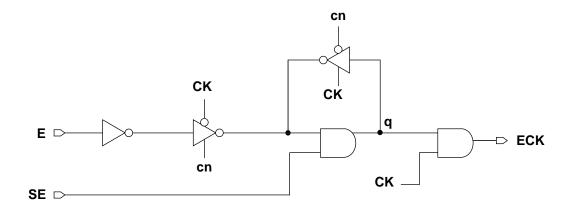
- Note: q is an internal node and is not accessible.

#### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
PREICGX0P5BA10TR	2.00	3.60
PREICGX0P6BA10TR	2.00	3.60
PREICGX0P7BA10TR	2.00	3.60
PREICGX0P8BA10TR	2.00	3.60
PREICGX1BA10TR	2.00	3.60
PREICGX1P2BA10TR	2.00	3.80
PREICGX1P4BA10TR	2.00	3.80
PREICGX1P7BA10TR	2.00	3.80
PREICGX2BA10TR	2.00	3.80
PREICGX2P5BA10TR	2.00	4.00
PREICGX3BA10TR	2.00	4.00
PREICGX3P5BA10TR	2.00	4.60
PREICGX4BA10TR	2.00	4.60
PREICGX5BA10TR	2.00	4.80
PREICGX6BA10TR	2.00	5.20
PREICGX7P5BA10TR	2.00	6.20
PREICGX9BA10TR	2.00	6.60
PREICGX11BA10TR	2.00	7.40
PREICGX13BA10TR	2.00	7.80
PREICGX16BA10TR	2.00	9.20



Pin				Power (u	ıW/MHz)			
F 1111	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B
Е	0.0018	0.0018	0.0018	0.0018	0.0019	0.0019	0.0019	0.0020
SE	0.0023	0.0023	0.0023	0.0023	0.0024	0.0024	0.0024	0.0025
CK	0.0022	0.0022	0.0023	0.0023	0.0023	0.0024	0.0025	0.0026
ECK	0.0039	0.0041	0.0042	0.0043	0.0045	0.0051	0.0053	0.0056

# AC Power (Cont'd.)

Pin				Power (u	ıW/MHz)			
FIII	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B
Е	0.0020	0.0021	0.0022	0.0024	0.0024	0.0028	0.0030	0.0035
SE	0.0025	0.0026	0.0027	0.0029	0.0030	0.0034	0.0036	0.0047
CK	0.0027	0.0030	0.0032	0.0036	0.0039	0.0044	0.0048	0.0059
ECK	0.0060	0.0071	0.0077	0.0089	0.0095	0.0113	0.0129	0.0157

# AC Power (Cont'd.)

Pin	Power (uW/MHz)							
FIII	X9P0B	X11P0B	X13P0B	X16P0B				
Е	0.0042	0.0049	0.0053	0.0062				
SE	0.0055	0.0062	0.0069	0.0079				
CK	0.0067	0.0079	0.0089	0.0107				
ECK	0.0182	0.0221	0.0246	0.0297				

# Pin Capacitance

Pin				Capacita	nce (pF)			
• •••	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B
Е	0.0009	0.0009	0.0009	0.0009	0.0009	0.0009	0.0009	0.0009
SE	0.0011	0.0011	0.0011	0.0011	0.0011	0.0011	0.0011	0.0011
CK	0.0027	0.0027	0.0027	0.0027	0.0027	0.0029	0.0029	0.0030

# Pin Capacitance (Cont'd.)

Pin				Capacita	nce (pF)			
F	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B
Е	0.0009	0.0009	0.0009	0.0010	0.0010	0.0011	0.0011	0.0012
SE	0.0011	0.0011	0.0012	0.0012	0.0013	0.0013	0.0014	0.0018
CK	0.0031	0.0034	0.0036	0.0043	0.0045	0.0050	0.0054	0.0068

# Pin Capacitance (Cont'd.)

Pin	Capacitance (pF)							
	X9P0B	X11P0B	X13P0B	X16P0B				
Е	0.0014	0.0015	0.0016	0.0018				
SE	0.0021	0.0023	0.0025	0.0027				
CK	0.0074	0.0088	0.0096	0.0117				

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)								
	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B	
CK → ECK ↑	0.0374	0.0389	0.0398	0.0409	0.0397	0.0387	0.0379	0.0370	
$CK \to ECK \downarrow$	0.0327	0.0341	0.0349	0.0358	0.0349	0.0344	0.0338	0.0334	

#### Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)								
	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B	
CK → ECK ↑	0.0364	0.0361	0.0352	0.0342	0.0337	0.0336	0.0328	0.0321	
$CK \to ECK \downarrow$	0.0333	0.0334	0.0330	0.0326	0.0329	0.0323	0.0319	0.0304	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	Intrinsic Delay (ns)					
	X9P0B	X11P0B	X13P0B	X16P0B		
CK → ECK ↑	0.0315	0.0316	0.0305	0.0307		
$CK \to ECK \downarrow$	0.0304	0.0305	0.0302	0.0298		

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)							
	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B
CK → ECK ↑	4.5747	3.8821	3.3774	2.9877	2.4823	1.9540	1.6912	1.4034
$CK \to ECK \downarrow$	3.9749	3.4027	2.9288	2.6109	2.1196	1.6855	1.4488	1.2319

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description				K <sub>load</sub> (ns/pF)				
	X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B
CK → ECK ↑	1.2185	0.9486	0.8036	0.6708	0.5918	0.4737	0.3904	0.3102
$CK \to ECK \downarrow$	1.0476	0.8930	0.7306	0.6048	0.5318	0.4199	0.3506	0.2799

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)					
	X9P0B	X11P0B	X13P0B	X16P0B		
CK → ECK ↑	0.2585	0.2108	0.1793	0.1452		
$CK \to ECK \downarrow$	0.2326	0.1888	0.1649	0.1350		

Pin	Por	Requirement				Interval (ns)								
	Requirement			11	X0P5B	X0P6B	X0P7B	X0P8B	X1P0B	X1P2B	X1P4B	X1P7B		
	setup	$\uparrow$	$\rightarrow$	CK	0.0586	0.0586	0.0586	0.0586	0.0586	0.0586	0.0586	0.0586		
E	setup	$\downarrow$	$\rightarrow$	CK	0.0664	0.0664	0.0664	0.0664	0.0664	0.0664	0.0664	0.0703		
	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273	-0.0273		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0508	-0.0508	-0.0508	-0.0508	-0.0508	-0.0508	-0.0508	-0.0508		
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0625	0.0625	0.0625	0.0625	0.0625	0.0625	0.0625		
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0703	0.0703	0.0703	0.0703	0.0703	0.0703	0.0703		
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312	-0.0312		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0508	-0.0508	-0.0547	-0.0508	-0.0547	-0.0547	-0.0547	-0.0547		
CK		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830		

# Timing Constraints at 25°C,1.0V, Typical Process (Cont'd.)

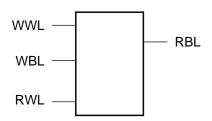
Pin	Pin Requireme		mor	<b>.</b> +				Interv	al (ns)			
F III	Nequirement			X2P0B	X2P5B	X3P0B	X3P5B	X4P0B	X5P0B	X6P0B	X7P5B	
	setup	$\uparrow$	$\rightarrow$	CK	0.0586	0.0586	0.0586	0.0547	0.0547	0.0508	0.0508	0.0469
Е	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0703	0.0703	0.0664	0.0664	0.0625	0.0625	0.0586
	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0273	-0.0273	-0.0234	-0.0234	-0.0234	-0.0195	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0508	-0.0508	-0.0508	-0.0508	-0.0508	-0.0469	-0.0469	-0.0430
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0586	0.0586	0.0586	0.0586	0.0547	0.0508	0.0508
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0703	0.0703	0.0664	0.0664	0.0664	0.0625	0.0625
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0312	-0.0312	-0.0312	-0.0273	-0.0273	-0.0234	-0.0234	-0.0234
	hold	$\downarrow$	$\rightarrow$	CK	-0.0547	-0.0547	-0.0547	-0.0508	-0.0508	-0.0508	-0.0469	-0.0469
CK		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830	0.8830

Pin	Por	anir.	emer	<b>1</b>	Interval (ns)					
F	ive.	quii	CIIICI	11	X9P0B	X11P0B	X13P0B	X16P0B		
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0469	0.0430	0.0430		
E	setup	$\downarrow$	$\rightarrow$	CK	0.0586	0.0547	0.0547	0.0508		
_	hold	$\uparrow$	$\rightarrow$	CK	-0.0195	-0.0195	-0.0156	-0.0156		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0430	-0.0430	-0.0391	-0.0391		
	setup	$\uparrow$	$\rightarrow$	CK	0.0508	0.0508	0.0508	0.0469		
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0586	0.0586	0.0547		
J.	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0234	-0.0195	-0.0195		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0469	-0.0469	-0.0430	-0.0430		
CK	minpwl			0.8830	0.8830	0.8830	0.8830			

#### **Cell Description**

The RF1R1WS is a one write-port and one read-port register file cell. All word-lines are single rail and active-high. All bit-lines are single rail. The cell is marked not to be used by synthesis flows.

#### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
RF1R1WSX1MA10TR	2.00	3.20
RF1R1WSX1P4MA10TR	2.00	4.00
RF1R1WSX2MA10TR	2.00	4.00

#### **Function Table**

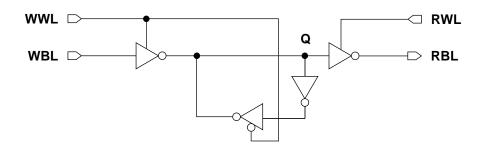
WBL	WWL	nm[n+1]
0	1	1
1	1	0
Х	0	nm[n]

<sup>-</sup> Functions for Write Operations

# Function Table (Cont'd.)

RWL	nm	RBL
1	0	1
1	1	0
0	0	Hi-Z
0	1	Hi-Z

<sup>-</sup> Functions for Read Operations



Pin	Power (uW/MHz)						
-	X1P0M	X1P4M	X2P0M				
WWL	0.0026	0.0028	0.0029				
WBL	0.0069	0.0088	0.0102				
RWL	0.0018	0.0024	0.0029				
RBL	0.0046	0.0066	0.0080				

# Pin Capacitance

Pin	Capacitance (pF)						
F 1111	X1P0M	X1P4M	X2P0M				
WWL	0.0022	0.0024	0.0024				
WBL	0.0016	0.0017	0.0018				
RWL	0.0015	0.0020	0.0024				
RBL	0.0013	0.0013	0.0016				

# Delays at 25°C,1.0V, Typical Process

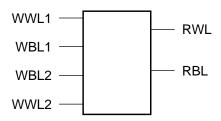
Desc	ription		Intri	Intrinsic Delay (ns) K <sub>load</sub> (ns			Հ <sub>load</sub> (ns/pF	s/pF)	
			X1P0M	X1P4M	X2P0M	X1P0M	X1P4M	X2P0M	
WWL ->	RBL	<b>↑</b>	0.0350	0.0367	0.0368	3.3470	2.3002	1.6700	
$WWL \rightarrow$	RBL	$\downarrow$	0.0523	0.0543	0.0551	2.3778	1.6398	1.1722	
$WBL  \rightarrow $	RBL	$\uparrow$	0.0411	0.0423	0.0421	3.3470	2.3003	1.6703	
$WBL  \rightarrow $	RBL	$\downarrow$	0.0533	0.0558	0.0569	2.3783	1.6398	1.1722	
$RWL \rightarrow$	RBL	$\uparrow$	0.0118	0.0100	0.0094	3.3134	2.2826	1.6578	
$RWL \rightarrow$	RBL	$\downarrow$	0.0060	0.0051	0.0050	2.3435	1.6125	1.1500	

Pin	Poquiroment				lı	nterval (ns	5)
F	I. C	Requirement		X1P0M	X1P4M	X2P0M	
WWL	minpwh				0.8830	0.8830	0.8830
	setup	$\uparrow$	$\rightarrow$	WWL	0.0352	0.0391	0.0391
WBL	setup	$\downarrow$	$\rightarrow$	WWL	0.0391	0.0391	0.0430
VVDL	hold	$\uparrow$	$\rightarrow$	WWL	-0.0273	-0.0273	-0.0273
	hold	$\downarrow$	$\rightarrow$	WWL	-0.0234	-0.0273	-0.0273

#### **Cell Description**

The RF1R2WS is a two write-port and one read-port register file cell. All word-lines are single rail and active-high. The user is required to ensure the two write word-lines are never active at the same time. All bit-lines are single rail. The cell is marked not to be used by synthesis flows.

#### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
RF1R2WSX1MA10TR	2.00	4.80
RF1R2WSX1P4MA10TR	2.00	5.60
RF1R2WSX2MA10TR	2.00	5.60

#### **Function Table**

WBL1	WBL2	WWL1	WWL2	nm[n+1]
1	0	1	1	х
0	1	1	1	Х
1	1	1	1	0
0	0	1	1	1
1	х	1	0	0
0	х	1	0	1
х	1	0	1	0
х	0	0	1	1
Х	Х	0	0	nm[n]

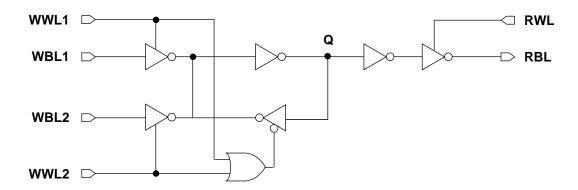
<sup>-</sup> Functions for Write Operations

#### Function Table (Cont'd.)

RWL	nm	RBL
1	0	1
1	1	0
0	0	Hi-Z
0	1	Hi-Z

- Functions for Read Operations

RF1R2WS



Pin	Power (uW/MHz)					
' '''	X1P0M	X1P4M	X2P0M			
WBL1	0.0084	0.0103	0.0117			
WBL2	0.0085	0.0104	0.0118			
WWL1	0.0049	0.0068	0.0079			
WWL2	0.0052	0.0071	0.0082			
RWL	0.0021	0.0028	0.0033			
RBL	0.0018	0.0018	0.0022			

# Pin Capacitance

Pin	Capacitance (pF)					
F III	X1P0M	X1P4M	X2P0M			
WBL1	0.0015	0.0015	0.0015			
WBL2	0.0015	0.0015	0.0015			
WWL1	0.0016	0.0017	0.0017			
WWL2	0.0016	0.0017	0.0017			
RWL	0.0015	0.0021	0.0025			
RBL	0.0013	0.0015	0.0017			

# Delays at 25°C,1.0V, Typical Process

De	scrip	otion		Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)		
				X1P0M	X1P4M	X2P0M	X1P0M	X1P4M	X2P0M
WBL1	$\rightarrow$	RBL	1	0.0487	0.0513	0.0526	3.3217	2.2812	1.6595
WBL1	$\rightarrow$	RBL	$\downarrow$	0.0610	0.0669	0.0701	2.3719	1.6646	1.1998
WBL2	$\rightarrow$	RBL	1	0.0489	0.0522	0.0535	3.3231	2.2826	1.6604
WBL2	$\rightarrow$	RBL	$\downarrow$	0.0639	0.0687	0.0715	2.3787	1.6675	1.2015
WWL1	$\rightarrow$	RBL	$\rightarrow$	0.0426	0.0454	0.0466	3.3216	2.2811	1.6594
WWL1	$\rightarrow$	RBL	$\downarrow$	0.0592	0.0638	0.0661	2.3720	1.6643	1.1998
WWL2	$\rightarrow$	RBL	$\uparrow$	0.0437	0.0467	0.0478	3.3233	2.2825	1.6603
WWL2	$\rightarrow$	RBL	$\downarrow$	0.0613	0.0652	0.0674	2.3783	1.6673	1.2014
RWL	$\rightarrow$	RBL	$\uparrow$	0.0119	0.0097	0.0091	3.2840	2.2606	1.6438
RWL	$\rightarrow$	RBL	$\downarrow$	0.0061	0.0054	0.0052	2.3206	1.6212	1.1635

RF1R2WS

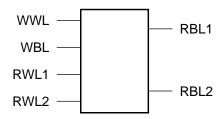
# Process Technology: CLN65G+

Pin	Requirement				Interval (ns)			
""		Requirement			X1P0M	X1P4M	X2P0M	
	setup	$\uparrow$	$\rightarrow$	WWL1	0.0469	0.0469	0.0508	
WBL1	setup	$\downarrow$	$\rightarrow$	WWL1	0.0469	0.0547	0.0547	
WBLI	hold	$\uparrow$	$\rightarrow$	WWL1	-0.0312	-0.0352	-0.0352	
	hold	$\downarrow$	$\rightarrow$	WWL1	-0.0312	-0.0352	-0.0352	
	setup	$\uparrow$	$\rightarrow$	WWL2	0.0430	0.0469	0.0508	
WBL2	setup	$\downarrow$	$\rightarrow$	WWL2	0.0469	0.0508	0.0547	
VVDLZ	hold	$\uparrow$	$\rightarrow$	WWL2	-0.0312	-0.0352	-0.0391	
	hold	$\downarrow$	$\rightarrow$	WWL2	-0.0312	-0.0352	-0.0391	
WWL1		miı	npwh		0.8830	0.8830	0.8830	
WWL2		miı	npwh		0.8830	0.8830	0.8830	

## **Cell Description**

The RF2R1WS is a one write-port and two read-port register file cell. The word-line is single rail and active-high. All bit-lines are single rail. The cell is marked not to be used by synthesis flows.

#### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
RF2R1WSX1MA10TR	2.00	4.40
RF2R1WSX1P4MA10TR	2.00	6.00
RF2R1WSX2MA10TR	2.00	6.00

#### **Function Table**

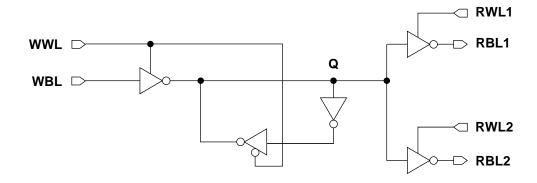
WBL	WWL	nm[n+1]
0	1	1
1	1	0
Х	0	nm[n]

<sup>-</sup> Functions for Write Operations

## Function Table (Cont'd.)

	-	-
RWL1/rdwl2	nm	RBL1/rdbl2
1	1	0
1	0	1
0	0	Hi-Z
0	1	Hi-Z

<sup>-</sup> Functions for Read Operations



Pin	Power (uW/MHz)					
""	X1P0M	X1P4M	X2P0M			
WBL	0.0103	0.0139	0.0172			
WWL	0.0062	0.0103	0.0127			
RWL1	0.0020	0.0027	0.0032			
RWL2	0.0020	0.0027	0.0033			
RBL1	0.0027	0.0034	0.0043			

# Pin Capacitance

Pin	Capacitance (pF)					
""	X1P0M	X1P4M	X2P0M			
WBL	0.0018	0.0018	0.0017			
WWL	0.0017	0.0017	0.0017			
RWL1	0.0017	0.0023	0.0028			
RWL2	0.0017	0.0024	0.0029			
RBL1	0.0013	0.0013	0.0015			
RBL2	0.0013	0.0014	0.0017			

## Delays at 25°C,1.0V, Typical Process

D	Description			Intri	nsic Delay	(ns)	K <sub>load</sub> (ns/pF)		
				X1P0M	X1P4M	X2P0M	X1P0M	X1P4M	X2P0M
WBL	$\rightarrow$	RBL1	$\uparrow$	0.0456	0.0537	0.0587	3.3201	2.3022	1.6794
WBL	$\rightarrow$	RBL1	$\downarrow$	0.0619	0.0755	0.0828	2.3240	1.6671	1.1995
WWL	$\rightarrow$	RBL1	$\uparrow$	0.0403	0.0488	0.0532	3.3198	2.3019	1.6794
WWL	$\rightarrow$	RBL1	$\downarrow$	0.0595	0.0725	0.0784	2.3242	1.6671	1.1995
RWL1	$\rightarrow$	RBL1	$\uparrow$	0.0115	0.0089	0.0085	3.2836	2.2786	1.6599
RWL1	$\rightarrow$	RBL1	$\downarrow$	0.0058	0.0051	0.0049	2.2707	1.6053	1.1466
WBL	$\rightarrow$	RBL2	1	0.0459	0.0542	0.0587	3.2919	2.2901	1.6677
WBL	$\rightarrow$	RBL2	$\downarrow$	0.0623	0.0760	0.0829	2.3484	1.6764	1.2016
WWL	$\rightarrow$	RBL2	$\uparrow$	0.0405	0.0493	0.0532	3.2916	2.2899	1.6677
WWL	$\rightarrow$	RBL2	$\downarrow$	0.0599	0.0730	0.0784	2.3485	1.6767	1.2016
RWL2	$\rightarrow$	RBL2	1	0.0118	0.0099	0.0093	3.2541	2.2649	1.6473
RWL2	$\rightarrow$	RBL2	$\downarrow$	0.0061	0.0050	0.0050	2.2967	1.6171	1.1495

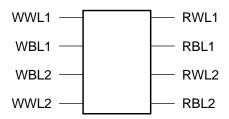
Pin	Requirement		Interval (ns)				
	176	Requirement		X1P0M	X1P4M	X2P0M	
	setup	$\uparrow$	$\rightarrow$	WWL	0.0430	0.0469	0.0547
WBL	setup	$\downarrow$	$\rightarrow$	WWL	0.0469	0.0547	0.0625
VVDL	hold	$\uparrow$	$\rightarrow$	WWL	-0.0273	-0.0352	-0.0391
	hold	$\downarrow$	$\rightarrow$	WWL	-0.0273	-0.0352	-0.0391
WWL		min	pwh		0.8830	0.8830	0.8830

Process Technology:	RF2R1WS
CLN65G+	
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#### **Cell Description**

The RF2R2WS is a two write-port and two read-port register file cell. All word-lines are single rail and active-high. The user is required to ensure the two write word-lines are never active at the same time. All bit-lines are single rail. The cell is marked not to be used by synthesis flows.

#### **Logic Symbol**



#### **Cell Size**

Drive Strength	Height (um)	Width (um)
RF2R2WSX1MA10TR	2.00	6.00
RF2R2WSX1P4MA10TR	2.00	7.60
RF2R2WSX2MA10TR	2.00	7.60

#### **Function Table**

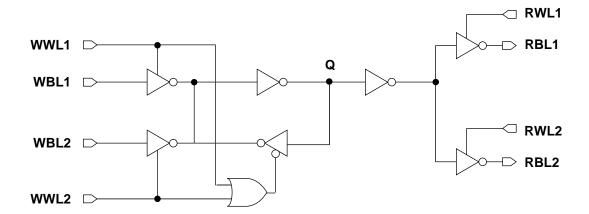
WBL1	WBL2	WWL1	WWL2	nm[n+1]
1	0	1	1	х
0	1	1	1	х
1	1	1	1	0
0	0	1	1	1
1	х	1	0	0
0	х	1	0	1
х	1	0	1	0
х	0	0	1	1
х	х	0	0	nm[n]

<sup>-</sup> Functions for Write Operations

#### Function Table (Cont'd.)

		-
RWL1/rdwl2	nm	RBL1/rdbl2
1	1	0
1	0	1
0	0	Hi-Z
0	1	Hi-Z

<sup>-</sup> Functions for Read Operations



Pin	Power (uW/MHz)					
FIII	X1P0M	X1P4M	X2P0M			
WBL1	0.0114	0.0156	0.0193			
WBL2	0.0116	0.0158	0.0194			
WWL1	0.0074	0.0110	0.0137			
WWL2	0.0077	0.0113	0.0139			
RWL1	0.0023	0.0030	0.0035			
RWL2	0.0023	0.0031	0.0037			
RBL1	0.0027	0.0034	0.0043			

# Pin Capacitance

Pin	Capacitance (pF)					
""	X1P0M	X1P4M	X2P0M			
WBL1	0.0015	0.0015	0.0015			
WBL2	0.0015	0.0015	0.0015			
WWL1	0.0016	0.0017	0.0017			
WWL2	0.0016	0.0017	0.0017			
RWL1	0.0014	0.0020	0.0023			
RWL2	0.0017	0.0024	0.0029			
RBL1	0.0013	0.0013	0.0016			
RBL2	0.0013	0.0013	0.0017			

# Delays at 25°C,1.0V, Typical Process

Description			Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)			
				X1P0M	X1P4M	X2P0M	X1P0M	X1P4M	X2P0M
WBL1	$\rightarrow$	RBL1	$\uparrow$	0.0567	0.0639	0.0678	3.3103	2.2872	1.6701
WBL1	$\rightarrow$	RBL1	$\downarrow$	0.0752	0.0868	0.0930	2.3827	1.7301	1.2481
WBL2	$\rightarrow$	RBL1	$\uparrow$	0.0577	0.0643	0.0679	3.3128	2.2881	1.6708
WBL2	$\rightarrow$	RBL1	$\downarrow$	0.0780	0.0883	0.0935	2.3892	1.7322	1.2481
WWL1	$\rightarrow$	RBL1	<b>↑</b>	0.0514	0.0583	0.0616	3.3103	2.2868	1.6699
WWL1	$\rightarrow$	RBL1	$\downarrow$	0.0725	0.0827	0.0875	2.3829	1.7302	1.2482
WWL2	$\rightarrow$	RBL1	$\uparrow$	0.0529	0.0592	0.0621	3.3125	2.2884	1.6707
WWL2	$\rightarrow$	RBL1	$\downarrow$	0.0747	0.0839	0.0878	2.3889	1.7320	1.2480
RWL1	$\rightarrow$	RBL1	$\uparrow$	0.0116	0.0094	0.0091	3.2651	2.2562	1.6466
RWL1	$\rightarrow$	RBL1	$\downarrow$	0.0058	0.0051	0.0050	2.2956	1.6490	1.1829
WBL1	$\rightarrow$	RBL2	$\uparrow$	0.0571	0.0645	0.0680	3.3022	2.2912	1.6667
WBL1	$\rightarrow$	RBL2	$\downarrow$	0.0753	0.0873	0.0931	2.3853	1.7047	1.2219
WBL2	$\rightarrow$	RBL2	$\uparrow$	0.0582	0.0649	0.0681	3.3046	2.2923	1.6673
WBL2	$\rightarrow$	RBL2	$\downarrow$	0.0782	0.0887	0.0936	2.3919	1.7068	1.2219
WWL1	$\rightarrow$	RBL2	$\uparrow$	0.0518	0.0589	0.0618	3.3021	2.2911	1.6670
WWL1	$\rightarrow$	RBL2	$\downarrow$	0.0726	0.0832	0.0876	2.3853	1.7048	1.2220
WWL2	$\rightarrow$	RBL2	$\uparrow$	0.0533	0.0598	0.0624	3.3044	2.2927	1.6672
WWL2	$\rightarrow$	RBL2	$\downarrow$	0.0748	0.0843	0.0879	2.3915	1.7066	1.2218
RWL2	$\rightarrow$	RBL2	$\uparrow$	0.0118	0.0101	0.0094	3.2563	2.2598	1.6429

Process Technology:

CLN65G+

RF2R2WS

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

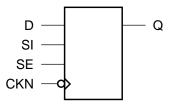
Description	Intrinsic Delay (ns)			K <sub>load</sub> (ns/pF)		
	X1P0M	X1P4M	X2P0M	X1P0M	X1P4M	X2P0M
RWL2 → RBL2 ↓	0.0061	0.0051	0.0051	2.2997	1.6235	1.1556

Pin	Requirement				Interval (ns)			
""		<del>c</del> qu	II CIII	511L	X1P0M	X1P4M	X2P0M	
	setup	$\uparrow$	$\rightarrow$	WWL1	0.0508	0.0586	0.0625	
WBL1	setup	$\downarrow$	$\rightarrow$	WWL1	0.0586	0.0664	0.0742	
WBLI	hold	$\uparrow$	$\rightarrow$	WWL1	-0.0391	-0.0430	-0.0469	
	hold	$\downarrow$	$\rightarrow$	WWL1	-0.0391	-0.0469	-0.0508	
	setup	$\uparrow$	$\rightarrow$	WWL2	0.0508	0.0586	0.0625	
WBL2	setup	$\downarrow$	$\rightarrow$	WWL2	0.0586	0.0664	0.0703	
VVDLZ	hold	$\uparrow$	$\rightarrow$	WWL2	-0.0391	-0.0430	-0.0469	
	hold	$\downarrow$	$\rightarrow$	WWL2	-0.0430	-0.0469	-0.0508	
WWL1	minpwh				0.8830	0.8830	0.8830	
WWL2		miı	npwh		0.8830	0.8830	0.8830	

#### **Cell Description**

The SDFFNQ cell is a negative-edge triggered, static D-type flip-flop with scan input (SI) and active-high scan enable (SE).

# **Logic Symbol**

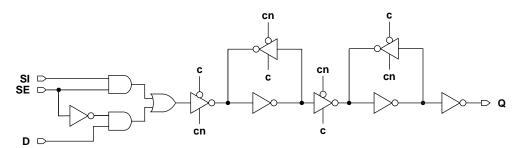


#### **Function Table**

D	SI	SE	CKN	Q[n+1]
1	Х	0	_	1
0	Х	0	_	0
Х	Х	Х		Q[n]
Х	1	1		1
Х	0	1		0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFNQX1MA10TR	2.00	5.20
SDFFNQX2MA10TR	2.00	5.60
SDFFNQX3MA10TR	2.00	6.00



Pin	Power (uW/MHz)							
F	X1P0M	X2P0M	X3P0M					
SI	0.0067	0.0079	0.0085					
SE	0.0063	0.0073	0.0078					
D	0.0058	0.0068	0.0071					
CKN	0.0048	0.0054	0.0061					
Q	0.0049	0.0066	0.0085					

# Pin Capacitance

Pin	Capacitance (pF)						
' ""	X1P0M	X2P0M	X3P0M				
SI	0.0007	0.0007	0.0007				
SE	0.0023	0.0025	0.0025				
D	0.0014	0.0016	0.0016				
CKN	0.0010	0.0010	0.0011				

# Delays at 25°C,1.0V, Typical Process

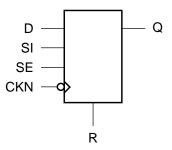
Description	Intri	nsic Delay	(ns)	K <sub>load</sub> (ns/pF)		
	X1P0M	X2P0M	X3P0M	X1P0M	X2P0M	X3P0M
CKN → Q ↑	0.0908	0.0858	0.0873	2.3366	1.1589	0.7819
$CKN \ \to \ Q \ \downarrow$	0.0855	0.0837	0.0870	1.4532	0.7200	0.4594

Pin	Po	Au ii	omo	nŧ	Interval (ns)		
F	Requirement				X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CKN	0.0664	0.0742	0.0781
SI	setup	$\downarrow$	$\rightarrow$	CKN	0.1172	0.1289	0.1367
31	hold	$\uparrow$	$\rightarrow$	CKN	-0.0352	-0.0430	-0.0469
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0742	-0.0742	-0.0820
	setup	$\uparrow$	$\rightarrow$	CKN	0.1250	0.1367	0.1445
SE	setup	$\downarrow$	$\rightarrow$	CKN	0.0508	0.0430	0.0430
SE	hold	$\uparrow$	$\rightarrow$	CKN	-0.0312	-0.0430	-0.0430
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0234	-0.0195	-0.0195
	setup	1	$\rightarrow$	CKN	0.0273	0.0195	0.0195
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0469	0.0430	0.0430
	hold	$\uparrow$	$\rightarrow$	CKN	-0.0039	0.0000	0.0000
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0273	-0.0234	-0.0234
CKN		min	pwl		0.8830	0.8830	0.8830
CININ		min	pwh		0.8830	0.8830	0.8830

#### **Cell Description**

The SDFFNRPQ cell is a negative-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and asynchronous active-high reset (R).

# **Logic Symbol**

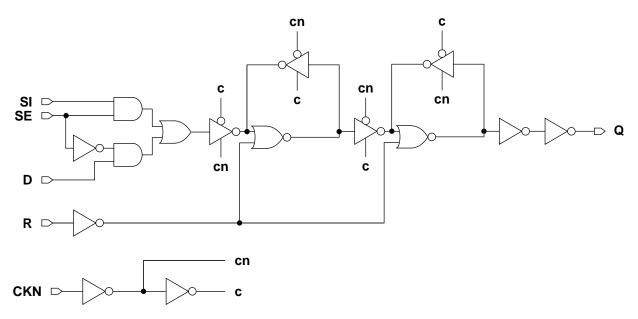


#### **Function Table**

	R	D	SI	SE	CKN	Q[n+1]
Ī	1	Х	Х	Х	_	0
Ī	0	1	Х	0	_	1
Ī	0	0	Х	0		0
Ī	0	Х	0	1	_	0
Ī	0	Х	1	1		1
Į	0	Х	Х	Х		Q[n]

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFNRPQX1MA10TR	2.00	5.80
SDFFNRPQX2MA10TR	2.00	6.40
SDFFNRPQX3MA10TR	2.00	6.60



Pin	Power (uW/MHz)							
	X1P0M	X2P0M	X3P0M					
SI	0.0067	0.0077	0.0082					
SE	0.0071	0.0084	0.0087					
D	0.0059	0.0069	0.0073					
CKN	0.0050	0.0056	0.0062					
R	0.0016	0.0021	0.0024					
Q	0.0056	0.0071	0.0090					

# Pin Capacitance

Pin	Capacitance (pF)					
FIII	X1P0M	X2P0M	X3P0M			
SI	0.0007	0.0007	0.0007			
SE	0.0023	0.0025	0.0025			
D	0.0013	0.0016	0.0016			
CKN	0.0010	0.0010	0.0011			
R	0.0016	0.0017	0.0017			

# Delays at 25°C,1.0V, Typical Process

Description				Intri	nsic Delay	(ns)	K <sub>load</sub> (ns/pF)		
				X1P0M	X2P0M	X3P0M	X1P0M	X2P0M	X3P0M
CKN	$\rightarrow$	Q	$\uparrow$	0.1037	0.0945	0.0981	2.3118	1.1484	0.7781
CKN	$\rightarrow$	Q	$\downarrow$	0.0976	0.0938	0.0969	1.4570	0.7093	0.4560
R	$\rightarrow$	Q	$\downarrow$	0.0566	0.0578	0.0658	1.4547	0.7084	0.4557

**SDFFNRPQ** 

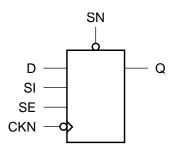
# Process Technology: CLN65G+

Din	Pin Requirement			Interval (ns)			
FIII	, Ne	quii	eme	111	X1P0M	X2P0M	X3P0M
SI	setup	$\uparrow$	$\rightarrow$	CKN	0.0703	0.0781	0.0781
	setup	$\downarrow$	$\rightarrow$	CKN	0.1211	0.1367	0.1406
Si	hold	$\uparrow$	$\rightarrow$	CKN	-0.0352	-0.0391	-0.0430
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0820	-0.0898	-0.0859
	setup	$\uparrow$	$\rightarrow$	CKN	0.1250	0.1445	0.1484
SE	setup	$\downarrow$	$\rightarrow$	CKN	0.0547	0.0469	0.0469
	hold	$\uparrow$	$\rightarrow$	CKN	-0.0312	-0.0391	-0.0391
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0234	-0.0195	-0.0195
	setup	$\uparrow$	$\rightarrow$	CKN	0.0352	0.0234	0.0234
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0469	0.0430	0.0469
	hold	$\uparrow$	$\rightarrow$	CKN	-0.0039	0.0039	0.0039
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0312	-0.0273	-0.0273
CKN		min	pwl		0.8830	0.8830	0.8830
CKIN		min	pwh		0.8830	0.8830	0.8830
		min	pwh		0.8830	0.8830	0.8830
R		reco	very		-0.0234	-0.0273	-0.0273
	removal				0.0625	0.0703	0.0703

#### **Cell Description**

The SDFFNSQ cell is a negative-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and asynchronous active-low set (SN).

# **Logic Symbol**

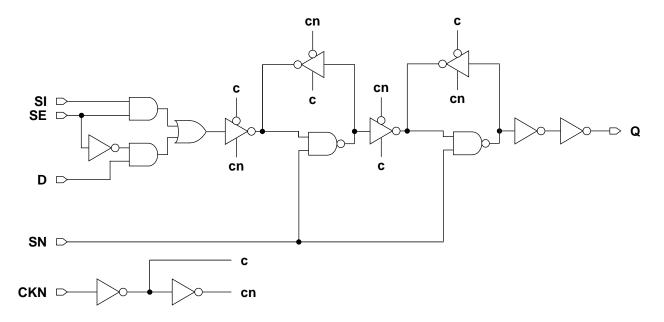


#### **Function Table**

SN	D	SI	SE	CKN	Q
1	1	Х	0	_	1
1	0	Х	0	_	0
1	Х	Х	Х		Q[n]
1	Х	1	1	_	1
1	Х	0	1	_	0
0	Х	Х	Х	Х	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFNSQX1MA10TR	2.00	6.20
SDFFNSQX2MA10TR	2.00	6.40
SDFFNSQX3MA10TR	2.00	7.00



Pin	Power (uW/MHz)								
F 1111	X1P0M	X2P0M	X3P0M						
SI	0.0069	0.0080	0.0084						
SE	0.0073	0.0083	0.0087						
D	0.0062	0.0072	0.0076						
CKN	0.0051	0.0057	0.0064						
SN	0.0017	0.0021	0.0024						
Q	0.0053	0.0070	0.0092						

# Pin Capacitance

Pin	Capacitance (pF)							
F 1111	X1P0M	X2P0M	X3P0M					
SI	0.0007	0.0007	0.0007					
SE	0.0023	0.0025	0.0025					
D	0.0014	0.0017	0.0017					
CKN	0.0010	0.0010	0.0011					
SN	0.0017	0.0018	0.0018					

# Delays at 25°C,1.0V, Typical Process

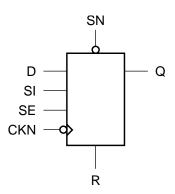
De	scrip	tion		Intri	nsic Delay	(ns)	K <sub>load</sub> (ns/pF)		
				X1P0M	X2P0M	X3P0M	X1P0M	X2P0M	X3P0M
CKN	$\rightarrow$	Q	<b>↑</b>	0.0951	0.0921	0.0958	2.3355	1.1640	0.7815
CKN	$\rightarrow$	Q	$\downarrow$	0.0920	0.0901	0.0962	1.4538	0.7258	0.4603
SN	$\rightarrow$	Q	1	0.0575	0.0608	0.0699	2.3329	1.1639	0.7813

g								
Pin	Re	auir	-ama	nt	Interval (ns)			
' '''	Requirement			X1P0M	X2P0M	X3P0M		
	setup	$\uparrow$	$\rightarrow$	CKN	0.0742	0.0820	0.0859	
SI	setup	$\downarrow$	$\rightarrow$	CKN	0.1133	0.1211	0.1289	
31	hold	$\uparrow$	$\rightarrow$	CKN	-0.0391	-0.0469	-0.0469	
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0703	-0.0703	-0.0703	
	setup	$\uparrow$	$\rightarrow$	CKN	0.1211	0.1328	0.1367	
SE	setup	$\downarrow$	$\rightarrow$	CKN	0.0547	0.0469	0.0508	
SE	hold	$\uparrow$	$\rightarrow$	CKN	-0.0352	-0.0469	-0.0469	
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0273	-0.0195	-0.0234	
	setup	$\uparrow$	$\rightarrow$	CKN	0.0352	0.0273	0.0273	
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0430	0.0391	0.0430	
	hold	$\uparrow$	$\rightarrow$	CKN	-0.0078	0.0000	0.0000	
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0273	-0.0195	-0.0195	
CKN		min	pwl		0.8830	0.8830	0.8830	
CINI		min	pwh		0.8830	0.8830	0.8830	
		min	pwl		0.8830	0.8830	0.8830	
SN		reco	very	·	-0.0234	-0.0234	-0.0195	
		rem	oval		0.0469	0.0508	0.0469	

### **Cell Description**

The SDFFNSRPQ cell is a negative-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), asynchronous active-high reset (R) and asynchronous active-low set (SN). Set (SN) is dominant over reset (R) if both are asserted.

### **Logic Symbol**



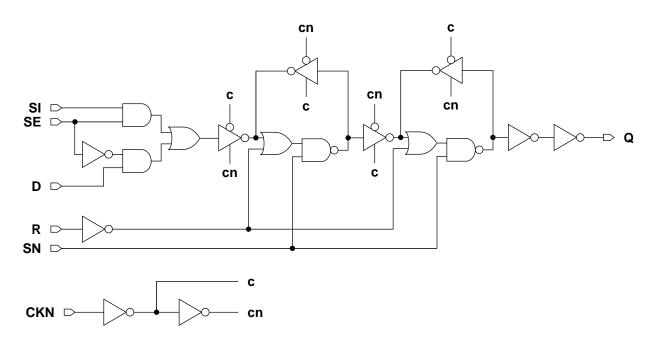
### **Function Table**

SN	R	۵	S	SE	CKN	Q[n+1]
1	0	1	Х	0	_	1
1	0	0	Х	0	_	0
1	0	Х	Х	Х		1
1	0	Х	1	1	_	1
1	0	Х	0	1	_	0
1	1	Х	Х	Х	Х	0
0	0	Х	Х	Х	Х	1
0	1	Х	Х	Х	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFNSRPQX1MA10TR	2.00	7.00
SDFFNSRPQX2MA10TR	2.00	7.40
SDFFNSRPQX3MA10TR	2.00	7.60

Process Technology: SDFFNSRPQ CLN65G+



Pin	Power (uW/MHz)							
FIII	X1P0M	X2P0M	X3P0M					
SI	0.0066	0.0078	0.0082					
SE	0.0071	0.0082	0.0085					
D	0.0060	0.0071	0.0074					
CKN	0.0048	0.0054	0.0059					
SN	0.0018	0.0022	0.0024					
R	0.0020	0.0024	0.0027					
Q	0.0052	0.0071	0.0091					

# Pin Capacitance

Pin	Capacitance (pF)							
FIII	X1P0M	X2P0M	X3P0M					
SI	0.0007	0.0007	0.0007					
SE	0.0023	0.0025	0.0025					
D	0.0013	0.0016	0.0016					
CKN	0.0010	0.0010	0.0011					
SN	0.0026	0.0029	0.0028					
R	0.0019	0.0021	0.0021					

# Delays at 25°C,1.0V, Typical Process

De	scrip	tion		Intri	nsic Delay	(ns)	K <sub>load</sub> (ns/pF)		
				X1P0M	X2P0M	X3P0M	X1P0M	X2P0M	X3P0M
CKN	$\rightarrow$	Q	$\uparrow$	0.1121	0.1077	0.1084	2.3372	1.1523	0.7823
CKN	$\rightarrow$	Q	$\downarrow$	0.1083	0.1084	0.1072	1.4583	0.7165	0.4618
SN	$\rightarrow$	Q	$\uparrow$	0.0622	0.0680	0.0723	2.3337	1.1516	0.7821
SN	$\rightarrow$	Q	$\downarrow$	0.0746	0.0824	0.0885	1.4567	0.7159	0.4616
R	$\rightarrow$	Q	$\downarrow$	0.0727	0.0811	0.0869	1.4566	0.7159	0.4616

Process Technology: SDFFNSRPQ

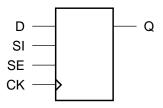
# CLN65G+

Din	Pin Requirement			nt	Interval (ns)			
FIII	Requirement				X1P0M	X2P0M	X3P0M	
	setup	$\uparrow$	$\rightarrow$	CKN	0.0781	0.0820	0.0898	
SI	setup	$\downarrow$	$\rightarrow$	CKN	0.1289	0.1367	0.1406	
31	hold	1	$\rightarrow$	CKN	-0.0273	-0.0352	-0.0391	
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0781	-0.0781	-0.0781	
	setup	$\uparrow$	$\rightarrow$	CKN	0.1367	0.1445	0.1484	
SE	setup	$\downarrow$	$\rightarrow$	CKN	0.0625	0.0586	0.0586	
SE	hold	$\uparrow$	$\rightarrow$	CKN	-0.0234	-0.0352	-0.0391	
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0195	-0.0195	-0.0195	
	setup	$\uparrow$	$\rightarrow$	CKN	0.0430	0.0352	0.0391	
D	setup	$\downarrow$	$\rightarrow$	CKN	0.0547	0.0469	0.0469	
D	hold	$\uparrow$	$\rightarrow$	CKN	0.0000	0.0000	0.0000	
	hold	$\downarrow$	$\rightarrow$	CKN	-0.0273	-0.0234	-0.0234	
CKN		min	pwl		0.8830	0.8830	0.8830	
CKIN		min	pwh		0.8830	0.8830	0.8830	
		min	pwl		0.8830	0.8830	0.8830	
SN		reco	very		0.0000	-0.0078	-0.0039	
		rem	oval		0.0195	0.0273	0.0234	
		min	pwh		0.8830	0.8830	0.8830	
R		reco	very		-0.0078	-0.0117	-0.0078	
		rem	oval		0.0430	0.0430	0.0430	

### **Cell Description**

The SDFFQ cell is a positive-edge triggered, static D-type flip-flop with scan input (SI) and active-high scan enable (SE). The cell has a single output (Q).

# **Logic Symbol**

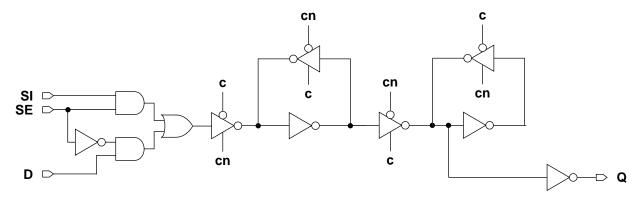


### **Function Table**

D	SI	SE	CK	Q[n+1]
1	Х	0		1
0	Х	0		0
Х	Х	Х		Q[n]
Х	1	1		1
Х	0	1		0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFQX0P5MA10TR	2.00	5.00
SDFFQX1MA10TR	2.00	5.40
SDFFQX2MA10TR	2.00	5.60
SDFFQX3MA10TR	2.00	6.00
SDFFQX4MA10TR	2.00	6.60



### **AC Power**

Pin		Power (uW/MHz)										
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M							
SI	0.0051	0.0065	0.0081	0.0092	0.0096							
SE	0.0053	0.0063	0.0076	0.0082	0.0086							
D	0.0046	0.0057	0.0070	0.0077	0.0081							
CK	0.0036	0.0041	0.0047	0.0053	0.0057							
Q	0.0032	0.0043	0.0059	0.0082	0.0108							

# Pin Capacitance

Pin	Capacitance (pF)										
F	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M						
SI	0.0006	0.0007	0.0007	0.0007	0.0007						
SE	0.0020	0.0023	0.0024	0.0024	0.0024						
D	0.0012	0.0014	0.0018	0.0018	0.0018						
CK	0.0009	0.0009	0.0010	0.0011	0.0011						

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)						
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
CK → Q ↑	0.0922	0.0795	0.0736	0.0736	0.0745		
$CK \ \to \ Q \ \downarrow$	0.1024	0.0867	0.0804	0.0820	0.0763		

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

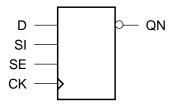
Description		ŀ	K <sub>load</sub> (ns/pF)				
	X0P5M X1P0M X2P0M X3P0M X4P0						
$CK \to Q \uparrow$	4.1882	2.3320	1.1598	0.7824	0.5809		
$CK \ \to \ Q \ \downarrow$	2.5367	1.3338	0.6608	0.4570	0.3311		

Pin	Por	Requirement				Interval (ns)						
PIII	Kec	<sub>4</sub> uire	HIIEI	ıı	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M			
	setup	$\uparrow$	$\rightarrow$	CK	0.0742	0.0820	0.0977	0.0977	0.1016			
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1094	0.1016	0.1211	0.1328	0.1328			
SI	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0547	-0.0625	-0.0664	-0.0664			
	hold	$\downarrow$	$\rightarrow$	CK	-0.0547	-0.0547	-0.0625	-0.0703	-0.0664			
	setup	$\uparrow$	$\rightarrow$	CK	0.1289	0.1172	0.1445	0.1523	0.1562			
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0664	0.0586	0.0547	0.0547	0.0586			
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0508	-0.0625	-0.0625	-0.0625			
	hold	$\downarrow$	$\rightarrow$	CK	-0.0195	-0.0117	-0.0117	-0.0156	-0.0156			
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0352	0.0273	0.0312	0.0312			
D	setup	$\downarrow$	$\rightarrow$	CK	0.0586	0.0391	0.0391	0.0430	0.0430			
	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0156	-0.0156	-0.0156			
	hold	$\downarrow$	$\rightarrow$	CK	-0.0234	-0.0117	-0.0117	-0.0156	-0.0156			
СК	r	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830			
		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830			

### **Cell Description**

The SDFFQN cell is a positive-edge triggered, static D-type flip-flop with scan input (SI) and active-high scan enable (SE). The cell has a single output (QN).

# **Logic Symbol**

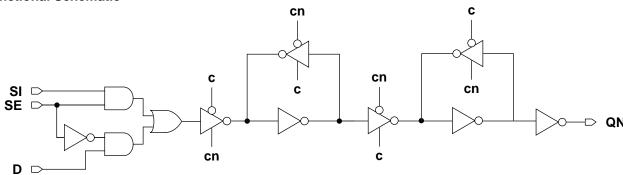


### **Function Table**

D	SI	SE	CK	QN[n+1]
1	Х	0		0
0	Х	0		1
Х	Х	Х		QN[n]
Х	1	1		0
Х	0	1		1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFQNX0P5MA10TR	2.00	5.00
SDFFQNX1MA10TR	2.00	5.40
SDFFQNX2MA10TR	2.00	5.60
SDFFQNX3MA10TR	2.00	6.00



Pin	Power (uW/MHz)									
	X0P5M	X1P0M	X2P0M	X3P0M						
SI	0.0051	0.0068	0.0081	0.0094						
SE	0.0052	0.0064	0.0074	0.0080						
D	0.0046	0.0059	0.0070	0.0078						
CK	0.0035	0.0040	0.0046	0.0055						
QN	0.0033	0.0039	0.0059	0.0076						

# Pin Capacitance

Pin	Capacitance (pF)									
	X0P5M	X1P0M	X2P0M	X3P0M						
SI	0.0006	0.0007	0.0007	0.0007						
SE	0.0020	0.0023	0.0024	0.0024						
D	0.0012	0.0014	0.0018	0.0018						
CK	0.0009	0.0009	0.0010	0.0012						

# Delays at 25°C,1.0V, Typical Process

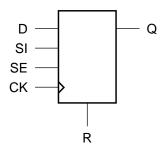
Description		Intrinsic I	Delay (ns)		K <sub>load</sub> (ns/pF)			
	X0P5M X1P0M X2P0M X3P0M				X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0878	0.0746	0.0724	0.0653	4.2610	2.3449	1.1715	0.7900
$CK \to QN \downarrow$	0.0868	0.0720	0.0756	0.0712	2.9475	1.5475	0.7844	0.5380

Pin	Por	vi i i r	amar	\ <b>+</b>	Interval (ns)				
F 1111	Requirement		X0P5M	X1P0M	X2P0M	X3P0M			
	setup	$\uparrow$	$\rightarrow$	CK	0.0781	0.0859	0.1016	0.1094	
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1133	0.1094	0.1289	0.1367	
31	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0547	-0.0625	-0.0625	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0508	-0.0508	-0.0586	-0.0586	
	setup	$\uparrow$	$\rightarrow$	CK	0.1289	0.1250	0.1484	0.1562	
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0586	0.0586	0.0586	
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0508	-0.0586	-0.0586	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0156	-0.0117	-0.0117	-0.0117	
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0352	0.0312	0.0352	
D	setup	$\downarrow$	$\rightarrow$	CK	0.0586	0.0430	0.0391	0.0430	
	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0156	-0.0156	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0195	-0.0117	-0.0117	-0.0117	
СК	r	ninp	wh		0.8830	0.8830	0.8830	0.8830	
		min	owl		0.8830	0.8830	0.8830	0.8830	

### **Cell Description**

The SDFFRPQ cell is a positive-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and asynchronous active-high reset (R). The cell has a single inverted output (Q).

# **Logic Symbol**

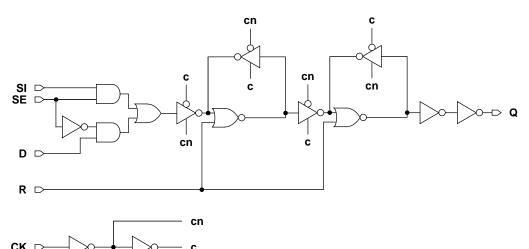


#### **Function Table**

R	D	SI	SE	CK	Q
1	Х	Х	Х		0
0	1	Х	0		1
0	0	Х	0		0
0	Х	0	1		0
0	Х	1	1		1
0	Х	Х	Х		Q

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFRPQX0P5MA10TR	2.00	5.80
SDFFRPQX1MA10TR	2.00	5.80
SDFFRPQX2MA10TR	2.00	6.40
SDFFRPQX3MA10TR	2.00	6.60
SDFFRPQX4MA10TR	2.00	7.40



Pin	Power (uW/MHz)									
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M					
SI	0.0053	0.0069	0.0082	0.0086	0.0089					
SE	0.0057	0.0075	0.0089	0.0094	0.0098					
D	0.0047	0.0061	0.0073	0.0076	0.0080					
CK	0.0039	0.0044	0.0051	0.0056	0.0059					
R	0.0015	0.0017	0.0022	0.0024	0.0027					
Q	0.0035	0.0048	0.0065	0.0084	0.0110					

# Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
SI	0.0007	0.0007	0.0007	0.0007	0.0007				
SE	0.0020	0.0022	0.0024	0.0024	0.0024				
D	0.0011	0.0014	0.0018	0.0018	0.0018				
CK	0.0008	0.0009	0.0010	0.0011	0.0011				
R	0.0015	0.0016	0.0018	0.0018	0.0019				

# Delays at 25°C,1.0V, Typical Process

Description				Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
CK	$\rightarrow$	Q	$\uparrow$	0.1055	0.0895	0.0799	0.0820	0.0792	
CK	$\rightarrow$	Q	$\downarrow$	0.1145	0.0941	0.0857	0.0894	0.0860	
R	$\rightarrow$	Q	$\downarrow$	0.0597	0.0516	0.0558	0.0632	0.0707	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

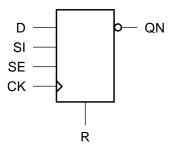
Description					ŀ	< <sub>load</sub> (ns/pF	)		
				X0P5M X1P0M X2P0M X3P0M X4I					
CK	$\rightarrow$	Q	$\uparrow$	4.1638	2.3356	1.1474	0.7776	0.5842	
CK	$\rightarrow$	Q	$\downarrow$	2.6356	1.3329	0.6515	0.4548	0.3347	
R	$\rightarrow$	Q	$\downarrow$	2.6236	1.3312	0.6513	0.4547	0.3348	

Pin	Por	anir.	amar			Interval (ns)					
PIII	Ked	<sub>4</sub> uii e	emer	ıı	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M		
	setup	$\uparrow$	$\rightarrow$	CK	0.0938	0.0898	0.1016	0.1055	0.1094		
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1172	0.1133	0.1328	0.1367	0.1445		
31	hold	$\uparrow$	$\rightarrow$	CK	-0.0508	-0.0586	-0.0664	-0.0664	-0.0625		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0586	-0.0664	-0.0742	-0.0781	-0.0781		
	setup	$\uparrow$	$\rightarrow$	CK	0.1289	0.1289	0.1523	0.1562	0.1641		
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0859	0.0625	0.0625	0.0625	0.0664		
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0547	-0.0625	-0.0625	-0.0586		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0234	-0.0195	-0.0156	-0.0156	-0.0195		
	setup	$\uparrow$	$\rightarrow$	CK	0.0625	0.0430	0.0352	0.0352	0.0391		
D	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0508	0.0430	0.0430	0.0469		
	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0156	-0.0156	-0.0156		
	hold	$\downarrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0156	-0.0156	-0.0195		
СК	r	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830		
CIX	minpwl			0.8830	0.8830	0.8830	0.8830	0.8830			
	minpwh			0.8830	0.8830	0.8830	0.8830	0.8830			
R	r	ecov	/ery		0.0234	0.0000	0.0039	0.0039	0.0039		
	r	emo	oval		0.0117	0.0391	0.0391	0.0430	0.0352		

### **Cell Description**

The SDFFRPQN cell is a positive-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and asynchronous active-high reset (R). The cell has a single inverted output (QN).

# **Logic Symbol**

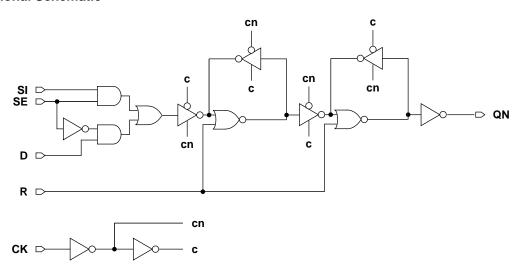


#### **Function Table**

R	D	SI	SE	CK	QN
1	Х	Х	Х		1
0	1	Х	0		0
0	0	Х	0		1
0	Х	0	1		1
0	Х	1	1		0
0	Х	Х	Х		QN

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFRPQNX0P5MA10TR	2.00	5.80
SDFFRPQNX1MA10TR	2.00	5.80
SDFFRPQNX2MA10TR	2.00	6.40
SDFFRPQNX3MA10TR	2.00	7.00



Pin	Power (uW/MHz)								
• •••	X0P5M	X1P0M	X2P0M	X3P0M					
SI	0.0053	0.0069	0.0082	0.0086					
SE	0.0056	0.0075	0.0087	0.0092					
D	0.0048	0.0062	0.0073	0.0077					
CK	0.0038	0.0043	0.0048	0.0056					
R	0.0014	0.0015	0.0020	0.0022					
QN	0.0038	0.0046	0.0068	0.0093					

# Pin Capacitance

Pin	Capacitance (pF)								
F III	X0P5M	X1P0M	X2P0M	X3P0M					
SI	0.0007	0.0007	0.0007	0.0007					
SE	0.0020	0.0023	0.0024	0.0025					
D	0.0011	0.0015	0.0018	0.0018					
CK	0.0009	0.0009	0.0010	0.0012					
R	0.0015	0.0016	0.0018	0.0019					

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)				K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	POM         X2P0M         X3P0M         X0P5M         X1P0M				X2P0M	X3P0M
CK → QN ↑	0.0931	0.0809	0.0747	0.0738	4.2525	2.3532	1.1673	0.7923
$CK \to QN \downarrow$	0.0995	0.0864	0.0836	0.0874	2.9953	1.5847	0.7513	0.5508
$R \rightarrow QN \uparrow$	0.0359	0.0389	0.0501	0.0600	4.1897	2.3428	1.1670	0.7916

**SDFFRPQN** 

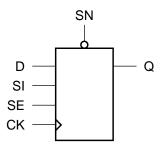
# Process Technology: CLN65G+

Pin	Por	ir	amar	.4		Interv	al (ns)	
Pin	Red	Requirement				X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0977	0.0938	0.1055	0.1094
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1172	0.1133	0.1367	0.1445
SI	hold	$\uparrow$	$\rightarrow$	CK	-0.0508	-0.0586	-0.0625	-0.0547
	hold	$\downarrow$	$\rightarrow$	CK	-0.0547	-0.0625	-0.0703	-0.0703
	setup	$\uparrow$	$\rightarrow$	CK	0.1328	0.1328	0.1562	0.1641
SE.	setup	$\downarrow$	$\rightarrow$	CK	0.0859	0.0625	0.0625	0.0664
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0547	-0.0586	-0.0508
	hold	$\downarrow$	$\rightarrow$	CK	-0.0234	-0.0156	-0.0117	-0.0156
	setup	$\uparrow$	$\rightarrow$	CK	0.0664	0.0391	0.0352	0.0391
D	setup	$\downarrow$	$\rightarrow$	CK	0.0664	0.0469	0.0430	0.0469
D	hold	1	$\rightarrow$	CK	-0.0234	-0.0156	-0.0156	-0.0117
	hold	$\downarrow$	$\rightarrow$	CK	-0.0234	-0.0156	-0.0117	-0.0156
СК	ı	minp	wh		0.8830	0.8830	0.8830	0.8830
CIX	minpwl			0.8830	0.8830	0.8830	0.8830	
	1	minpwh			0.8830	0.8830	0.8830	0.8830
R	r	ecov	ery		0.0273	0.0039	0.0000	0.0039
	ı	emo	oval		0.0117	0.0352	0.0352	0.0312

### **Cell Description**

The SDFFSQ cell is a high-speed, positive-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and asynchronous active-low set (SN). The cell has a single output (Q).

### **Logic Symbol**

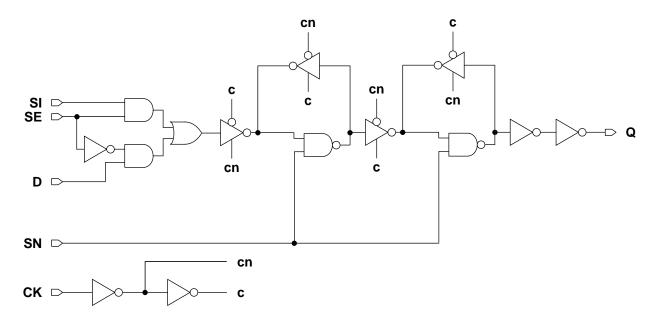


### **Function Table**

SN	D	SI	SE	CK	Q[n+1]
1	1	Х	0		1
1	0	Х	0		0
1	Х	Х	Х	_	Q[n]
1	Х	1	1		1
1	Х	0	1		0
0	Х	Х	Х	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFSQX0P5MA10TR	2.00	6.20
SDFFSQX1MA10TR	2.00	6.20
SDFFSQX2MA10TR	2.00	6.40
SDFFSQX3MA10TR	2.00	6.80
SDFFSQX4MA10TR	2.00	7.40



Pin	Power (uW/MHz)								
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
SI	0.0056	0.0065	0.0084	0.0088	0.0091				
SE	0.0054	0.0070	0.0088	0.0093	0.0097				
D	0.0050	0.0059	0.0075	0.0078	0.0081				
CK	0.0037	0.0042	0.0049	0.0055	0.0058				
SN	0.0014	0.0019	0.0024	0.0026	0.0029				
Q	0.0035	0.0049	0.0065	0.0083	0.0111				

# Pin Capacitance

Pin	Capacitance (pF)								
	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
SI	0.0007	0.0007	0.0007	0.0007	0.0007				
SE	0.0021	0.0022	0.0024	0.0024	0.0024				
D	0.0011	0.0013	0.0018	0.0018	0.0018				
CK	0.0009	0.0009	0.0010	0.0011	0.0012				
SN	0.0018	0.0022	0.0027	0.0027	0.0026				

# Delays at 25°C,1.0V, Typical Process

De	scrip	otior	1	Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
CK	$\rightarrow$	Q	<b>↑</b>	0.0991	0.0860	0.0772	0.0778	0.0771	
CK	$\rightarrow$	Q	$\downarrow$	0.1085	0.0950	0.0874	0.0898	0.0856	
SN	$\rightarrow$	→ Q ↑ 0.0680		0.0640	0.0673	0.0713	0.0782		

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

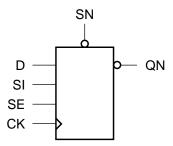
De	escri	ptior	า		ŀ	์ <sub>load</sub> (ns/pF	)	
				X0P5M	X1P0M	X3P0M	X4P0M	
CK	$\rightarrow$	Q	$\uparrow$	4.2368	2.3328	1.1602	0.7816	0.5811
CK	$\rightarrow$	Q	$\downarrow$	2.5781	1.3345	0.6625	0.4580	0.3327
SN	$\rightarrow$	Q	1	4.2394	2.3328	1.1602	0.7818	0.5810

Pin	Bos	:				lı	nterval (ns	s)	
Pin	Requirement			X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
	setup	$\uparrow$	$\rightarrow$	CK	0.0820	0.0859	0.1055	0.1055	0.1133
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1133	0.0977	0.1211	0.1250	0.1328
31	hold	$\uparrow$	$\rightarrow$	CK	-0.0508	-0.0586	-0.0703	-0.0703	-0.0703
	hold	$\downarrow$	$\rightarrow$	CK	-0.0547	-0.0508	-0.0625	-0.0664	-0.0664
	setup	$\uparrow$	$\rightarrow$	CK	0.1289	0.1172	0.1445	0.1484	0.1523
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0703	0.0625	0.0586	0.0586	0.0625
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0547	-0.0664	-0.0703	-0.0664
	hold	$\downarrow$	$\rightarrow$	CK	-0.0195	-0.0156	-0.0117	-0.0156	-0.0156
	setup	$\uparrow$	$\rightarrow$	CK	0.0469	0.0391	0.0312	0.0352	0.0391
D	setup	$\downarrow$	$\rightarrow$	CK	0.0586	0.0469	0.0391	0.0391	0.0430
	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0195	-0.0156	-0.0156	-0.0195
	hold	$\downarrow$	$\rightarrow$	CK	-0.0195	-0.0156	-0.0117	-0.0156	-0.0156
СК	r	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830
CIX		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830
		minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830
SN	r	ecov	ery		-0.0273	-0.0312	-0.0312	-0.0312	-0.0234
	r	emo	oval		0.0508	0.0586	0.0625	0.0625	0.0508

### **Cell Description**

The SDFFSQN cell is a positive-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and asynchronous active-low set (SN). The cell has a single output (QN).

# **Logic Symbol**

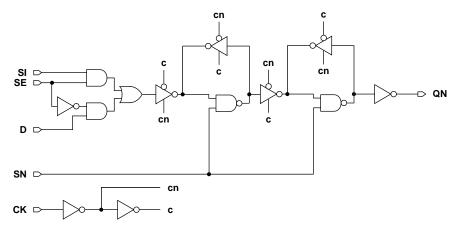


### **Function Table**

SN	D	SI	SE CK		QN
1	1	Х	0		0
1	0	Х	0		1
1	Х	Х	Х	_	QN[n]
1	Х	1	1		0
1	Х	0	1		1
0	Х	Х	Х	Х	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFSQNX0P5MA10TR	2.00	6.20
SDFFSQNX1MA10TR	2.00	6.20
SDFFSQNX2MA10TR	2.00	6.40
SDFFSQNX3MA10TR	2.00	6.80



### **AC Power**

Pin		Power (u	ıW/MHz)	
F 111	X0P5M	X1P0M	X2P0M	X3P0M
SI	0.0057	0.0070	0.0083	0.0087
SE	0.0054	0.0073	0.0086	0.0090
D	0.0051	0.0062	0.0075	0.0078
CK	0.0036	0.0042	0.0048	0.0055
SN	0.0015	0.0019	0.0024	0.0027
QN	0.0036	0.0043	0.0065	0.0090

# Pin Capacitance

Pin	Capacitance (pF)							
F 111	X0P5M	X1P0M	X2P0M	X3P0M				
SI	0.0007	0.0007	0.0007	0.0007				
SE	0.0021	0.0022	0.0024	0.0024				
D	0.0011	0.0013	0.0018	0.0018				
CK	0.0009	0.0009	0.0010	0.0012				
SN	0.0019	0.0025	0.0027	0.0027				

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)				K <sub>load</sub> (ns/pF)			
	X0P5M	X1P0M	X2P0M	X3P0M	X0P5M	X1P0M	X2P0M	X3P0M
$CK \to QN \uparrow$	0.0930	0.0807	0.0805	0.0781	4.3121	2.3485	1.1755	0.7955
$CK \to QN \downarrow$	0.0896	0.0772	0.0805	0.0831	3.0691	1.5367	0.7699	0.5320
$SN \  o \ QN \ \downarrow$	0.0536	0.0558	0.0701	0.0844	2.8649	1.4957	0.7563	0.5243

**SDFFSQN** 

# CLN65G+

Pin	Dod			.4		Interv	al (ns)	
Pin	Ked	Requirement			X0P5M	X1P0M	X2P0M	X3P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0859	0.0938	0.1055	0.1094
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1094	0.1016	0.1211	0.1289
Si	hold	$\uparrow$	$\rightarrow$	CK	-0.0508	-0.0625	-0.0703	-0.0664
	hold	$\downarrow$	$\rightarrow$	CK	-0.0469	-0.0469	-0.0547	-0.0586
	setup	$\uparrow$	$\rightarrow$	CK	0.1250	0.1172	0.1445	0.1523
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0742	0.0664	0.0586	0.0625
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0586	-0.0664	-0.0664
	hold	$\downarrow$	$\rightarrow$	CK	-0.0195	-0.0156	-0.0078	-0.0117
	setup	$\uparrow$	$\rightarrow$	CK	0.0508	0.0430	0.0312	0.0352
D	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0469	0.0391	0.0430
	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0156	-0.0156
	hold	$\downarrow$	$\rightarrow$	CK	-0.0234	-0.0156	-0.0078	-0.0117
СК	ı	minp	wh		0.8830	0.8830	0.8830	0.8830
CIX		minp	owl		0.8830	0.8830	0.8830	0.8830
		minp	lwc		0.8830	0.8830	0.8830	0.8830
SN	r	ecov	ery/		-0.0312	-0.0352	-0.0312	-0.0234
	r	emo	oval		0.0547	0.0664	0.0625	0.0547

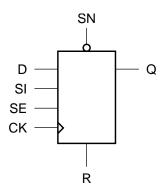
Process Technology: SDFFSRPQ

# CLN65G+

### **Cell Description**

The SDFFSRPQ cell is a positive-edge triggered, static D-type flip-flop with scan input (SI), active-high scan enable (SE), and asynchronous active-low reset (R) and set (SN). Set (SN) dominates reset (R).

# **Logic Symbol**



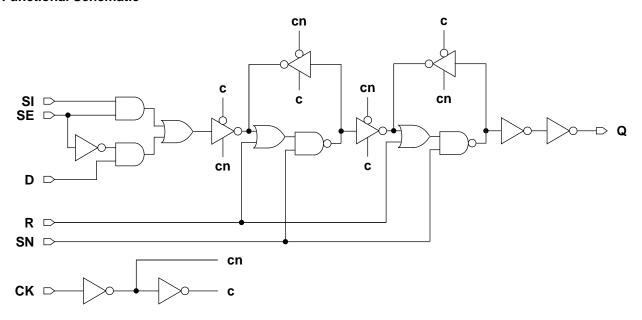
### **Function Table**

SN	R	D	SI	SE	CK	Q
1	0	1	Х	0		1
1	0	0	Х	0		0
1	0	Х	Х	Х		1
1	0	Х	1	1		1
1	0	Х	0	1		0
1	1	Х	Х	Х	Х	0
0	0	Х	Х	Х	Х	1
0	1	Х	Х	Х	Х	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFSRPQX0P5MA10TR	2.00	7.00
SDFFSRPQX1MA10TR	2.00	7.00
SDFFSRPQX2MA10TR	2.00	7.20
SDFFSRPQX3MA10TR	2.00	7.60
SDFFSRPQX4MA10TR	2.00	8.20

Process Technology: SDFFSRPQ CLN65G+



Pin	Power (uW/MHz)								
' '''	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
SI	0.0054	0.0070	0.0082	0.0086	0.0089				
SE	0.0060	0.0075	0.0087	0.0091	0.0095				
D	0.0049	0.0063	0.0074	0.0078	0.0081				
CK	0.0051	0.0056	0.0064	0.0070	0.0073				
SN	0.0014	0.0021	0.0024	0.0026	0.0029				
R	0.0015	0.0022	0.0026	0.0029	0.0032				
Q	0.0041	0.0054	0.0072	0.0090	0.0120				

# Pin Capacitance

Pin	Capacitance (pF)								
F 1111	X0P5M	X1P0M	X2P0M	X3P0M	X4P0M				
SI	0.0007	0.0007	0.0007	0.0007	0.0007				
SE	0.0021	0.0023	0.0024	0.0024	0.0025				
D	0.0011	0.0014	0.0018	0.0018	0.0018				
CK	0.0009	0.0010	0.0011	0.0011	0.0011				
SN	0.0023	0.0028	0.0029	0.0029	0.0029				
R	0.0016	0.0020	0.0021	0.0022	0.0023				

# Delays at 25°C,1.0V, Typical Process

Description			)	Intrinsic Delay (ns)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
CK	$\rightarrow$	Q	$\uparrow$	0.1188	0.0970	0.0926	0.0911	0.0894	
CK	$\rightarrow$	Q	$\downarrow$	0.1317	0.1026	0.1011	0.1012	0.0989	
SN	$\rightarrow$	Q	$\uparrow$	0.0699	0.0694	0.0752	0.0767	0.0817	
SN	$\rightarrow$	Q	$\downarrow$	0.0753	0.0666	0.0751	0.0821	0.0913	
R	$\rightarrow$	Q	$\downarrow$	0.0737	0.0648	0.0736	0.0804	0.0895	

**SDFFSRPQ** 

# CLN65G+

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

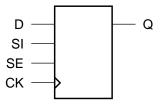
Description				K <sub>load</sub> (ns/pF)					
				X0P5M	X1P0M	X2P0M	X3P0M	X4P0M	
CK	$\rightarrow$	Q	$\uparrow$	4.2379	2.3323	1.1542	0.7824	0.5853	
CK	$\rightarrow$	Q	$\downarrow$	2.6099	1.3465	0.6737	0.4591	0.3331	
SN	$\rightarrow$	Q	$\uparrow$	4.2355	2.3330	1.1542	0.7825	0.5851	
SN	$\rightarrow$	Q	$\downarrow$	2.5921	1.3445	0.6733	0.4590	0.3332	
R	$\rightarrow$	Q	$\downarrow$	2.5922	1.3445	0.6732	0.4590	0.3331	

	<u> </u>				, 1.0 v, 1ypi		nterval (ns	s)	
Pin	Rec	Requirement				X1P0M	X2P0M	X3P0M	X4P0M
	setup	$\uparrow$	$\rightarrow$	CK	0.0977	0.0977	0.1094	0.1133	0.1172
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1250	0.1250	0.1445	0.1445	0.1523
SI	hold	$\uparrow$	$\rightarrow$	CK	-0.0508	-0.0547	-0.0586	-0.0586	-0.0547
	hold	$\downarrow$	$\rightarrow$	CK	-0.0664	-0.0625	-0.0703	-0.0742	-0.0703
	setup	$\uparrow$	$\rightarrow$	CK	0.1367	0.1406	0.1641	0.1641	0.1719
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0859	0.0664	0.0664	0.0703	0.0742
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0469	-0.0508	-0.0547	-0.0586	-0.0508
	hold	$\downarrow$	$\rightarrow$	CK	-0.0273	-0.0156	-0.0117	-0.0156	-0.0156
	setup	$\uparrow$	$\rightarrow$	CK	0.0664	0.0469	0.0391	0.0430	0.0469
D	setup	$\downarrow$	$\rightarrow$	CK	0.0664	0.0508	0.0469	0.0469	0.0547
	hold	$\uparrow$	$\rightarrow$	CK	-0.0273	-0.0195	-0.0117	-0.0156	-0.0117
	hold	$\downarrow$	$\rightarrow$	CK	-0.0273	-0.0156	-0.0117	-0.0156	-0.0156
СК	r	ninp	wh		0.8830	0.8830	0.8830	0.8830	0.8830
CK	ı	minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830
	!	minp	owl		0.8830	0.8830	0.8830	0.8830	0.8830
SN	re	ecov	ery		-0.0156	-0.0156	-0.0117	-0.0117	-0.0039
	r	emo	oval		0.0352	0.0352	0.0352	0.0312	0.0234
	r	minp	wh		0.8830	0.8830	0.8830	0.8830	0.8830
R	re	ecov	ery		0.0234	0.0117	0.0117	0.0156	0.0195
	r	emo	oval		0.0156	0.0234	0.0234	0.0195	0.0156

### **Cell Description**

The SDFFYQ cell is a positive-edge triggered, static D-type flip-flop with scan input (SI) and active-high scan enable (SE). The cell has a single output (Q) and overdriven feedback loops to increase mean time between failure (MTBF) due to metastability.

### **Logic Symbol**

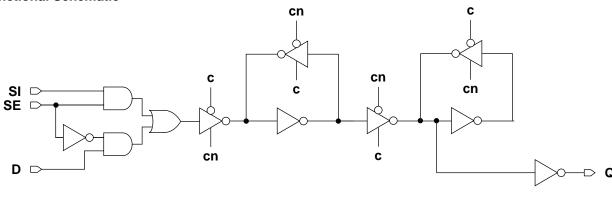


#### **Function Table**

D	SI	SE	CK	Q[n+1]
1	Х	0		1
0	Х	0		0
Х	Х	Х		Q[n]
Х	1	1		1
Х	0	1		0

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
SDFFYQX1MA10TR	2.00	5.20
SDFFYQX2MA10TR	2.00	5.60
SDFFYQX3MA10TR	2.00	6.00
SDFFYQX4MA10TR	2.00	6.40



Pin	Power (uW/MHz)							
	X1P0M	X2P0M	X3P0M	X4P0M				
SI	0.0074	0.0089	0.0091	0.0099				
SE	0.0072	0.0083	0.0091	0.0095				
D	0.0064	0.0077	0.0078	0.0085				
CK	0.0053	0.0066	0.0064	0.0074				
Q	0.0049	0.0066	0.0091	0.0120				

# Pin Capacitance

Pin	Capacitance (pF)							
F III	X1P0M	X2P0M	X3P0M	X4P0M				
SI	0.0007	0.0007	0.0007	0.0007				
SE	0.0024	0.0025	0.0025	0.0025				
D	0.0015	0.0018	0.0018	0.0018				
CK	0.0013	0.0017	0.0012	0.0014				

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)					K <sub>load</sub> (	ns/pF)	
	X1P0M	X2P0M	X3P0M	X4P0M	X1P0M	X2P0M	X3P0M	X4P0M
$CK \to Q \uparrow$	0.0756	0.0665	0.0752	0.0710	2.3407	1.1620	0.7832	0.5845
$CK \ \to \ Q \ \downarrow$	0.0793	0.0723	0.0850	0.0756	1.4560	0.6637	0.4582	0.3344

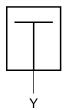
Pin	Requirement			Interval (ns)					
F III	Requiremen		11	X1P0M	X2P0M	X3P0M	X4P0M		
	setup	$\uparrow$	$\rightarrow$	CK	0.0898	0.1055	0.1016	0.1055	
SI	setup	$\downarrow$	$\rightarrow$	CK	0.1172	0.1367	0.1406	0.1445	
31	hold	$\uparrow$	$\rightarrow$	CK	-0.0625	-0.0703	-0.0703	-0.0703	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0703	-0.0781	-0.0820	-0.0781	
	setup	$\uparrow$	$\rightarrow$	CK	0.1328	0.1562	0.1602	0.1641	
SE	setup	$\downarrow$	$\rightarrow$	CK	0.0625	0.0625	0.0586	0.0625	
SE	hold	$\uparrow$	$\rightarrow$	CK	-0.0625	-0.0703	-0.0664	-0.0664	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0195	-0.0195	-0.0156	-0.0195	
	setup	$\uparrow$	$\rightarrow$	CK	0.0391	0.0352	0.0352	0.0391	
D	setup	$\downarrow$	$\rightarrow$	CK	0.0469	0.0469	0.0430	0.0469	
	hold	$\uparrow$	$\rightarrow$	CK	-0.0234	-0.0195	-0.0195	-0.0195	
	hold	$\downarrow$	$\rightarrow$	CK	-0.0195	-0.0195	-0.0156	-0.0195	
СК	minpwh			0.8830	0.8830	0.8830	0.8830		
CIC	minpwl			0.8830	0.8830	0.8830	0.8830		

### **Cell Description**

The TIEHI cell drives the output (Y) to a logic high. The output is driven through diffusion and not tied directly to the power rail to provide some ESD protection. The output (Y) is represented by the logic equation:

Y = 1

### **Logic Symbol**

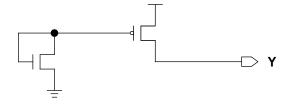


### **Function Table**

Υ	
1	

### **Cell Size**

Drive Strength	Height (um)	Width (um)	
TIEHIX1MA10TR	2.00	0.80	

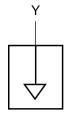


### **Cell Description**

The TIELO cell drives the output (Y) to a logic low. The output is driven through diffusion and not tied directly to the power rail to provide some ESD protection. The output (Y) is represented by the logic equation:

Y = 0

### **Logic Symbol**

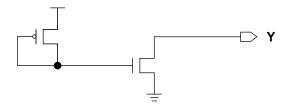


### **Function Table**

Υ
0

### **Cell Size**

Drive Strength	Height (um)	Width (um)		
TIELOX1MA10TR	2.00	0.80		



### **Cell Description**

The XNOR2 cell provides a logical EXCLUSIVE NOR of two inputs (A,B). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (A \bullet B) + (\overline{A} \bullet \overline{B})$$

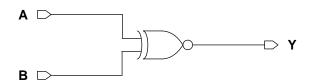
# **Logic Symbol**

### **Function Table**

Α	В	Υ
0	0	1
0	1	0
1	0	0
1	1	1

#### **Cell Size**

Drive Strength	Height (um)	Width (um)
XNOR2X0P5MA10TR	2.00	2.00
XNOR2X0P7MA10TR	2.00	2.00
XNOR2X1MA10TR	2.00	2.00
XNOR2X1P4MA10TR	2.00	3.20
XNOR2X2MA10TR	2.00	3.60
XNOR2X3MA10TR	2.00	4.00
XNOR2X4MA10TR	2.00	6.20



Pin	Power (uW/MHz)								
F 1111	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M		
Α	0.0033	0.0038	0.0046	0.0067	0.0086	0.0119	0.0165		
В	0.0035	0.0043	0.0054	0.0084	0.0110	0.0156	0.0215		

# Pin Capacitance

Pin	Capacitance (pF)									
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
Α	0.0020	0.0021	0.0024	0.0030	0.0041	0.0054	0.0073			
В	0.0011	0.0014	0.0017	0.0026	0.0033	0.0049	0.0064			

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
$A \rightarrow Y \uparrow$	0.0173	0.0164	0.0155	0.0188	0.0171	0.0150	0.0157
$A \rightarrow Y \downarrow$	0.0198	0.0184	0.0176	0.0200	0.0183	0.0165	0.0176
$B \to Y \uparrow$	0.0342	0.0297	0.0265	0.0359	0.0283	0.0261	0.0271
$B \to Y \downarrow$	0.0357	0.0321	0.0291	0.0293	0.0285	0.0267	0.0276

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
$A \rightarrow Y \uparrow$	6.7218	5.0666	3.6681	3.2709	1.8264	1.1996	0.9026
$A \rightarrow Y \downarrow$	4.6670	3.4315	2.4373	1.7550	1.2963	0.8375	0.6375
$B \to Y \uparrow$	6.6934	5.0166	3.6357	3.2974	1.8253	1.2070	0.9047
$B \to Y \downarrow$	4.7272	3.4705	2.4395	1.8042	1.2840	0.8316	0.6289

XNOR3

# CLN65G+

### **Cell Description**

The XNOR3 cell provides a logical EXCLUSIVE NOR of three inputs (A,B,C). The output (Y) is represented by the following equation:

 $Y = \overline{A \oplus B \oplus C}$ 

# **Logic Symbol**

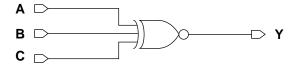


### **Function Table**

Α	В	С	Υ
0	0	0	1
0	0	1	0
0	1	0	0
0	1	1	1
1	0	0	0
1	0	1	1
1	1	0	1
1	1	1	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
XNOR3X0P5MA10TR	2.00	3.80
XNOR3X0P7MA10TR	2.00	3.80
XNOR3X1MA10TR	2.00	3.80
XNOR3X1P4MA10TR	2.00	6.00
XNOR3X2MA10TR	2.00	6.80
XNOR3X3MA10TR	2.00	8.00
XNOR3X4MA10TR	2.00	10.20



Pin	Power (uW/MHz)									
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
Α	0.0044	0.0055	0.0065	0.0083	0.0110	0.0153	0.0192			
В	0.0077	0.0091	0.0107	0.0153	0.0201	0.0266	0.0346			
С	0.0087	0.0109	0.0128	0.0186	0.0238	0.0328	0.0424			

# Pin Capacitance

Pin	Capacitance (pF)									
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
Α	0.0015	0.0017	0.0018	0.0023	0.0027	0.0037	0.0045			
В	0.0020	0.0024	0.0027	0.0035	0.0046	0.0059	0.0078			
С	0.0012	0.0015	0.0017	0.0026	0.0031	0.0047	0.0059			

# Delays at 25°C,1.0V, Typical Process

Description		Intrinsic Delay (ns)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	
$A \rightarrow Y \uparrow$	0.0477	0.0443	0.0444	0.0415	0.0433	0.0395	0.0395	
$A \ \rightarrow \ Y \ \downarrow$	0.0458	0.0421	0.0426	0.0413	0.0430	0.0406	0.0401	
$B \to Y \uparrow$	0.0780	0.0703	0.0694	0.0725	0.0705	0.0646	0.0639	
$B \ \to \ Y \ \downarrow$	0.0893	0.0803	0.0816	0.0798	0.0793	0.0712	0.0713	
$C \rightarrow Y \uparrow$	0.0929	0.0852	0.0823	0.0830	0.0816	0.0743	0.0735	
$C \rightarrow Y \downarrow$	0.1034	0.0947	0.0932	0.0898	0.0897	0.0809	0.0810	

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description		K <sub>load</sub> (ns/pF)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	
$A \ \rightarrow \ Y \ \uparrow$	4.5688	3.3407	2.4079	1.6438	1.1866	0.7861	0.5960	
$A \ \rightarrow \ Y \ \downarrow$	2.9777	2.1359	1.5454	1.0527	0.7699	0.5127	0.3817	
$B \to Y \uparrow$	4.5300	3.3142	2.3881	1.6322	1.1783	0.7818	0.5923	
$B \to Y \downarrow$	3.0487	2.1834	1.5733	1.0766	0.7846	0.5178	0.3859	
$C \rightarrow Y \uparrow$	4.5297	3.3142	2.3882	1.6321	1.1782	0.7818	0.5923	
$C \rightarrow Y \downarrow$	3.0491	2.1837	1.5735	1.0769	0.7847	0.5185	0.3859	

### **Cell Description**

The XOR2 cell provides a logical EXCLUSIVE OR of two inputs (A,B). The output (Y) is represented by the logic equation:

$$\mathsf{Y} = (A \bullet \overline{B}) + (\overline{A} \bullet B)$$

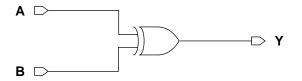
# **Logic Symbol**

### **Function Table**

Α	В	Υ
0	0	0
0	1	1
1	0	1
1	1	0

### **Cell Size**

Drive Strength	Height (um)	Width (um)
XOR2X0P5MA10TR	2.00	2.00
XOR2X0P7MA10TR	2.00	2.00
XOR2X1MA10TR	2.00	2.00
XOR2X1P4MA10TR	2.00	3.20
XOR2X2MA10TR	2.00	3.60
XOR2X3MA10TR	2.00	4.20
XOR2X4MA10TR	2.00	6.20



### **AC Power**

Pin	Power (uW/MHz)									
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
Α	0.0032	0.0037	0.0046	0.0068	0.0086	0.0121	0.0164			
В	0.0039	0.0047	0.0061	0.0093	0.0121	0.0172	0.0239			

# Pin Capacitance

Pin	Capacitance (pF)									
FIII	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M			
Α	0.0019	0.0021	0.0024	0.0035	0.0045	0.0059	0.0079			
В	0.0011	0.0014	0.0018	0.0026	0.0033	0.0048	0.0064			

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
$A \rightarrow Y \uparrow$	0.0181	0.0165	0.0152	0.0199	0.0172	0.0153	0.0160
$A \rightarrow Y \downarrow$	0.0188	0.0178	0.0170	0.0190	0.0168	0.0159	0.0165
$B \to Y \uparrow$	0.0335	0.0288	0.0261	0.0349	0.0272	0.0248	0.0260
$B \to Y \downarrow$	0.0362	0.0326	0.0301	0.0301	0.0292	0.0271	0.0285

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

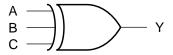
Description	K <sub>load</sub> (ns/pF)							
	X0P5M	X0P5M						
$A \ \rightarrow \ Y \ \uparrow$	6.7127	4.9960	3.5946	3.2937	1.8267	1.1957	0.9066	
$A \ \rightarrow \ Y \ \downarrow$	4.6549	3.4221	2.4053	1.8055	1.2810	0.8262	0.6270	
$B \to Y \uparrow$	6.7045	5.0246	3.6180	3.2921	1.8251	1.1950	0.9060	
$B \ \to \ Y \ \downarrow$	4.7329	3.4729	2.4368	1.8292	1.2840	0.8321	0.6272	

### **Cell Description**

The XOR3 cell provides a logical EXCLUSIVE OR of three inputs (A,B,C). The output (Y) is represented by the following equation:

 $Y = A \oplus B \oplus C$ 

# **Logic Symbol**

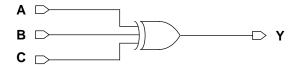


### **Function Table**

Α	В	С	Υ
0	0	0	0
0	0	1	1
0	1	0	1
0	1	1	0
1	0	0	1
1	0	1	0
1	1	0	0
1	1	1	1

### **Cell Size**

Drive Strength	Height (um)	Width (um)
XOR3X0P5MA10TR	2.00	3.80
XOR3X0P7MA10TR	2.00	3.80
XOR3X1MA10TR	2.00	3.80
XOR3X1P4MA10TR	2.00	6.00
XOR3X2MA10TR	2.00	7.00
XOR3X3MA10TR	2.00	8.00
XOR3X4MA10TR	2.00	10.40



Pin	Power (uW/MHz)						
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
Α	0.0044	0.0054	0.0065	0.0081	0.0110	0.0150	0.0191
В	0.0082	0.0095	0.0113	0.0160	0.0209	0.0278	0.0362
С	0.0092	0.0113	0.0134	0.0193	0.0246	0.0339	0.0440

# Pin Capacitance

Pin	Capacitance (pF)							
F	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M	
Α	0.0023	0.0027	0.0031	0.0036	0.0047	0.0063	0.0078	
В	0.0021	0.0023	0.0027	0.0035	0.0047	0.0059	0.0078	
С	0.0012	0.0016	0.0017	0.0026	0.0031	0.0046	0.0059	

# Delays at 25°C,1.0V, Typical Process

Description	Intrinsic Delay (ns)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
$A \rightarrow Y \uparrow$	0.0428	0.0407	0.0398	0.0367	0.0397	0.0366	0.0364
$A \ \rightarrow \ Y \ \downarrow$	0.0510	0.0481	0.0494	0.0449	0.0488	0.0443	0.0446
$B \to Y \uparrow$	0.0784	0.0710	0.0697	0.0723	0.0697	0.0651	0.0646
$B \ \to \ Y \ \downarrow$	0.0898	0.0807	0.0818	0.0797	0.0791	0.0713	0.0713
$C \rightarrow Y \uparrow$	0.0932	0.0851	0.0826	0.0827	0.0805	0.0750	0.0743
$C \rightarrow Y \downarrow$	0.1037	0.0945	0.0934	0.0895	0.0893	0.0810	0.0810

# Delays at 25°C,1.0V, Typical Process (Cont'd.)

Description	K <sub>load</sub> (ns/pF)						
	X0P5M	X0P7M	X1P0M	X1P4M	X2P0M	X3P0M	X4P0M
$A \rightarrow Y \uparrow$	4.5296	3.3222	2.3824	1.6316	1.1756	0.7818	0.5803
$A \ \rightarrow \ Y \ \downarrow$	3.0210	2.1684	1.5624	1.0705	0.7697	0.5091	0.3791
$B \to Y \uparrow$	4.5304	3.3224	2.3813	1.6318	1.1762	0.7818	0.5805
$B \to Y \downarrow$	3.0483	2.1845	1.5725	1.0785	0.7740	0.5113	0.3808
$C \rightarrow Y \uparrow$	4.5296	3.3220	2.3814	1.6318	1.1760	0.7818	0.5804
$C \rightarrow Y \downarrow$	3.0488	2.1848	1.5727	1.0798	0.7740	0.5117	0.3809